

Cypress Semiconductor Corporation, 198 Champion Court, San Jose, CA 95134. Tel: (408) 943-2600

PRODUCT CHANGE NOTIFICATION

PCN: PCN193601

Date: September 04, 2019

Subject: Qualification of XMC as an Additional Wafer Fab Site for Automotive GL-S NOR Flash Memory Products

To: FUTURE ELECTRONICS FUTURE ELE pcn.system@futureelectronics.com

Change Type: Major

Description of Change:

Cypress announces the qualification of Wuhan Xinxin Semiconductor Manufacturing Co., Ltd. (XMC, 18 Gaoxin 4TH Road, East Lake High-Tech Development Zone, Wuhan, Hubei, China) as an additional wafer fab site for GL-S automotive NOR Flash Memory products that are currently fabricated at Fab 25 (5204 East Ben White Boulevard, Austin, TX 78741, USA).

Benefit of Change:

Qualification of alternate manufacturing sites is part of the ongoing flexible manufacturing initiative announced by Cypress. The goal of the flexible manufacturing initiative is to provide the means for Cypress to continue to meet delivery commitments through dynamic, changing market conditions.

Part Numbers Affected: 263

See the attached 'Affected Parts List' file for the list of part numbers affected by this change. The 'Affected Parts List' includes the customer PPAP Part number (marketing part number) and the corresponding sample part number. Note that any new parts that are introduced after the publication of this PCN will include all changes outlined in this PCN.

Qualification Status:

The change has been qualified through a series of tests documented in Qualification Test Plans summarized in the table below. The QTP reports can be found as attachments to this notification.

QTP Number	PBO Qualification Test Plan
002-28003	PBO Protection Layer for S29GLXXXS, 65nm, XMC
184906	GL01GS XMC PBO Qualification

Sample Status:

Qualification samples are not built ahead of time for all part numbers affected by this change. Please refer to the affected parts list file for a list of affected part numbers with their associated sample ordering part numbers. If you require qualification samples, please contact your sales representative as soon as possible, but within 60 days of the date of this PCN. Estimated lead time for qualified samples is 2 - 4 weeks from order entry.

Approximate Implementation Date:

Effective 90 days from the date of notification or upon customer approval, whichever comes first, all shipments of Automotive non-PPAP part numbers in the attached file will be supplied from XMC.

For Automotive PPAP part numbers, this change will be effective upon customer approval.

Anticipated Impact:

Products fabricated at the new site are completely compatible with existing products from form, fit, functional, parametric and quality performance perspectives.

Cypress also recommends that customers take this opportunity to review these changes against current application notes, system design considerations and customer environment conditions to assess impact (if any) to their application.

Method of Identification:

Cypress maintains traceability of product to wafer level, including wafer fabrication location, through the lot number marked on the package.

Response Required:

No response is required.

For additional information regarding this change, contact your local sales representative or contact the PCN Administrator at <u>pcn_adm@cypress.com</u>.

Sincerely,

Cypress PCN Administration



Cypress Semiconductor Reliability Qualification Report

QTP# 184906, 185103, 185104, 185105, 185106 Version **

Qualification of XMC PBO for GL-S Products

Qualification of S29GL-S, 1G, 3.0 Volt-only Page Mode Flash Memory featuring 65 nm MirrorBit® Eclipse process technology

FOR ANY QUESTIONS ON THIS REPORT, PLEASE CONTACT reliability@cypress.com or via a CYLINK CRM CASE

Prepared By: Eng Keat Ng Reliability Engineer Reviewed By: Yusaku Ohta Reliability Manager

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David Hoffman Reliability Director



I.A. Product and Package Information

Type:

MirrorBit Eclipse

 Product Description:
 S29GL01GS
 Cypress Division:
 Memory Product Division

 1G, 3.0 Volt-only Page Mode Flash Memory featuring 65 nm MirrorBit® Eclipse process technology

Package: TS056 QTP: 184906 Description: (20 x 14 x 1.2mm) 56 Lead, Thin Small Outline Package (TSOP) Flammability: O2 Index: UL-V0 >28 Assembly: Cypress Thailand Molding Compound: Hitachi CEL 9200HF10-U Electrical Test: Cypress Thailand Substrate/Leadframe: Copper Leadframe Die Attachment: Ablestik 8340 Lead Finish: 100% Matte Sn Plating Bond Wire: Copper **Comments:** 55 °C 125 °C **Est. Field Temperature:** Life Test Temperature: **Est. DC Field Current:** 25 mA mΑ Life Test Dynamic Current: 10 **Est. Field Voltage:** 3.0 V ۷ Life Test Voltage: 3.6 mWatts **Est. Stress Power Dissipation:** mWatts **Est. Field Power Dissipation:** 75 36 98661B2 **Die Size:** Die: 6.80 x 7.45 mm Process: CS239LS (65nm) Fab: WXIC

Density:

1G



I.B. Product and Package Information

Type:

MirrorBit Eclipse

 Product Description:
 S29GL01GS
 Cypress Division:
 Memory Product Division

 1G, 3.0 Volt-only Page Mode Flash Memory featuring 65 nm MirrorBit® Eclipse process technology

Package: LAE064 QTP: 185103 **Description:** (9 x 9 x 1.4mm) 64 Ball, Fortified Ball Grid Array Package (fFBGA) Flammability: O2 Index: UL-V0 >28 Assembly: Cypress Thailand Molding Compound: ShinEtsu KMC 3580LVA Electrical Test: Cypress Thailand Substrate/Leadframe: Laminate Substrate Die Attachment: QMI 546 Lead Finish: 96.5Sn3.0Ag0.5Cu Spheres Bond Wire: Copper **Comments:** 55 °C 125 °C **Est. Field Temperature:** Life Test Temperature: **Est. DC Field Current:** 25 mA mΑ Life Test Dynamic Current: 10 **Est. Field Voltage:** 3.0 V ۷ Life Test Voltage: 3.6 mWatts **Est. Stress Power Dissipation:** mWatts **Est. Field Power Dissipation:** 75 36 98661B2 **Die Size:** Die: 6.80 x 7.45 mm Process: CS239LS (65nm) Fab: WXIC

Density:

1G



I.C. Product and Package Information

Type:

MirrorBit Eclipse

Product Description: S29GL01GS Cypress Division: Memory Product Division 1G, 3.0 Volt-only Page Mode Flash Memory featuring 65 nm MirrorBit® Eclipse process technology

Package: TS056 **QTP:** 185104 Description: (20 x 14 x 1.2mm) 56 Lead, Thin Small Outline Package (TSOP) Flammability: O2 Index: UL-V0 >28 Assembly: Cypress Thailand Molding Compound: Hitachi CEL 9200HF10-U Electrical Test: Cypress Thailand Substrate/Leadframe: Copper Leadframe Die Attachment: Ablestik 8340 Lead Finish: 100% Matte Sn Plating Bond Wire: Copper **Comments:** 55 °C 125 °C **Est. Field Temperature:** Life Test Temperature: **Est. DC Field Current:** 25 mA mΑ Life Test Dynamic Current: 10 **Est. Field Voltage:** 3.0 V ۷ Life Test Voltage: 3.6 mWatts **Est. Stress Power Dissipation:** mWatts **Est. Field Power Dissipation:** 75 36 98661B2 **Die Size:** Die: 6.80 x 7.45 mm Process: CS239LS (65nm) Fab: WXIC Density:

1G



I.D. Product and Package Information

Product Description	n: S29GL51	2S	Cypress D	Division: M	emory Prod	uct Division	
	1G, 3.0 V	olt-only Page Moc	le Flash Memory featuri	ng 65 nm Mirro	orBit® Eclips	e process technolo	ogy
Package:	VBU056		QTP: 185105				
Description:	(9.0 x 7.0 x 1.	0mm) 56 Ball, Ver	y Thin Fine Pitch Ball G	rid Array Pack	age (FBGA)	Flammabilit	y: O2 Index:
Assembly:	Cypress Thail	and M	olding Compound:	ShinEtsu KM	C 3580LVA	UL-V0	>28
Electrical Test:	Cypress Thail	and					
Substrate/Leadframe:	Laminate Sub	ostrate	Die Attachment:	QMI 546			
Lead Finish:	96.5Sn3.0Ag	0.5Cu Spheres	Bond Wire:	Copper			
Comments:							
Est. Field Ten	nperature:	55 °C	Life Test	Temperatur	e: 125 °	ŶĊ	
Est. DC Fiel	d Current:	25 mA	Life Test Dyna	amic Curren	n t: 10 i	nA	
Est. Fiel	d Voltage:	3.0 V	Life	Test Voltag	e: 3.6 ^v	V	
Est. Field Power Di	ssipation:	75 mWatts	Est. Stress Powe	r Dissipatio	n: 36	mWatts	
	Die:	98290B2		Die Size:	6.80 x	5.02 mm	
	Process:	CS239LS (65nm	1)	Fab:	WXIC		
	Туре:	MirrorBit Eclipse	•	Density:	512M		



I.E. Product and Package Information

Product Description: S29GL01GS Cypress Division: Memory Product Division 1G, 3.0 Volt-only Page Mode Flash Memory featuring 65 nm MirrorBit® Eclipse process technology Package: LAA064 QTP: 185106 Description: (13.0 x 11.0 x 1.4mm) 64 Ball, Fortified Ball Grid Array Package (FBGA) Flammability: O2 Index: UL-V0 >28 Assembly: Cypress Thailand Molding Compound: ShinEtsu KMC 3580LVA Electrical Test: Cypress Thailand Substrate/Leadframe: Laminate Substrate Die Attachment: QMI 546 Lead Finish: 96.5Sn3.0Ag0.5Cu Spheres Bond Wire: Copper **Comments:** 55 °C 125 °C **Est. Field Temperature:** Life Test Temperature: **Est. DC Field Current:** 25 mA mΑ Life Test Dynamic Current: 10 **Est. Field Voltage:** 3.0 V ۷ Life Test Voltage: 3.6 mWatts **Est. Stress Power Dissipation:** mWatts **Est. Field Power Dissipation:** 75 36 98661B2 **Die Size:** Die: 6.80 x 7.45 mm Process: CS239LS (65nm) Fab: WXIC Density: Type: MirrorBit Eclipse 1G



II. Summary of Stress Test Results

Stress Test	Stress Condition	Package Type	Sample Size	Num. of Lots	Num. of Fails	Failure Rate %	Comments
Data Fro	m Qualification 184906	6, 185103	s, 1851	04, 18	5105,	18510	6:
ELFR	(3.6V, 150°C)	TS056 ¹	348	3	0	0.00	48 hours
HTOL (EL)	(3.6V, 150°C)	TS056 ¹	348	3	0	0.00	168 hours
HTOL (IL)	(3.6V, 150°C)	TS056 ¹	348	3	0	0.00	500 Hours
	(3.6V, 150°C)	TS056 ¹	231	3	0	0.00	1000 hours
LTOL	(-40°C, 3.6V)	TS056 ¹	64	1	0	0.00	1000 hours
ESD CDM	N/A	LAE064 ²	6	1	Passe	d 500V	
	N/A	TS056 ³	18	3	Pass (500V	
	N/A	VBU056 ⁴	6	1	Passe	d 500V	
	N/A	LAA064 ⁵	18	3	Passe	d 500V	
Endurance (10k)	(105°C, 3.6V)	TS056 ¹	240	3	0	0.00	10k cycles
Endurance (100k)	(105°C, 3.6V)	TS056 ¹	239	3	0	0.00	100k cycles
Decade Cycling + DRB	(25°C, 3.6V, DRB 500h @ 25°C)	TS056 ¹	239	3	0	0.00	100k cycles
	(85°C, 3.6V, DRB 105h @ 150°C)	TS056 ¹	192	3	0	0.00	100k cycles
Preconditioning	(PC2/260°C, +0°C/-5°C)	LAE064 ²	77	1	Passe	d Jedec L3	
	(PC2/260°C, +0°C/-5°C)	TS056 ³	552	3	Passe	d Jedec L3	
	(PC2/260°C, +0°C/-5°C)	VBU056 ⁴	77	1	Passe	d Jedec L3	
	(PC2/260°C, +0°C/-5°C)	LAA064 ⁵	552	3	Passe	d Jedec L3	
Precon+Temp Cycle	(PC2/260°C, -65°C/150°C)	TS056 ³	291	3	0	0.00	500 cycles
	(PC2/260°C, -65°C/150°C)	LAA064 ⁵	291	3	0	0.00	500 cycles
Precon+Temp Cycle (Ext.)	(PC2/260°C, -65°C/150°C)	TS056 ³	260	3	0	0.00	1000 cycles
	(PC2/260°C, -65°C/150°C)	LAA064 ⁵	260	3	0	0.00	1000 cycles
Precon+HAST	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ³	261	3	0	0.00	96 hours
	(PC2/260°C, Biased, 110°C/85% RH)	LAA064 ⁵	261	3	0	0.00	264 hours
Precon+HAST (Ext.)	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ³	143	3	0	0.00	192 hours
	(PC2/260°C, Biased, 110°C/85% RH)	LAA064 ⁵	231	3	0	0.00	528 hours
3x Reflow+HTS	(175°C)	TS056 ³	163	3	0	0.00	500 hours
	(175°C)	TS056 ³	132	3	0	0.00	1000 hours
	(150°C)	LAA064 ⁵	128	3	0	0.00	2000 hours
	(150°C)	LAA064 ⁵	159	3	0	0.00	1000 hours
Decade Cycling + HTOL	(85°C, 3.6V, 125C HTOL@1000hrs)	TS056 ¹	238	3	0	0.00	100k cycles



Generic Reference Data:

Preconditioning	(PC2/260°C, +0°C/-5°C)	TS056 ⁶	77	1	Passed Jedec L3
	(PC2/260°C, +0°C/-5°C)	TS056 ⁷	77	1	Passed Jedec L3
	(PC2/260°C, +0°C/-5°C)	TS056 ⁸	77	1	Passed Jedec L3
Precon+HAST	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ⁶	77	1	96 hours
	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ⁷	77	1	96 hours
	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ⁸	77	1	96 hours
Precon+HAST (Ext.)	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ⁶	70	1	192 hours
	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ⁷	70	1	192 hours
	(PC2/260°C, Biased, 130°C/85% RH)	TS056 ⁸	70	1	192 hours



Notes / Justification: 1) Results from Qual 184906, S29GL01GS, CS239LS (65nm) MirrorBit Eclipse in 56 Lead TSOP (20 x 14 x 1.2mm)

- 2) Results from Qual 185103, S29GL01GS, CS239LS (65nm) MirrorBit Eclipse in 64 Ball fFBGA (9 x 9 x 1.4mm)
- 3) Results from Qual 185104, S29GL01GS, CS239LS (65nm) MirrorBit Eclipse in 56 Lead TSOP (20 x 14 x 1.2mm)
- 4) Results from Qual 185105, S29GL512S, CS239LS (65nm) MirrorBit Eclipse in 56 Ball vFBGA (9 x 7 x 1mm)
- 5) Results from Qual 185106, S29GL01GS, CS239LS (65nm) MirrorBit Eclipse in 64 Ball fFBGA (13 x 11 x 1.4mm)
- 6) Results from Qual 185105c, S29GL512S in 56 Lead TSOP (20 x 14 x 1.2mm) Same XMC PBO GL-S Product in TSOP56
- 7) Results from Qual 185105d, S29GL256S in 56 Lead TSOP (20 x 14 x 1.2mm) Same XMC PBO GL-S Product in TSOP56
- 8) Results from Qual 185105e, S29GL128S in 56 Lead TSOP (20 x 14 x 1.2mm) Same XMC PBO GL-S Product in TSOP56

Preconditioning Flows: PC2 (JEDEC L3): Bake 125°C, 24hr => Soak @ 30°C/60%RH, 192hr => 3x Reflow

Reliability Tests Performed per Specification Requirements

Stress	Condition	Specification Reference
3x Reflow+HTS	(150°C)	JESD22-A117
3x Reflow+HTS	(175°C)	JESD22-A117
Decade Cycling + DRB	(25°C, 3.6V, DRB 500h @ 25°C)	JESD47 / JESD22-A117 / AEC-Q100 /AEC-Q100-005
Decade Cycling + DRB	(85°C, 3.6V, DRB 105h @ 150°C)	JESD47 / JESD22-A117 / AEC-Q100 /AEC-Q100-005
Decade Cycling + HTOL	(85°C, 3.6V, 125C HTOL@1000hrs)	JESD47 / JESD22-A117 / AEC-Q100 /AEC-Q100-005
ELFR	(3.6V, 150°C)	JESD22-A108 / AEC-Q100-008
Endurance (100k)	(105°C, 3.6V)	JESD47 / JESD22-A117 / AEC-Q100 /AEC-Q100-005
Endurance (10k)	(105°C, 3.6V)	JESD47 / JESD22-A117 / AEC-Q100 /AEC-Q100-005
ESD CDM	N/A	JS002 / AEC-Q100-011
HTOL (EL)	(3.6V, 150°C)	JESD22-A108
HTOL (IL)	(3.6V, 150°C)	JESD22-A108
LTOL	(-40°C, 3.6V)	JESD22-A108
Precon+HAST	(PC2/260°C, Biased, 110°C/85% RH)	JESD22-A110
Precon+HAST	(PC2/260°C, Biased, 130°C/85% RH)	JESD22-A110
Precon+HAST (Ext.)	(PC2/260°C, Biased, 110°C/85% RH)	JESD22-A110
Precon+HAST (Ext.)	(PC2/260°C, Biased, 130°C/85% RH)	JESD22-A110
Precon+Temp Cycle	(PC2/260°C, -65°C/150°C)	JESD22-A104
Precon+Temp Cycle (Ext.)	(PC2/260°C, -65°C/150°C)	JESD22-A104
Preconditioning	(PC2/260°C, +0°C/-5°C)	J-STD-020



III. Revision History

Document Number: 002-27990

Document Title: Qualification of XMC PBO for GL-S Products

Rev.	Issue Date	ECN#	Originator	Description
**	7/24/2019	6635304	EKNG	Initial Release.

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S29GL01GS/S29GL512S S29GL256S/S29GL128S

1-Gbit (128 Mbyte)/512-Mbit (64 Mbyte)/ 256-Mbit (32 Mbyte)/128-Mbit (16 Mbyte), 3.0 V, GL-S Flash Memory

General Description

The Cypress[®] S29GL01G/512/256/128S are MirrorBit[®] Eclipse flash products fabricated on 65 nm process technology. These devices offer a fast page access time as fast as 15 ns with a corresponding random access time as fast as 90 ns. They feature a Write Buffer that allows a maximum of 256 words/512 bytes to be programmed in one operation, resulting in faster effective programming time than standard programming algorithms. This makes these devices ideal for today's embedded applications that require higher density, better performance and lower power consumption.

Distinctive Characteristics

- CMOS 3.0 Volt Core with Versatile I/O
- 65 nm MirrorBit Eclipse Technology
- Single supply (V_{CC}) for read / program / erase (2.7 V to 3.6 V)
- Versatile I/O Feature
 - Wide I/O voltage range (V_{IO}): 1.65 V to V_{CC}
- ×16 data bus
- Asynchronous 32-byte Page read
- 512-byte Programming Buffer
 - Programming in Page multiples, up to a maximum of 512 bytes
- Single word and multiple program on same word options
- Automatic Error Checking and Correction (ECC) internal hardware ECC with single bit error correction
- Sector Erase
 - Uniform 128-kbyte sectors
- Suspend and Resume commands for Program and Erase operations

- Status Register, Data Polling, and Ready/Busy pin methods to determine device status
- Advanced Sector Protection (ASP)
 - Volatile and non-volatile protection methods for each sector
- Separate 1024-byte One Time Program (OTP) array with two lockable regions
- Common Flash Interface (CFI) parameter table
- Temperature Range / Grade
 - Industrial (-40 °C to +85 °C)
 - Industrial Plus(-40 °C to +105 °C)
 - Automotive, AEC-Q100 Grade 3 (-40 °C to +85 °C)
 - Automotive, AEC-Q100 Grade 2 (-40 °C to +105 °C)
- 100,000 Program / Erase Cycles
- 20 Years Data Retention
- Packaging Options
 - 56-pin TSOP
 - 64-ball LAA Fortified BGA, 13 mm × 11 mm
 - 64-ball LAE Fortified BGA, 9 mm × 9 mm
 - 56-ball VBU Fortified BGA, 9 mm × 7 mm

198 Champion Court



Performance Summary

Maximum Read Access Times						
Density	Voltage Range	Random Access Time (t _{ACC})	Page Access Time (t _{PACC})	CE# Access Time (t _{CE})	OE# Access Time (t _{OE})	
128 Mb	Full V _{CC} = V _{IO}	90	15	90	25	
	VersatileIO V _{IO}	100	25	100	35	
256 Mb	Full V _{CC} = V _{IO}	90	15	90	25	
200 1010	VersatileIO V _{IO}	100	25	100	35	
510 Mb	Full V _{CC} = V _{IO}	100	15	100	25	
	VersatileIO V _{IO}	110	25	110	35	
1 Gb	Full V _{CC} = V _{IO}	100	15	100	25	
	VersatileIO V _{IO}	110	25	110	35	

Typical Program and Erase Rates				
Buffer Programming (512 bytes)	1.5 MB/s			
Sector Erase (128 kbytes)	477 kB/s			

Maximum Current Consumption					
Active Read at 5 MHz, 30 pF	60 mA				
Program	100 mA				
Erase	100 mA				
Standby	100 µA				



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1. Product Overview

The GL-S family consists of 128-Mbit to 1Gbit, 3.0 V core, Versatile I/O, non-volatile, flash memory devices. These devices have a 16-bit (word) wide data bus and use only word boundary addresses. All read accesses provide 16 bits of data on each bus transfer cycle. All writes take 16 bits of data from each bus transfer cycle.



Figure 1.1 Block Diagram

Note:

 $^{**}A_{MAX}\,GL01GS = A25,\,A_{MAX}\,GL512S = A24,\,A_{MAX}\,GL256S = A23,\,A_{MAX}\,GL128S = A22$

The GL-S family combines the best features of eXecute In Place (XIP) and Data Storage flash memories. This family has the fast random access of XIP flash along with the high density and fast program speed of Data Storage flash.

Read access to any random location takes 90 ns to 120 ns depending on device density and I/O power supply voltage. Each random (initial) access reads an entire 32-byte aligned group of data called a Page. Other words within the same Page may be read by changing only the low order 4 bits of word address. Each access within the same Page takes 15 ns to 30 ns. This is called Page Mode read. Changing any of the higher word address bits will select a different Page and begin a new initial access. All read accesses are asynchronous.



Table 1.1 S29GL-S Address Map

Туре	Count	Addresses
Address within Page	16	A3–A0
Address within Write Buffer	256	A7–A0
Page	4096	A15–A4
Write-Buffer-Line	256	A15–A8
Sector	1024 (1 Gb) 512 (512 Mb) 256 (256 Mb) 128 (128 Mb)	A _{MAX} –A16

The device control logic is subdivided into two parallel operating sections, the Host Interface Controller (HIC) and the Embedded Algorithm Controller (EAC). HIC monitors signal levels on the device inputs and drives outputs as needed to complete read and write data transfers with the host system. HIC delivers data from the currently entered address map on read transfers; places write transfer address and data information into the EAC command memory; notifies the EAC of power transition, hardware reset, and write transfers. The EAC looks in the command memory, after a write transfer, for legal command sequences and performs the related Embedded Algorithms.

Changing the non-volatile data in the memory array requires a complex sequence of operations that are called Embedded Algorithms (EA). The algorithms are managed entirely by the device internal EAC. The main algorithms perform programming and erase of the main array data. The host system writes command codes to the flash device address space. The EAC receives the commands, performs all the necessary steps to complete the command, and provides status information during the progress of an EA.

The erased state of each memory bit is a logic 1. Programming changes a logic 1 (High) to a logic 0 (Low). Only an Erase operation is able to change a 0 to a 1. An erase operation must be performed on an entire 128-kbyte aligned and length group of data call a Sector. When shipped from Cypress all Sectors are erased.

Programming is done via a 512-byte Write Buffer. It is possible to write from 1 to 256 words, anywhere within the Write Buffer before starting a programming operation. Within the flash memory array, each 512-byte aligned group of 512 bytes is called a Line. A programming operation transfers volatile data from the Write Buffer to a non-volatile memory array Line. The operation is called Write Buffer Programming.

As the device transfers each 32-byte aligned page of data that was loaded into the Write buffer to the 512-byte Flash array line, internal logic programs an ECC Code for the Page into a portion of the memory array not visible to the host system software. The internal logic checks the ECC information during the initial access of every array read operation. If needed, the ECC information corrects a one bit error during the initial access time.

The Write Buffer is filled with 1's after reset or the completion of any operation using the Write Buffer. Any locations not written to a 0 by a Write to Buffer command are by default still filled with 1's. Any 1's in the Write Buffer do not affect data in the memory array during a programming operation.

As each Page of data that was loaded into the Write Buffer is transferred to a memory array Line.

Sectors may be individually protected from program and erase operations by the Advanced Sector Protection (ASP) feature set. ASP provides several, hardware and software controlled, volatile and non-volatile, methods to select which sectors are protected from program and erase operations.



Software Interface

2. Address Space Maps

There are several separate address spaces that may appear within the address range of the flash memory device. One address space is visible (entered) at any given time.

- Flash Memory Array: the main non-volatile memory array used for storage of data that may be randomly accessed by asynchronous read operations.
- ID/CFI: a memory array used for Cypress factory programmed device characteristics information. This area contains the Device Identification (ID) and Common Flash Interface (CFI) information tables.
- Secure Silicon Region (SSR): a One Time Programmable (OTP) non-volatile memory array used for Cypress factory programmed permanent data, and customer programmable permanent data.
- Lock Register: an OTP non-volatile word used to configure the ASP features and lock the SSR.
- Persistent Protection Bits (PPB): a non-volatile flash memory array with one bit for each Sector. When programmed, each bit protects the related Sector from erasure and programming.
- PPB Lock: a volatile register bit used to enable or disable programming and erasure of the PPB bits.
- Password: an OTP non-volatile array used to store a 64-bit password used to enable changing the state of the PPB Lock Bit when using Password Mode sector protection.
- Dynamic Protection Bits (DYB): a volatile array with one bit for each Sector. When set, each bit protects the related Sector from erasure and programming.
- Status Register: a volatile register used to display Embedded Algorithm status.
- Data Polling Status: a volatile register used as an alternate, legacy software compatible, way to display Embedded Algorithm status.
- ECC Status: provides the status of any error detection or correction action taken when reading the selected Page.

The main Flash Memory Array is the primary and default address space but, it may be overlaid by one other address space, at any one time. Each alternate address space is called an Address Space Overlay (ASO).

Each ASO replaces (overlays) the entire flash device address range. Any address range not defined by a particular ASO address map, is reserved for future use. All read accesses outside of an ASO address map returns non-valid (undefined) data. The locations will display actively driven data but the meaning of whatever 1's or 0's appear are not defined.

There are four device operating modes that determine what appears in the flash device address space at any given time:

- Read Mode
- Data Polling Mode
- Status Register (SR) Mode
- Address Space Overlay (ASO) Mode

In Read Mode the entire Flash Memory Array may be directly read by the host system memory controller. The memory device Embedded Algorithm Controller (EAC), puts the device in Read mode during Power-on, after a Hardware Reset, after a Command Reset, or after an Embedded Algorithm (EA) is suspended. Read accesses and command writes are accepted in read mode. A subset of commands are accepted in read mode when an EA is suspended.

While in any mode, the Status Register read command may be issued to cause the Status Register ASO to appear at every word address in the device address space. In this Status Register ASO Mode, the device interface waits for a read access and, any write access is ignored. The next read access to the device accesses the content of the status register, exits the Status Register ASO, and returns to the previous (calling) mode in which the Status Register read command was received.

In EA mode the EAC is performing an Embedded Algorithm, such as programming or erasing a non-volatile memory array. While in EA mode, none of the main Flash Memory Array is readable because the entire flash device address space is replaced by the Data Polling Status ASO. Data Polling Status will appear at every word location in the device address space.



While in EA mode, only a Program / Erase suspend command or the Status Register Read command will be accepted. All other commands are ignored. Thus, no other ASO may be entered from the EA mode.

When an Embedded Algorithm is suspended, the Data Polling ASO is visible until the device has suspended the EA. When the EA is suspended the Data Polling ASO is exited and Flash Array data is available. The Data Polling ASO is reentered when the suspended EA is resumed, until the EA is again suspended or finished. When an Embedded Algorithm is completed, the Data Polling ASO is exited and the device goes to the previous (calling) mode (from which the Embedded Algorithm was started).

In ASO mode, one of the remaining overlay address spaces is entered (overlaid on the main Flash Array address map). Only one ASO may be entered at any one time. Commands to the device affect the currently entered ASO. Only certain commands are valid for each ASO. These are listed in the Table 7.1 on page 55, in each ASO related section of the table.

The following ASOs have non-volatile data that may be programmed to change 1's to 0's:

- Secure Silicon Region
- Lock Register
- Persistent Protection Bits (PPB)
- Password
- Only the PPB ASO has non-volatile data that may be erased to change 0's to 1's

When a program or erase command is issued while one of the non-volatile ASOs is entered, the EA operates on the ASO. The ASO is not readable while the EA is active. When the EA is completed the ASO remains entered and is again readable. Suspend and Resume commands are ignored during an EA operating on any of these ASOs.

2.1 Flash Memory Array

The S29GL-S family has uniform sector architecture with a sector size of 128 kB. Table 2.1 to Table 2.4 shows the sector architecture of the four devices.

Table 2.1 S29GL01GS Sector and Memory Address Map

Sector Size (kbyte)	Sector Count	Sector Range	Address Range (16-Bit)	Notes
		SA00	0000000h-000FFFFh	Sector Starting Address
128	1024	:		-
		SA1023	3FF0000h-3FFFFFh	Sector Ending Address

Table 2.2 S29GL512S Sector and Memory Address Map

Sector Size (kbyte)	Sector Count	Sector Range	Address Range (16-Bit)	Notes
		SA00	0000000h-000FFFFh	Sector Starting Address
128	512	:	:	-
		SA511	1FF0000h-1FFFFFh	Sector Ending Address

Table 2.3 S29GL256S Sector and Memory Address Map

Sector Size (kbyte)	Sector Count	Sector Range	Address Range (16-Bit)	Notes
	256	SA00	0000000h-000FFFFh	Sector Starting Address
128		:	:	-
		SA255	0FF0000h-0FFFFFh	Sector Ending Address



Table 2.4 S29GL128S Sector and Memory Address Map

Sector Size (kbyte)	Sector Count	Sector Range	Address Range (16-Bit)	Notes
		SA00	0000000h-000FFFFh	Sector Starting Address
128	128	:	:	-
		SA127	07F0000h-07FFFFh	Sector Ending Address

Note: These tables have been condensed to show sector related information for an entire device on a single page Sectors and their address ranges that are not explicitly listed (such as SA001-SA510) have sectors starting and ending addresses that form the same pattern as all other sectors of that size. For example, all 128 kB sectors have the pattern XXX0000h–XXXFFFFh.

2.2 Device ID and CFI (ID-CFI) ASO

There are two traditional methods for systems to identify the type of flash memory installed in the system. One has traditionally been called Autoselect and is now referred to as Device Identification (ID). The other method is called Common Flash Interface (CFI).

For ID, a command is used to enable an address space overlay where up to 16 word locations can be read to get JEDEC manufacturer identification (ID), device ID, and some configuration and protection status information from the flash memory. The system can use the manufacturer and device IDs to select the appropriate driver software to use with the flash device.

CFI also uses a command to enable an address space overlay where an extendable table of standard information about how the flash memory is organized and operates can be read. With this method the driver software does not have to be written with the specifics of each possible memory device in mind. Instead the driver software is written in a more general way to handle many different devices but adjusts the driver behavior based on the information in the CFI table.

Traditionally these two address spaces have used separate commands and were separate overlays. However, the mapping of these two address spaces are non-overlapping and so can be combined in to a single address space and appear together in a single overlay. Either of the traditional commands used to access (enter) the Autoselect (ID) or CFI overlay will cause the now combined ID-CFI address map to appear.

The ID-CFI address map appears within, and overlays the Flash Array data of, the sector selected by the address used in the ID-CFI enter command. While the ID-CFI ASO is entered the content of all other sectors is undefined.

The ID-CFI address map starts at location 0 of the selected sector. Locations above the maximum defined address of the ID-CFI ASO to the maximum address of the selected sector have undefined data. The ID-CFI enter commands use the same address and data values used on previous generation memories to access the JEDEC Manufacturer ID (Autoselect) and Common Flash Interface (CFI) information, respectively. See Figure 11.16 on page 87 for ASO Entry timing requirements.

Table 2.5 ID-CFI Address Map Overvie

Word Address	Description	Read / Write
(SA) + 0000h to 000Fh	Device ID (traditional Autoselect values)	Read Only
(SA) + 0010h to 0079h	CFI data structure	Read Only
(SA) + 0080h to FFFFh	Undefined	Read Only

For the complete address map see Table 7.2 on page 58.



2.3 Device ID and Common Flash Interface (ID-CFI) ASO Map — Automotive Only

Word Address	Data Field	# of bytes	Data Format	Example of Actual Data	Hex Read Out of Example Data
(SA) + 0080h	Size of Electronic Marking	1	Hex	19	0013h
(SA) + 0081h	Revision of Electronic Marking	1	Hex	1	0001h
(SA) + 0082h	Fab Lot #	7	Ascii	LD87270	004Ch, 0044h, 0038h, 0037h, 0032h, 0037h, 0030h
(SA) + 0089h	Wafer #	1	Hex	23	0017h
(SA) + 008Ah	Die X Coordinate	1	Hex	10	000Ah
(SA) + 008Bh	Die Y Coordinate	1	Hex	15	000Fh
(SA) + 008Ch	Class Lot #	7	Ascii	BR33150	0042h, 0052h, 0033h, 0033h, 0031h, 0035h, 0030h
(SA) + 0093h	Reserved for Future	13	n/a	n/a	undefined

Fab Lot # + Wafer # + Die X Coordinate + Die Y Coordinate gives a unique ID for each device.

2.3.1 Device ID

The Joint Electron Device Engineering Council (JEDEC) standard JEP106T defines the manufacturer ID for a compliant memory. Common industry usage defined a method and format for reading the manufacturer ID and a device specific ID from a memory device. The manufacturer and device ID information is primarily intended for programming equipment to automatically match a device with the corresponding programming algorithm. Cypress has added additional fields within this 32-byte address space.

The original industry format was structured to work with any memory data bus width e. g. ×8, ×16, ×32. The ID code values are traditionally byte wide but are located at bus width address boundaries such that incrementing the device address inputs will read successive byte, word, or double word locations with the ID codes always located in the least significant byte location of the data bus. Because the device data bus is word wide each code byte is located in the lower half of each word location. The original industry format made the high order byte always 0. Cypress has modified the format to use both bytes in some words of the address space. For the detail description of the Device ID address map see Table 7.2 on page 58.

2.3.2 Common Flash Memory Interface

The JEDEC Common Flash Interface (CFI) specification (JESD68.01) defines a standardized data structure that may be read from a flash memory device, which allows vendor-specified software algorithms to be used for entire families of devices. The data structure contains information for system configuration such as various electrical and timing parameters, and special functions supported by the device. Software support can then be device-independent, Device ID-independent, and forward-and-backward-compatible for entire Flash device families.

The system can read CFI information at the addresses within the selected sector as shown in Device ID and Common Flash Interface (ID-CFI) ASO Map on page 58.

Like the Device ID information, CFI information is structured to work with any memory data bus width e. g. ×8, ×16, ×32. The code values are always byte wide but are located at data bus width address boundaries such that incrementing the device address reads successive byte, word, or double word locations with the codes always located in the least significant byte location of the data bus. Because the data bus is word wide each code byte is located in the lower half of each word location and the high order byte is always 0.

For further information, please refer to the *Cypress CFI Specification, Version 1.4* (or later), and the *JEDEC publications JEP137-A* and *JESD68.01*. Please contact JEDEC (http://www.jedec.org) for their standards and the Cypress CFI Specification may be found at the Cypress Website (http://www.cypress.com/cypressappnotes) at the time of this document's publication), or contact the local Cypress sales office listed in the website.



2.4 Status Register ASO

The Status Register ASO contains a single word of registered volatile status for Embedded Algorithms. When the Status Register read command is issued, the current status is captured (by the rising edge of WE#) into the register and the ASO is entered. The Status Register content appears on all word locations. The first read access exits the Status Register ASO (with the rising edge of CE# or OE#) and returns to the address space map in use when the Status Register read command was issued. Write commands will not exit the Status Register ASO state.

2.5 Data Polling Status ASO

The Data Polling Status ASO contains a single word of volatile memory indicating the progress of an EA. The Data Polling Status ASO is entered immediately following the last write cycle of any command sequence that initiates an EA. Commands that initiate an EA are:

- Word Program
- Program Buffer to Flash
- Chip Erase
- Sector Erase
- Erase Resume / Program Resume
- Program Resume Enhanced Method
- Blank Check
- Lock Register Program
- Password Program
- PPB Program
- All PPB Erase

Engineering Note: The reset and write buffer abort reset commands require very short time to execute so data polling is not supported for these commands. The Data Polling Status word appears at all word locations in the device address space. When an EA is completed the Data Polling Status ASO is exited and the device address space returns to the address map mode where the EA was started.

2.6 Secure Silicon Region ASO

The Secure Silicon Region (SSR) provides an extra flash memory area that can be programmed once and permanently protected from further changes i. e. it is a One Time Program (OTP) area. The SSR is

1024 bytes in length. It consists of 512 bytes for Factory Locked Secure Silicon Region and 512 bytes for Customer Locked Secure Silicon Region.

The sector address supplied during the Secure Silicon Entry command selects the Flash Memory Array sector that is overlaid by the Secure Silicon Region address map. See Figure 11.16 on page 87 for ASO Entry timing requirements. The SSR is overlaid starting at location 0 in the selected sector. Use of the sector 0 address is recommended for future compatibility. While the SSR ASO is entered the content of all other sectors is undefined. Locations above the maximum defined address of the SSR ASO to the maximum address of the selected sector have undefined data.

Word Address Range	Content	Size
(SA) + 0000h to 00FFh	Factory Locked Secure Silicon Region	512 bytes
(SA) + 0100h to 01FFh	Customer Locked Secure Silicon Region	512 bytes
(SA) + 0200h to FFFFh	Undefined	127 kbytes

Table 2.6 Secure Silicon Region



2.7 Sector Protection Control

2.7.1 Lock Register ASO

The Lock register ASO contains a single word of OTP memory. When the ASO is entered the Lock Register appears at all word locations in the device address space. See Figure 11.16 on page 87 for ASO Entry timing requirements. However, it is recommended to read or program the Lock Register only at location 0 of the device address space for future compatibility.

2.7.2 Persistent Protection Bits (PPB) ASO

The PPB ASO contains one bit of a Flash Memory Array for each Sector in the device. When the PPB ASO is entered, the PPB bit for a sector appears in the Least Significant Bit (LSB) of each address in the sector. See Figure 11.16 on page 87 for ASO Entry timing requirements. Reading any address in a sector displays data where the LSB indicates the non-volatile protection status for that sector. However, it is recommended to read or program the PPB only at address 0 of the sector for future compatibility. If the bit is 0 the sector is protected against programming and erase operations. If the bit is 1 the sector is not protected by the PPB. The sector may be protected by other features of ASP.

2.7.3 PPB LOCK ASO

The PPB Lock ASO contains a single bit of volatile memory. The bit controls whether the bits in the PPB ASO may be programmed or erased. If the bit is 0 the PPB ASO is protected against programming and erase operations. If the bit is 1 the PPB ASO is not protected. When the PPB Lock ASO is entered the PPB Lock bit appears in the Least Significant Bit (LSB) of each address in the device address space. See Figure 11.16 on page 87 for ASO Entry timing requirements. However, it is recommended to read or program the PPB Lock only at address 0 of the device for future compatibility.

2.7.4 Password ASO

The Password ASO contains four words of OTP memory. When the ASO is entered the Password appears starting at address 0 in the device address space. See Figure 11.16 on page 87 for ASO Entry timing requirements. All locations above the forth word are undefined.

2.7.5 Dynamic Protection Bits (DYB) ASO

The DYB ASO contains one bit of a volatile memory array for each Sector in the device. When the DYB ASO is entered, the DYB bit for a sector appears in the Least Significant Bit (LSB) of each address in the sector. See Figure 11.16 on page 87 for ASO Entry timing requirements. Reading any address in a sector displays data where the LSB indicates the non-volatile protection status for that sector. However, it is recommended to read, set, or clear the DYB only at address 0 of the sector for future compatibility. If the bit is 0 the sector is protected against programming and erase operations. If the bit is 1 the sector is not protected by the DYB. The sector may be protected by other features of ASP.

2.8 ECC Status ASO

The system can access the ECC Status ASO by issuing the ECC Status entry command sequence during Read Mode. The ECC Status ASO provides the status of a Single Bit Error correction when reading the selected page. *Automatic ECC* on page 22 describes the ECC function in more detail. See Figure 11.16 on page 87 for ASO Entry timing requirements.

The ECC Status ASO allows the following activities:

- Read ECC Status for the selected page.
- ASO Exit.

2.8.1 ECC Status

The contents of the ECC Status ASO indicates, for the selected ECC page, whether ECC protection has corrected an error in the eight-bit error correction code or the 16 Words of data in the ECC page. The address specified in the ECC Status Read Command, provided in Table 7.1 on page 55 selects the ECC Page.





Table 2.7 ECC Status Word – Upper Byte

Bit	15	14	13	12	11	10	9	8
Name	RFU							
Value	Х	Х	Х	Х	Х	Х	Х	Х

Table 2.8 ECC Status Word – Lower Byte

Bit	7	6	5	4	3	2	1	0
Name	RFU	RFU	RFU	RFU	RFU	Single Bit Error corrected in the 8-bit error correction code	Single Bit Error corrected in 16 words of data	RFU
Value	х	х	х	х	х	0 = No Error Corrected 1 = Single Bit Error Corrected	0 = No Error Corrected 1 = Single Bit Error Corrected	х



3. Data Protection

The device offers several features to prevent malicious or accidental modification of any sector via hardware means.

3.1 Device Protection Methods

3.1.1 Power-Up Write Inhibit

RESET#, CE#, WE#, and, OE# are ignored during Power-On Reset (POR). During POR, the device can not be selected, will not accept commands on the rising edge of WE#, and does not drive outputs. The Host Interface Controller (HIC) and Embedded Algorithm Controller (EAC) are reset to their standby states, ready for reading array data, during POR. CE# or OE# must go to V_{IH} before the end of POR (t_{VCS}).

At the end of POR the device conditions are:

- all internal configuration information is loaded,
- the device is in read mode,
- the Status Register is at default value,
- all bits in the DYB ASO are set to un-protect all sectors,
- the Write Buffer is loaded with all 1's,
- the EAC is in the standby state.

3.1.2 Low V_{CC} Write Inhibit

When V_{CC} is less than V_{LKO} , the HIC does not accept any write cycles and the EAC resets. This protects data during V_{CC} power-up and power-down. The system must provide the proper signals to the control pins to prevent unintentional writes when V_{CC} is greater than V_{LKO} .

3.2 Command Protection

Embedded Algorithms are initiated by writing command sequences into the EAC command memory. The command memory array is not readable by the host system and has no ASO. Each host interface write is a command or part of a command sequence to the device. The EAC examines the address and data in each write transfer to determine if the write is part of a legal command sequence. When a legal command sequence is complete the EAC will initiate the appropriate EA.

Writing incorrect address or data values, or writing them in an improper sequence, will generally result in the EAC returning to its Standby state. However, such an improper command sequence may place the device in an unknown state, in which case the system must write the reset command, or possibly provide a hardware reset by driving the RESET# signal Low, to return the EAC to its Standby state, ready for random read.

The address provided in each write may contain a bit pattern used to help identify the write as a command to the device. The upper portion of the address may also select the sector address on which the command operation is to be performed. The Sector Address (SA) includes A_{MAX} through A16 flash address bits (system byte address signals a_{max} through a17). A command bit pattern is located in A10 to A0 flash address bits (system byte address signals a11 through a1).

The data in each write may be: a bit pattern used to help identify the write as a command, a code that identifies the command operation to be performed, or supply information needed to perform the operation. See Table 7.1 on page 55 for a listing of all commands accepted by the device.

3.3 Secure Silicon Region (OTP)

The Secure Silicon Region (SSR) provides an extra flash memory area that can be programmed once and permanently protected from further changes i. e. it is a One Time Program (OTP) area. The SSR is 1024 bytes in length. It consists of 512 bytes for Factory Locked Secure Silicon Region and 512 bytes for Customer Locked Secure Silicon Region.



3.4 Sector Protection Methods

3.4.1 Write Protect Signal

If WP# = V_{IL} , the lowest or highest address sector is protected from program or erase operations independent of any other ASP configuration. Whether it is the lowest or highest sector depends on the device ordering option (model) selected. If WP# = V_{IH} , the lowest or highest address sector is not protected by the WP# signal but it may be protected by other aspects of ASP configuration. WP# has an internal pull-up; when unconnected, WP# is at V_{IH} .

3.4.2 ASP

Advanced Sector Protection (ASP) is a set of independent hardware and software methods used to disable or enable programming or erase operations, individually, in any or all sectors. This section describes the various methods of protecting data stored in the memory array. An overview of these methods is shown in Figure 3.1.



Figure 3.1 Advanced Sector Protection Overview

Every main flash array sector has a non-volatile (PPB) and a volatile (DYB) protection bit associated with it. When either bit is 0, the sector is protected from program and erase operations.

The PPB bits are protected from program and erase when the PPB Lock bit is 0. There are two methods for managing the state of the PPB Lock bit, Persistent Protection and Password Protection.



The Persistent Protection method sets the PPB Lock to 1 during POR or Hardware Reset so that the PPB bits are unprotected by a device reset. There is a command to clear the PPB Lock bit to 0 to protect the PPB bits. There is no command in the Persistent Protection method to set the PPB Lock bit therefore the PPB Lock bit will remain at 0 until the next power-off or hardware reset. The Persistent Protection method allows boot code the option of changing sector protection by programming or erasing the PPB, then protecting the PPB from further change for the remainder of normal system operation by clearing the PPB Lock bit. This is sometimes called Boot-code controlled sector protection.

The Password method clears the PPB Lock bit to 0 during POR or Hardware Reset to protect the PPB. A 64-bit password may be permanently programmed and hidden for the password method. A command can be used to provide a password for comparison with the hidden password. If the password matches the PPB Lock bit is set to 1 to unprotect the PPB. A command can be used to clear the PPB Lock bit to 0.

The selection of the PPB Lock management method is made by programming OTP bits in the Lock Register so as to permanently select the method used.

The Lock Register also contains OTP bits, for protecting the SSR.

The PPB bits are erased so that all main flash array sectors are unprotected when shipped from Cypress. The Secured Silicon Region can be factory protected or left unprotected depending on the ordering option (model) ordered.

3.4.3 PPB Lock

The Persistent Protection Bit Lock is a volatile bit for protecting all PPB bits. When cleared to 0, it locks all PPBs and when set to 1, it allows the PPBs to be changed. There is only one PPB Lock Bit per device.

The PPB Lock command is used to clear the bit to 0. The PPB Lock Bit must be cleared to 0 only after all the PPBs are configured to the desired settings.

In Persistent Protection mode, the PPB Lock is set to 1 during POR or a hardware reset. When cleared, no software command sequence can set the PPB Lock, only another hardware reset or power-up can set the PPB Lock bit.

In the Password Protection mode, the PPB Lock is cleared to 0 during POR or a hardware reset. The PPB Lock can only set to 1 by the Password Unlock command sequence. The PPB Lock can be cleared by the PPB Lock Bit Clear command.

3.4.4 Persistent Protection Bits (PPB)

The Persistent Protection Bits (PPB) are located in a separate nonvolatile flash array. One of the PPB bits is assigned to each sector. When a PPB is 0 its related sector is protected from program and erase operations. The PPB are programmed individually but must be erased as a group, similar to the way individual words may be programmed in the main array but an entire sector must be erased at the same time. Preprogramming and verification prior to erasure are handled by the EAC.

Programming a PPB bit requires the typical word programming time. During a PPB bit programming operation or PPB bit erasing, Data polling Status DQ6 Toggle Bit I will toggle until the operation is complete. Erasing all the PPBs requires typical sector erase time.

If the PPB Lock is 0, the PPB Program or erase commands do not execute and time-out without programming or erasing the PPB.

The protection state of a PPB for a given sector can be verified by executing a PPB Status Read command when entered in the PPB ASO.

3.4.5 Dynamic Protection Bits (DYB)

Dynamic Protection Bits are volatile and unique for each sector and can be individually modified. DYBs only control protection for sectors that have their PPBs erased. By issuing the DYB Set or Clear command sequences, the DYB are set to 0 or cleared to 1, thus placing each sector in the protected or unprotected state respectively, if the PPB for the Sector is 1. This feature allows software to easily protect sectors against inadvertent changes, yet does not prevent the easy removal of protection when changes are needed.

The DYB can be set to 0 or cleared to 1 as often as needed.



3.4.6 Sector Protection States Summary

Each sector can be in one of the following protection states:

- Unlocked The sector is unprotected and protection can be changed by a simple command. The protection state defaults to unprotected after a power cycle or hardware reset.
- Dynamically Locked A sector is protected and protection can be changed by a simple command. The protection state is not saved across a power cycle or hardware reset.
- Persistently Locked A sector is protected and protection can only be changed if the PPB Lock Bit is set to 1. The protection state is non-volatile and saved across a power cycle or hardware reset. Changing the protection state requires programming or erase of the PPB bits.

	Protection Bit Values	5	Soctor State
PPB Lock	PPB	DYB	- Sector State
1	1	1	Unprotected - PPB and DYB are changeable
1	1	0	Protected - PPB and DYB are changeable
1	0	1	Protected - PPB and DYB are changeable
1	0	0	Protected - PPB and DYB are changeable
0	1	1	Unprotected - PPB not changeable, DYB is changeable
0	1	0	Protected - PPB not changeable, DYB is changeable
0	0	1	Protected - PPB not changeable, DYB is changeable
0	0	0	Protected - PPB not changeable, DYB is changeable

Table 3.1 Sector Protection States

3.4.7 Lock Register

The Lock Register holds the non-volatile OTP bits for controlling protection of the SSR, and determining the PPB Lock bit management method (protection mode).

Bit	Default Value	Default Value Name		
15-9	1	Reserved		
8	0	Reserved		
7	Х	Reserved		
6	1	SSR Region 1 (Customer) Lock Bit		
5	1	Reserved		
4	1	Reserved		
3	1	Reserved		
2	1	Password Protection Mode Lock Bit		
1	1	Persistent Protection Mode Lock Bit		
0	0	SSR Region 0 (Factory) Lock Bit		

Table 3.2 Lock Register

The Secure Silicon Region (SSR) protection bits must be used with caution, as once locked, there is no procedure available for unlocking the protected portion of the Secure Silicon Region and none of the bits in the protected Secure Silicon Region memory space can be modified in any way. Once the Secure Silicon Region area is protected, any further attempts to program in the area will fail with status indicating the area being programmed is protected. The Region 0 Indicator Bit is located in the Lock Register at bit location 0 and Region 1 in bit location 6.



As shipped from the factory, all devices default to the Persistent Protection method, with all sectors unprotected, when power is applied. The device programmer or host system can then choose which sector protection method to use. Programming either of the following two, one-time programmable, non-volatile bits, locks the part permanently in that mode:

- Persistent Protection Mode Lock Bit (DQ1)
- Password Protection Mode Lock Bit (DQ2)

If both lock bits are selected to be programmed at the same time, the operation will abort. Once the Password Mode Lock Bit is programmed, the Persistent Mode Lock Bit is permanently disabled and no changes to the protection scheme are allowed. Similarly, if the Persistent Mode Lock Bit is programmed, the Password Mode is permanently disabled.

If the password mode is to be chosen, the password must be programmed prior to setting the corresponding lock register bit. Setting the Password Protection Mode Lock Bit is programmed, a power cycle, hardware reset, or PPB Lock Bit Set command is required to set the PPB Lock bit to 0 to protect the PPB array.

The programming time of the Lock Register is the same as the typical word programming time. During a Lock Register programming EA, Data polling Status DQ6 Toggle Bit I will toggle until the programming has completed. The system can also determine the status of the lock register programming by reading the Status Register. See Status Register on page 34 for information on these status bits.

The user is not required to program DQ2 or DQ1, and DQ6 or DQ0 bits at the same time. This allows the user to lock the SSR before or after choosing the device protection scheme. When programming the Lock Bits, the Reserved Bits must be 1 (masked).

3.4.8 Persistent Protection Mode

The Persistent Protection method sets the PPB Lock to 1 during POR or Hardware Reset so that the PPB bits are unprotected by a device reset. There is a command to clear the PPB Lock bit to 0 to protect the PPB. There is no command in the Persistent Protection method to set the PPB Lock bit to 1 therefore the PPB Lock bit will remain at 0 until the next power-off or hardware reset.

3.4.9 Password Protection Mode

3.4.9.1 PPB Password Protection Mode

PPB Password Protection Mode allows an even higher level of security than the Persistent Sector Protection Mode, by requiring a 64-bit password for setting the PPB Lock. In addition to this password requirement, after power up and reset, the PPB Lock is cleared to 0 to ensure protection at power-up. Successful execution of the Password Unlock command by entering the entire password sets the PPB Lock to 1, allowing for sector PPB modifications.

Password Protection Notes:

- The Password Program Command is only capable of programming 0's.
- The password is all 1's when shipped from Cypress. It is located in its own memory space and is accessible through the use of the Password Program and Password Read commands.
- All 64-bit password combinations are valid as a password.
- Once the Password is programmed and verified, the Password Mode Locking Bit must be set in order to prevent reading or modification of the password.
- The Password Mode Lock Bit, once programmed, prevents reading the 64-bit password on the data bus and further password programming. All further program and read commands to the password region are disabled (data is read as 1's) and these commands are ignored. There is no means to verify what the password is after the Password Protection Mode Lock Bit is programmed. Password verification is only allowed before selecting the Password Protection mode.
- The Password Mode Lock Bit is not erasable.
- The exact password must be entered in order for the unlocking function to occur.
- The addresses can be loaded in any order but all 4 words are required for a successful match to occur.



- The Sector Addresses and Word Line Addresses are compared while the password address/data are loaded. If the Sector Address don't match than the error will be reported at the end of that write cycle. The status register will return to the ready state with the Program Status Bit set to 1, Program Status Register Bit set to 1, and Write Buffer Abort Status Bit set to 1 indicating a failed programming operation. It is a failure to change the state of the PPB Lock bit because it is still protected by the lack of a valid password. The data polling status will remain active, with DQ7 set to the complement of the DQ7 bit in the last word of the password unlock command, and DQ6 toggling. RY/BY# will remain low.
- The specific address and data are compared after the Program Buffer To Flash command has been given. If they don't match to the internal set value than the status register will return to the ready state with the Program Status Bit set to 1 and Program Status Register Bit set to 1 indicating a failed programming operation. It is a failure to change the state of the PPB Lock bit because it is still protected by the lack of a valid password. The data polling status will remain active, with DQ7 set to the complement of the DQ7 bit in the last word of the password unlock command, and DQ6 toggling. RY/BY# will remain low.
- The device requires approximately 100 µs for setting the PPB Lock after the valid 64-bit password is given to the device.
- The Password Unlock command cannot be accepted any faster than once every 100 µs ± 20 µs. This makes it take an unreasonably long time (58 million years) for a hacker to run through all the 64-bit combinations in an attempt to correctly match a password. The EA status checking methods may be used to determine when the EAC is ready to accept a new password command.
- If the password is lost after setting the Password Mode Lock Bit, there is no way to clear the PPB Lock.



4. Read Operations

4.1 Asynchronous Read

Each read access may be made to any location in the memory (random access). Each random access is self-timed with the same latency from CE# or address to valid data (t_{ACC} or t_{CE}).

4.2 Page Mode Read

Each random read accesses an entire 32-byte Page in parallel. Subsequent reads within the same Page have faster read access speed. The Page is selected by the higher address bits (A_{MAX} -A4), while the specific word of that page is selected by the least significant address bits A3-A0. The higher address bits are kept constant and only A3-A0 changed to select a different word in the same Page. This is an asynchronous access with data appearing on DQ15-DQ0 when CE# remains Low, OE# remains Low, and the asynchronous Page access time (t_{PACC}) is satisfied. If CE# goes High and returns Low for a subsequent access, a random read access is performed and time is required (t_{ACC} or t_{CE}).



5. Embedded Operations

5.1 Embedded Algorithm Controller (EAC)

The EAC takes commands from the host system for programming and erasing the flash memory array and performs all the complex operations needed to change the non-volatile memory state. This frees the host system from any need to manage the program and erase processes.

There are four EAC operation categories:

- Standby (Read Mode)
- Address Space Switching
- Embedded Algorithms (EA)
- Advanced Sector Protection (ASP) Management

5.1.1 EAC Standby

In the standby mode current consumption is greatly reduced. The EAC enters its standby mode when no command is being processed and no Embedded Algorithm is in progress. If the device is deselected

(CE# = High) during an Embedded Algorithm, the device still draws active current until the operation is completed (I_{CC3}). I_{CC4} in DC Characteristics on page 72 represents the standby current specification when both the Host Interface and EAC are in their Standby state.

5.1.2 Address Space Switching

Writing specific address and data sequences (command sequences) switch the memory device address space from the main flash array to one of the Address Space Overlays (ASO).

Embedded Algorithms operate on the information visible in the currently active (entered) ASO. The system continues to have access to the ASO until the system issues an ASO Exit command, performs a Hardware RESET, or until power is removed from the device. An ASO Exit Command switches from an ASO back to the main flash array address space. The commands accepted when a particular ASO is entered are listed between the ASO enter and exit commands in the command definitions table. See Command Summary on page 55 for address and data requirements for all command sequences.

5.1.3 Embedded Algorithms (EA)

Changing the non-volatile data in the memory array requires a complex sequence of operations that are called Embedded Algorithms (EA). The algorithms are managed entirely by the device internal Embedded Algorithm Controller (EAC). The main algorithms perform programming and erasing of the main array data and the ASO's. The host system writes command codes to the flash device address space. The EAC receives the commands, performs all the necessary steps to complete the command, and provides status information during the progress of an EA.



5.2 **Program and Erase Summary**

Flash data bits are erased in parallel in a large group called a sector. The Erase operation places each data bit in the sector in the logical 1 state (High). Flash data bits may be individually programmed from the erased 1 state to the programmed logical 0 (low) state. A data bit of 0 cannot be programmed back to a 1. A succeeding read shows that the data is still 0. Only erase operations can convert a 0 to a 1. Programming the same word location more than once with different 0 bits will result in the logical AND of the previous data and the new data being programmed.

The duration of program and erase operations is shown in Embedded Algorithm Performance Table on page 43.

Program and erase operations may be suspended.

- An erase operation may be suspended to allow either programming or reading of another sector (not in the erase sector). No other erase operation can be started during an erase suspend.
- A program operation may be suspended to allow reading of another location (not in the Line being programmed).
- No other program or erase operation may be started during a suspended program operation program or erase commands will be ignored during a suspended program operation.
- After an intervening program operation or read access is complete the suspended erase or program operation may be resumed. The resume can happen at any time after the suspend assuming the device is not in the process of executing another command.
- Program and Erase operations may be interrupted as often as necessary but in order for a program or erase operation to progress to completion there must be some periods of time between resume and the next suspend commands greater than or equal to t_{PRS} or t_{ERS} in Embedded Algorithm Performance Table on page 43.
- When an Embedded Algorithm (EA) is complete, the EAC returns to the operation state and address space from which the EA was started (Erase Suspend or EAC Standby).

The system can determine the status of a program or erase operation by reading the Status Register or using Data Polling Status. Refer to Status Register on page 34 for information on these status bits. Refer to Data Polling Status on page 35 for more information.

Any commands written to the device during the Embedded Program Algorithm are ignored except the Program Suspend, and Status Read command.

Any commands written to the device during the Embedded Erase Algorithm are ignored except Erase Suspend and Status Read command.

A hardware reset immediately terminates any in progress program / erase operation and returns to read mode after t_{RPH} time. The terminated operation should be reinitiated once the device has returned to the idle state, to ensure data integrity.

For performance and reliability reasons reading and programming is internally done on full 32-byte Pages.

I_{CC3} in DC Characteristics on page 72 represents the active current specification for a write (Embedded Algorithm) operation.

5.2.1 Program Granularity

The S29GL-S supports two methods of programming, Word or Write Buffer Programming. Each Page can be programmed by either method. Pages programmed by different methods may be mixed within a Line for the Industrial Temperature version (-40 °C to +85 °C). For the In-Cabin version (-40 °C to +105 °C) the device will only support one programming operation on each 32-byte page between erase operations and Single Word Programming command is not supported.

Word programming examines the data word supplied by the command and programs 0's in the addressed memory array word to match the 0's in the command data word.

Write Buffer Programming examines the write buffer and programs 0's in the addressed memory array Pages to match the 0's in the write buffer. The write buffer does not need to be completely filled with data. It is allowed to program as little as a single bit, several bits, a single word, a few words, a Page, multiple Pages, or the entire buffer as one programming operation. Use of the write buffer method reduces host system overhead in writing program commands and reduces memory device internal overhead in programming operations to make Write Buffer Programming more efficient and thus faster than programming individual words with the Word Programming command.



5.2.2 Incremental Programming

The same word location may be programmed more than once, by either the Word or Write Buffer Programming methods, to incrementally change 1's to 0's. Note that if additional programming is performed on a page its ECC coverage is disabled.

5.3 Automatic ECC

5.3.1 ECC Overview

The Automatic ECC feature works transparently with normal program, erase, and read operations. As the device transfers each Page of data from the Write Buffer is to the memory array, internal ECC logic programs ECC Code for the Page into a portion of the memory array that is not visible to the host system. The device evaluates the Page data and the ECC Code during each initial Page access. If needed, the internal ECC logic corrects a one bit error during the initial access.

Programming more than once to a particular Page will disable the ECC function for that Page. The ECC function will remain disabled for that Page until the next time the host system erases the Sector containing that Page. The host system may read data stored in that Page following multiple programming operations; however, ECC is disabled and an error in that Page will not be detected or corrected.

5.3.2 Program and Erase Summary

For performance and reliability reasons, GL-S devices perform reading and programming on full 32-byte Pages in parallel. The GL-S device provides ECC on each Page by adding an ECC Code to each Page when it is first programmed. The ECC Code is automatic and transparent to the host system.

5.3.3 ECC Implementation

Each 32-byte Page in the main flash array and OTP regions features an associated ECC Code. The ECC Code, in combination with ECC logic, is able to detect and correct any single bit error found in a Page during a read access.

The first Write Buffer program operation applied to a Page programs the ECC Code for that Page. Subsequent programming operations that occur more than once on a particular Page disable the ECC function for that Page. This allows bit or word programming; however, note that multiple programming operations to the same Page will disable the ECC function on the Page where incremental programming occurs. An erase of the Sector containing a Page with ECC disabled will re-enable the ECC function for that Page.

The ECC function is automatic and transparent to the user. The transparency of the Automatic ECC function enhances data integrity for typical programming operations that write data once to each Page. The ECC function also facilitates software compatibility to previous generations of GL Family products by allowing single word programming and bit walking where the same Page or word is programmed more than once. When a Page has Automatic ECC disabled, the ECC function will not detect or correct an error on a data read from that Page.

5.3.4 Word Programming

Word programming programs a single word anywhere in the main Flash Memory Array. Programming multiple words in the same 32-byte page disables Automatic ECC protection on that Page. A sector erase of the sector containing that Page will re-enable Automatic ECC following word programming on that Page.

5.3.5 Write Buffer Programming

Each Write Buffer Program operation allows for programming of 1 bit up to 512 bytes. A 32-byte Page is the smallest program granularity that features Automatic ECC protection. Programming the same Page more than once will disable the Automatic ECC on that Page. Cypress recommends that a Write Buffer programming operation program multiple Pages in an operation and write each Page only once. This keeps the Automatic ECC protection enabled on each Page. For the very best performance, program in full Lines of 512 bytes aligned on 512-byte boundaries.



5.4 Command Set

5.4.1 Program Methods

5.4.1.1 Word Programming

Word programming is used to program a single word anywhere in the main Flash Memory Array.

The Word Programming command is a four-write-cycle sequence. The program command sequence is initiated by writing two unlock write cycles, followed by the program set up command. The program address and data are written next, which in turn initiate the Embedded Word Program algorithm. The system is not required to provide further controls or timing. The device automatically generates the program pulses and verifies the programmed cell margin internally. When the Embedded Word Program algorithm is complete, the EAC then returns to its standby mode.

The system can determine the status of the program operation by using Data Polling Status, reading the Status Register, or monitoring the RY/BY# output. See Status Register on page 34 for information on these status bits. See Data Polling Status on page 35 for information on these status bits. See Figure 5.1 on page 23 for a diagram of the programming operation.

Any commands other than Program Suspend written to the device during the Embedded Program algorithm are ignored. Note that a hardware reset (RESET# = V_{IL}) immediately terminates the programming operation and returns the device to read mode after t_{RPH} time. To ensure data integrity, the Program command sequence should be reinitiated once the device has completed the hardware reset operation.

A modified version of the Word Programming command, without unlock write cycles, is used for programming when entered into the Lock Register, Password, and PPBASOs. The same command is used to change volatile bits when entered in to the PPB Lock, and DYB ASOs. See Table 7.1 on page 55 for program command sequences.



Figure 5.1 Word Program Operation



5.4.1.2 Write Buffer Programming

A write buffer is used to program data within a 512-byte address range aligned on a 512-byte boundary (Line). Thus, a full Write Buffer Programming operation must be aligned on a Line boundary. Programming operations of less than a full 512 bytes may start on any word boundary but may not cross a Line boundary. At the start of a Write Buffer programming operation all bit locations in the buffer are all 1's (FFFFh words) thus any locations not loaded will retain the existing data. See Product Overview on page 4 for information on address map.

Write Buffer Programming allows up to 512 bytes to be programmed in one operation. It is possible to program from 1 bit up to 512 bytes in each Write Buffer Programming operation. It is recommended that a multiple of Pages be written and each Page written only once. For the very best performance, programming should be done in full Lines of 512 bytes aligned on 512-byte boundaries.

Write Buffer Programming is supported only in the main flash array or the SSR ASO.

The Write Buffer Programming operation is initiated by first writing two unlock cycles. This is followed by a third write cycle of the Write to Buffer command with the Sector Address (SA), in which programming is to occur. Next, the system writes the number of word locations minus 1. This tells the device how many write buffer addresses are loaded with data and therefore when to expect the Program Buffer to flash confirm command. The Sector Address must match in the Write to Buffer command and the Write Word Count command. The Sector to be programmed must be unlocked (unprotected).

The system then writes the starting address / data combination. This starting address is the first address / data pair to be programmed, and selects the write-buffer-Line address. The Sector address must match the Write to Buffer Sector Address or the operation will abort and return to the initiating state. All subsequent address / data pairs must be in sequential order. All write buffer addresses must be within the same Line. If the system attempts to load data outside this range, the operation will abort and return to the initiating state.

The counter decrements for each data load operation. Note that while counting down the data writes, every write is considered to be data being loaded into the write buffer. No commands are possible during the write buffer loading period. The only way to stop loading the write buffer is to write with an address that is outside the Line of the programming operation. This invalid address will immediately abort the Write to Buffer command.

Once the specified number of write buffer locations has been loaded, the system must then write the Program Buffer to Flash command at the Sector Address. The device then goes busy. The Embedded Program algorithm automatically programs and verifies the data for the correct data pattern. The system is not required to provide any controls or timings during these operations. If an incorrect number of write buffer locations have been loaded the operation will abort and return to the initiating state. The abort occurs when anything other than the Program Buffer to Flash is written when that command is expected at the end of the word count.

The write-buffer embedded programming operation can be suspended using the Program Suspend command. When the Embedded Program algorithm is complete, the EAC then returns to the EAC standby or Erase Suspend standby state where the programming operation was started.

The system can determine the status of the program operation by using Data Polling Status, reading the Status Register, or monitoring the RY/BY# output. See Status Register on page 34 for information on these status bits. See Data Polling Status on page 35 for information on these status bits. See Figure 5.2 on page 25 for a diagram of the programming operation.

The Write Buffer Programming Sequence will be Aborted under the following conditions:

- Load a Word Count value greater than the buffer size (255).
- Write an address that is outside the Line provided in the Write to Buffer command.
- The Program Buffer to Flash command is not issued after the Write Word Count number of data words is loaded.

When any of the conditions that cause an abort of write buffer command occur the abort will happen immediately after the offending condition, and will indicate a Program Fail in the Status Register at bit location 4 (PSB = 1) due to Write Buffer Abort bit location 3 (WBASB = 1). The next successful program operation will clear the failure status or a Clear Status Register may be issued to clear the PSB status bit.

The Write Buffer Programming Sequence can be stopped by the following: Hardware Reset or Power cycle. However, these using either of these methods may leave the area being programmed in an intermediate state with invalid or unstable data values. In this case the same area will need to be reprogrammed with the same data or erased to ensure data values are properly programmed or erased.




Figure 5.2 Write Buffer Programming Operation with Data Polling Status

Notes:

- 1. DQ7 should be rechecked even if DQ5 = 1 because DQ7 may change simultaneously with DQ5.
- If this flowchart location was reached because DQ5 = 1, then the device FAILED. If this flowchart location was reached because DQ1 = 1, then the Write Buffer
 operation was ABORTED. In either case the proper RESET command must be written to the device to return the device to READ mode. Write-Buffer-ProgrammingAbort-Rest if DQ1 = 1, either Software RESET or Write-Buffer-Programming-Abort-Reset if DQ5 = 1.
- 3. See Table 7.1 on page 55 for the command sequence as required for Write Buffer Programming.
- 4. When Sector Address is specified, any address in the selected sector is acceptable. However, when loading Write-Buffer address locations with data, all addresses MUST fall within the selected Write-Buffer Page.





Figure 5.3 Write Buffer Programming Operation with Status Register

Notes:

1. See Table 7.1 on page 55 for the command sequence as required for Write Buffer Programming.

2. When Sector Address is specified, any address in the selected sector is acceptable. However, when loading Write-Buffer address locations with data, all addresses MUST fall within the selected Write-Buffer Page.



Table 5.1 Write Buffer Programming Command Sequence

Sequence	Address	Data	Comment
Issue Unlock Command 1	555/AAA	AA	
Issue Unlock Command 2	2AA/555	55	
Issue Write to Buffer Command at Sector Address	SA	0025h	
Issue Number of Locations at Sector Address	SA	WC	WC = number of words to program - 1
Example: WC of 0 = 1 words to pgm			
WC of 1 = 2 words to pgm			
Load Starting Address / Data pair	Starting Address	PD	Selects Write-Buffer-Page and loads first Address/Data Pair.
Load next Address / Data pair	WBL	PD	All addresses MUST be within the selected write-buffer- page boundaries, and have to be loaded in sequential order.
Load LAST Address/Data pair	WBL	PD	All addresses MUST be within the selected write-buffer- page boundaries, and have to be loaded in sequential order.
Issue Write Buffer Program Confirm at Sector Address	SA	0029h	This command MUST follow the last write buffer location loaded, or the operation will ABORT.
Device goes busy.			

Legend:

SA = Sector Address (Non-Sector Address bits are don't care. Any address within the Sector is sufficient.)

WBL = Write Buffer Location (MUST be within the boundaries of the Write-Buffer-Line specified by the Starting Address.)

WC =Word Count

PD = Program Data

5.4.2 Program Suspend / Program Resume Commands

The Program Suspend command allows the system to interrupt an embedded programming operation so that data can read from any non-suspended Line. When the Program Suspend command is written during a programming process, the device halts the programming operation within t_{PSL} (program suspend latency) and updates the status bits. Addresses are don't-cares when writing the Program Suspend command.

There are two commands available for program suspend. The legacy combined Erase / Program suspend command (B0h command code) and the separate Program Suspend command (51h command code). There are also two commands for Program resume. The legacy combined Erase / Program resume command (30h command code) and the separate Program Resume command (50h command code). It is recommended to use the separate program suspend and resume commands for programming and use the legacy combined command only for erase suspend and resume.

After the programming operation has been suspended, the system can read array data from any non-suspended Line. The Program Suspend command may also be issued during a programming operation while an erase is suspended. In this case, data may be read from any addresses not in Erase Suspend or Program Suspend.

After the Program Resume command is written, the device reverts to programming and the status bits are updated. The system can determine the status of the program operation by reading the Status Register or using Data Polling. Refer to Status Register on page 34 for information on these status bits. Refer to Data Polling Status on page 35 for more information.

Accesses and commands that are valid during Program Suspend are:

- Read to any other non-erase-suspended sector
- Read to any other non-program-suspended Line
- Status Read command
- Exit ASO or Command Set Exit
- Program Resume command



The system must write the Program Resume command to exit the Program Suspend mode and continue the programming operation. Further writes of the Program Resume command are ignored. Another Program Suspend command can be written after the device has resumed programming.

Program operations can be interrupted as often as necessary but in order for a program operation to progress to completion there must be some periods of time between resume and the next suspend command greater than or equal to t_{PRS} in Embedded Algorithm Controller (EAC) on page 20.

Program suspend and resume is not supported while entered in an ASO. While in program suspend entry into ASO is not supported.

5.4.3 Blank Check

The Blank Check command will confirm if the selected main flash array sector is erased. The Blank Check command does not allow for reads to the array during the Blank Check. Reads to the array while this command is executing will return unknown data.

To initiate a Blank Check on a Sector, write 33h to address 555h in the Sector, while the EAC is in the standby state

The Blank Check command may not be written while the device is actively programming or erasing or suspended.

Use the Status Register read to confirm if the device is still busy and when complete if the sector is blank or not. Bit 7 of the Status Register will show if the device is performing a Blank Check (similar to an erase operation). Bit 5 of the Status Register will be cleared to 0 if the sector is erased and set to 1 if not erased.

As soon as any bit is found to not be erased, the device will halt the operation and report the results.

Once the Blank Check is completed, the EAC will return to the Standby State.

5.4.4 Erase Methods

5.4.4.1 Chip Erase

The chip erase function erases the entire main Flash Memory Array. The device does not require the system to preprogram prior to erase. The Embedded Erase algorithm automatically programs and verifies the entire memory for an all 0 data pattern prior to electrical erase. After a successful chip erase, all locations within the device contain FFFFh. The system is not required to provide any controls or timings during these operations. The chip erase command sequence is initiated by writing two unlock cycles, followed by a set up command. Two additional unlock write cycles are then followed by the chip erase command, which in turn invokes the Embedded Erase algorithm. When WE# goes high, at the end of the 6th cycle, the RY/BY# goes low.

When the Embedded Erase algorithm is complete, the EAC returns to the standby state. Note that while the Embedded Erase operation is in progress, the system can not read data from the device. The system can determine the status of the erase operation by reading RY/BY#, the Status Register or using Data Polling. Refer to Status Register on page 34 for information on these status bits. Refer to Data Polling Status on page 35 for more information.

Once the chip erase operation has begun, only a Status Read, Hardware RESET or Power cycle are valid. All other commands are ignored. However, a Hardware Reset or Power Cycle immediately terminates the erase operation and returns to read mode after t_{RPH} time. If a chip erase operation is terminated, the chip erase command sequence must be reinitiated once the device has returned to the idle state to ensure data integrity.

See Table 5.4 on page 43, Asynchronous Write Operations on page 82 and Alternate CE# Controlled Write Operations on page 88 for parameters and timing diagrams.

Sectors protected by the ASP DYB and PPB lock bits will not be erased. See ASP on page 14. If a sector is protected during chip erase, chip erase will skip the protected sector and continue with next sector erase. The status register erase status bit and sector lock bit are not set to 1 by a failed erase on a protected sector.



5.4.4.2 Sector Erase

The sector erase function erases one sector in the memory array. The device does not require the system to preprogram prior to erase. The Embedded Erase algorithm automatically programs and verifies the entire sector for an all 0 data pattern prior to electrical erase. After a successful sector erase, all locations within the erased sector contain FFFFh. The system is not required to provide any controls or timings during these operations. The sector erase command sequence is initiated by writing two unlock cycles, followed by a set up command. Two additional unlock write cycles are then followed by the address of the sector to be erased, and the sector erase command. When WE# goes high, at the end of the 6th cycle, the RY/BY# goes low.

The system can determine the status of the erase operation by reading the Status Register or using Data Polling. Refer to Status Register on page 34 for information on these status bits. Refer to Data Polling Status on page 35 for more information.

Once the sector erase operation has begun, the Status Register Read and Erase Suspend commands are valid. All other commands are ignored. However, note that a hardware reset immediately terminates the erase operation and returns to read mode after t_{RPH} time. If a sector erase operation is terminated, the sector erase command sequence must be reinitiated once the device has reset operation to ensure data integrity.

See Embedded Algorithm Controller (EAC) on page 20 for parameters and timing diagrams.

Sectors protected by the ASP DYB and PPB lock bits will not be erased. See ASP on page 14.



Figure 5.4 Sector Erase Operation



5.4.5 Erase Suspend / Erase Resume

The Erase Suspend command allows the system to interrupt a sector erase operation and then read data from, or program data to, the main flash array. This command is valid only during sector erase or program operation. The Erase Suspend command is ignored if written during the chip erase operation.

When the Erase Suspend command is written during the sector erase operation, the device requires a maximum of t_{ESL} (erase suspend latency) to suspend the erase operation and update the status bits.

After the erase operation has been suspended, the part enters the erase-suspend mode. The system can read data from or program data to the main flash array. Reading at any address within erase-suspended sectors produces undetermined data. The system can determine if a sector is actively erasing or is erase-suspended by reading the Status Register or using Data Polling. Refer to Status Register on page 34 for information on these status bits. Refer to Data Polling Status on page 35 for more information.

After an erase-suspended program operation is complete, the EAC returns to the erase-suspend state. The system can determine the status of the program operation by reading the Status Register, just as in the standard program operation.

If a program failure occurs during erase suspend the Clear or Reset commands will return the device to the erase suspended state. Erase will need to be resumed and completed before again trying to program the memory array.

Accesses and commands that are valid during Erase Suspend are:

- Read to any other non-suspended sector
- Program to any other non-suspended sector
- Status Register Read
- Status Register Clear
- Enter DYB ASO
- DYB Set
- DYB Clear
- DYB Status Read
- Exit ASO or Command Set Exit
- Erase Resume command

To resume the sector erase operation, the system must write the Erase Resume command. The device will revert to erasing and the status bits will be updated. Further writes of the Resume command are ignored. Another Erase Suspend command can be written after the chip has resumed erasing.

Erase suspend and resume is not supported while entered in an ASO. While in erase suspend entry into ASO is not supported.



5.4.6 ASO Entry and Exit

5.4.6.1 ID-CFI ASO

The system can access the ID-CFI ASO by issuing the ID-CFI Entry command sequence during Read Mode. This entry command uses the Sector Address (SA) in the command to determine which sector will be overlaid and which sector's protection state is reported in word location 2h. See the detail description Table 7.2 on page 58.

The ID-CFI ASO allows the following activities:

- Read ID-CFI ASO, using the same SA as used in the entry command.
- Read Sector Protection State at Sector Address (SA) + 2h. Location 2h provides volatile information on the current state of sector protection for the sector addressed. Bit 0 of the word at location 2h shows the logical NAND of the PPB and DYB bits related to the addressed sector such that if the sector is protected by either the PPB=0 or the DYB=0 bit for that sector the state shown is protected. (1= Sector protected, 0= Sector unprotected). This protection state is shown only for the SA selected when entering ID-CFI ASO. Reading other SA provides undefined data. To read a different SA protection state ASO exit command must be used and then enter ID-CFI ASO again with the new SA.
- ASO Exit.

The following is a C source code example of using the CFI Entry and Exit functions. Refer to the *Cypress Low Level Driver User's Guide* (available on www.cypress.com) for general information on Cypress flash memory software development guidelines.

```
/* Example: CFI Entry command */
*( (UINT16 *)base_addr + 0x55 ) = 0x0098; /* write CFI entry command */
/* Example: CFI Exit command */
*( (UINT16 *)base_addr + 0x000 ) = 0x00F0; /* write cfi exit command */
```

5.4.6.2 Status Register ASO

The Status Register ASO contains a single word of registered volatile status for Embedded Algorithms. When the Status Register read command is issued, the current status is captured (by the rising edge of WE#) into the register and the ASO is entered. The Status Register content appears on all word locations. The first read access exits the Status Register ASO (with the rising edge of CE# or OE#) and returns to the address space map in use when the Status Register read command was issued. Write commands will not exit the Status Register ASO state.

5.4.6.3 Secure Silicon Region ASO

The system can access the Secure Silicon Region by issuing the Secure Silicon Region Entry command sequence during Read Mode. This entry command uses the Sector Address (SA) in the command to determine which sector will be overlaid.

The Secure Silicon Region ASO allows the following activities:

- Read Secure Silicon Regions.
- Programming the customer Secure Silicon Region is allowed using the Word or Write Buffer Programming commands.
- ASO Exit using legacy Secure Silicon Exit command for backward software compatibility.
- ASO Exit using the common exit command for all ASO alternative for a consistent exit method.



5.4.6.4 Lock Register ASO

The system can access the Lock Register by issuing the Lock Register entry command sequence during Read Mode. This entry command does not use a sector address from the entry command. The Lock Register appears at word location 0 in the device address space. All other locations in the device address space are undefined.

The Lock Register ASO allows the following activities:

- Read Lock Register, using device address location 0.
- Program the customer Lock Register using a modified Word Programming command.
- ASO Exit using legacy Command Set Exit command for backward software compatibility.
- ASO Exit using the common exit command for all ASO alternative for a consistent exit method.

5.4.6.5 Password ASO

The system can access the Password ASO by issuing the Password entry command sequence during Read Mode. This entry command does not use a sector address from the entry command. The Password appears at word locations 0 to 3 in the device address space. All other locations in the device address space are undefined.

The Password ASO allows the following activities:

- Read Password, using device address location 0 to 3.
- Program the Password using a modified Word Programming command.
- Unlock the PPB Lock bit with the Password Unlock command.
- ASO Exit using legacy Command Set Exit command for backward software compatibility.
- ASO Exit using the common exit command for all ASO alternative for a consistent exit method.

5.4.6.6 PPB ASO

The system can access the PPB ASO by issuing the PPB entry command sequence during Read Mode. This entry command does not use a sector address from the entry command. The PPB bit for a sector appears in bit 0 of all word locations in the sector.

The PPB ASO allows the following activities:

- Read PPB protection status of a sector in bit 0 of any word in the sector.
- Program the PPB bit using a modified Word Programming command.
- Erase all PPB bits with the PPB erase command.
- ASO Exit using legacy Command Set Exit command for backward software compatibility.
- ASO Exit using the common exit command for all ASO alternative for a consistent exit method.

5.4.6.7 PPB Lock ASO

The system can access the PPB Lock ASO by issuing the PPB Lock entry command sequence during Read Mode. This entry command does not use a sector address from the entry command. The global PPB Lock bit appears in bit 0 of all word locations in the device.

The PPB Lock ASO allows the following activities:

- Read PPB Lock protection status in bit 0 of any word in the device address space.
- Set the PPB Lock bit using a modified Word Programming command.
- ASO Exit using legacy Command Set Exit command for backward software compatibility.
- ASO Exit using the common exit command for all ASO alternative for a consistent exit method.



5.4.6.8 DYB ASO

The system can access the DYB ASO by issuing the DYB entry command sequence during Read Mode. This entry command does not use a sector address from the entry command. The DYB bit for a sector appears in bit 0 of all word locations in the sector.

The DYB ASO allows the following activities:

- Read DYB protection status of a sector in bit 0 of any word in the sector.
- Set the DYB bit using a modified Word Programming command.
- Clear the DYB bit using a modified Word Programming command.
- ASO Exit using legacy Command Set Exit command for backward software compatibility.
- ASO Exit using the common exit command for all ASO alternative for a consistent exit method.

5.4.6.9 Software (Command) Reset / ASO exit

Software reset is part of the command set (See Table 7.1 on page 55) that also returns the EAC to standby state and must be used for the following conditions:

- Exit ID/CFI mode
- Clear timeout bit (DQ5) for data polling when timeout occurs

Software Reset does not affect EA mode. Reset commands are ignored once programming or erasure has begun, until the operation is complete. Software Reset does not affect outputs; it serves primarily to return to Read Mode from an ASO mode or from a failed program or erase operation.

Software Reset may cause a return to Read Mode from undefined states that might result from invalid command sequences. However, a Hardware Reset may be required to return to normal operation from some undefined states.

There is no software reset latency requirement. The reset command is executed during the t_{WPH} period.

5.4.6.10 ECC Status ASO

The system can access the ECC Status ASO by issuing the ECC Status entry command sequence during Read Mode. The contents of the ECC Status ASO indicates, for the selected ECC page, whether ECC protection has corrected an error in the eight-bit error correction code or the 16 Words of data in the ECC page.

The ECC Status ASO allows the following activities:

Read ECC Status for the selected page.



5.5 Status Monitoring

There are three methods for monitoring EA status. Previous generations of the S29GL flash family used the methods called Data Polling and Ready/Busy# (RY/BY#) Signal. These methods are still supported by the S29GL-S family. One additional method is reading the Status Register.

5.5.1 Status Register

The status of program and erase operations is provided by a single 16-bit status register. The status is receiver by writing the Status Register Read command followed by a read access. When the Status Register read command is issued, the current status is captured (by the rising edge of WE#) into the register and the ASO is entered. The contents of the status register is aliased (overlaid) on the full memory address space. Any valid read (CE# and OE# low) access while in the Status Register ASO will exit the ASO (with the rising edge of CE# or OE# for t_{CEPH}/t_{OEPH} time) and return to the address space map in use when the Status Register Read command was issued.

The status register contains bits related to the results - success or failure - of the most recently completed Embedded Algorithms (EA):

- Erase Status (bit 5),
- Program Status (bit 4),
- Write Buffer Abort (bit 3),
- Sector Locked Status (bit 1),
- RFU (bit 0).

and, bits related to the current state of any in process EA:

- Device Busy (bit 7),
- Erase Suspended (bit 6),
- Program Suspended (bit 2),

The current state bits indicate whether an EA is in process, suspended, or completed.

The upper 8 bits (bits 15:8) are reserved. These have undefined High or Low value that can change from one status read to another. These bits should be treated as don't care and ignored by any software reading status.

The Soft Reset Command will clear to 0 bits [5, 4, 1, 0] of the status register if Status Register bit 3 =0. It will not affect the current state bits. The Clear Status Register Command will clear to 0 the results related bits of the status register but will not affect the current state bits.

Tab	ole	5.2	Status	Register	
-----	-----	-----	--------	----------	--

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Bit #	15:8	7	6	5	4	3	2	1	0
Bit Description	Reserved	Device Ready Bit	Erase Suspend Status Bit	Erase Status Bit	Program Status Bit	Write Buffer Abort Status Bit	Program Suspend Status Bit	Sector Lock Status Bit	Reserved
Bit Name		DRB	ESSB	ESB	PSB	WBASB	PSSB	SLSB	
Reset Status	Х	1	0	0	0	0	0	0	0
Busy Status	Invalid	0	Invalid	Invalid	Invalid	Invalid	Invalid	Invalid	Invalid
Ready Status	Х	1	0 = No Erase in Suspension 1 = Erase in Suspension	0 = Erase successful 1 = Erase fail	0 = Program successful 1 = Program fail	0 = Program not aborted 1 = Program aborted during Write to Buffer command	0 = No Program in suspension 1 = Program in suspension	0 = Sector not locked during operation 1 = Sector locked error	Х

Notes:

1. Bits 15 thru 8, and 0 are reserved for future use and may display as 0 or 1. These bits should be ignored (masked) when checking status.

2. Bit 7 is 1 when there is no Embedded Algorithm in progress in the device.

^{3.} Bits 6 thru 1 are valid only if Bit 7 is 1.

^{4.} All bits are put in their reset status by cold reset or warm reset.



- 5. Bits 5, 4, 3, and 1 are cleared to 0 by the Clear Status Register command or Reset command.
- 6. Upon issuing the Erase Suspend Command, the user must continue to read status until DRB becomes 1.
- 7. ESSB is cleared to 0 by the Erase Resume Command.
- 8. ESB reflects success or failure of the most recent erase operation.
- 9. PSB reflects success or failure of the most recent program operation.
- 10. During erase suspend, programming to the suspended sector, will cause program failure and set the Program status bit to 1.
- 11. Upon issuing the Program Suspend Command, the user must continue to read status until DRB becomes 1.
- 12. PSSB is cleared to 0 by the Program Resume Command.
- 13. SLSB indicates that a program or erase operation failed because the sector was locked.
- 14. SLSB reflects the status of the most recent program or erase operation.

5.5.2 Data Polling Status

During an active Embedded Algorithm the EAC switches to the Data Polling ASO to display EA status to any read access. A single word of status information is aliased in all locations of the device address space. In the status word there are several bits to determine the status of an EA. These are referred to as DQ bits as they appear on the data bus during a read access while an EA is in progress. DQ bits 15 to 8, DQ4, and DQ0 are reserved and provide undefined data. Status monitoring software must mask the reserved bits and treat them as don't care. Table 5.3 on page 39 and the following subsections describe the functions of the remaining bits.

5.5.2.1 DQ7: Data# Polling

The Data# Polling bit, DQ7, indicates to the host system whether an Embedded Algorithm is in progress or has completed. Data# Polling is valid after the rising edge of the final WE# pulse in the program or erase command sequence. Note that the Data# Polling is valid only for the last word being programmed in the write-buffer-page during Write Buffer Programming. Reading Data# Polling status on any word other than the last word to be programmed in the write-buffer-page will return false status information.

During the Embedded Program algorithm, the device outputs on DQ7 the complement of the data bit programmed to DQ7. This DQ7 status also applies to programming during Erase Suspend. When the Embedded Program algorithm is complete, the device outputs the data bit programmed to bit 7 of the last word programmed. In case of a Program Suspend, the device allows only reading array data. If a program address falls within a protected sector, Data# Polling on DQ7 is active for approximately 20 µs, then the device returns to reading array data.

During the Embedded Erase or Blank Check algorithms, Data# Polling produces a 0 on DQ7. When the algorithm is complete, or if the device enters the Erase Suspend mode, Data# Polling produces a 1 on DQ7. This is analogous to the complement / true datum output described for the Embedded Program algorithm: the erase function changes all the bits in a sector to 1; prior to this, the device outputs the complement or '0'. The system must provide an address within the sector selected for erasure to read valid status information on DQ7.

After an erase command sequence is written, if the sector selected for erasing is protected, Data# Polling on DQ7 is active for approximately 100 µs, then the device returns to reading array data.

When the system detects DQ7 has changed from the complement to true data, it can read valid data at DQ15-DQ0 on the following read cycles. This is because DQ7 may change asynchronously with DQ6-DQ0 while Output Enable (OE#) is asserted Low. This is illustrated in Figure 11.17 on page 87. Table 5.3 on page 39 shows the outputs for Data# polling on DQ7. Figure 5.2 on page 25 shows the Data# polling algorithm use in Write Buffer Programming.

Valid DQ7 data polling status may only be read from:

- the address of the last word loaded into the Write Buffer for a Write Buffer programming operation;
- the location of a single word programming operation;
- or a location in a sector being erased or blank checked;
- or a location in any sector during chip erase.





Figure 5.5 Data# Polling Algorithm

Note:

1. DQ7 should be rechecked even if DQ5 = 1 because DQ7 may change simultaneously with DQ5.

5.5.2.2 DQ6: Toggle Bit I

Toggle Bit I on DQ6 indicates whether an Embedded Program or Erase algorithm is in progress or complete, or whether the device has entered the Program Suspend or Erase Suspend mode. Toggle Bit I may be read at any address, and is valid after the rising edge of the final WE# pulse in the command sequence (prior to the program or erase operation).

During an Embedded Program or Erase algorithm operation, successive read cycles to any address cause DQ6 to toggle. (The system may use either OE# or CE# to control the read cycles). When the operation is complete, DQ6 stops toggling.

After an erase command sequence is written, if the sector selected for erasing is protected, DQ6 toggles for approximately 100 µs, then the EAC returns to standby (Read Mode). If the selected sector is not protected, the Embedded Erase algorithm erases the unprotected sector.

The system can use DQ6 and DQ2 together to determine whether a sector is actively erasing or erase-suspended. When the device is actively erasing (that is, the Embedded Erase algorithm is in progress), DQ6 toggles. When the device enters the Program Suspend mode or Erase Suspend mode, DQ6 stops toggling. However, the system must also use DQ2 to determine which sectors are erasing, or erase-suspended. Alternatively, the system can use DQ7 (see DQ7: Data# Polling on page 35).

DQ6 also toggles during the erase-suspend-program mode, and stops toggling once the Embedded Program algorithm is complete.

Table 5.3 on page 39 shows the outputs for Toggle Bit I on DQ6. Figure 5.6 on page 37 shows the toggle bit algorithm in flowchart form, and the Reading Toggle Bits DQ6/DQ2 on page 37 explains the algorithm. Figure 5.6 on page 37 shows the toggle bit timing diagrams. Figure 5.2 on page 25 shows the differences between DQ2 and DQ6 in graphical form. See also DQ2: Toggle Bit II on page 37.

5.5.2.3 DQ3: Sector Erase Timer

After writing a sector erase command sequence, the system may read DQ3 to determine whether or not erasure has begun. See Sector Erase on page 29 for more details.

After the sector erase command is written, the system should read the status of DQ7 (Data# Polling) or DQ6 (Toggle Bit I) to ensure that the device has accepted the command sequence, and then read DQ3. If DQ3 is 1, the Embedded Erase algorithm has begun; all further commands (except Erase Suspend) are ignored until the erase operation is complete. Table 5.3 on page 39 shows the status of DQ3 relative to the other status bits.



5.5.2.4 DQ2: Toggle Bit II

Toggle Bit II on DQ2, when used with DQ6, indicates whether a particular sector is actively erasing (that is, the Embedded Erase algorithm is in progress), or whether that sector is erase-suspended. Toggle Bit II is valid after the rising edge of the final WE# pulse in the command sequence.

DQ2 toggles when the system reads at addresses within the sector selected for erasure. (The system may use either OE# or CE# to control the read cycles). But DQ2 cannot distinguish whether the sector is actively erasing or is erase-suspended. DQ6, by comparison, indicates whether the device is actively erasing, or is in Erase Suspend, but cannot distinguish if the sector is selected for erasure. Thus, both status bits are required for sector and mode information. Refer to Table 5.3 on page 39 to compare outputs for DQ2 and DQ6. Figure 5.5 on page 36 shows the toggle bit algorithm in flowchart form, and the Reading Toggle Bits DQ6/DQ2 on page 37 explains the algorithm. See also Figure 5.6 on page 37 shows the toggle bit timing diagram. Figure 5.2 on page 25 shows the differences between DQ2 and DQ6 in graphical form.

5.5.2.5 Reading Toggle Bits DQ6/DQ2

Refer to Figure 5.5 on page 36 for the following discussion. Whenever the system initially begins reading toggle bit status, it must read DQ7-DQ0 at least twice in a row to determine whether a toggle bit is toggling. Typically, the system would note and store the value of the toggle bit after the first read. After the second read, the system would compare the new value of the toggle bit is not toggling, the device has completed the program or erases operation. The system can read array data on DQ15-DQ0 on the following read cycle.

However, if after the initial two read cycles, the system determines that the toggle bit is still toggling, the system also should note whether the value of DQ5 is High (see DQ5: Exceeded Timing Limits on page 38). If it is, the system should then determine again whether the toggle bit is toggling, since the toggle bit may have stopped toggling just as DQ5 went High. If the toggle bit is no longer toggling, the device has successfully completed the program or erase operation. If it is still toggling, the device did not complete the operation successfully, and the system must write the reset command to return to reading array data.

The remaining scenario is that the system initially determines that the toggle bit is toggling and DQ5 has not gone High. The system may continue to monitor the toggle bit and DQ5 through successive read cycles, determining the status as described in the previous paragraph. Alternatively, it may choose to perform other system tasks. In this case, the system must start at the beginning of the algorithm when it returns to determine the status of the operation (top of Figure 5.6 on page 37).



Figure 5.6 Toggle Bit Program

Notes:

^{1.} Read toggle bit twice to determine whether or not it is toggling. See text.

^{2.} Recheck toggle bit because it may stop toggling as DQ5 changes to 1. See text.



5.5.2.6 DQ5: Exceeded Timing Limits

DQ5 indicates whether the program or erase time has exceeded a specified internal pulse count limit. Under these conditions DQ5 produces a 1. This is a failure condition that indicates the program or erase cycle was not successfully completed. The system must issue the reset command to return the device to reading array data.

When a timeout occurs, the software must send a reset command to clear the timeout bit (DQ5) and to return the EAC to read array mode. In this case, it is possible that the flash will continue to communicate busy for up to 2 µs after the reset command is sent.





5.5.2.7 DQ1: Write-to-Buffer Abort

DQ1 indicates whether a Write-to-Buffer operation was aborted. Under these conditions DQ1 produces a 1. The system must issue the Write-to-Buffer-Abort-Reset command sequence to return the EAC to standby (Read Mode) and the Status Register failed bits are cleared. See Write Buffer Programming on page 24 for more details.

Table 5.3 Data Polling Status

	Operation	DQ7 (Note 2)	DQ6	DQ5 (Note 1)	DQ3	DQ2 (Note 2)	DQ1 (Note 4)	RY/BY#
	Embedded Program Algorithm	DQ7#	Toggle	0	N/A	No Toggle	0	0
Standard Mode	Reading within Erasing Sector	0	Toggle	0	1	Toggle	N/A	0
	Reading Outside erasing Sector	0	Toggle	0	1	No Toggle	N/A	0
ſ		INVALID	INVALID	INVALID	INVALID	INVALID	INVALID	
Program Suspend Mode	Reading within Program Suspended Sector	(Not Allowed)	(Not Allowed)	(Not Allowed)	(Not Allowed)	(Not Allowed)	(Not Allowed)	1
(Note 3)	Reading within Non-Program Suspended Sector	Data	Data	Data	Data	Data	Data	1
Erase	Reading within Erase Suspended Sector	1	No Toggle	0	N/A	Toggle	N/A	1
Suspend	Reading within Non-Erase Suspend Sector	Data	Data	Data	Data	Data	Data	1
Mode	Programming within Non-Erase Suspended Sector	DQ7#	Toggle	0	N/A	N/A	N/A	0
Write-to- Buffer	BUSY State	DQ7#	Toggle	0	N/A	No Toggle	0	0
(Notes 4,	Exceeded Timing Limits	DQ7#	Toggle	1	N/A	N/A	0	0
5)	ABORT State	DQ7#	Toggle	0	N/A	N/A	1	0

Notes:

1. DQ5 switches to '1' when an Embedded Program or Embedded Erase operation has exceeded the maximum timing limits. See DQ5: Exceeded Timing Limits on page 38 for more information.

2. DQ7 and DQ2 require a valid address when reading status information. Refer to the appropriate subsection for further details.

3. Data are invalid for addresses in a Program Suspended Line. All addresses other than the program suspended line can be read for valid data.

4. DQ1 indicates the Write-to-Buffer ABORT status during Write-Buffer-Programming operations.

5. Applies only to program operations.





5.6 Error Types and Clearing Procedures

There are three types of errors reported by the embedded operation status methods. Depending on the error type, the status reported and procedure for clearing the error status is different. Following is the clearing of error status:

- If an ASO was entered before the error the device remains entered in the ASO awaiting ASO read or a command write.
- If an erase was suspended before the error the device returns to the erase suspended state awaiting flash array read or a command write.
- Otherwise, the device will be in standby state awaiting flash array read or a command write.

5.6.1 Embedded Operation Error

If an error occurs during an embedded operation (program, erase, blank check, or password unlock) the device (EAC) remains busy. The RY/BY# output remains Low, data polling status continues to be overlaid on all address locations, and the status register shows ready with valid status bits. The device remains busy until the error status is detected by the host system status monitoring and the error status is cleared.

During embedded algorithm error status the Data Polling status will show the following:

- DQ7 is the inversion of the DQ7 bit in the last word loaded into the write buffer or last word of the password in the case of the password unlock command. DQ7 = 0 for an erase or blank check failure
- DQ6 continues to toggle
- DQ5 = 1; Failure of the embedded operation
- DQ4 is RFU and should be treated as don't care (masked)
- DQ3 = 1 to indicate embedded sector erase in progress
- DQ2 continues to toggle, independent of the address used to read status
- DQ1 = 0; Write buffer abort error
- DQ0 is RFU and should be treated as don't care (masked)

During embedded algorithm error status the Status Register will show the following:

- SR[7] = 1; Valid status displayed
- SR[6] = X; May or may not be erase suspended during the EA error
- SR[5] = 1 on erase or blank check error; else = 0
- SR[4] = 1 on program or password unlock error; else = 0
- SR[3] = 0; Write buffer abort
- SR[2] = 0; Program suspended
- SR[1] = 0; Protected sector
- SR[0] = X; RFU, treat as don't care (masked)

When the embedded algorithm error status is detected, it is necessary to clear the error status in order to return to normal operation, with RY/BY# High, ready for a new read or command write. The error status can be cleared by writing:

- Reset command
- Status Register Clear command

Commands that are accepted during embedded algorithm error status are:

- Status Register Read
- Reset command
- Status Register Clear command



5.6.2 Protection Error

If an embedded algorithm attempts to change data within a protected area (program, or erase of a protected sector or OTP area) the device (EAC) goes busy for a period of 20 to 100 μ s then returns to normal operation. During the busy period the RY/BY# output remains Low, data polling status continues to be overlaid on all address locations, and the status register shows not ready with invalid status bits (SR[7] = 0).

During the protection error status busy period the data polling status will show the following:

- DQ7 is the inversion of the DQ7 bit in the last word loaded into the write buffer. DQ7 = 0 for an erase failure
- DQ6 continues to toggle, independent of the address used to read status
- DQ5 = 0; to indicate no failure of the embedded operation during the busy period
- DQ4 is RFU and should be treated as don't care (masked)
- DQ3 = 1 to indicate embedded sector erase in progress
- DQ2 continues to toggle, independent of the address used to read status
- DQ1 = 0; Write buffer abort error
- DQ0 is RFU and should be treated as don't care (masked)

Commands that are accepted during the protection error status busy period are:

Status Register Read

When the busy period ends the device returns to normal operation, the data polling status is no longer overlaid, RY/BY# is High, and the status register shows ready with valid status bits. The device is ready for flash array read or write of a new command.

After the protection error status busy period the Status Register will show the following:

- SR[7] = 1; Valid status displayed
- SR[6] = X; May or may not be erase suspended after the protection error busy period
- SR[5] = 1 on erase error, else = 0
- SR[4] = 1 on program error, else = 0
- SR[3] = 0; Program not aborted
- SR[2] = 0; No Program in suspension
- SR[1] = 1; Error due to attempting to change a protected location
- SR[0] = X; RFU, treat as don't care (masked)

Commands that are accepted after the protection error status busy period are:

Any command



5.6.3 Write Buffer Abort

If an error occurs during a Write to Buffer command the device (EAC) remains busy. The RY/BY# output remains Low, data polling status continues to be overlaid on all address locations, and the status register shows ready with valid status bits. The device remains busy until the error status is detected by the host system status monitoring and the error status is cleared.

During write to buffer abort (WBA) error status the Data Polling status will show the following:

- DQ7 is the inversion of the DQ7 bit in the last word loaded into the write buffer
- DQ6 continues to toggle, independent of the address used to read status
- DQ5 = 0; to indicate no failure of the programming operation. WBA is an error in the values input by the Write to Buffer command before the programming operation can begin
- DQ4 is RFU and should be treated as don't care (masked)
- DQ3 is don't care after program operation as no erase is in progress. If the Write Buffer Program operation was started after an erase operation had been suspended then DQ3 = 1. If there was no erase operation in progress then DQ3 is a don't care and should be masked.
- DQ2 does not toggle after program operation as no erase is in progress. If the Write Buffer Program operation was started after an erase operation had been suspended then DQ2 will toggle in the sector where the erase operation was suspended and not in any other sector. If there was no erase operation in progress then DQ2 is a don't care and should be masked.
- DQ1 = 1: Write buffer abort error
- DQ0 is RFU and should be treated as don't care (masked)

During embedded algorithm error status the Status Register will show the following:

- SR[7] = 1; Valid status displayed
- SR[6] = X; May or may not be erase suspended during the WBA error status
- SR[5] = 0; Erase successful
- SR[4] = 1; Programming related error
- SR[3] = 1; Write buffer abort
- SR[2] = 0; No Program in suspension
- SR[1] = 0; Sector not locked during operation
- SR[0] = X; RFU, treat as don't care (masked)

When the WBA error status is detected, it is necessary to clear the error status in order to return to normal operation, with RY/BY# High, ready for a new read or command write. The error status can be cleared and device returned to normal operation by writing:

Write Buffer Abort Reset command

-Clears the status register and returns to normal operation

Status Register Clear command

Commands that are accepted during embedded algorithm error status are:

- Status Register Read
- Write Buffer Abort Reset command
- Status Register Clear command



5.7 Embedded Algorithm Performance Table

Table 5.4 Embedded Algorithm Characteristics (-40°C to +85°C)

Parameter		Typ (Note 2)	Max (Note 3)	Unit	Comments
Sector Erase Time 128 kbyte		275	1100	ms	Includes pre-programming prior to erasure (Note 5)
Single Word Programming Time (Note 1)	125	400	μs	
	2-byte (Note 1)	125	750		
	32-byte (Note 1)	160	750		
Duffer Drearemain a Time	64-byte (Note 1)	175	750		
Builer Programming Time	128-byte (Note 1)	198	750	μs	
	256-byte (Note 1)	239	750		
	512-byte	340	750		
Effective Write Buffer Program Operation per Word	ective Write Buffer Program 512-byte 512-byte		-	μs	
Sector Programming Time 128 kE Programming)	3 (full Buffer	108	192	ms	(Note 6)
Erase Suspend/Erase Resume (t	ESL)	_	40	μs	
Program Suspend/Program Resu	me (t _{PSL})	-	40	μs	
Erase Resume to next Erase Sus	pend (t _{ERS})	100	_	μs	Minimum of 60 ns but \ge typical periods are needed for Erase to progress to completion.
Program Resume to next Program	n Suspend (t _{PRS})	100	_	μs	Minimum of 60 ns but ≥ typical periods are needed for Program to progress to completion.
Blank Check	6.2	8.5	ms		
NOP (Number of Program-operat	ions, per Line)	-	256		

Notes:

1. Not 100% tested.

2. Typical program and erase times assume the following conditions: 25 °C, 3.0 V V_{CC} , 10,000 cycle, and a random data pattern.

3. Under worst case conditions of 90 °C, V_{CC} = 2.70 V, 100,000 cycles, and a random data pattern.

4. Effective write buffer specification is based upon a 512-byte write buffer operation.

5. In the pre-programming step of the Embedded Erase algorithm, all words are programmed to 0000h before Sector and Chip erasure.

6. System-level overhead is the time required to execute the bus-cycle sequence for the program command. See Table 7.1 on page 55 for further information on command definitions.



Table 5.5 Embedded Algorithm Characteristics (-40°C to +105°C)

Parameter		Typ (Note 2)	Max (Note 3)	Unit	Comments
Sector Erase Time 128 kbyte		275	1100	ms	Includes pre-programming prior to erasure (Note 5)
Single Word Programming Time (Note 1)	125	400	μs	
	2-byte (Note 1)	150	1050		
	32-byte (Note 1)	200	1050		
Buffer Drearemming Time	64-byte (Note 1)	220	1050	110	
Builer Programming Time	128-byte (Note 1)	250	1050	μs	
	256-byte (Note 1)	320	1050		
	512-byte	420	1050		
ffective Write Buffer Program 512-byte Speration per Word		1.64	-	μs	
Sector Programming Time 128 kE Programming)	3 (full Buffer	108	269	ms	(Note 6)
Erase Suspend/Erase Resume (t	ESL)	_	50	μs	
Program Suspend/Program Resu	me (t _{PSL})	_	50	μs	
Erase Resume to next Erase Sus	pend (t _{ERS})	100	_	μs	Minimum of 60 ns but \ge typical periods are needed for Erase to progress to completion.
Program Resume to next Program	100	_	μs	Minimum of 60 ns but \geq typical periods are needed for Program to progress to completion.	
Blank Check	7.6	9.0	ms		
NOP (Number of Program-operat	ions, per Line)	-	1 per 16 word		

Notes:

1. Not 100% tested.

2. Typical program and erase times assume the following conditions: 25 °C, 3.0 V V_{CC}. 10,000 cycle, and a random data pattern.

3. Under worst case conditions of 105 °C, V_{CC} = 2.70 V, 100,000 cycles, and a random data pattern.

4. Effective write buffer specification is based upon a 512-byte write buffer operation.

5. In the pre-programming step of the Embedded Erase algorithm, all words are programmed to 0000h before Sector and Chip erasure.

6. System-level overhead is the time required to execute the bus-cycle sequence for the program command. See Table 7.1 on page 55 for further information on command definitions.



5.7.1 Command State Transitions

Table 5.6 Read Command State Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Blank Check	CFI Entry
	Address	RA	xh	x555h	x555h	x555h	(SA)555h	(SA)55h
	Data	RD	xF0h	x70h	x71h	xAAh	x33h	x98h
READ	– Read Protect = False	READ	READ	READSR (READ)	READ	READUL1	– BLCK	CFI
READSR	_	(return)	_				_	_

Table 5.7 Read Unlock Command State Transition

Current State	Command and Condition	Read	Status Register Read Enter	Unlock 2	Word Program Entry	Write to Buffer Enter	Erase Enter	ID (Auto- select) Entry	SSR Entry	Lock Register Entry	Password ASO Entry	PPB Entry	PPB Lock Entry	DYB ASO Entry
	Address	RA	x555h	x2AAh	x555h	(SA)xh	x555h	(SA)555 h	(SA)555 h	x555h	x555h	x555h	x555h	x555h
	Data	RD	x70h	x55h	xA0h	x25h	x80h	x90h	x88h	x40h	x60h	xC0h	x50h	xE0h
READUL1	-	READU L1	READSR (READ)	READU L2	-	-	-	-	-	-	-	-	-	-
	Read Protect = True				-	-	-		-	-			-	-
READUL2	Read Protect = False	READU	READSR (READ)	_				CFI			PP		DDPI	
READUL2	Read Protect = False and LR(8) = 0	L2			PG1	PG1 WB	WB ER	ER	SSR	LR		PPB	B	DYB

Table 5.8 Erase State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Unlock 2	Chip Erase Start	Sector Erase Start	Erase Suspend Enhanced Method (2)
	Address	RA	xh	x555h	x555h	x555h	x2AAh	x555h	(SA)xh	xh
	Data	RD	xF0h	x70h	x71h	xAAh	x55h	x10h	x30h	xB0h
ER	-	ER	-	READSR (READ)		ERUL1	-	_	-	-
ERUL1	-	ERUL1	-	READSR (READ)	-	-	ERUL2	_	-	-
ERUL2	-	ERUL2	-	READSR (READ)	-	-	-	CER	SER	_
CER (1)	-	CER	-	ERSR (CER)	-	-	-	_	-	_
SED (1)	SR(7) = 0	QED	-	ERSR	-					
3ER (1)	SR(7) = 1	SER	READ	(SER)	READ	_	_	_	_	ESK (ES)
	SR(7) = 0	PL CK	-	ERSR	-					
BLCK (1)	SR(7) = 1	- BLCK	READ (BLCK) READ	_	—	_	-			
ERSR	_	(return)	_	-	-	-	_	_	-	_

Notes:

1. State will automatically move to READ state at the completion of the operation.

2. Also known as Erase Suspend/Program Suspend Legacy Method.



Table 5.9 Erase Suspend State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Sector Erase Start
	Address	RA	xh	x555h	x555h	x555h	(SA)xh
	Data	RD	xF0h	x70h	x71h	xAAh	x30h
ESR (1)	_	ESR	_	ERSR (ESR)	_	-	-
EQ	SR(7) = 0	EQ	EQ		EQ		-
ES	SR(7) = 1	ES	ES	E33K (E3)	E3	ESOLI	SER
ESSR	_	(return)	_	_	_	_	_

Note:

1. State will automatically move to ES state by t_{ESL} .

Table 5.10 Erase Suspend Unlock State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Unlock 1	Word Progra m Entry	Write to Buffer Enter	Write- to- Buffer- Abort Reset Start	Erase Resume Enhance d Method (1)	DYB ASO Entry	NOT a Abo	NOT a valid "Write-to-Buff Abort Reset" Command		
	Address	RA	xh	x555h	x2AAh	x555h	(SA)xh	x555h	xh	x555h	NOT x555h	xh	NOT x2AAh	xh
	Data	RD	xF0h	x70h	x55h	xA0h	x25h	xF0h	x30h	xE0h	xh	NOT xF0h	xh	NOT x55h
	-												-	-
ESUL1	SR(3) = 1	ESUL1	-	ESSR (ES)	ESUL2	-	_	-	-	-	-	-	ESDC	ESPC
	DQ(1) = 1			(==)									LOFG	
	-									-				
ESUL2	Read Protect = False	ESUL2	ES	ESSR (ES)	_	ESPG1	ES_W B	-	SER	ESDYB	-	-	_	_
	SR(3) = 1		_					ES	1		ESPC	ESPC		
	DQ(1) = 1							L3			1310	LOFG		

Note:

1. Also known as Erase Resume/Program Resume Legacy Method.

Table 5.11 Erase Suspend - DYB State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Command Set Exit Entry	Command Set Exit	DYB Set/ Clear Entry	Password Word Count
	Address	RA	xh	x555h	x555h	xh	xh	xh	xh
	Data	RD	xF0h	x70h	x71h	x90h	x00h	xA0h	x03h
ESDYB	_	ESDYB	ES	ESSR (ESDYB)	ESDYB	ESDYBEXT	-	ESDYBSE T	_
ESDYBSET	_	ESDYBSET	_	_	-	-	-	-	-
ESDYBEXT	_	ESDYBEXT	-	-	-	-	ES	-	ES



Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Erase Suspend Enhanced Method (1)	ProgramSuspend Enhanced Method	Write Data
	Address	RA	xh	x555h	x555h	x555h	xh	xh	xh
	Data	RD	xF0h	x70h	x71h	xAAh	xB0h	x51h	xh
	WC > 256 or SA ≠ SA		_	_	_	_	_	_	ESPG
ES_WB	WC ≤ 256 and SA = SA			_					ES_WB_D
	WC < 0 or Write Buffer≠ Write Buffer		_		_		_		ESPG
L3_WB_D	WC > 0 and Write Buffer = Write Buffer	L3_WB_D							ES_WB_D
ESPG1	-	ESPG1	-	-	-	-	-	-	ESPG
ESPC	SR(7) = 0	ESDO	-	ESPGSR	-	-	ESPSR		ESPC
ESPG -	SR(7) = 1	2070	ES	(ESPG)	ES	ESUL1	(ESPG)		LOFG
ESPGSR	_	(return)	_	_	_	_	-	_	(return)

Table 5.12 Erase Suspend - Program Command State Transition

Note:

1. Also known as Erase Suspend/Program Suspend Legacy Method.

Table 5.13 Erase Suspend - Program Suspend Command State Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Unlock 2	Erase Resume Enhanced Method (2)	Program Resume Enhanced Method
	Address	RA	xh	x555h	x555h	x555h	x2AAh	xh	xh
	Data	RD	xF0h	x70h	x71h	xAAh	x55h	x30h	x50h
ESPSR (1)	_	ESPSR	_	ESPGSR (ESPSR)	_	-	-	-	-
ESPS	_	ESPS	ESPS	ESPSSR (ESSP)	ESPS	ESPSUL1	-	ESPG	ESPG
ESPSSR	-	(return)	-	-	-	-	-	-	-
ESPSUL1	-	ESPSUL1	-	ESPSSR (ESPS)	-	-	ESPSUL2	-	-
ESPSUL2	_	ESPSUL2	_	ESPSSR (ESPS)	_	-	-	ESPG	ESPG

Notes:

1. State will automatically move to ESPS state by t_{PSL} .

2. Also known as Erase Resume/Program Resume Legacy Method.

Table 5.14 Program State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Program Buffer to flash (confirm)	Erase Suspend Enhanced Method (2)	Program Suspend Enhanced Method	Write Data
	Address	RA	xh	x555h	x555h	x555h	(SA)xh	xh	xh	xh
	Data	RD	xF0h	x70h	x71h	xAAh	x29h	xB0h	x51h	xh



Table 5.14 Program State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Program Buffer to flash (confirm)	Erase Suspend Enhanced Method (2)	Program Suspend Enhanced Method	Write Data
\ \ /R	WC > 256 or SA ≠ SA	\ \/ /R	_	_	_		_	_		PG
	$WC \le 256$ and SA = SA	VVD	_	-	-	-	-	-		WB_D
	Write Buffer ≠ Write Buffer	WB_D					_	PG		
WB D	WC = 0		_	_	_	_	_	_	_	PBF
	WC > 0 and Write Buffer = Write Buffer									WB_D
PBF	-	_	-	-	_	_	PG	_	_	PG
PG1	-	PG1	-	-	-	-	-	-	-	PG
	SR(7) = 0		_		-	-		PSR (PG)	PSR (PG)	
PG (1)	SR(7) = 1	PG		PGSR (PG)			_			PG
	SR(7) = 1 and SR(1) = 0		READ		READ	WBUL1		-	-	

Notes:

1. State will automatically move to READ state at the completion of the operation.

2. Also known as Erase Suspend/Program Suspend Legacy Method.

Table 5.15 Program Unlock State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Unlock 2	NOT a vali	d "Write-to-Buff	er-Abort Reset"	Command
	Address	RA	xh	x555h	x2AAh	NOT x555h	xh	NOT x2AAh	xh
	Data	RD	xF0h	x70h	x55h	xh	NOT xF0h	xh	NOT x55h
	-							PG	-
WBUL1	SR(3) = 1	WBUL1	-	– WBUL	WBUL2	-	_		PG
	DQ(1) = 1							FG	FG
	-					-	-		
WBUL2	SR(3) = 1	WBUL2	READ	-	-	DC.	DC	_	-
	DQ(1) = 1					PG	PG		
PGSR	-	(return)	-	_	_	_	_	_	_

Table 5.16 Program Suspend State Command Transition

Current State	Command and Condition	Read	Status Register Read Enter	Status Register Clear	Erase Resume Enhanced Method (2)	Program Resume Enhanced Method
	Address	RA	x555h	x555h	xh	xh
	Data	RD	x70h	x71h	x30h	x50h
PSR (1)	-	PSR	PGSR (PSR)	-	-	-
PS	-	PS	PSSR (PS)	PS	PG	PG
PSSR	-	(return)	—	-	-	-

Notes:

1. State will automatically move to PS state by t_{PSL} .

2. Also known as Erase Resume/Program Resume Legacy Method.



Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Command Set Exit Entry	Command Set Exit	PPB Lock Bit Set Entry	Password Word Count
	Address	RA	xh	x555h	x555h	xh	xh	xh	Xh
	Data	RD	xF0h	x70h	x71h	x90h	x00h	xA0h	x03h
LR	_	LR	READ	LRSR (LR)	LR	LREXT	-	LRPG1	-
LRPG1	-	LRPG1	-	-	-	-	-	-	-
LRPG	_	LRPG	-	LRSR (LRPG)	-	-	1	-	-
LRSR	_	(return)	-	-	-	-	-	-	-
LREXT	-	LREXT	-	-	-	-	READ	-	READ

Table 5.17 Lock Register State Command Transition

Table 5.18 CFI State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear
	Address	RA	xh	x555h	x555h
	Data	RD	xF0h	x70h	x71h
CFI	-	CFI	READ	CFISR (CFI)	CFI
CFISR	-	(return)	-	-	-

Table 5.19 Secure Silicon Sector State Command Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1
	Address	RA	xh	x555h	x555h	x555h
	Data	RD	xF0h	x70h	x71h	xAAh
SSR	-	SSR	READ	SSRSR (SSR)	SSR	SSRUL1

Table 5.20 Secure Silicon Sector	Jnlock State Command Transition
--	---------------------------------

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Unlock 2	Word Program Entry	Write to Buffer Enter	Comman d Set Exit Entry	NOT a va	NOT a valid "Write-to-Buffer-Abort Reset" Command		
	Address	RA	xh	x555h	x2AAh	x555h	(SA)xh	x555h	NOT x555h	xh	NOT x2AAh	xh
	Data	RD	xF0h	x70h	x55h	xA0h	x25h	x90h	xh	NOT xF0h	xh	NOT x55h
	-										-	_
SSRUL1	DQ(1) = 1	SSRUL1	READ	SSRSR (SSR)	SSRUL2	-	-	_	_	-	CODO	SEDDO
	SR(3) = 1			()					SSRPC		JORFO	SSRPG
	_								-	_		
SSRUL2	DQ(1) = 1	SSRUL2	SSR	-	-	SSRPG1	SSR_WB	SSREXT	SSBBC	SSBBC	—	-
	SR(3) = 1								JUNE	JUNE		



Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Unlock 1	Command Set Exit	
	Address	RA	xh	x555h	x555h	x555h	xh	
	Data	RD	xF0h	x70h	x71h	xAAh	x00h	
SSRPG1	-	SSRPG1	-	_	SSRPG1	-	_	
	WC > 256 or SA ≠ SA		_	_				
33K_WD	WC ≤ 256 and SA = SA	33K_WB						
	WC < 0 or Write Buffer ≠ Write Buffer		_	_			_	
331_100_0	WC > 0 and Write Buffer = Write Buffer	33K_WD_D				x555h xAAh — — — — — — — — — — — — — — — — — —		
	SR(7) = 0		_		_			
	SR(7) = 1					_		
SSRPG	SR(7) = 1 and DQ(1) = 0	SSRPG	READ	SSRSR (SSRPG)	SSR		_	
	DQ(1) = 1		_					
	SR(3) = 1				_	SSRULI		
SSRSR	_	(return)	_	_	_	_	_	
SSREXT	_	SSREXT	_	SSRSR (SSR)	_	_	READ	

Table 5.21 Secure Silicon Sector Program State Command Transition

 Table 5.22
 Password Protection Command State Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Password ASO Unlock Enter	Password ASO Unlock Start	Command Set Exit Entry	Command Set Exit	Program Entry	Password Word Count
	Address	RA	xh	x555h	x555h	0h	0h	xh	xh	xh	Xh
	Data	RD	xF0h	x70h	x71h	x25h	x29h	x90h	x00h	xA0h	x03h
PP	-	PP	READ	PPSR (PP)	PP	PPWB25	-	PPEXT	-	PPPG1	-
PPWB25	_	PPWB25	-	-	-	-	-	-	-	-	PPD
DDD	WC > 0	PPD					-				
PPD	$WC \le 0$	-	_	_	-	_	PPPG	_	_	_	_
PPPG1	-	PPPG1	-	-	_	-	-	-	-	-	-
PPPG	-	PPPG	-	PPSR (PPPG)	_	-	-	-	-	_	-
PPSR	-	(return)	-	-	-	-	-	-	-	-	-
PPEXT	-	PPEXT	_	-	_	-	-	_	READ	-	-



Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Command Set Exit Entry	Command Set Exit	Program Entry	DYB Set Start	All PPB Erase Enter	All PPB Erase Start
	Address	RA	xh	x555h	x555h	xh	xh	xh	(SA)xh	Xh	Oh
	Data	RD	xF0h	x70h	x71h	x90h	x00h	xA0h	x00h	x80h	x30h
PPB	_	PPB	READ	PPBSR (PPB)	PPB	PPBEXT	_	PPBPG1	_	PPBPG1	_
PPBPG1	-	PPBPG1	READ	-	-	-	PPBPG	I	PPB	I	PPBER
PDBDG	SR(7) = 0	PPRPG	_	PPBSR	_	_	_	_	_	_	_
FFBFG	SR(7) = 1	FFBFG	READ	(PPBPG)	READ	—	_	_	-	-	-
	SR(7) = 0		_	PPBSR	_	_	_	_		_	
FFDER	SR(7) = 1	FFDER	READ	(PPBER)	READ			_	_	_	_
PPBSR	_	(return)	_	-	-	_	_	-	-	-	-
PPBEXT	_	PPBEXT	-	-	-	-	READ	-	-	-	-

Table 5.23 Non-Volatile Protection Command State Transition

Table 5.24 PPB Lock Bit Command State Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Command Set Exit Entry	Command Set Exit	Program Entry
	Address	RA	xh	x555h	x555h	xh	xh	xh
	Data	RD	xF0h	x70h	x71h	x90h	x00h	xA0h
PPBLB	_	PPBLB	READ	PPBLBSR (PPBLB)	PPBLB	PPBLBEXT	_	PPBLBSET
PPBLBSR	_	(return)	_	_	I	1	_	_
PPBLBSET	 LR(2) = 0 and LR(5) = 0	PPBLBSET	-	_	-	-	PPBLB	_
PPBLBEXT	_	PPBLBEXT	—	—	_	_	READ	—

 Table 5.25
 Volatile Sector Protection Command State Transition

Current State	Command and Condition	Read	Software Reset / ASO Exit	Status Register Read Enter	Status Register Clear	Command Set Exit Entry	Command Set Exit	Program Entry	DYB Set Start	DYB Clear Start
	Address	RA	xh	x555h	x555h	xh	xh	xh	(SA)xh	(SA)xh
	Data	RD	xF0h	x70h	x71h	x90h	x00h	xA0h	x00h	x01h
DYB	_	DYB	READ	DYBSR (DYB)	DYB	DTBEXT	_	DYBSET	_	_
DYBSR	-	(return)	-	-	-	-	-	-	-	-
DYBSET	_	DYBSET	_	-	_	-	_	_	DYB	DYB
DYBEXT	_	DYBEXT	-	-	-	_	READ	-	_	-



Table 5.26 State Transition Definitions

Current State	Command Transition	Definition
BLCK	Table 5.8	Blank Check
CER	Table 5.8	Chip Erase Start
CFI	Table 5.18	ID (Autoselect)
CFISR	Table 5.18	ID (Autoselect) - Status Register Read
DYB	Table 5.25	DYB ASO
DYBEXT	Table 5.25	DYB ASO - Command Exit
DYBSET	Table 5.25	DYB ASO - Set
DYBSR	Table 5.25	DYB ASO - Status Register Read
ER	Table 5.8	Erase Enter
ERSR	Table 5.8	Erase - Status Register Read
ERUL1	Table 5.8	Erase - Unlock Cycle 1
ERUL2	Table 5.8	Erase - Unlock Cycle 2
ES	Table 5.9	Erase Suspended
ESDYB	Table 5.11	Erase Suspended - DYB ASO
ESDYBEXT	Table 5.11	Erase Suspended - DYB Command Exit
ESDYBSET	Table 5.11	Erase Suspended - DYB Set/Clear
ESPG	Table 5.12	Erase Suspended - Program
ESPGSR	Table 5.12	Erase Suspended - Program - Status Register Read
ESPG1	Table 5.12	Erase Suspended - Word Program
ESPS	Table 5.13	Erase Suspended - Program Suspended
ESPSR	Table 5.13	Erase Suspended - Program Suspend
ESPSSR	Table 5.13	Erase Suspended - Program Suspend - Status Register Read
ESPSUL1	Table 5.13	Erase Suspended - Program Suspend - Unlock 1
ESPSUL2	Table 5.13	Erase Suspended - Program Suspend - Unlock 2
ESR	Table 5.9	Erase Suspend Request
ESSR	Table 5.9	Erase Suspended - Status Register Read
ESUL1	Table 5.10	Erase Suspended - Unlock Cycle 1
ESUL2	Table 5.10	Erase Suspended - Unlock Cycle 2
ES_WB	Table 5.12	Erase Suspended - Write to Buffer
ES_WB_D	Table 5.12	Erase Suspended - Write to Buffer Data
LR	Table 5.17	Lock Register
LREXT	Table 5.17	Lock Register - Command Exit
LRPG	Table 5.17	Lock Register - Program
LRPG1	Table 5.17	Lock Register - Program Start
LRSR	Table 5.17	Lock Register - Status Register Read
PBF	Table 5.14	Page Buffer Full
PG	Table 5.14	Program
PGSR	Table 5.15	Program - Status Register Read
PG1	Table 5.14	Word Program



Table 5.26 State Transition Definitions (Continued)

Current State	Command Transition	Definition
PP	Table 5.22	Password ASO
PPB	Table 5.23	РРВ
PPBER	Table 5.23	PPB - Erase
PPBEXT	Table 5.23	PPB - Command Exit
PPBLB	Table 5.24	PPB Lock Bit
PPBLBEXT	Table 5.24	PPB Lock Bit - Command Exit
PPBLBSET	Table 5.24	PPB Lock Bit - Set
PPBLBSR	Table 5.24	PPB Lock Bit - Status Register Read
PPBPG	Table 5.23	PPB - Program
PPBPG1	Table 5.23	PPB - Program Request
PPBSR	Table 5.23	PPB - Status Register Read
PPD	Table 5.22	Password ASO - Data
PPEXT	Table 5.22	Password ASO - Command Exit
PPPG	Table 5.22	Password ASO - Program
PPPG1	Table 5.22	Password ASO - Program Request
PPSR	Table 5.22	Password ASO - Status Register Read
PS	Table 5.16	Program Suspended
PSR	Table 5.16	Program Suspend Request
PSSR	Table 5.16	Program Suspended - Status Register Read
PPWB25	Table 5.22	Password ASO - Unlock
READ	Table 5.6	Read Array
READSR	Table 5.6	Read Status Register
READUL1	Table 5.7	Read - Unlock Cycle 1
READUL2	Table 5.7	Read - Unlock Cycle 2
SER	Table 5.8	Sector Erase Start
SSR	Table 5.19	Secure Silicon
SSREXT	Table 5.21	Secure Silicon - Command Exit
SSRPG	Table 5.21	Secure Silicon - Program
SSRPG1	Table 5.21	Secure Silicon - Word Program
SSRSR	Table 5.21	Secure Silicon - Status Register Read
SSRUL1	Table 5.20	Secure Silicon - Unlock Cycle 1
SSRUL2	Table 5.20	Secure Silicon - Unlock Cycle 2
SSR_WB	Table 5.21	Secure Silicon - Write to Buffer
SSR_WB_D	Table 5.21	Secure Silicon - Write to Buffer - Write Data
WB	Table 5.14	Write to Buffer
WBUL1	Table 5.15	Write Buffer - Unlock Cycle 1
WBUL2	Table 5.15	Write Buffer - Unlock Cycle 2
WB_D	Table 5.14	Write to Buffer Write Data



6. Data Integrity

6.1 Erase Endurance

Table 6.1 Erase Endurance

Parameter	Minimum	Unit
Program/Erase cycles per main Flash array sectors	100K	P/E cycle
Program/Erase cycles per PPB array or non-volatile register array	100K	P/E cycle

Note:

1. Each write command to a non-volatile register causes a P/E cycle on the entire non-volatile register array. OTP bits and registers internally reside in a separate array that is not P/E cycled.

6.2 Data Retention

Table 6.2 Data Retention

Parameter	Test Conditions	Minimum Time	Unit
Data Rotantian Timo	10K Program/Erase Cycles	20	Years
	100K Program/Erase Cycles	2	Years

Contact Cypress Sales or an FAE representative for additional information on the data integrity. An application note is available at http://www.cypress.com/appnotes.



7. Software Interface Reference

7.1 Command Summary

Table 7.1 Command Definitions

Command Sequence		S						Bu	s Cycles	(Notes 2	-5)					
	(Note 1)	vcle	Fi	rst	Sec	ond	Th	ird	Fou	urth	Fi	fth	Siz	xth	Sev	enth
		Ő.	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
Rea	d (Note 6)	1	RA	RD												
Res	et/ASO Exit (Notes 7, 16)	1	XXX	F0												
Stat	us Register Read	2	555	70	XXX	RD										
Status Register Clear		1	555	71												
Word Program		4	555	AA	2AA	55	555	A0	PA	PD						
Writ	e to Buffer	6	555	AA	2AA	55	SA	25	SA	WC	WBL	PD	WBL	PD		
Pro (coi	gram Buffer to Flash nfirm)	1	SA	29												
Writ (No	e-to-Buffer-Abort Reset te 11)	3	555	AA	2AA	55	555	FO								
Chi	o Erase	6	555	AA	2AA	55	555	80	555	AA	2AA	55	555	10		
Sec	tor Erase	6	555	AA	2AA	55	555	80	555	AA	2AA	55	SA	30		
Era: Sus	se Suspend/Program pend acy Method (Note 9)	1	~~~	BO												
Era: Met	se Suspend Enhanced		~~~	DU												
Era: Res Leg	se Resume/Program sume acy Method (Note 10)	1	xxx	30												
Erase Resume Enhanced Method			,,,,,,	00												
Program Suspend Enhanced Method		1	XXX	51												
Pro Met	gram Resume Enhanced hod	1	ххх	50												
Blai	nk Check	1	(SA) 555	33												
ASO	ID (Autoselect) Entry	3	555	AA	2AA	55	(SA) 555	90								
select)	CFI Enter (Note 8)	1	(SA) 55	98												
uto	ID-CFI Read	1	RA	RD												
ID-CFI (A	Reset/ASO Exit (Notes 7, 16)	1	ххх	F0												
					Secur	e Silicon	Region	Comman	nd Definit	ions						
õ	SSR Entry	3	555	AA	2AA	55	(SA) 555	88								
) AS	Read (Note 6)	1	RA	RD												
SSR	Word Program	4	555	AA	2AA	55	555	A0	PA	PD						
9) L	Write to Buffer	6	555	AA	2AA	55	SA	25	SA	WC	WBL	PD	WBL	PD		
Silicon Region	Program Buffer to Flash (confirm)	1	SA	29												
	Write-to-Buffer-Abort Reset (Note 11)	3	555	AA	2AA	55	555	F0								
oure	SSR Exit (Note 11)	4	555	AA	2AA	55	555	90	XX	0						
Sei	Reset/ASO Exit (Notes 7, 16)	1	XXX	F0												



Table 7.1 Command Definitions (Continued)

Command Convense		s						Bu	s Cycles	(Notes 2	5)					
	Command Sequence	/cle	Fi	rst	Sec	ond	Th	ird	Fo	urth	Fi	fth	Si	xth	Sev	enth
	(Note I)	σ	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
	Lock Register Command Set Definitions															
	Lock Register Entry	3	555	AA	2AA	55	555	40								
ASC	Program (Note 15)	2	XXX	A0	XXX	PD										
ter,	Read (Note 15)	1	0	RD												
< Regis	Command Set Exit (Notes 12, 16)	2	ХХХ	90	ХХХ	0										
Loci	Reset/ASO Exit (Notes 7, 16)	1	ХХХ	F0												
	Password Protection Command Set Definitions															
	Password ASO Entry	3	555	AA	2AA	55	555	60								
	Program (Note 14)	2	ХХХ	A0	PWA ×	PWDx										
ASO	Read (Note 13)	4	0	PWD0	1	PWD1	2	PWD2	3	PWD 3						
ssword	Unlock	7	0	25	0	3	0	PWD0	1	PWD 1	2	PWD2	3	PWD 3	0	29
Pas	Command Set Exit (Notes 12, 16)	2	XXX	90	XXX	0										
	Reset/ASO Exit (Notes 7, 16)	1	ххх	F0												
				No	n-Volatile	e Sector I	Protectio	n Comm	and Set	Definition	IS					J
(u	PPB Entry	3	555	AA	2AA	55	555	C0								
ectic	PPB Program (Note 17)	2	XXX	A0	SA	0										
Prote	All PPB Erase (Note 17)	2	XXX	80	0	30										
tor F	PPB Read (Note 17)	1	SA	RD (0)												
ile Sec	Command Set Exit (Notes 12, 16)	2	ХХХ	90	XXX	0										
PPB (Non-Volat	Reset/ASO Exit (Notes 7, 16)	1	xxx	FO												
			G	ilobal Noi	n-Volatile	e Sector I	Protectio	n Freeze	Comma	nd Set De	efinitions	3				
	PPB Lock Entry	3	555	AA	2AA	55	555	50								
т,	PPB Lock Bit Cleared	2	XXX	A0	XXX	0										
Lock	PPB Lock Status Read (Note 17)	1	XXX	RD (0)												
РРВ	Command Set Exit (Notes 12, 16)	2	XXX	90	XXX	0										
	Reset/ASO Exit (Note 16)	1	XXX	F0												



Table 7.1 Command Definitions (Continued)

	Command Sequence	s						Bu	s Cycles	(Notes 2	5)					
	(Note 1)	ycle	Fi	rst	Sec	ond	Th	ird	Fourth		Fifth		Sixth		Sev	enth
	(Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
				1	/olatile S	ector Pro	otection	Comman	d Set Dei	finitions						
õ	DYB ASO Entry	3	555	AA	2AA	55	555	E0								
) As	DYB Set (Note 17)	2	XXX	A0	SA	0										
stion	DYB Clear (Note 17)	2	XXX	A0	SA	1										
otec	DYB Status Read (Note 17)	1	SA	RD (0)												
ector Pro	Command Set Exit (Notes 12, 16)	2	ХХХ	90	ХХХ	0										
DYB (Volatile Se	Reset/ASO Exit (Note 16)	1	xxx	FO												
						Comma	and Set D	Definition	s ECC							
0	ECC ASO Entry	3	555	AA	2AA	55	555	75								
ECC ASC	ECC Status Read	1	RA	RD												
	Command Set Exit (Notes 12, 16)	1	ХХХ	F0												

Legend:

X = Don't care.

RA = Address of the memory to be read.

RD = Data read from location RA during read operation.

PA = Address of the memory location to be programmed.

PD = Data to be programmed at location PA.

SA = Address of the sector selected. Address bits A_{MAX} -A16 uniquely select any sector.

WBL = Write Buffer Location. The address must be within the same Line.

WC = Word Count is the number of write buffer locations to load minus 1.

PWAx = Password address for word0 = 00h, word1 = 01h, word2 = 02h, and word3 = 03h.

PWDx = Password data word0, word1, word2, and word3.

Notes:

1. See Table 9.1 on page 66 for description of bus operations.

2. All values are in hexadecimal.

- Except for the following, all bus cycles are write cycle: read cycle during Read, ID/CFI Read (Manufacturing ID / Device ID), Indicator Bits, Secure Silicon Region Read, SSR Lock Read, and 2nd cycle of Status Register Read.
- 4. Data bits DQ15–DQ8 are don't care in command sequences, except for RD, PD, WC and PWD.
- 5. Address bits A_{MAX}–A11 are don't cares for unlock and command cycles, unless SA or PA required. (A_{MAX} is the Highest Address pin.).
- 6. No unlock or command cycles required when reading array data.
- 7. The Reset command is required to return to reading array data when device is in the ID-CFI (autoselect) mode, or if DQ5 goes High (while the device is providing status data).
- 8. Command is valid when device is ready to read array data or when device is in ID-CFI (autoselect) mode.
- 9. The system can read and program/program suspend in non-erasing sectors, or enter the ID-CFI ASO, when in the Erase Suspend mode. The Erase Suspend command is valid only during a sector erase operation.
- 10. The Erase Resume/Program Resume command is valid only during the Erase Suspend/Program Suspend modes.
- 11. Issue this command sequence to return to READ mode after detecting device is in a Write-to-Buffer-Abort state. IMPORTANT: the full command sequence is required if resetting out of ABORT.
- 12. The Exit command returns the device to reading the array.
- 13. The password portion can be entered or read in any order as long as the entire 64-bit password is entered or read.
- 14. For PWDx, only one portion of the password can be programmed per each A0 command. Portions of the password must be programmed in sequential order (PWD0–PWD3).
- 15. All Lock Register bits are one-time programmable. The program state = 0 and the erase state = 1. Also, both the Persistent Protection Mode Lock Bit and the Password Protection Mode Lock Bit cannot be programmed at the same time or the Lock Register Bits Program operation aborts and returns the device to read mode. Lock Register bits that are reserved for future use are undefined and may be 0's or 1's.
- 16. If any of the Entry commands was issued, an Exit command must be issued to reset the device into read mode.
- 17. Protected State = 00h, Unprotected State = 01h. The sector address for DYB set, DYB clear, or PPB Program command may be any location within the sector the lower order bits of the sector address are don't care.



7.2 Device ID and Common Flash Interface (ID-CFI) ASO Map

The Device ID portion of the ASO (word locations 0h to 0Fh) provides manufacturer ID, device ID, Sector Protection State, and basic feature set information for the device.

ID-CFI Location 02h displays sector protection status for the sector selected by the sector address (SA) used in the ID-CFI enter command. To read the protection status of more than one sector it is necessary to exit the ID ASO and enter the ID ASO using the new SA. The access time to read location 02h is always t_{ACC} and a read of this location requires CE# to go High before the read and return Low to initiate the read (asynchronous read access). Page mode read between location 02h and other ID locations is not supported. Page mode read between ID locations other than 02h is supported.

For additional information see ID-CFI ASO on page 31.

Description	Address	Read Data
Manufacture ID	(SA) + 0000h	0001h
Device ID	(SA) + 0001h	227Eh
Protection Verification	(SA) + 0002h	Sector Protection State (1= Sector protected, 0 = Sector unprotected). This protection state is shown only for the SA selected when entering ID-CFI ASO. Reading other SA provides undefined data. To read a different SA protection state ASO exit command must be used and then enter ID-CFI ASO again with the new SA.
Indicator Bits	(SA) + 0003h	DQ15-DQ08 = 1 (Reserved) DQ7 - Factory Locked Secure Silicon Region 1 = Locked, 0 = Not Locked DQ6 - Customer Locked Secure Silicon Region 1 = Locked 0 = Not Locked DQ5 = 1 (Reserved) DQ4 - WP# Protects 0 = lowest address Sector 1 = highest address Sector DQ3 - DQ0 = 1 (Reserved)
	(SA) + 0004h	Reserved
	(SA) + 0005h	Reserved
	(SA) + 0006h	Reserved
RELL	(SA) + 0007h	Reserved
	(SA) + 0008h	Reserved
	(SA) + 0009h	Reserved
	(SA) + 000Ah	Reserved
	(SA) + 000Bh	Reserved

Table 7.2 ID (Autoselect) Address Map



Table 7.2 ID (Autoselect) Address Map (Continued)

Description	Address	Read Data
Lower Software Bits	(SA) + 000Ch	Bit 0 - Status Register Support 1 = Status Register Supported 0 = Status Register not supported Bit 1 - DQ polling Support 1 = DQ bits polling supported 0 = DQ bits polling not supported Bit 3-2 - Command Set Support 11 = reserved 10 = reserved 01 = Reduced Command Set 00 = Classic Command set Bits 4-15 - Reserved = 0
Upper Software Bits	(SA) + 000Dh	Reserved
Device ID	(SA) + 000Eh	2228h = 1 Gb 2223h = 512 Mb 2222h = 256 Mb 2221h = 128 Mb
Device ID	(SA) + 000Fh	2201h

Table 7.3 CFI Query Identification String

Word Address	Data	Description
(SA) + 0010h	0051h	
(SA) + 0011h	0052h	Query Unique ASCII string "QRY"
(SA) + 0012h	0059h	
(SA) + 0013h	0002h	Primary OEM Command Sat
(SA) + 0014h	0000h	
(SA) + 0015h	0040h	Address for Primary Extended Table
(SA) + 0016h	0000h	Address for Phinary Extended Table
(SA) + 0017h	0000h	Alternate OEM Command Set
(SA) + 0018h	0000h	(00h = none exists)
(SA) + 0019h	0000h	Address for Alternate OEM Extended Table
(SA) + 001Ah	0000h	(00h = none exists)



Table 7.4 CFI System Interface String

Word Address	Data	Description
(SA) + 001Bh	0027h	V _{CC} Min. (erase/program) (D7–D4: volts, D3–D0: 100 mV)
(SA) + 001Ch	0036h	V _{CC} Max. (erase/program) (D7–D4: volts, D3–D0: 100 mV)
(SA) + 001Dh	0000h	V _{PP} Min. voltage (00h = no V _{PP} pin present)
(SA) + 001Eh	0000h	V _{PP} Max. voltage (00h = no V _{PP} pin present)
(SA) + 001Fh	0008h	Typical timeout per single word write $2^{N} \mu s$
(SA) + 0020h	0009h	Typical timeout for max multi-byte program, 2 ^N μs (00h = not supported)
(SA) + 0021h	0008h	Typical timeout per individual block erase 2 ^N ms
(SA) + 0022h	0012h (1 Gb) 0011h (512 Mb) 0010h (256 Mb) 000Fh (128 Mb)	Typical timeout for full chip erase 2 ^N ms (00h = not supported)
(SA) + 0023h	0001h	Max. timeout for single word write 2 ^N times typical
(SA) + 0024h	0002h	Max. timeout for buffer write 2 ^N times typical
(SA) + 0025h	0003h	Max. timeout per individual block erase 2 ^N times typical
(SA) + 0026h	0003h	Max. timeout for full chip erase 2 ^N times typical (00h = not supported)

Table 7.5 CFI Device Geometry Definition

Word Address	Data	Description
(SA) + 0027h	001Bh (1 Gb) 001Ah (512 Mb) 0019h (256 Mb) 0018h (128 Mb)	Device Size = 2 ^N byte;
(SA) + 0028h	0001h	- Flash Device Interface Description 0 = ×8-only, 1 = ×16-only, 2 = ×8/×16 capable
(SA) + 0029h	0000h	
(SA) + 002Ah	0009h	Max. number of byte in multi-byte write = 2 ^N (00 = not supported)
(SA) + 002Bh	0000h	
(SA) + 002Ch	0001h	Number of Erase Block Regions within device 1 = Uniform Device, 2 = Boot Device
(SA) + 002Dh	00XXh	Erase Block Region 1 Information (refer to JEDEC JESD68-01 or JEP137 specifications) 00FFh, 0003h, 0000h, 0002h =1 Gb 00FFh, 0001h, 0000h, 0002h = 512 Mb 00FFh, 0000h, 0000h, 0002h = 256 Mb 007Fh, 0000h, 0000h, 0002h = 128 Mb
(SA) + 002Eh	000Xh	
(SA) + 002Fh	0000h	
(SA) + 0030h	000Xh	
(SA) + 0031h	0000h	Erase Block Region 2 Information (refer to CFI publication 100)
(SA) + 0032h	0000h	
(SA) + 0033h	0000h	
(SA) + 0034h	0000h	


Word Address	Data	Description			
(SA) + 0035h	0000h				
(SA) + 0036h	0000h	Frace Block Begins 2 Information (refer to CEL nublication 100)			
(SA) + 0037h	0000h				
(SA) + 0038h	0000h				
(SA) + 0039h	0000h				
(SA) + 003Ah	0000h	Frace Block Begins 4 Information (refer to CEL nublication 100)			
(SA) + 003Bh	0000h				
(SA) + 003Ch	0000h				
(SA) + 003Dh	FFFFh	Reserved			
(SA) + 003Eh	FFFFh	Reserved			
(SA) + 003Fh	FFFFh	Reserved			

Table 7.5 CFI Device Geometry Definition (Continued)

Table 1.0 Of IT finally Vehice Opeonio Extended Gaery

Word Address	Data	Description
(SA) + 0040h	0050h	
(SA) + 0041h	0052h	Query-unique ASCII string "PRI"
(SA) + 0042h	0049h	7
(SA) + 0043h	0031h	Major version number, ASCII
(SA) + 0044h	0035h	Minor version number, ASCII
(SA) + 0045h	001Ch	Address Sensitive Unlock (Bits 1–0) 00b = Required 01b = Not Required Process Technology (Bits 5–2) $0000b = 0.23 \ \mu m$ Floating Gate $0001b = 0.17 \ \mu m$ Floating Gate $0010b = 0.23 \ \mu m$ MirrorBit $0011b = 0.13 \ \mu m$ Floating Gate $0100b = 0.11 \ \mu m$ MirrorBit $0101b = 0.09 \ \mu m$ MirrorBit $0110b = 0.09 \ \mu m$ Floating Gate $0111b = 0.065 \ \mu m$ MirrorBit Eclipse $1000b = 0.045 \ \mu m$ MirrorBit $1001b = 0.045 \ \mu m$ MirrorBit
(SA) + 0046h	0002h	Erase Suspend 0 = Not Supported 1 = Read Only 2 = Read and Write
(SA) + 0047h	0001h	Sector Protect 00 = Not Supported X = Number of sectors in smallest group
(SA) + 0048h	0000h	Temporary Sector Unprotect 00 = Not Supported 01 = Supported



Table 7.6	CEL Primary	/ Vendor-S	necific Ex	tended Quer	v (Continued)
	CITINNA	y venuor-o	респіс цл		y (Continueu)

Word Address	Data	Description				
(SA) + 0049h	0008h	Sector Protect/Unprotect Scheme 04 = High Voltage Method 05 = Software Command Locking Method 08 = Advanced Sector Protection Method				
(SA) + 004Ah	0000h	Simultaneous Operation 00 = Not Supported X = Number of banks				
(SA) + 004Bh	0000h	Burst Mode Type 00 = Not Supported 01 = Supported				
(SA) + 004Ch	0003h	Page Mode Type 00 = Not Supported 01 = 4 Word Page 02 = 8 Word Page 03 = 16 Word Page				
(SA) + 004Dh	0000h	ACC (Acceleration) Supply Minimum 00 = Not Supported D7–D4: Volt D3–D0: 100 mV				
(SA) + 004Eh	0000h	ACC (Acceleration) Supply Maximum 00 = Not Supported D7–D4: Volt D3–D0: 100 mV				
(SA) + 004Fh	0004h (Bottom) 0005h (Top)	 WP# Protection 00h = Flash device without WP Protect (No Boot) 01h = Eight 8 kB Sectors at TOP and Bottom with WP (Dual Boot) 02h = Bottom Boot Device with WP Protect (Bottom Boot) 03h = Top Boot Device with WP Protect (Top Boot) 04h = Uniform, Bottom WP Protect (Uniform Bottom Boot) 05h = Uniform, Top WP Protect (Uniform Top Boot) 06h = WP Protect for all sectors 07h = Uniform, Top and Bottom WP Protect 				
(SA) + 0050h	0001h	Program Suspend 00 = Not Supported 01 = Supported				
(SA) +0051h	0000h	Unlock Bypass 00 = Not Supported 01 = Supported				
(SA) + 0052h	0009h	Secured Silicon Sector (Customer OTP Area) Size 2 ^N (bytes)				
(SA) + 0053h	008Fh	Software Features bit 0: status register polling (1 = supported, 0 = not supported) bit 1: DQ polling (1 = supported, 0 = not supported) bit2: newprogramsuspend/resume commands(1=supported,0=notsupported) bit 3: word programming (1 = supported, 0 = not supported) bit 4: bit-field programming (1 = supported, 0 = not supported) bit 5: autodetect programming (1 = supported, 0 = not supported) bit 6: RFU bit 6: RFU bit 7: multiple writes per Line (1 = supported, 0 = not supported)				



Table 7.6 CFI Primary Vendor-Specific Extended Query (Continued)	
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Word Address	Data	Description
(SA) + 0054h	0005h	Page Size = 2 ^N bytes
(SA) + 0055h	0006h	Erase Suspend Timeout Maximum < 2^{N} (µs)
(SA) + 0056h	0006h	Program Suspend Timeout Maximum < 2 ^Ν (μs)
(SA) + 0057h to (SA) + 0077h	FFFFh	Reserved
(SA) + 0078h	0006h	Embedded Hardware Reset Timeout Maximum < 2 ^Ν (μs) Reset with Reset Pin
(SA) + 0079h	0009h	Non-Embedded Hardware Reset Timeout Maximum < 2 ^N (μs) Power on Reset

7.3 Device ID and Common Flash Interface (ID-CFI) ASO Map Table 7.7 Device ID and Common Flash Interface (ID-CFI) ASO Map

Word Address	Data Field	# of bytes	Data Format	Example of Actual Data	Hex Read Out of Example Data				
(SA) + 0080h	Size of Electronic Marking	1	Hex	19	0013h				
(SA) + 0081h	Revision of Electronic Marking	1	Hex	1	0001h				
(SA) + 0082h	Fab Lot #	7	Ascii	LD87270	004Ch, 0044h, 0038h, 0037h, 0032h, 0037h, 0030h				
(SA) + 0089h	Wafer #	1	Hex	23	0017h				
(SA) + 008Ah	Die X Coordinate	1	Hex	10	000Ah				
(SA) + 008Bh	Die Y Coordinate	1	Hex	15	000Fh				
(SA) + 008Ch	Class Lot#	7	Ascii	BR33150	0042h, 0052h, 0033h, 0033h, 0031h, 0035h, 0030h				
(SA) + 0093h	Reserved for Future	13	n/a	n/a	undefined				
Fab Lot # + Wafer	ab Lot # + Wafer # + Die X Coordinate + Die Y Coordinate gives a unique ID for each device.								



Hardware Interface

8. Signal Descriptions

8.1 Address and Data Configuration

Address and data are connected in parallel (ADP) via separate signal inputs and I/Os.

8.2 Input/Output Summary

Table 8.1 I/O Summary

Symbol	Туре	Description
RESET#	Input	Hardware Reset. At V_{IL} causes the device to reset control logic to its standby state, ready for reading array data.
CE#	Input	Chip Enable. At V_{IL} selects the device for data transfer with the host memory controller.
OE#	Input	Output Enable. At V _{IL} , causes outputs to be actively driven. At V _{IH} , causes outputs to be high impedance (High-Z).
WE#	Input	Write Enable. At V_{IL} indicates data transfer from host to device. At V_{IH} indicates data transfer is from device to host.
A _{MAX} -A0	Input	Address inputs. A25–A0 for S29GL01GS A24–A0 for S29GL512S A23–A0 for S29GL256S A22–A0 for S29GL128S
DQ15-DQ0	Input/Output	Data inputs and outputs
WP#	Input	Write Protect. At V _{IL} , disables program and erase functions in the lowest or highest address 64-kword (128-kB) sector of the device. At V _{IH} , the sector is not protected. WP# has an internal pull up; When unconnected WP# is at V _{IH} .
RY/BY#	Output - open drain	Ready/Busy. Indicates whether an Embedded Algorithm is in progress or complete. At V_{IL} , the device is actively engaged in an Embedded Algorithm such as erasing or programming. At High-Z, the device is ready for read or a new command write - requires external pull-up resistor to detect the High-Z state. Multiple devices may have their RY/BY# outputs tied together to detect when all devices are ready.
V _{CC}	Power Supply	Core power supply
V _{IO}	Power Supply	Versatile IO power supply.
V _{SS}	Power Supply	Power supplies ground
NC	No Connect	Not Connected internally. The pin/ball location may be used in Printed Circuit Board (PCB) as part of a routing channel.
RFU	No Connect	Reserved for Future Use. Not currently connected internally but the pin/ball location should be left unconnected and unused by PCB routing channel for future compatibility. The pin/ball may be used by a signal in the future.
DNU	Reserved	Do Not Use. Reserved for use by Cypress. The pin/ball is connected internally. The input has an internal pull down resistance to V_{SS} . The pin/ball can be left open or tied to V_{SS} on the PCB.



8.3 Versatile I/O Feature

The maximum output voltage level driven by, and input levels acceptable to, the device are determined by the V_{IO} power supply. This supply allows the device to drive and receive signals to and from other devices on the same bus having interface signal levels different from the device core voltage.

8.4 Ready/Busy# (RY/BY#)

RY/BY# is a dedicated, open drain output pin that indicates whether an Embedded Algorithm, Power-On Reset (POR), or Hardware Reset is in progress or complete. The RY/BY# status is valid after the rising edge of the final WE# pulse in a command sequence, when V_{CC} is above V_{CC} minimum during POR, or after the falling edge of RESET#. Since RY/BY# is an open drain output, several RY/BY# pins can be tied together in parallel with a pull up resistor to V_{IO} .

If the output is Low (Busy), the device is actively erasing, programming, or resetting. (This includes programming in the Erase Suspend mode). If the output is High (Ready), the device is ready to read data (including during the Erase Suspend mode), or is in the standby mode.

Table 5.3, Data Polling Status on page 39 shows the outputs for RY/BY# in each operation.

If an Embedded algorithm has failed (Program / Erase failure as result of max pulses or Sector is locked), RY/BY# will stay Low (busy) until status register bits 4 and 5 are cleared and the reset command is issued. This includes Erase or Programming on a locked sector.

8.5 Hardware Reset

The RESET# input provides a hardware method of resetting the device to standby state. When RESET# is driven Low for at least a period of t_{RP}, the device immediately:

- terminates any operation in progress,
- exits any ASO,
- tristates all outputs,
- resets the Status Register,
- resets the EAC to standby state.
- CE# is ignored for the duration of the reset operation (t_{RPH}).
- To meet the Reset current specification (I_{CC5}) CE# must be held High.

To ensure data integrity any operation that was interrupted should be reinitiated once the device is ready to accept another command sequence.



9. Signal Protocols

The following sections describe the host system interface signal behavior and timing for the 29GL-S family flash devices.

9.1 Interface States

Table 9.1 describes the required value of each interface signal for each interface state.

Table 9.1 Interface States

Interface State	V _{CC}	V _{IO}	RESET#	CE#	OE#	WE#	A _{MAX} -A0	DQ15-DQ0
Power-Off with Hardware Data Protection	< V _{LKO}	$\leq V_{CC}$	Х	Х	Х	Х	Х	High-Z
Power-On (Cold) Reset	\geq V _{CC} min	$\geq V_{IO} \min$ $\leq V_{CC}$	Х	Х	Х	Х	Х	High-Z
Hardware (Warm) Reset	\geq V _{CC} min	$\geq V_{IO} \min$ $\leq V_{CC}$	L	Х	Х	х	Х	High-Z
Interface Standby	$\geq V_{CC} \min$	$\geq V_{IO} \min$ $\leq V_{CC}$	Н	Η	Х	Х	Х	High-Z
Automatic Sleep (Notes 1, 3)	\geq V _{CC} min	$\geq V_{IO} \min$ $\leq V_{CC}$	Н	L	Х	Х	Valid	Output Available
Read with Output Disable (Note 2)	$\geq V_{CC} \min$	$\geq V_{IO} \min$ $\leq V_{CC}$	Н	L	Н	Н	Valid	High-Z
Random Read	$\geq V_{CC}$ min	$\geq V_{ O} \min$	Н	L	L	Н	Valid	Output Valid
Page Read	$\geq V_{CC}$ min	$\geq V_{IO} \min$ $\leq V_{CC}$	Н	L	L	Н	A _{MAX} –A4 Valid A3–A0 Modified	Output Valid
Write	$\geq V_{CC} \min$	\geq V _{IO} min \leq V _{CC}	Н	L	Н	L	Valid	Input Valid

Legend:

 $L = V_{IL}$

 $H = V_{IH}$

 $X = either V_{IL} or V_{IH}$

L/H = rising edgeH/L = falling edge

Valid = all bus signals have stable L or H level

Modified = valid state different from a previous valid state

Available = read data is internally stored with output driver controlled by OE#

Notes:

1. WE# and OE# can not be at V_{IL} at the same time.

2. Read with Output Disable is a read initiated with OE# High.

3. Automatic Sleep is a read/write operation where data has been driven on the bus for an extended period, without CE# going High and the device internal logic has gone into standby mode to conserve power.

9.2 Power-Off with Hardware Data Protection

The memory is considered to be powered off when the core power supply (V_{CC}) drops below the lock-out voltage (V_{LKO}). When V_{CC} is below V_{LKO} , the entire memory array is protected against a program or erase operation. This ensures that no spurious alteration of the memory content can occur during power transition. During a power supply transition down to Power-Off, V_{IO} should remain less than or equal to V_{CC} .

If V_{CC} goes below V_{RST} (Min) then returns above V_{RST} (Min) to V_{CC} minimum, the Power-On Reset interface state is entered and the EAC starts the Cold Reset Embedded Algorithm.



9.3 **Power Conservation Modes**

9.3.1 Interface Standby

Standby is the default, low power, state for the interface while the device is not selected by the host for data transfer (CE# = High). All inputs are ignored in this state and all outputs except RY/BY# are high impedance. RY/BY# is a direct output of the EAC, not controlled by the Host Interface.

9.3.2 Automatic Sleep

The automatic sleep mode reduces device interface energy consumption to the sleep level (I_{CC6}) following the completion of a random read access time. The device automatically enables this mode when addresses remain stable for t_{ACC} + 30 ns. While in sleep mode, output data is latched and always available to the system. Output of the data depends on the level of the OE# signal but, the automatic sleep mode current is independent of the OE# signal level. Standard address access timings (t_{ACC} or t_{PACC}) provide new data when addresses are changed. I_{CC6} in DC Characteristics on page 72 represents the automatic sleep mode current specification.

Automatic sleep helps reduce current consumption especially when the host system clock is slowed for power reduction. During slow system clock periods, read and write cycles may extend many times their length versus when the system is operating at high speed. Even though CE# may be Low throughout these extended data transfer cycles, the memory device host interface will go to the Automatic Sleep current at t_{ACC} + 30 ns. The device will remain at the Automatic Sleep current for t_{ASSB} . Then the device will transition to the standby current level. This keeps the memory at the Automatic Sleep or standby power level for most of the long duration data transfer cycles, rather than consuming full read power all the time that the memory device is selected by the host system.

However, the EAC operates independent of the automatic sleep mode of the host interface and will continue to draw current during an active Embedded Algorithm. Only when both the host interface and EAC are in their standby states is the standby level current achieved.

9.4 Read

9.4.1 Read With Output Disable

When the CE# signal is asserted Low, the host system memory controller begins a read or write data transfer. Often there is a period at the beginning of a data transfer when CE# is Low, Address is valid, OE# is High, and WE# is High. During this state a read access is assumed and the Random Read process is started while the data outputs remain at high impedance. If the OE# signal goes Low, the interface transitions to the Random Read state, with data outputs actively driven. If the WE# signal is asserted Low, the interface transitions to the Write state. Note, OE# and WE# should never be Low at the same time to ensure no data bus contention between the host system and memory.

9.4.2 Random (Asynchronous) Read

When the host system interface selects the memory device by driving CE# Low, the device interface leaves the Standby state. If WE# is High when CE# goes Low, a random read access is started. The data output depends on the address map mode and the address provided at the time the read access is started.

The data appears on DQ15-DQ0 when CE# is Low, OE# is Low, WE# remains High, address remains stable, and the asynchronous access times are satisfied. Address access time (t_{ACC}) is equal to the delay from stable addresses to valid output data. The chip enable access time (t_{CE}) is the delay from stable CE# to valid data at the outputs. In order for the read data to be driven on to the data outputs the OE# signal must be Low at least the output enable time (t_{CE}) before valid data is available.

At the completion of the random access time from CE# active (t_{CE}), address stable (t_{ACC}), or OE# active (t_{OE}), whichever occurs latest, the data outputs will provide valid read data from the currently active address map mode. If CE# remains Low and any of the A_{MAX} to A4 address signals change to a new value, a new random read access begins. If CE# remains Low and OE# goes High the interface transitions to the Read with Output Disable state. If CE# remains Low, OE# goes High, and WE# goes Low, the interface transitions to the Write state. If CE# returns High, the interface goes to the Standby state. Back to Back accesses, in which CE# remains Low between accesses, requires an address change to initiate the second access. See Asynchronous Read Operations on page 78.



9.4.3 Page Read

After a Random Read access is completed, if CE# remains Low, OE# remains Low, the A_{MAX} to A4 address signals remain stable, and any of the A3 to A0 address signals change, a new access within the same Page begins. The Page Read completes much faster (t_{PACC}) than a Random Read access.

9.5 Write

9.5.1 Asynchronous Write

When WE# goes Low after CE is Low, there is a transition from one of the read states to the Write state. If WE# is Low before CE# goes Low, there is a transition from the Standby state directly to the Write state without beginning a read access.

When CE# is Low, OE# is High, and WE# goes Low, a write data transfer begins. Note, OE# and WE# should never be Low at the same time to ensure no data bus contention between the host system and memory. When the asynchronous write cycle timing requirements are met the WE# can go High to capture the address and data values in to EAC command memory.

Address is captured by the falling edge of WE# or CE#, whichever occurs later. Data is captured by the rising edge of WE# or CE#, whichever occurs earlier.

When CE# is Low before WE# goes Low and stays Low after WE# goes High, the access is called a WE# controlled Write. When WE# is High and CE# goes High, there is a transition to the Standby state. If CE# remains Low and WE# goes High, there is a transition to the Read with Output Disable state.

When WE# is Low before CE# goes Low and remains Low after CE# goes High, the access is called a CE# controlled Write. A CE# controlled Write transitions to the Standby state.

If WE# is Low before CE# goes Low, the write transfer is started by CE# going Low. If WE# is Low after CE# goes High, the address and data are captured by the rising edge of CE#. These cases are referred to as CE# controlled write state transitions.

Write followed by Read accesses, in which CE# remains Low between accesses, requires an address change to initiate the following read access.

Back to Back accesses, in which CE# remains Low between accesses, requires an address change to initiate the second access.

The EAC command memory array is not readable by the host system and has no ASO. The EAC examines the address and data in each write transfer to determine if the write is part of a legal command sequence. When a legal command sequence is complete the EAC will initiate the appropriate EA.

9.5.2 Write Pulse "Glitch" Protection

Noise pulses of less than 5 ns (typical) on WE# will not initiate a write cycle.

9.5.3 Logical Inhibit

Write cycles are inhibited by holding OE# at V_{IL} , or CE# at V_{IH} , or WE# at V_{IH} . To initiate a write cycle, CE# and WE# must be Low (V_{IL}) while OE# is High (V_{IH}) .



10. Electrical Specifications

10.1 Absolute Maximum Ratings

Table 10.1 Absolute Maximum Ratings

Storage Temperature Plastic Packages	-65 °C to +150 °C		
Ambient Temperature with Power Applied	-65 °C to +125 °C		
Voltage with Respect to Ground			
All pins other than RESET# (Note 1)	-0.5 V to (V _{IO} + 0.5 V)		
RESET# (Note 1)	-0.5 V to (V _{CC} + 0.5 V)		
Output Short Circuit Current (Note 2)	100 mA		
V _{CC}	-0.5 V to +4.0 V		
V _{IO}	-0.5 V to +4.0 V		

Notes:

 Minimum DC voltage on input or I/O pins is -0.5 V. During voltage transitions, input or I/O pins may undershoot V_{SS} to -2.0 V for periods of up to 20 ns. See Figure 10.3 on page 71. Maximum DC voltage on input or I/O pins is V_{CC} + 0.5 V. During voltage transitions, input or I/O pins may overshoot to V_{CC} + 2.0 V for periods up to 20 ns. See Figure 10.4 on page 71

2. No more than one output may be shorted to ground at a time. Duration of the short circuit should not be greater than one second.

3. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this data sheet is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

10.2 Latchup Characteristics

This product complies with JEDEC standard JESD78C latchup testing requirements.

10.3 Thermal Resistance

Table 10.2 Thermal Resistance

Parameter	Description	LAA064	LAE064	TS056	Unit
Theta Ja	Thermal resistance (junction to ambient)	25	27.3	46.2	°C/W

10.4 Operating Ranges

10.4.1 Temperature Ranges

Deremotor	Symbol		Sp	Unit		
Parameter	Symbol	Device	Min	Мах	Onit	
	T _A	Industrial (I)	-40	+85		
Ambiant Tomporatura		Industrial Plus (V)	-40	+105	°C	
		Automotive, AEC-Q100 Grade 3 (A)	-40	+85		
		Automotive, AEC-Q100 Grade 2 (B)	-40	+105		



10.4.2 Power Supply Voltages

V _{CC}	2.7 V to 3.6 V
V _{IO}	1.65 V to V _{CC} +200 mV

Operating ranges define those limits between which the functionality of the device is guaranteed.

10.4.3 Power-Up and Power-Down

During power-up or power-down V_{CC} must always be greater than or equal to V_{IO} (V_{CC} \ge V_{IO}).

The device ignores all inputs until a time delay of t_{VCS} has elapsed after the moment that V_{CC} and V_{IO} both rise above, and stay above, the minimum V_{CC} and V_{IO} thresholds. During t_{VCS} the device is performing power on reset operations.

During power-down or voltage drops below V_{CC} Lockout maximum (V_{LKO}), the V_{CC} and V_{IO} voltages must drop below V_{CC} Reset (V_{RST}) minimum for a period of t_{PD} for the part to initialize correctly when V_{CC} and V_{IO} again rise to their operating ranges. See Figure 10.2 on page 71. If during a voltage drop the V_{CC} stays above V_{LKO} maximum the part will stay initialized and will work correctly when V_{CC} is again above V_{CC} minimum. If the part locks up from improper initialization, a hardware reset can be used to initialize the part correctly.

Normal precautions must be taken for supply decoupling to stabilize the V_{CC} and V_{IO} power supplies. Each device in a system should have the V_{CC} and V_{IO} power supplies decoupled by a suitable capacitor close to the package connections (this capacitor is generally on the order of 0.1 μ F). At no time should V_{IO} be greater then 200 mV above V_{CC} (V_{CC} \geq V_{IO} -200 mV).

Symbol	Parameter	Min	Мах	Unit
V _{CC}	V _{CC} Power Supply	2.7	3.6	V
V _{LKO}	V _{CC} level below which re-initialization is required (Note 1)	2.25	2.5	V
V _{RST}	V_{CC} and V_{IO} Low voltage needed to ensure initialization will occur (Note 1)	1.0	_	V
^t vcs	V_{CC} and $V_{IO} \ge$ minimum to first access (Note 1)	300	-	μs
t _{PD}	Duration of $V_{CC} \leq V_{RST}(min)$ (Note 1)	15	_	μs

 Table 10.3
 Power-Up/Power-Down Voltage and Timing

Note:

1. Not 100% tested.





Figure 10.2 Power-down and Voltage Drop



10.4.4 Input Signal Overshoot





Figure 10.4 Maximum Positive Overshoot Waveform





10.5 DC Characteristics

Table 10.4 DC Characteristics (-40 °C to +85 °C)

Parameter	Description	Test Conditions	Min	Typ (Note 2)	Max	Unit
lu	Input Load Current	$V_{IN} = V_{SS}$ to V_{CC} , $V_{CC} = V_{CC}$ max	-	+0.02	±1.0	μA
ILO	Output Leakage Current	$V_{OUT} = V_{SS}$ to V_{CC} , $V_{CC} = V_{CC}$ max	-	+0.02	±1.0	μA
I _{CC1}	V _{CC} Active Read Current	CE# = V _{IL} , OE# = V _{IH} , Address switching @ 5 MHz, V _{CC} = V _{CC} max	-	55	60	mA
I _{CC2}	V _{CC} Intra-Page Read Current	CE# = V _{IL} , OE# = V _{IH} , Address switching @ 33 MHz, V _{CC} = V _{CC} max	-	9	25	mA
I _{CC3}	V _{CC} Active Erase/Program Current (Notes 1, 2)	$CE# = V_{IL}, OE# = V_{IH}, V_{CC} = V_{CC} max$	-	45	100	mA
I _{CC4}	V _{CC} Standby Current	CE#, RESET#, OE# = V _{IH} , V _{IH} = V _{IO} V _{IL} = V _{SS} , V _{CC} = V _{CC} max	-	70	100	μA
I _{CC5}	V _{CC} Reset Current (Notes 2, 7)	CE# = V _{IH} , RESET# = V _{IL} , V _{CC} = V _{CC} max	-	10	20	mA
1	Automatic Sloop Made (Note 3)	V _{IH} = V _{IO} , V _{IL} = V _{SS} , V _{CC} = V _{CC} max, t _{ACC} + 30 ns	-	3	6	mA
'CC6	Automatic Sleep Mode (Note 5)	V _{IH} = V _{IO} , V _{IL} = V _{SS} , V _{CC} = V _{CC} max, t _{ASSB}	-	100	150	μA
I _{CC7}	V _{CC} Current during power up (Notes 2, 6)	$\begin{array}{l} RESET\# = V_{IO},CE\# = V_{IO}, \; OE\# = V_{IO}, \\ V_{CC} = V_{CC} \; max, \end{array}$	-	53	80	mA
V _{IL}	Input Low Voltage (Note 4)		-0.5	-	0.3 × V _{IO}	V
V _{IH}	Input High Voltage (Note 4)		0.7 × V _{IO}	_	V _{IO} + 0.4	V
V _{OL}	Output Low Voltage (Notes 4, 8)	I _{OL} = 100 μA for DQ15–DQ0; I _{OL} = 2 mA for RY/BY#	-	-	0.15 × V _{IO}	V
V _{OH}	Output High Voltage (Note 4)	Ι _{ΟΗ} = 100 μΑ	0.85 × V _{IO}	-	-	V
V _{LKO}	Low V _{CC} Lock-Out Voltage (Note 2)		2.25	-	2.5	V
V _{RST}	Low V _{CC} Power on Reset Voltage (Note 2)		-	1.0	_	V

Notes:

1. I_{CC} active while Embedded Algorithm is in progress.

2. Not 100% tested.

3. Automatic sleep mode enables the lower power mode when addresses remain stable for the specified designated time.

4. $V_{IO} = 1.65V$ to V_{CC} or 2.7V to V_{CC} depending on the model.

5. $V_{CC} = 3V$ and $V_{IO} = 3V$ or 1.8V. When V_{IO} is at 1.8V, I/O pins cannot operate at >1.8V.

6. During power-up there are spikes of current demand, the system needs to be able to supply this current to insure the part initializes correctly.

7. If an embedded operation is in progress at the start of reset, the current consumption will remain at the embedded operation specification until the embedded operation is stopped by the reset. If no embedded operation is in progress when reset is started, or following the stopping of an embedded operation, I_{CC5} will be drawn during the remainder of t_{RPH}. After the end of t_{RPH} the device will go to standby mode until the next read or write.

8. The recommended pull-up resistor for RY/BY# output is 5k to 10k Ohms.



Table 10.5 DC Characteristics (-40°C to +105°C)

Parameter	Description	Test Conditions	Min	Typ (Note 2)	Max	Unit
ι _{LI}	Input Load Current	$V_{IN} = V_{SS}$ to V_{CC} , $V_{CC} = V_{CC}$ max	-	+0.02	±1.0	μA
ILO	Output Leakage Current	$V_{OUT} = V_{SS}$ to V_{CC} , $V_{CC} = V_{CC}$ max	-	+0.02	±1.0	μA
I _{CC1}	V _{CC} Active Read Current	CE# = V _{IL} , OE# = V _{IH} , Address switching @ 5 MHz, V _{CC} = V _{CC} max	-	55	60	mA
I _{CC2}	V _{CC} Intra-Page Read Current	CE# = V _{IL} , OE# = V _{IH} , Address switching @ 33 MHz, V _{CC} = V _{CC} max	-	9	25	mA
I _{CC3}	V _{CC} Active Erase/Program Current (Notes 1, 2)	$CE\# = V_{IL}, OE\# = V_{IH}, V_{CC} = V_{CC} max$	_	45	100	mA
I _{CC4}	V _{CC} Standby Current	CE#, RESET#, OE# = V _{IH} , V _{IH} = V _{IO} V _{IL} = V _{SS} , V _{CC} = V _{CC} max	-	70	200	μA
I _{CC5}	V _{CC} Reset Current (Notes 2, 7)	CE# = V _{IH} , RESET# = V _{IL} , V _{CC} = V _{CC} max	-	10	20	mA
1	Automatic Slean Made (Note 2)	V _{IH} = V _{IO} , V _{IL} = V _{SS} , V _{CC} = V _{CC} max, t _{ACC} + 30 ns	-	3	6	mA
ICC6	Automatic Sleep Mode (Note 5)	V _{IH} = V _{IO} , V _{IL} = V _{SS} , V _{CC} = V _{CC} max, t _{ASSB}	-	100	200	μA
I _{CC7}	V _{CC} Current during power-up (Notes 2, 6)	$\begin{array}{l} RESET\# = V_{IO}, CE\# = V_{IO}, \; OE\# = V_{IO}, \\ V_{CC} = V_{CC} \; max, \end{array}$	-	53	80	mA
VIL	Input Low Voltage (Note 4)		-0.5	-	0.3 × V _{IO}	V
V _{IH}	Input High Voltage (Note 4)		0.7 × V _{IO}	-	V _{IO} + 0.4	V
V _{OL}	Output Low Voltage (Notes 4, 8)	I _{OL} = 100 μA for DQ15–DQ0; I _{OL} = 2 mA for RY/BY#	-	_	0.15 × V _{IO}	V
V _{OH}	Output High Voltage (Note 4)	I _{OH} = 100 μA	0.85 × V _{IO}	-	-	V
V _{LKO}	Low V _{CC} Lock-Out Voltage (Note 2)		2.25	-	2.5	V
V _{RST}	Low V _{CC} Power on Reset Voltage (Note 2)		-	1.0	-	V

Notes:

1. I_{CC} active while Embedded Algorithm is in progress.

2. Not 100% tested.

3. Automatic sleep mode enables the lower power mode when addresses remain stable for the specified designated time.

4. $V_{IO} = 1.65$ V to V_{CC} or 2.7 V to V_{CC} depending on the model.

5. V_{CC} = 3 V and V_{IO} = 3 V or 1.8 V. When V_{IO} is at 1.8 V, I/O pins cannot operate at >1.8 V.

6. During power-up there are spikes of current demand, the system needs to be able to supply this current to insure the part initializes correctly.

7. If an embedded operation is in progress at the start of reset, the current consumption will remain at the embedded operation specification until the embedded operation is stopped by the reset. If no embedded operation is in progress when reset is started, or following the stopping of an embedded operation, I_{CC7} will be drawn during the remainder of t_{RPH}. After the end of t_{RPH} the device will go to standby mode until the next read or write.

8. The recommended pull-up resistor for RY/BY# output is 5k to 10k Ohms.



10.6 Capacitance Characteristics

Table 10.6 Connector Capacitance for FBGA (LAA) Package

Parameter Symbol	Parameter Description	Test Setup	Тур	Max	Unit
C _{IN}	Input Capacitance	V _{IN} = 0	8	9	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0	5	7	pF
C _{IN2}	Control Pin Capacitance	V _{IN} = 0	4	8	pF
RY/BY#	Output Capacitance	V _{OUT} = 0	3	4	pF

Notes:

1. Sampled, not 100% tested.

2. Test conditions $T_A = 25 \text{ °C}$, f = 1.0 MHz.

Table 10.7 Connector Capacitance for FBGA (LAE) Package

Parameter Symbol	Parameter Description	Test Setup	Тур	Max	Unit
C _{IN}	Input Capacitance	V _{IN} = 0	7	8	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0	5	6	pF
C _{IN2}	Control Pin Capacitance	V _{IN} = 0	3	7	pF
RY/BY#	Output Capacitance	V _{OUT} = 0	3	4	pF

Notes:

1. Sampled, not 100% tested.

2. Test conditions $T_A = 25$ °C, f = 1.0 MHz.

Table 10.8 Connector Capacitance for TSOP Package

Parameter Symbol	Parameter Description	Test Setup	Тур	Max	Unit
C _{IN}	Input Capacitance	V _{IN} = 0	7	8	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0	5	6	pF
C _{IN2}	Control Pin Capacitance	V _{IN} = 0	3	7	pF
RY/BY#	Output Capacitance	V _{OUT} = 0	3	4	pF

Notes:

1. Sampled, not 100% tested.

2. Test conditions $T_A = 25$ °C, f = 1.0 MHz.



11. Timing Specifications

11.1 Key to Switching Waveforms

Waveform	Inputs	Outputs		
	Steady			
	Changing from H to L			
	Changing from L to H			
	Don't Care, Any Change Permitted	Changing, State Unknown		
	Does Not Apply	Center Line is High Impedance State (High-Z)		

11.2 AC Test Conditions

Figure 11.1 Test Setup



Table 11.1 Test Specification

Parameter	All Speeds	Units
Output Load Capacitance, C _L	30	pF
Input Rise and Fall Times (Note 1)	1.5	ns
Input Pulse Levels	0.0–V _{IO}	V
Input timing measurement reference levels	V _{IO} /2	V
Output timing measurement reference levels	V _{IO} /2	V

Note:

1. Measured between V_{IL} max and V_{IH} min.







11.3 Power-On Reset (POR) and Warm Reset

Normal precautions must be taken for supply decoupling to stabilize the V_{CC} and V_{IO} power supplies. Each device in a system should have the V_{CC} and V_{IO} power supplies decoupled by a suitable capacitor close to the package connections (this capacitor is generally on the order of 0.1 μ F).

Parameter	Description	Limit	Value	Unit
t _{VCS}	V _{CC} Setup Time to first access (Notes 1, 2)	Min	300	μs
^t vios	V _{IO} Setup Time to first access (Notes 1, 2)	Min	300	μs
t _{RPH}	RESET# Low to CE# Low	Min	35	μs
t _{RP}	RESET# Pulse Width	Min	200	ns
t _{RH}	Time between RESET# (High) and CE# (low)	Min	50	ns
^t сен	CE# Pulse Width High	Min	20	ns

Table 11.2 Power ON and Reset Parameters

Notes:

1. Not 100% tested.

3. RESET# Low is optional during POR. If RESET is asserted during POR, the later of t_{RPH}, t_{VIOS}, or t_{VCS} will determine when CE# may go Low. If RESET# remains Low after t_{VIOS}, or t_{VCS} is satisfied, t_{RPH} is measured from the end of t_{VIOS}, or t_{VCS}. RESET must also be High t_{RH} before CE# goes Low.

4. $V_{CC} \ge V_{IO}$ - 200 mV during power-up.

5. V_{CC} and V_{IO} ramp rate can be non-linear.

6. Sum of t_{RP} and t_{RH} must be equal to or greater than t_{RPH} .

11.3.1 Power-On (Cold) Reset (POR)

During the rise of power supplies the V_{IO} supply voltage must remain less than or equal to the V_{CC} supply voltage. V_{IH} also must remain less than or equal to the V_{IO} supply.

The Cold Reset Embedded Algorithm requires a relatively long, hundreds of μ s, period (t_{VCS}) to load all of the EAC algorithms and default state from non-volatile memory. During the Cold Reset period all control signals including CE# and RESET# are ignored. If CE# is Low during t_{VCS} the device may draw higher than normal POR current during t_{VCS} but the level of CE# will not affect the Cold Reset EA. CE# or OE# must transition from High to Low after t_{VCS} for a valid read or write operation. RESET# may be High or Low during t_{VCS} . If RESET# is Low during t_{VCS} it may remain Low at the end of t_{VCS} to hold the device in the Hardware Reset state. If RESET# is High at the end of t_{VCS} the device will go to the Standby state.

When power is first applied, with supply voltage below V_{RST} then rising to reach operating range minimum, internal device configuration and warm reset activities are initiated. CE# is ignored for the duration of the POR operation (t_{VCS} or t_{VIOS}). RESET# Low during this POR period is optional. If RESET# is driven Low during POR it must satisfy the Hardware Reset parameters t_{RP} and t_{RPH} . In which case the Reset operations will be completed at the later of t_{VCS} or t_{VIOS} or t_{RPH} .

During Cold Reset the device will draw I_{CC7} current.

^{2.} Timing measured from V_{CC} reaching V_{CC} minimum and V_{IO} reaching V_{IO} minimum to V_{IH} on Reset and V_{IL} on CE#.



Figure 11.3 Power-Up Diagram



11.3.2 Hardware (Warm) Reset

During Hardware Reset (t_{RPH}) the device will draw I_{CC5} current.

When RESET# continues to be held at V_{SS} , the device draws CMOS standby current (I_{CC4}). If RESET# is held at V_{IL} , but not at V_{SS} , the standby current is greater.

If a Cold Reset has not been completed by the device when RESET# is asserted Low after t_{VCS}, the Cold Reset# EA will be performed instead of the Warm RESET#, requiring t_{VCS} time to complete.

See Figure 11.4 on page 77.

After the device has completed POR and entered the Standby state, any later transition to the Hardware Reset state will initiate the Warm Reset Embedded Algorithm. A Warm Reset is much shorter than a Cold Reset, taking tens of µs (t_{RPH}) to complete. During the Warm Reset EA, any in progress Embedded Algorithm is stopped and the EAC is returned to its POR state without reloading EAC algorithms from non-volatile memory. After the Warm Reset EA completes, the interface will remain in the Hardware Reset state if RESET# remains Low. When RESET# returns High the interface will transit to the Standby state. If RESET# is High at the end of the Warm Reset EA, the interface will directly transit to the Standby state.

If POR has not been properly completed by the end of t_{VCS}, a later transition to the Hardware Reset state will cause a transition to the Power-on Reset interface state and initiate the Cold Reset Embedded Algorithm. This ensures the device can complete a Cold Reset even if some aspect of the system Power-On voltage ramp-up causes the POR to not initiate or complete correctly. The RY/ BY# pin is Low during cold or warm reset as an indication that the device is busy performing reset operations.

Hardware Reset is initiated by the RESET# signal going to VIL.





11.4 AC Characteristics

11.4.1 Asynchronous Read Operations

Table 11.3 Read Operation $V_{IO} = V_{CC} = 2.7$ V to 3.6 V (-40 °C to +85 °C)

Parameter		Description		Tost Sotup		Speed Option			Unit
JEDEC	Std	Description	lest Setu	, ,	90	100	110	Unit	
+	+	Read Cycle Time (Note 1)		128 Mb, 256 Mb	Min	90	100	_	-
LAVAV	4RC			512 Mb, 1 Gb		-	100	110	ns
+	+	Address to Output Dolov	CE# = V _{IL}	128 Mb, 256 Mb	Max	90	100	-	ne
^L AVQV	ACC	Address to Output Delay	$OE# = V_{IL}$	512 Mb, 1 Gb	IVIAX	_	100	110	115
+	+	Chin Enchla ta Output Dalay		128 Mb, 256 Mb	Max	90	100	-	ne
^L ELQV	'CE	Chip Enable to Output Delay	0E# - VIL	512 Mb, 1 Gb	Wax	-	100	110	ns
	÷	Daga Assass Time	•	128 Mb, 256 Mb	Max	15	20	_	n c
	PACC			512 Mb, 1 Gb	Wax	-	15	20	115
^t glqv	t _{OE}	Output Enable to Output Delay			Max	25		ns	
t _{AXQX}	t _{он}	Output Hold time from addresse Whichever Occurs First	es, CE# or OE#,		Min	0		ns	
t _{EHQZ}	t _{DF}	Chip Enable or Output Enable to Output High-Z (Note 1)			Max	15			ns
		Output Enable Hold Time	Read		Min		0		ns
toe⊦	^t оен	(Note 1)	Toggle and Data# Polling		Min	10			ns
	t	Automatic Sleen to Standby tim	e (Note 1)	CE# = V _{IL} ,	Тур	5			μs
	'ASSB		Address stable		Max	8			μs

Note:

1. Not 100% tested.

Table 11.4 Read Operation V_{IO} = 1.65 V to V_{CC} , V_{CC} = 2.7 V to 3.6 V (-40 °C to +85 °C)

Param	eter	Description		Teat Satu	Tost Sotup		Speed Options		
JEDEC	Std	Description		Test Setu	þ	100	110	120	Unit
+	+	Road Cycle Time (Note 1)		128 Mb, 256 Mb	Min	100	110	-	nc
'AVAV	ЧRС			512 Mb, 1 Gb	101111	-	110	120	115
+	+	$CE\# = V_{IL}$		128 Mb, 256 Mb	Max	100	110	-	nc
'AVQV	ACC	Address to Output Delay	$OE# = V_{IL}$	512 Mb, 1 Gb	wax	-	110	120	ns
+	+	Chin Enchle to Output Deleve	hin Enchlate Output Delay, OF# = \/		Mox	100	110	-	ns
ΈLQV			OE = VIL	512 Mb, 1 Gb	WIAX	-	110	120	
	+	Daga Aasaa Tima	•	128 Mb, 256 Mb	Mox	25	30	-	ns
	ФАСС	rage Access Time		512 Mb, 1 Gb	IVIAX	-	25	30	
t _{glav}	t _{oe}	Output Enable to Output Dela	у		Max		35		ns
t _{AXQX}	tон	Output Hold time from addres OE#, Whichever Occurs First		Min	0		ns		
t _{EHQZ}	t _{DF}	Chip Enable or Output Enable Z (Note 1)	to Output High-		Max		20		ns



Table 11.4 Read Operation V_{IO} = 1.65 V to V_{CC} , V_{CC} = 2.7 V to 3.6 V (-40 °C to +85 °C) (Continued)

Parameter		Description		Toot Sotup		Speed Options			Unit
JEDEC	Std	Description	Description		5	100	110	120	
		Output Enchlo Hold Time	Read		Min		0		ns
t _{оен}		(Note 1)	Toggle and Data# Polling		Min		10		ns
+ Δ		Automatic Sleen to Standby ti	Automatic Sloop to Standby time (Note 1)		Тур		5		μs
ASSB	Automatic Sleep to Standby time (Note T)		Address stable Max			8		μs	

Note:

1. Not 100% tested.

Table 11.5 Read Operation $V_{IO} = V_{CC} = 2.7$ V to 3.6 V (-40 °C to +105 °C)

Para	meter	Description		Tost Satur		SI	beed Opti	on	Unit
JEDEC	Std	Description		Test Setup		100	110	120	Unit
+	+	Road Cycle Time (Note 1)		128 Mb, 256 Mb	Min	100	110	-	nc
YAVAV	RC	Read Cycle Time (Note T)				-	110	120	115
t	t	Address to Output Delay	CE# = V _{IL}	128 Mb, 256 Mb	Мах	100	110	-	ne
YAVQV YACC	Address to Odiput Delay	$OE\# = V_{IL}$	512 Mb, 1 Gb	IVIAX	-	110	120	115	
+ +	Chip Enable to Output	OE = 1	128 Mb, 256 Mb	Mox	100	110	-	nc	
'ELQV	^I CE Delay		0E# - VIL	512 Mb, 1 Gb	wax	-	110	120	115
	+	Page Access Time		128 Mb, 256 Mb	Max	15	20	-	ns
PACC				512 Mb, 1 Gb	IVIAX	_	15	20	113
t _{GLQV}	t _{OE}	Output Enable to Output De	elay		Max	25			ns
t _{AXQX}	^t он	Output Hold time from addr OE#, Whichever Occurs Fi	resses, CE# or rst		Min	0			ns
t _{EHQZ}	t _{DF}	Chip Enable or Output Ena High-Z (Note 1)	ble to Output		Max	15			ns
		Output Enable Hold Time	Read		Min		0		ns
t _{OEH}		(Note 1)	Toggle and Data# Polling		Min	Min 10			ns
	t	Automatic Sleep to Standby	v time (Note 1)	CE# = V _{IL} , Address	Тур	5			μs
	'ASSB			stable	Max		8		μs

Note:

1. Not 100% tested.

Table 11.6 Read Operation V_{IO} = 1.65 V to V_{CC} , V_{CC} = 2.7 V to 3.6 V (-40 °C to +105 °C)

Parameter		Description		Teat Satur	Test Satur		Speed Option		
JEDEC	Std	Description	lesi Selup		110	120	130	Unit	
+	t Deed Cycle Time (Note 1)			128 Mb, 256 Mb	Min	110	120	-	ns
AVAV IRC Read Cycle Time (Note T)			512 Mb, 1 Gb		-	120	130		
+	+	Address to Output Delay	CE# = V _{IL}	128 Mb, 256 Mb	Max	110	120	-	ns
AVQV ACC	'ACC	Address to Output Delay	$OE# = V_{IL}$	512 Mb, 1 Gb		-	120	130	
+	+	Chip Enable to Output	128 Mb, 256 Mb	Max	110	120	-	ns	
	Delay	02# - VIL	512 Mb, 1 Gb	Wax	-	120	130		



Para	meter	Description		Teat Satur		Sp	peed Option	on	Unit
JEDEC	Std	Description		lest Setup		110	120	130	om
		Paga Access Time			Max	25	30	-	
PACC	Page Access Time		512 Mb, 1 Gb	IVIAX	Ι	25	30	115	
t _{glqv}	t _{OE}	Output Enable to Output De	Output Enable to Output Delay		Max	35		ns	
t _{AXQX}	^t он	Dutput Hold time from addresses, CE# or DE#, Whichever Occurs First			Min	0		ns	
t _{EHQZ}	t _{DF}	Chip Enable or Output Enable to Output High-Z (Note 1)			Max	20		ns	
		Output Enable Hold Time	Read		Min		0		ns
^t оен	(Note 1)	Toggle and Data# Polling		Min		10		ns	
	t	Automatic Slaan to Standby time (Nate 1)		CE# = V _{IL} , Address	Тур		5		μs
	^L ASSB			stable	Max	8		μs	

Table 11.6 Read Operation V_{IO} = 1.65 V to V_{CC} , V_{CC} = 2.7 V to 3.6 V (-40 °C to +105 °C) (Continued)

Note:

1. Not 100% tested.











Note:

Back to Back operations, in which CE# remains Low between accesses, requires an address change to initiate the second access.



Figure 11.7 Page Read Timing Diagram



Note:

Word Configuration: Toggle A0, A1, A2, and A3.



11.4.2 Asynchronous Write Operations

 Table 11.7
 Write Operations

Para	meter	Departmen		V _{IO} = 2.7 V	V _{IO} = 1.65 V	Unit	
JEDEC	Std	Description		to V _{CC}	to V _{CC}	Unit	
t _{AVAV}	t _{WC}	Write Cycle Time (Note 1)	Min	6	60		
t _{AVWL}	t _{AS}	Address Setup Time	Min	(0		
	t _{ASO}	Address Setup Time to OE# Low during toggle bit polling	Min	1	15		
t _{WLAX}	t _{AH}	Address Hold Time	Min	4	5	ns	
	t _{AHT}	Address Hold Time From CE# or OE# High during toggle bit polling	Min	0		ns	
t _{DVWH}	t _{DS}	Data Setup Time	Min	30		ns	
t _{WHDX}	t _{DH}	Data Hold Time	Min	()	ns	
	t _{OEPH}	Output Enable High during toggle bit polling or following status register read.	Min	2	0	ns	
^t GHWL	t _{GHWL}	Read Recovery Time Before Write (OE# High to WE# Low)	Recovery Time Before Write Min 0)	ns	
t _{ELWL}	tcs	CE# Setup Time Min 0)	ns		
t _{WHEH}	^t сн	CE# Hold Time	Min	0		ns	
t _{WLWH}	t _{WP}	WE# Pulse Width Min		25		ns	
t _{WHWL}	twPH	WE# Pulse Width High	Min	2	0	ns	

Note:

1. Not 100% tested.



Figure 11.8 Back to Back Write Operation Timing Diagram





Figure 11.9 Back to Back (CE#VIL) Write Operation Timing Diagram











Figure 11.11 Write to Read (t_{CE}) Operation Timing Diagram







Figure 11.13 Read to Write (CE# Toggle) Operation Timing Diagram

Table 11.8 Erase/Program Operations

Parameter		Description		V _{IO} = 2.7 V	V _{IO} = 1.65 V	Unit		
JEDEC	Std	Description		to V _{CC}	to V _{CC}	Unit		
		Write Buffer Program Operation	Typ (Note 3)		te 3)	μs		
t _{WHWH1}	t _{WHWH1}	Effective Write Buffer Program Operation per Word		(Not	te 3)	μs		
		Program Operation per Word or Page	Тур	(Note 3)		μs		
t _{WHWH2}	t _{WHWH2}	Sector Erase Operation (Note 1)	Тур	(Note 3)		ms		
	t _{BUSY}	Erase/Program Valid to RY/BY# Delay	Max	8	0	ns		
	t _{SR/W}	Latency between Read and Write operations (Note 2)	Min	1	0	ns		
	t _{ESL}	Erase Suspend Latency Max (Note 3)		te 3)	μs			
	t _{PSL}	Program Suspend Latency	Max	(Note 3)		(Note 3)		μs
	t _{RB}	RY/BY# Recovery Time	Min	(0			

Notes:

1. Not 100% tested.

2. Upon the rising edge of WE#, must wait $t_{SR/W}$ before switching to another address.

3. See Table 5.4 on page 43 and Table 5.5 on page 44 for specific values.





Note:

1. PA = program address, PD = program data, D_{OUT} is the true data at the program address.



Figure 11.15 Chip/Sector Erase Operation Timing Diagram

Note:

1. SA = sector address (for sector erase), VA = valid address for reading status data.



Table 11.9 ASO Entry Timing

t _{asostart}	Falling edge of CE# or address change whichever comes last
t _{asoend}	Rising edge of CE# or Rising edge of WE# whichever comes first
t _{asoentry}	25 ns < t _{ASOENTRY} < 50 ns or t _{ASOENTRY} > 150 ns

Note:

1. If this timing cannot be achieved, perform the following steps immediately after ASO Exit and before resuming normal processing: read one word from each of 64 unique 32 byte-aligned pages.



Note:

1. Applicable to any ASO entry command.





Note:

1. VA = Valid address. Illustration shows first status cycle after command sequence, last status read cycle, and array data read cycle.





Figure 11.18 Toggle Bit Timing Diagram (During Embedded Algorithms)

Note:

1. DQ6 will toggle at any read address while the device is busy. DQ2 will toggle if the address is within the actively erasing sector.



Figure 11.19 DQ2 vs. DQ6 Relationship Diagram

Note:

1. The system may use OE# or CE# to toggle DQ2 and DQ6. DQ2 toggles only when read at an address within the erase-suspended sector.

11.4.3 Alternate CE# Controlled Write Operations

Table 11.10 Alternate CE# Controlled Write Operations

Para	meter	Description		V _{IO} = 2.7 V	V _{IO} = 1.65 V	Unit	
JEDEC	Std	Description		to V _{CC}	to V _{CC}	Onit	
t _{AVAV}	t _{WC}	Write Cycle Time (Note 1)	Min	6	60		
t _{AVWL}	t _{AS}	Address Setup Time	Min	()	ns	
	t _{aso}	Address Setup Time to OE# Low during toggle bit polling	Min	15		ns	
t _{WLAX}	t _{AH}	Address Hold Time	Min	45		ns	
	t _{AHT}	Address Hold Time From CE# or OE# High during toggle bit polling	Min	0		ns	
t _{DVWH}	t _{DS}	Data Setup Time	Min	3	0	ns	
t _{WHDX}	t _{DH}	Data Hold Time	Min		D	ns	
	t _{CEPH}	CE# High during toggle bit polling	Min	20		ns	
	t _{OEPH}	OE# High during toggle bit polling	Min	2	:0	ns	



Table 11.10 Alternate CE# Controlled Write Operations (Continued)

Parameter		Description		V _{IO} = 2.7 V	V _{IO} = 1.65 V	Unit
JEDEC	Std	Description		to V _{CC}	to V _{CC}	Onic
^t GHEK	t _{GHEL}	Read Recovery Time Before Write (OE# High to WE# Low)	Min	0		ns
t _{WLEL}	t _{WS}	WE# Setup Time	Min	0		ns
t _{ELWH}	t _{WH}	WE# Hold Time	Min	0		ns
t _{ELEH}	t _{CP}	CE# Pulse Width Min 25		5	ns	
t _{EHEL}	^t CPH	CE# Pulse Width High Min 20		0	ns	

Note:

1. Not 100% tested.





Figure 11.21 (CE#) Write to Read Operation Timing Diagram





12. Physical Interface

12.1 56-pin TSOP

12.1.1 Connection Diagram



Figure 12.1 56-pin Standard TSOP

Notes:

- Pin 28, Do Not Use (DNU), a device internal signal is connected to the package connector. The connector may be used by Cypress for test or other purposes and is not intended for connection to any host system signal. Do not use these connections for PCB Signal routing channels. Though not recommended, the ball can be connected to V_{CC} or V_{SS} through a series resistor.
- 2. Pin 27, 30, and 53 Reserved for Future Use (RFU).



12.1.2 Physical Diagram



Figure 12.2 56-pin Thin Small Outline Package (TSOP), 14 × 20 mm

PACKAGE		TS 56			
JEDEC	M	D-142 (B) E	С		
SYMBOL	MIN.	NOM.	MAX.		
A			1.20		
A1	0.05		0.15		
A2	0.95	1.00	1.05		
b1	0.17	0.20	0.23		
b	0.17	0.22	0.27		
c1	0.10		0.16		
с	0.10		0.21		
D	19.80	20.00	20.20		
D1	18.30	18.40	18.50		
E	13.90	14.00	14.10		
е	(0.50 BASIC			
L	0.50	0.60	0.70		
ø	0°	-	8°		
R	0.08	·	0.20		
N	56				

NOTES:

- $\overline{1}$
- CONTROLLING DIMENSIONS ARE IN MILLIMETERS (mm). (DIMENSIONING AND TOLERANCING CONFORMS TO ANSI Y14.5M-1982.) PIN 1 IDENTIFIER FOR STANDARD PIN OUT (DIE UP).
- 2
- $\underline{\mathbb{A}}$ TO BE DETERMINED AT THE SEATING PLANE $\,$ -C- $\,$. THE SEATING PLANE IS DEFINED AS THE PLANE OF CONTACT THAT IS MADE WHEN THE PACKAGE LEADS ARE ALLOWED TO REST FREELY ON A FLAT HORIZONTAL SURFACE.
- A DIMENSIONS D1 AND E DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTUSION IS 0.15 mm PER SIDE.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTUSION. ALLOWABLE DAMBAR PROTUSION SHALL BE 0.08 mm TOTAL IN EXCESS OF b DIMENSION AT MAX MATERIAL CONDITION. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD TO BE 0.07 mm.
- CHESE DIMESIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 mm AND 0.25 mm FROM THE LEAD TIP.
- LEAD COPLANARITY SHALL BE WITHIN 0.10 mm AS MEASURED FROM THE SEATING PLANE.
- A DIMENSION "e" IS MEASURED AT THE CENTERLINE OF THE LEADS.

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12.2 64-Ball FBGA

12.2.1 Connection Diagram



Notes:

- Ball E1, Do Not Use (DNU), a device internal signal is connected to the package connector. The connector may be used by Cypress for test or other purposes and is not intended for connection to any host system signal. Do not use these connections for PCB Signal routing channels. Though not recommended, the ball can be connected to V_{CC} or V_{SS} through a series resistor.
- 2. Balls F7 and G1, Reserved for Future Use (RFU).
- 3. Balls A1, A8, C1, D1, H1, and H8, No Connect (NC).





12.2.2 Physical Diagram – LAE064



Figure 12.4 LAE064—64-ball Fortified Ball Grid Array (FBGA), 9 × 9 mm

PACKAGE		LAE 064		
JEDEC		N/A		
	9.0	0 mm x 9.00 PACKAGE	mm	
SYMBOL	MIN	NOM	MAX	NOTE
A			1.40	PROFILE HEIGHT
A1	0.40			STANDOFF
A2	0.60			BODY THICKNESS
D		9.00 BSC.		BODY SIZE
E		9.00 BSC.		BODY SIZE
D1		7.00 BSC.		MATRIX FOOTPRINT
E1		7.00 BSC.		MATRIX FOOTPRINT
MD		8		MATRIX SIZE D DIRECTION
ME		8		MATRIX SIZE E DIRECTION
N		64		BALL COUNT
b	0.50	0.60	0.70	BALL DIAMETER
eD		1:00 BSC.		BALL PITCH - D DIRECTION
eE		1.00 BSC.		BALL PITCH - E DIRECTION
SD / SE		0.50 BSC.		SOLDER BALL PLACEMENT
?		NONE		DEPOPULATED SOLDER BALLS

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- 3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010?
- EXCEPT AS NOTED). 4. e REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL ROW MATRIX SIZE IN THE "D" DIRECTION.
 - SYMBOL "ME" IS THE BALL COLUMN MATRIX SIZE IN THE "E" DIRECTION.

N IS THE TOTAL NUMBER OF SOLDER BALLS.

DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.

 SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
 WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN ? THE OUTER ROW PARALLEL TO THE D OR E DIMENSION, RESPECTIVELY, SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = $\boxed{9/2}$

- 8. NOT USED.
- "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

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12.2.3 Physical Diagram – LAA064



PACKAGE	LAA 064			
JEDEC	N/A			
	13.00 mm x 11.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
А			1.40	PROFILE HEIGHT
A1	0.40			STANDOFF
A2	0.60			BODY THICKNESS
D	13.00 BSC.			BODY SIZE
E	11.00 BSC.			BODY SIZE
D1	7.00 BSC.			MATRIX FOOTPRINT
E1	7.00 BSC.			MATRIX FOOTPRINT
MD	8			MATRIX SIZE D DIRECTION
ME	8			MATRIX SIZE E DIRECTION
N	64			BALL COUNT
φb	0.50	0.60	0.70	BALL DIAMETER
eD	1.00 BSC.			BALL PITCH - D DIRECTION
eE	1.00 BSC.			BALL PITCH - E DIRECTION
SD / SE	0.50 BSC.			SOLDER BALL PLACEMENT
	NONE			DEPOPULATED SOLDER BALLS

- NOTES:
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- 3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010 (EXCEPT AS NOTED).
- 4. e REPRESENTS THE SOLDER BALL GRID PITCH.
- 5. SYMBOL "MD" IS THE BALL ROW MATRIX SIZE IN THE "D" DIRECTION.
- SYMBOL "ME" IS THE BALL COLUMN MATRIX SIZE IN THE "E" DIRECTION.
- N IS THE TOTAL NUMBER OF SOLDER BALLS.
- DIAMETER IN A PLANE PARALLEL TO DATUM C.
- A SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
 - WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW PARALLEL TO THE D OR E DIMENSION, RESPECTIVELY, SD AR SE = 0.000. WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = $\left[\frac{\theta}{2}\right]$ 8. NOT USED.

- 6. NOT USED.
- 9. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

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12.3 56-Ball FBGA

12.3.1 Connection Diagram

Figure 12.5 56-ball Fortified Ball Grid Array

TOP VIEW

Product Pinout



Notes:

- Ball G1, Do Not Use (DNU), a device internal signal is connected to the package connector. The connector may be used by Cypress[®] for test or other purposes and is not intended for connection to any host system signal. Do not use these connections for PCB Signal routing channels. Though not recommended, the ball can be connected to V_{CC} or V_{SS} through a series resistor.
- 2. Balls E7, F8, and H5, Reserved for Future Use (RFU).
- 3. Balls A3 and B3, No Connect (NC).



12.3.2 Physical Diagram - VBU 056



	1			
PACKAGE		VBU 056		
JEDEC	N/A			
	9.00 n	1m x 7.00 mr PACKAGE	m NOM	
SYMBOL	MIN	NOM	MAX	NOTE
A			1.00	OVERALL THICKNESS
A1	0.17			BALL HEIGHT
D	9.00 BSC.			BODY SIZE
E	7.00 BSC.			BODY SIZE
D1	5.60 BSC.			BALL FOOTPRINT
E1	5.60 BSC.			BALL FOOTPRINT
MD	8			ROW MATRIX SIZE D DIRECTION
ME	8			ROW MATRIX SIZE E DIRECTION
N	56			TOTAL BALL COUNT
øb	0.35	0.40	0.45	BALL DIAMETER
e	0.80 BSC.			BALL PITCH
SD/SE	0:40 BSC.			SOLDER BALL PLACEMENT
	A1,A8,D4,D5,E4,E5,H1,H8			DEPOPULATED SOLDER BALLS

NOTES:

- 1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JEP95, SECTION 4.3, SPP-010.
- 4. @ REPRESENTS THE SOLDER BALL GRID PITCH. 5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
- SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
- N IS THE TOTAL NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW. WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = 0/2

"+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS. 8.

A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

10. OUTLINE AND DIMENSIONS PER CUSTOMER REQUIREMENT. q1055\16-038.25\01.26.12

13. Special Handling Instructions for FBGA Package

Special handling is required for Flash Memory products in FBGA packages.

Flash memory devices in FBGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150 °C for prolonged periods of time.


14. Ordering Information

Valid Combinations — Standard

Table 14.1 lists configurations planned to be available in volume. The table will be updated as new combinations are released. Consult your local sales representative to confirm availability of specific combinations and to check on newly released combinations.

Table 14.1 S29GL-S Valid Combinations - Standard

S29GL-S Valid Combinations — Standard									
Base OPN	Speed (ns)	Package and Temperature	Model Number	Packing Type	Ordering Part Number (yy = Model Number, x = Packing Type)				
					S29GL01GS10DHlyyx				
	100	DHI FAI FHI TEI (Note 1)	01 02		S29GL01GS10FAlyyx				
	100		01, 02		S29GL01GS10FHlyyx				
					S29GL01GS10TFlyyx				
		DHV TEV (Note 1)	01 02	0.3	S29GL01GS11DHVyyx				
S29GL01GS			01, 02	(Note 2)	S29GL01GS11TFVyyx				
	110			(11010 2)	S29GL01GS11DHlyyx				
		DHI, FHI, TFI (Note 1)	V1, V2		S29GL01GS11FHlyyx				
					S29GL01GS11TFlyyx				
	120	DHV TEV (Note 1)	V1 V2		S29GL01GS12DHVyyxx				
	120		• 1, • 2		S29GL01GS12TFVyyxx				
					S29GL512S10DHlyyx				
		DHI, FAI, FHI, GHI, SFI, TFI (Note 1)	01, 02		S29GL512S10FAlyyx				
	100				S29GL512S10FHlyyx				
			,		S29GL512S10GHlyyx				
					S29GL512S10SFlyyx				
					S29GL512S10TFlyyx				
S29GI 512S	110	GHI (Note 1)	01, 02	0, 3	S29GL512S11GHlyyx				
010010110		DHV, TFV (Note 1)	01, 02	(Note 2)	S29GL512S11DHVyyx				
			,		S29GL512S11TFVyyx				
					S29GL512S11DHlyyx				
		DHI, FHI, TFI (Note 1)	V1, V2		S29GL512S11FHlyyx				
					S29GL512S11TFlyyx				
	120	DHV, TFV (Note 1)	V1, V2		S29GL512S12DHVyyxx				
		,			S29GL512S12TFVyyxx				
					S29GL256S90DHlyyx				
	90	DHI, FHI, GHI, TFI (Note 1)	01, 02		S29GL256S90FHlyyx				
					S29GL256S90GHIyyx				
					S29GL256S90TFTyyx				
		DHV, TFV (Note 1)	01, 02		S29GL256S10DHVyyx				
S29GL256S			,	0, 3	S29GL256S10TFVyyx				
	100			(Note 2)	S29GL256S10DHlyyx				
		DHI, FAI, FHI, TFI (Note 1)	V1. V2		S29GL256S10FAlyyx				
			,		S29GL256S10FHlyyx				
					S29GL256S10TFlyyx				
	110	DHV. TFV (Note 1)	V1. V2		S29GL256S11DHVyyxx				
			- ·, · -		S29GL256S11TFVyyxx				



Table 14.1 S29GL-S Valid Combinations — Standard (Continued)

S29GL-S Valid Combinations — Standard										
Base OPN	Speed (ns)	Speed (ns) Package and Temperature Model Number Ty		Packing Type	Ordering Part Number (yy = Model Number, x = Packing Type)					
	90	DHI, FAI, FHI, GHI, TFI (Note 1)	01, 02		S29GL128S90DHIyyx S29GL128S90FAlyyx S29GL128S90FHIyyx S29GL128S90GHIyyx S29GL128S90TFIyyx					
520GI 1285	100	DHV, TFV (Note 1)	01, 02	0, 3	S29GL128S10DHVyyx S29GL128S10TFVyyx					
529GL 1203		DHI, FAI, FHI, TFI (Note 1)	V1, V2	(Note 2)	S29GL128S10DHIyyx S29GL128S10FAlyyx S29GL128S10FHIyyx S29GL128S10TFIyyx					
	110	DHV, TFV, FHV (Note 1)	V1, V2		S29GL128S11DHVyyx S29GL128S11TFVyyx S29GL128S11FHVyyx					

Notes:

1. Additional speed, package, and temperature options maybe offered in the future. Check with your local sales representative for availability.

2. Package Type 0 is standard option.



Valid Combinations — Automotive Grade / AEC-Q100

Table 14.2 and Table 14.3 list configurations that are Automotive Grade / AEC-Q100 qualified and are planned to be available in volume. The table will be updated as new combinations are released. Consult your local sales representative to confirm availability of specific combinations and to check on newly released combinations.

Production Part Approval Process (PPAP) support is only provided for AEC-Q100 grade products.

Products to be used in end-use applications that require ISO/TS-16949 compliance must be AEC-Q100 grade products in combination with PPAP. Non–AEC-Q100 grade products are not manufactured or documented in full compliance with ISO/TS-16949 requirements.

AEC-Q100 grade products are also offered without PPAP support for end-use applications that do not require ISO/TS-16949 compliance.

S29GL-S Valid Combinations — Automotive Grade (-40 °C to +85 °C) Speed Package and Ordering Part Number (yy = Model Base OPN Model Number Packing Type (ns) Temperature Number, x = Packing Type) S29GL01GS10DHAyyx S29GL01GS10FHAyyx S29GL01GS10TFAyyx 100, 110 01, 02 S29GL01GS11DHAyyx S29GL01GS11FHAvvx S29GL01GS S29GL01GS11TFAyyx S29GL01GS11DHAyyx S29GL01GS11FHAyyx V1, V2 110 S29GL01GS11TFAyyx S29GL512S10DHAyyx 100 01, 02 S29GL512S10FHAyyx S29GL512S10TFAyyx S29GL512S S29GL512S11DHAvyx DHA, FHA, TFA 110 V1, V2 S29GL512S11FHAyyx 0, 3 (Note 2) (Note 1) S29GL512S11TFAyyx S29GL256S90DHAyyx 90 01, 02 S29GL256S90FHAyyx S29GL256S90TFAyyx S29GL256S S29GL256S10DHAvvx 100 V1, V2 S29GL256S10FHAyyx S29GL256S10TFAyyx S29GL128S90DHAyyx 90 01, 02 S29GL128S90FHAyyx S29GL128S90TFAyyx S29GL128S S29GL128S10DHAyyx 100 V1, V2 S29GL128S10FHAyyx S29GL128S10TFAyyx

Table 14.2 S29GL-S Valid Combinations — Automotive Grade (-40 °C to +85 °C)

Notes:

1. Additional speed, package, and temperature options maybe offered in the future. Check with your local sales representative for availability.

2. Package Type 0 is standard option.



S29GL-S Valid Combinations — Automotive Grade (-40 °C to +105 °C)									
Base OPN	Speed (ns)	Package and Temperature	Model Number	Packing Type	Ordering Part Number (yy = Model Number, x = Packing Type)				
S20CI 01CS	110		01, 02		S29GL01GS11DHByyx S29GL01GS11FHByyx S29GL01GS11TFByyx				
329GE01GG	120	*	V1, V2		S29GL01GS12DHByyx S29GL01GS12FHByyx S29GL01GS12TFByyx				
S20CI 512S	110	*	01, 02		S29GL512S11DHByyx S29GL512S11FHByyx S29GL512S11GHByyx S29GL512S11TFByyx				
329GL0123	120	DHB, FHB, TFB, GHB (Note 1)	V1, V2	0. 2 (Noto 2)	S29GL512S12DHByyx S29GL512S12FHByyx S29GL512S12GHByyx S29GL512S12TFByyx				
S29GL256S	100		01, 02	0, 3 (Note 2)	S29GL256S10DHByyx S29GL256S10FHByyx S29GL256S10TFByyx S29GL256S10GHByyx				
	110		V1, V2		S29GL256S11DHByyx S29GL256S11FHByyx S29GL256S11TFByyx				
S29GL128S	100		01, 02		S29GL128S10DHByyx S29GL128S10FHByyx S29GL128S10TFByyx S29GL128S10GHByyx				
	110		V1, V2		S29GL128S11DHByyx S29GL128S11FHByyx S29GL128S11TFByyx				

Table 14.3 S29GL-S Valid Combinations — Automotive Grade (-40 °C to +105 °C)

Notes:

1. Additional speed, package, and temperature options maybe offered in the future. Check with your local sales representative for availability.

2. Package Type 0 is standard option.



The ordering part number for the General Market device is formed by a valid combination of the following:



Note:

1. Halogen-free definition is in accordance with IEC 61249-2-21 specification.



15. Other Resources

15.1 Cypress Flash Memory Roadmap

http://www.cypress.com/Flash-Roadmap

15.2 Links to Software

http://www.cypress.com/software-and-drivers-cypress-flash-memory

15.3 Links to Application Notes

http://www.cypress.com/cypressappnotes



16. Revision History

Document History Page

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change	
**	_	BWHA	02/11/2011	Initial release.	
*A	_	BWHA	03/21/2011	Global: Modified document from "Advance Information" to "Preliminary" OPN: Added FBGA package offering for V1 & V2 Model Number Removed KGD information, which is documented in a separate Supplement Command Definitions Table: Removed duplicated commands Changed the number of command cycles for a CFI Enter from 3 to 1 Physical Interface: Updated 56-pin TSOP pinout figure Updated 64-ball FBGA pinout figure Other Resources: Added additional application notes in "Links to Application Notes" Lock Register Table: Changed the default value of bit 7 in the Lock register	
*В		BWHA	07/08/2011	Performance Summary: Updated table: Typical Program and Erase Rates Secure Silicon Region ASO: Corrected table: Secure Silicon Region DQ1: Write-to-Buffer Abort: Corrected table: Data Polling Status Embedded Algorithm Performance Table: Updated table: Embedded Algorithm Characteristics Command State Transitions: Corrected tables: changed Software Reset/ASO Exit Data value to from 00F0h to xF0h Corrected table: Erase Suspend Unlock State Command Transition Corrected table: Erase Suspend Unlock State Command Transition Corrected table: Program Unlock State Command Transition Corrected table: Deck Register State Command Transition Corrected table: Secure Silicon Sector Program State Command Transition Corrected table: Non-Volatile Protection Command State Transition Corrected table: Non-Volatile Protection Command State Transition Corrected table: Volatile Sector Protection Command State Transition Corrected table: Volatile Sector Protection Command State Transition Corrected table: On-Volatile Protection Command State Transition Corrected table: On-Volatile Protection Command State Transition Corrected table: Corrected CFI Primary Vendor-Specific Extended Query description for Word Address (SA) + 0045h	



Document 1-Gbit (128 Document	Title: S29GL Mbyte)/512- Number: 00	.01GS/S29G -Mbit (64 Mb 1-98285	L512S/S29GL2 oyte)/256-Mbit	256S/S29GL128S, (32 Mbyte)/128-Mbit (16 Mbyte), 3.0 V, GL-S Flash Memory
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*B (cont)	_	BWHA	07/08/2011	DC Characteristics: Updated VIL Max Updated Note Power-On Reset (POR) and Warm Reset: Updated table: added row to bottom of table Power-On (Cold) Reset (POR): Updated text Updated figure: Power-Up Diagram Hardware (Warm) Reset: Updated figure: Hardware Reset Asynchronous Write Operations: Added figure: Back to Back (CE#VIL) Write Operation Timing Diagram Updated table: Erase/Program Operations Physical Diagram - LAA064: Added figure
*C	-	BWHA	10/03/2011	Power-Up Write Inhibit: Minor correction PPB Password Protection Mode: Minor correction Embedded Algorithm Characteristics table: Updated Buffer Programming Time maximum limits Absolute Maximum Ratings table: Added clarification DC Characteristics table: Output High Voltage clarification Power-Up/Power-Down Voltage and Timing table: Added clarification Power-Up figure: Added clarification Power-On (Cold) Reset (POR): Added clarification Valid Combinations table: Updated table
*D	-	BWHA	12/14/2011	Global: Data sheet designation changed from Preliminary to Full Production Sector Erase: Updated Typical Erase Time Capacitance Characteristics: Updated section Ordering Information: Corrected note designation in valid combination table
*E	_	BWHA	03/16/2012	Global: Added 9 mm x 7 mm package Added 105°C offering Ordering Information: Updated Valid Combinations



Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*F	-	BWHA	12/21/2012	Distinctive Characteristics:
				Added In-Cabin temperature range
				Status Register ASO:
				Added clarification
				Advanced Sector Protection Overview:
				Updated figure
				PPB Lock:
				Added clarification
				Persistent Protection Bits (PPB):
				Added clarification
				Dynamic Protection Bits (DYB):
				Added clarification
				PPB Password Protection Mode:
				Added clarification
				Chip Erase:
				Added clarification
				Sector Erase:
				Added clarification
				Erase Suspend / Erase Resume:
				Added clarification
				Status Register ASO:
				Added clarification
				Status Register:
				Added clarification
				DQ7: Data# Polling:
				Added clarification
				DQ1: Write-to-Buffer Abort:
				Added clarification
				Data Polling Status:
				Updated table
				Embedded Operation Error:
				Added clarification
				Protection Error:
				Added clarification
				Write Buffer Abort:
				Added clarification
				Performance Table:
				Updated Embedded Algorithm Characteristics (-40°C to +105°C) table
				Device ID and Common Flash Interface (ID-CFI) ASO Map:
				Updated CFI Device Geometry Definition table
				Updated CFI Primary Vendor-Specific Extended Query table
				Asynchronous Read Operations:
				Added Read Operation VIO = 1.65 (-40°C to +105°C) table
				Asynchronous Write Operations:
				Updated Read to Write (CE# VIL) figure
				Updated Read to Write (CE# Toggle) figure
*G		Β\Λ/HΔ	10/09/2013	S29GL-S Valid Combinations Table
J			10,00,2010	Added VIO Models for Automotive In Cabin Temperature Range
*⊔	4871490	ᇟᄱ	08/13/2015	Undated to Cypress template
11	1 40/1400		1 00/10/2010	Topualed to Oppless template.



Document 1-Gbit (128 Document	Title: S29GL Mbyte)/512- Number: 00	.01GS/S29G -Mbit (64 Mb 1-98285	L512S/S29GL2 yte)/256-Mbit (256S/S29GL128S, (32 Mbyte)/128-Mbit (16 Mbyte), 3.0 V, GL-S Flash Memory
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*	5162387	RYSU	03/04/2016	Updated Ordering Information on page 97: Updated Table 14.1 on page 97: Updated part numbers. Replaced "In Cabin" with "Industrial Plus" in Ordering Code Definitions below Table 14.1 on page 97. Updated to new template.
*J	5428780	BWHA	09/06/2016	Updated Timing Specifications on page 75: Updated AC Characteristics on page 78: Updated Asynchronous Write Operations on page 82: Updated Table 11.9 on page 87. Updated Figure 11.16 on page 87.
*К	5446870	BWHA	11/10/2016	Added Automotive Grade related information in all instances across the document. Updated Address Space Maps on page 6: Added ECC Status ASO on page 11. Updated Embedded Operations on page 20: Added Automatic ECC on page 22. Updated Command Set on page 23: Added ECC Status ASO on page 33. Updated Data Integrity on page 54: Added Erase Endurance on page 54. Added Data Retention on page 54. Updated Software Interface Reference on page 55: Removed "Address and Data Configuration". Updated Command Summary on page 55: Updated Table 7.1 on page 55 (to include ECC ASO Commands). Updated Electrical Specifications on page 69: Added Thermal Resistance on page 69: Added Valid Combinations — Automotive Grade / AEC-Q100 on page 99. Updated Other Resources on page 102: Added Cypress Flash Memory Roadmap on page 102. Updated Links to Software on page 102: Updated Links to Application Notes on page 102: Updated Links to Application Bulletins". Removed "Specification Bulletins".
*L	5724042	NFB / PRIT	05/03/2017	Updated Software Interface Reference on page 55: Added Device ID and Common Flash Interface (ID-CFI) ASO Map on page 63. Updated Ordering Information on page 97: Updated Valid Combinations — Standard on page 97: Updated Table 14.1 on page 97: Updated part numbers. Updated to new template.



Document 1-Gbit (128 Document	Title: S29GL Mbyte)/512- Number: 001	.01GS/S29G Mbit (64 Mb 1-98285	iL512S/S29GL2 oyte)/256-Mbit	256S/S29GL128S, (32 Mbyte)/128-Mbit (16 Mbyte), 3.0 V, GL-S Flash Memory
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*M	5776117	SZZX	06/16/2017	Updated Software Interface Reference on page 55: Updated Command Summary on page 55: Updated Table 7.1 on page 55: Replaced "2" with "1" in "Cycles" column corresponding to "Command Set Exit" under "ECC ASO" Command Sequence.
*N	5827786	PRIT	07/21/2017	Updated Address Space Maps on page 6: Updated ECC Status ASO on page 11: Updated description. Updated ECC Status on page 11: Updated description. Updated Table 2.8 on page 12 (Updated "Name" corresponding to Bit 2 and Bit 1). Updated Embedded Operations on page 20: Updated Command Set on page 23: Updated ASO Entry and Exit on page 31: Updated ECC Status ASO on page 33: Updated description. Completing Sunset Review.
*0	5891084	PRIT	09/19/2017	Updated Ordering Information on page 97: Updated Valid Combinations — Standard on page 97: Updated Table 14.1 on page 97: Updated part numbers.
۴P	6061893	PRIT	03/30/2018	Updated Ordering Information on page 97: Updated Valid Combinations — Standard on page 97: Updated Table 14.1 on page 97: Updated part numbers. Updated Valid Combinations — Automotive Grade / AEC-Q100 on page 99: Updated Table 14.3 on page 100: Updated part numbers. Updated to new template.
*Q	6199062	PRIT	06/06/2018	Updated Electrical Specifications on page 69: Updated Thermal Resistance on page 69: Updated Table 10.2 on page 69: Changed value of Theta Ja parameter from 20.4 °C/W to 27.3 °C/W corresponding to "LAE064" package.
*R	6214196	PRIT	06/21/2018	Updated Ordering Information on page 97: Updated details corresponding to "F" and "H" under "Package Materials Set" in the diagram. Added a note "Halogen free definition is in accordance with IEC 61249-2-21 specification" and referred the same note in "F" and "H".



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Document Number: 001-98285 Rev. *R

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Automotive Electronics Council = Component Technical Committee



Cypress Semiconductor Automotive Reliability Qualification Report

AEC-Q100 Automotive Qualification Test Plan Report for

PBO Protection Layer for S29GLXXXS, 65nm, XMC, Grade 3 -40 to 85C

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Component Technical Committee



Q100 Qualification Test Plan

Automotive Grade Level = 3 -40 to +85C

MSL = 3

Supplier Name:	CYPRESS		General Specification:	AEC-Q100 Rev. H		
Supplier Code:			Supplier Wafer Fabrication:	XMC (China)		
Supplier Part Number:	S29GLXXXS		Supplier Wafer Test:	TEST25 (Austin)		
Supplier Contact:			Supplier Assembly Site: CYPRESS BKK (Thailand) (TS056, LAE064, VBU056, LAA064)		56, LAE064,	
Supplier Family Type:	TS056, LAE064,VBU056, LAA064		Supplier Final Test Site:	Site: CYPRESS BKK (Thailand)		
Device Description:	CS239LS 65nm CMOS 3.0 Volt-only Flash Memory		Supplier Reliability Signature:			
PPAP Submission Date:			Customer Test ID:			
Reason for Qualification:	New Part Qualification (XMC PBO)		Customer Part Number:			
Prepared by Signature:	EKNG Date: 24-07-19		Customer Approval Signature:		Date:	

Test	#	Reference	Test Conditions	Lots	S.S.	Total	Results Lot/Pass/Fail	Comments: (N/A =Not Applicable)			
	TEST GROUP A – ACCELERATED ENVIRONMENT STRESS TESTS										
PC	A1	JESD22 A113 J-STD-020	Preconditioning: (Test @ Rm) SMD only; Moisture Preconditioning for THB/HAST, AC/UHST, TC, & PTC; Peak Reflow Temp = 260C,0/-5C	Mi	Min. MSL = 3		MSL = 3				
			Temperature Humidity Bias: (Test @ Rm/Hot)					a Basulta (TS056) - 2 lata (221 Lipita (0 Faila			

THB or HAST	A2	JESD22 A101 JESD22 A110	Temperature Humidity Bias: (Test @ Rm/Hot) Highly Accelerated Stress Test: (Test @ Rm/Hot/) 130C/85%RH, 3.0V, 96Hrs, 192Hrs (TSOP) 110C/85%RH, 3.0V, 264Hrs, 528Hrs (FBGA)	3	77	231	0 of 231	a. Results (TS056) = 3 lots / 231 Units/ 0 Fails b. Results (VBU056) = 3 lots/ 231 Units/ 0 Fails c. Results (LAA064/LAE064) = 3 lots/ 231 Units/ 0 Fails
AC or UHST or TH	A3	JESD22 A102 JESD22 A118 or JESD22-A101	Autoclave: (Test @ Rm) Unbiased Highly Accelerated Stress Test: (Test @ Rm) Temperature Humidity without Bias: (Test @ Rm) 130C/85%RH, 96Hrs	3	77	231	0 of 231	a. Results (TS056) = 3 lots / 231 Units/ 0 Fails b. Results (VBU056) = 3 lots/ 231 Units/ 0 Fails c. Results (LAA064/LAE064/VBU056) = 3 lots/ 231 Units/ 0 Fails

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Test	#	Reference	Test Conditions	Lots	S.S.	Total	Results Lot/Pass/Fail	Comments: (N/A =Not Applicable)
тс	A4	JESD22 A104	Temperature Cycle: (Test @ Hot) - 65C to 150C, 500 and 1000 Cycles WBP Test after TC 500 Cycles and 1000 Cycles	3	77	231	0 of 231	a. Results (TS056) = 3 lots / 231 Units/ 0 Fails b. Results (LAA064/LAE064/VBU056) = 3 lots/ 231 Units/ 0 Fails * Note: Wire pull results: Passed
PTC	A5	JESD22 A105	Power Temperature Cycle: (Test @ Rm/Hot)	1	45	45	of	N/A.
HTSL	A6	JESD22 A103	High Temperature Storage Life: (Test @ Rm/Hot) 150C, 1000, 2000 Hrs and 175C, 500, 1000hrs	1	45	45	0 of 180	a. Results (TS056) = 3 lots / 135 Units/ 0 Fails b. Results (LAA064/LAE064/VBU056) = 3 lots/ 135 Units/ 0 Fails

TEST GROUP B – ACCELERATED LIFETIME SIMULATION TESTS

HTOL	B1	JESD22 A108	High Temp Operating Life: (Test @ Rm/Cold/Hot) 125C, 3.6V, 1000 Hrs	3	77	231	0 of 231	a. Results= 3 lots / 231 Units / 0 Fails.
ELFR	B2	AEC-Q100-008	Early Life Failure Rate: (Test @ Rm/Hot) 48 Hrs. @ 125C, 3.6V	3	800	2400	0 of 2400	a. Results= various lots/ 2400 Units/ 0 Fails
EDR	B3	AEC-Q100-005	NVM Endurance & Data Retention Test: (Test @ Rm/Hot) a.85C 100k cycles + 150C Bake (Meet 2years after 100k cycles at 55C, 20years after 10k cycles at 55C) b.85C 100k cycles + 125C HTOL 1khrs c.25C 100k cycles + 25C bake 1khrs	3	77	231	0 of 231	a. Results = 3 lots / 231 Units / 0 Fails b. Results = 3 lots / 231 Units / 0 Fails c. Results = 3 lots / 231 Units / 0 Fails

TEST GROUP C – PACKAGE ASSEMBLY INTEGRITY TESTS

WBS	C1	AEC-Q100-001 AEC-Q003	Wire Bond Shear Test: (Cpk > 1.67)	30 bonds	5 parts Min.	bonds	0 of 30	a. Results (TS056) =30 Bonds/ 0 Fails b. Results (LAE064/LAA064/VBU056) =30 Bonds/ 0 Fails
WBP	C2	Mil-STD-883, Method 2011 AEC-Q003	Wire Bond Pull: (Cpk > 1.67); Each bonder used	30 bonds	5 parts Min.	bonds	0 of 30	a. Results (TS056) =30 Bonds/ 0 Fails b. Results (LAE064/LAA064/VBU056) =30 Bonds/ 0 Fails
SD	C3	JESD22 B102 JSTD-002D	Solderability: (>95% coverage) 8hr steam aging prior to testing	1	15	15	0 of 15	a. Results (TS056) =1 lots / 15 Units/ 0 Fails
PD	C4	JESD22 B100, JESD22 B108 AEC-Q003	Physical Dimensions: (Cpk > 1.67)	3	10	30	0 of 30	a. Results (TS056) = 3 lots/ 30 Units/ 0 Fails b. Results (LAE064) =3 lots/ 30 Units/ 0 Fails c. Results (VBU056) = 3 lots/ 30 Units/ 0 Fails d. Results (LAA064) = 3 lots/ 30 Units/ 0 Fails

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Test	#	Reference	Test Conditions	Lots	S.S.	Total	Results Lot/Pass/Fail	Comments: (N/A =Not Applicable)
SBS	C5	AEC-Q100-010 AEC-Q003	Solder Ball Shear: (Cpk > 1.67); 5 balls from min. of 10 devices	3	50 balls	150	0 of 150	a. Results (LAA064/LAE064/VBU064) = 150 Balls / 0 Fails
Ц	C6	JESD22 B105	Lead Integrity: (No lead cracking or breaking); Through-hole only; 10 leads from each of 5 devices	1	50 leads	50	0 of 50	a. Results (TS056) = 50 Leads, 0 Fails

TEST GROUP D – DIE FABRICATION RELIABILITY TESTS

EM	D1	JESD61	Electromigration: Constant current 0.8MA/cm2 and 1.2MA/cm2 at 225C and 175C	-	-	-	Data Available TQ Generic Data Results = Pass 100khr operating equivalent
TDDB	D2	JESD35	Time Dependant Dielectric Breakdown: : Constant voltage 6-9MV/cm at 130C	-	-	-	Data Available TQ Generic Data Results = Pass 100khr operating equivalent
HCI	D3	JESD60 & 28	Hot Carrier Injection: Vg at Isubmax with 3 Vds conditions	-	-	-	Data Available TQ Generic Data Results = Pass 100khr operating equivalent
NBTI	D4	JESD90	Negative Bias Temperature Instability:	-	-	-	Data Available TQ Generic Data Results = Pass 100khr operating equivalent
SM	D5	JESD61, 87, & 202	Stress Migration:	-	-	-	Data Available TQ Generic Data Results = Pass 100khr operating equivalent

TEST GROUP E- ELECTRICAL VERIFICATION

TEST	E1	User/Supplier Specification	Pre and Post Stress Electrical Test: Test at 25C, 85C, & -40C	All	All	All	of	a. Performed on all qualification units
НВМ	E2	AEC-Q100-002	Electrostatic Discharge, Human Body Model: (Test @ Rm/Hot); (2KV HBM / Class 2 or better) HBM (100pF, 1,500 ohms)	1	42	42	0 of 168 ESD Level = 2	a. RQ Results (LAE064) = 1 lots/ 42 Units/ 0 Fails Pass +/-2.0kV HBM.
CDM	E3	AEC-Q100-011	Electrostatic Discharge, Charged Device Model: (Test @ Rm/Hot); (750V corner leads, 500V all other leads / Class C4B or better)	1	12	12	0 of 12 ESD Level = C4B	a. Results (TS056) = 1 lots/ 12 Units/ 0 Fails b. Results (LAE064) = 1 lots/12 Units/0 Fails c. Results (LAA064) = 1 lot/ 12 Units/0 Fails d. Results (VBU056) = 1 lot/ 12 Units/0 Fails Pass 500V/750V CDM
LU	E4	AEC-Q100-004	Latch-Up: (Test @ Rm/Hot) 125C +/- 100mA Class II	1	6	6	0 of 6	a. Result LAE064= 1 lots/ 6 units/ 0 fails

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Test	#	Reference	Test Conditions	Lots	S.S.	Total	Results Lot/Pass/Fail	Comments: (N/A =Not Applicable)
ED	E5	AEC-Q100-009 AEC-Q003	Electrical Distributions: (Test @ Rm/Hot/Cold) (where applicable, Cpk >1.67) (Test at 25C, 85C, & -40C Pre- and Post-)	3	30	90	of	Refer to characterization data in QDB
FG	E6	AEC-Q100-007	Fault Grading:	-	-	-	Fault Grade	N/A. But Cypress screens out the failures through Internal test mode and 100% tested to sort and class tests.
CHAR	E7	AEC-Q003	Characterization: (Test @ Rm/Hot/Cold) (at 25C, 85C, & -40C)	-	-	-	Requested Data	N/A
EMC	E9	SAE J1752/3	Electromagnetic Compatibility (Radiated Emissions):	1	1	1	1	Data available upon request
SC	E10	AEC Q100-012	Short Circuit Characterization	3	10	30		Applicable for smart power device only per AEC Q100.
SER	E11	JESD89-1 JESD89-2 JESD89-3	Soft Error Rate	1	3	3		N/A. But, Cypress performed some accelerated neutron irradiation tests on our product. Refer separate document for more information
LF	E12	AEC-Q005	Lead (Pb) Free: (see AEC-Q005)	-	-	-		Pass.
			TEST GROUP F – DEF	ECT S	CREE	NING ⁻	TESTS	
PAT	F1	AEC-Q001	Process Average Testing: (see AEC-Q001)	All	All	All	Reject units outside Avg.	Cypress incorporates the principle of PAT methodology
SBA	F2	AEC-Q002	Statistical Bin/Yield Analysis: (see AEC-Q002)	All	All	All	Reject units outside criteria	Cypress incorporates the principle of SBA methodology

TEST GROUP G - CAVITY PACKAGE INTEGRITY TESTS (for Ceramic Package testing only)

MS	G1	JESD22 B104	Mechanical Shock: (Test @ Rm)	1	15	15	of	N/A. Applicable for ceramic package only
VFV	G2	JESD22 B103	Variable Frequency Vibration: (Test @ Rm)	1	15	15	of	N/A. Applicable for ceramic package only
CA	G3	MIL-STD-883 Method 2001	Constant Acceleration: (Test @ Rm)	1	15	15	of	N/A. Applicable for ceramic package only

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Test	#	Reference	Test Conditions	Lots	S.S.	Total	Results Lot/Pass/Fail	Comments: (N/A =Not Applicable)
GFL	G4	MIL-STD-883 Method 1014	Gross and Fine Leak:	ross and Fine Leak: 1 15 15 of		of	N/A. Applicable for ceramic package only	
DROP	G5		Drop Test: (Test @ Rm) MEMS cavity parts only. Drop part on each of 6 axes once from a height of 1.2m onto a concrete surface.	1	5	5	of	N/A. Applicable for ceramic package only
LT	G6	MIL-STD-883 Method 2004	Lid Torque:	1	5	5	of	N/A. Applicable for ceramic package only
DS	G7	MIL-STD-883 Method 2019	Die Shear:	1	5	5	of	N/A. Applicable for ceramic package only
IWV	G8	MIL-STD-883 Method 1018	Internal Water Vapor:	1	5	5	of	N/A. Applicable for ceramic package only

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Document History Page

 Document Title:
 AEC-Q100 Automotive Qualification Test Plan Report for PBO Protection Layer for S29GLXXXS, 65nm, XMC Grade 3

 -40 to 85C
 002-28003

Rev.	ECN	Orig. of	Description of Change
	No.	Change	
**	6636270	EKNG	New Qualification report for PBO Protection Layer for S29GLXXXS, 65nm, XMC, Grade 3 - 40 to 85C

Document No. 002-28003 Rev: **

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CONFIDENTIAL

S29GL512S (XMC 85C 105C)



Qualification Database

Notice: The material in this report is confidential. It is prepared to assist in the qualification of our product. It is intended for the internal use of our customers only, and may be modified to meet the needs of specific customers.

Additionally, the package details (material set, assembly location, etc.) are specific to the qualification vehicle used. Alternate material sets and assembly locations may be qualified for the product. Production material can be assembled with any qualified material set and at any qualified assembly location.

Cypress Semiconductor Corporation • 198 Champion Court Document Number: 002-00479 Rev. *D

• San Jose, CA 95134-1709 • 408-943-2600 Revised August 02, 2019



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1. Introduction

The Cypress S29GL512S flash memory device has a die size of 6.803 x 5.027 mm.

2. Die Photograph



Note:

1. X in the diagram is pad #1. Count counter clockwise.



3. Pad Definition Table

Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA	Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA
1	NC			38	VCC	43	G5
2	A23	1	C8	39	VSS	33, 52	H7
3	A22	2	B8	40	VCC	43	G5
4	A15	3	D7	41	VSS	33, 52	H7
5	A14	4	C7	42	VSS	33, 52	H7
6	A13	5	A7	43	VCC	43	G5
7	A12	6	B7	44	A0	31	E2
8	A11	7	D6	45	CE#	32	F2
9	A10	8	C6	46	OE#	34	G2
10	A9	9	A6	47	NC		
11	A8	10	B6	48	DQ0	35	E3
12	A19	11	D5	49	DQ8	36	F3
13	A20	12	D4	50	VSS	33, 52	H2, E8
14	WE#	13	A5	51	VIO	29	F1, D8
15	VSS	33, 52	H7	52	DQ1	37	H3
16	VCC	43	G5	53	DQ9	38	G3
17	VSS	33, 52	H7	54	DQ2	39	E4
18	VCC	43	G5	55	DQ10	40	F4
19	NC			56	DQ3	41	H4
20	RESET#	14	B5	57	DQ11	42	G4
21	A21	15	C5	58	DQ4	44	H5
22	WP#	16	B4	59	DQ12	45	F5
23	RY/BY#	17	A4	60	DQ5	46	E5
24	VIO	29	D8, F1	61	DQ13	47	G6
25	VSS	33, 52	H7	62	NC		
26	A18	18	C4	63	VSS	33, 52	H7
27	A17	19	B3	64	VCC	43	G5
28	A7	20	A3	65	DQ6	48	H6
29	A6	21	C3	66	DQ14	49	F6
30	A5	22	D3	67	DQ7	50	E6
31	A4	23	B2	68	DQ15	51	G7
32	A3	24	A2	69	VIO	29	D8, F1
33	A2	25	C2	70	VSS	33, 52	E8, H2
34	A1	26	D2	71	A16	54	E7
35	DNU	28	E1	72	NC		
36	VCC	43	G5	73	A24	56	F8
37	VSS	33, 52	H7				



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4. Physical Sector Layout

Internal Use Row 43	Internal Use											
Row 42	504	505	506	507	508	509	510	511	Internal Use	Internal Use	Internal Use	Internal Use
Row 41	492	493	494	495	496	497	498	499	500	501	502	503
Row 3	36	37	38	39	40	41	42	43	44	45	46	47
Row 2	24	25	26	27	28	29	30	31	32	33	34	35
Row 1	12	13	14	15	16	17	18	19	20	21	22	23
Row 0	0	1	2	3	4	5	6	7	8	9	10	11
VerticalBank	0	1	2	3	0	1	2	3	0	1	2	3
Bank		()				1				2	

Figure 4.1 Physical Sector Layout



5. Sector Enlargement

Figure 5.1 Sector Enlargement

IO Organization

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1407
)-7 14

	11	12	13	14	15	Internal Use	Internal Use	Internal Use	Internal Use
M3BL	704-767	768-831	832-895	896-959	960-1023	1024-1063	1064-1071	1072-1079	0-7
M1BL	1408-1535	1536-1663	1664-1791	1792-1919	1920-2047	2048-2127	2128-2143	2144-2159	0-7



6. Die Processing Summary

The Cypress S29GL512S flash memory device is manufactured using the 65 nm MirrorBit[®] Eclipse[™] process technology.

The device is processed at WXIC, a 12-inch CMOS manufacturing facility located in Wuhan, China.

The device is manufactured on the highly reliable CS239LS process.





PERIPHERY



6.1 Key Features of the 65 nm MirrorBit Eclipse Process Technology

A. Technology

- CMOS Triple-well process
- Proven reliable Flash MirrorBit Eclipse Technology

B. Transistor Types

- n-channel enhancement
- n-channel intrinsic
- p-channel enhancement
- MirrorBit Eclipse core cell

C. Process Features

- ONO (oxide nitride oxide) gate dielectric
- Silicon Nitride (SiN) data storage layer

D. Cypress Highlights

- Volume Production Fab
- Solely dedicated to Non-Volatile Memories
- Ongoing Statistical Process Control program



7. Assembly Packaging Summary

7.1 LAE064

Product Description:	S29GL512S					
Froduct Description.	512-Mb, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse Process Technology					
Package:	LAE064	Qualification:	Q100156			
Description:	(9 x 9 x 1.4 mm) 64-ball, Fortifie	d Ball Grid Array Package (fFBGA)				
Con-code:	B40780KV-DWR-001	Theta Ja / Psi Jt:	30.4 °C/W / 17 °C/W			
Assembly Location:	Cypress Thailand	Molding Compound:	ShinEtsu KMC 3580LVA			
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	QMI 546			
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres	Bond Wire:	Copper			
Comments:						
Est. Field Temperature:	55 °C	Life Test Temperature:	125 °C			
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA			
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V			
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts			
Est. Field Delta Tj:	57.9 °C	Est. Stress Delta Tj:	126.4 °C			
Die:	98290B	Die Size:	6.803 x 5.027 mm			
Process:	CS239LS (65 nm)	Fab:	WXIC			
Туре:	MirrorBit Eclipse	Density:	512M			

7.2 TS056

Broduct Decoription:	S29GL512S						
Floduct Description.	512-Mb, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse Process Technology						
Package:	TS056	Qualification:	Q100125				
Description:	(18.4 x 14.0 x 1.0 mm) 56-lead, 1	(18.4 x 14.0 x 1.0 mm) 56-lead, Thin Small Outline Package (TSOP)					
Con-code:	A40786EF-TXA-001	Theta Ja / Psi Jt:	44 °C/W / 17 °C/W				
Assembly Location:	Cypress Thailand	Molding Compound:	Hitachi CEL 9200HF10-U				
Substrate/Leadframe:	Copper Leadframe	Die Attachment:	Ablebond 8340				
Lead Finish:	100% Matte Sn Plating	Bond Wire:	Copper				
Comments:							
Est. Field Temperature:	55 °C	Life Test Temperature:	125°C				
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA				
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V				
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts				
Est. Field Delta Tj:	58.0 °C	Est. Stress Delta Tj:	126.4 °C				
Die:	98290B	Die Size:	6.803 x 5.027 mm				
Process:	CS239LS (65 nm)	Fab:	WXIC				
Туре:	MirrorBit Eclipse	Density:	512M				



7.3 LAA064

Product Description:	S29GL512S						
i roduci Description.	512-Mb, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse Process Technology						
Package:	LAA064	Qualification:	Q100226				
Description:	(13.0 x 11.0 x 1.4 mm) 64-ball, F	(13.0 x 11.0 x 1.4 mm) 64-ball, Fortified Ball Grid Array Package (FBGA)					
Con-code:	B40781KV-DWR-001	Theta Ja / Psi Jt:	22.2 °C/W / 11 °C/W				
Assembly Location:	Cypress Thailand	Molding Compound:	ShinEtsu KMC 3580LVA				
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	QMI 546				
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres	Bond Wire:	Copper				
Comments:							
Est. Field Temperature:	55 °C	Life Test Temperature:	125°C				
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA				
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V				
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts				
Est. Field Delta Tj:	57.9 °C	Est. Stress Delta Tj:	126.4 °C				
Die:	98290B	Die Size:	6.803 x 5.027 mm				
Process:	CS239LS (65 nm)	Fab:	WXIC				
Туре:	MirrorBit Eclipse	Density:	512M				



8. Assembly Bonding Diagram

8.1 LAE064 Package



Figure 8.1 64-Ball—LAE064 Package



8.2 TS056 Package



Figure 8.2 56-Pin—TS056 Package



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8.3 LAA064 Package







9. Test Methodology

Testing includes

- 4 hour, 250°C Data Retention Bake (in wafer form)
- Special test mode for extended life operation
- Proprietary screens for endurance

Wafer Sort (Austin, Texas, USA)

At Wafer Sort, all die experience 100% testing for:

- DC Parametrics
- AC Functionality
- Programmability
- Erasability

Class Test (Bangkok, Thailand)

At Class Test, all devices are tested for:

- DC Parametrics
- AC Functionality
- AC Speed
- Programmability
- Erasability

Test Coverage

All parameters specified in the data sheet are 100% tested in production unless otherwise specified. Those parameters not tested in production are guaranteed by characterization or correlation to other tests. AC speed testing is performed at class test.

Test Correlation and Guard Banding

Tester correlation to bench set-up has been completed for all tested parameters. Tester repeatability studies have been run. These results have been evaluated and incorporated into the tester guard band strategy. Guard bands have been implemented which demonstrate acceptable yield, quality assurance and customer satisfaction.

Test Flow

See the generalized Test Flow for the S29GL512S in Section 10.



10. Generalized Test Flow

The S29GL512S Generalized Test Flow for Industrial Temperature Range:





11. Quality and Reliability Data

11.1 S29GL512S High Temperature Operating Life Test Configuration

Pin/Pad #	Function	Resistor	Bias/CLK
1	A23	2.7K	CLK23
2	A22	2.7K	CLK22
3	A15	2.7K	CLK15
4	A14	2.7K	CLK14
5	A13	10K	CLK13
6	A12	2.7K	CLK12
7	A11	2.7K	CLK11
8	A10	2.7K	CLK10
9	A9	2.7K	CLK9
10	A8	2.7K	CLK8
11	A19	2.7K	CLK19
12	A20	2.7K	CLK20
13	WE#	2.7K	VCC
14	RESET#	2.7K	VCC
15	A21	2.7K	CLK21
16	WP#	2.7K	VCC
17	RY/BY#	2.7K	VCC
18	A18	2.7K	CLK18
19	A17	2.7K	CLK17
20	A7	2.7K	CLK7
21	A6	2.7K	CLK6
22	A5	2.7K	CLK5
23	A4	2.7K	CLK4
24	A3	2.7K	CLK3
25	A2	2.7K	CLK2
26	A1	2.7K	CLK1
27	RFU		NC
28	RFU		NC

Pin/Pad #	Function	Resistor	Bias/CLK
56	A24	2.7K	CLK24
55	RFU		NC
54	A16	2.7K	CLK16
53	RFU		NC
52	VSS		GND
51	DQ15	2.7K	VCC
50	DQ7	2.7K	VCC
49	DQ14	2.7K	VCC
48	DQ6	2.7K	VCC
47	DQ13	2.7K	VCC
46	DQ5	2.7K	VCC
45	DQ12	2.7K	VCC
44	DQ4	2.7K	VCC
43	VCC		VCC
42	DQ11	2.7K	VCC
41	DQ3	2.7K	VCC
40	DQ10	2.7K	VCC
39	DQ2	2.7K	VCC
38	DQ9	2.7K	VCC
37	DQ1	2.7K	VCC
36	DQ8	2.7K	VCC
35	DQ0	2.7K	VCC
34	OE#	2.7K	VCC
33	VSS		GND
32	CE#	2.7K	GND
31	A0	2.7K	CLK0
30	RFU		NC
29	VIO	2.7K	VCC


11.2 CS239/L Life Test Failure Rate Calculation

HTOL Stress Temperature @ 125°C

	Read Points / Test Results			Мос	leling P	aramete	5°C	Average Failure Rate FITS @ 55°C, 60% Conf.		
Failure Mechanisms	24 hrs	168 hrs	1000 hrs	Ea eV	TAF	VAF	OAF	MTTF (yrs)	Early Life	Inherent Life
PLASTIC										
Sample Size	1745	3025	345							
Zero fails, Process ave. Ea	0 (1)	0	0	0.66	53	1	53		87	23
Totals	0	0	0					4963	87	23

Note:

1. Contributes to Early Life FITS.

Data Retention Bake @ 150°C

Reliability Stress	Number of Rejects	Sample Size	Failure Rate %	Failure Mechanism
500 hrs	0	300	0.00	No Failures
1000 hrs	0	300	0.00	No Failures



Table 11 1	Summary	of Stress	Test Results
	Ourrinary	0100033	restresults

Stress Test	Condition	Package Type	Samples Size	Num. of Lots	Number of Fails	Failure Rate %	Comments	
Data From Qualification Q100125, Q100226, Q100156:								
HTOL (EL)	3.6V, 125°C	LAE064 (3)	77	1	0	0.00	168 hrs	
	N/A	TS056 (1)	15	1		Passed 1.0	kV	
ESD CDM	N/A	LAA064 (2)	15	1		Passed 1.0	kV	
	N/A	LAE064 (3)	15			Passed 1.0	kV	
ESD HBM	(100 pF, 1500 Ohms)	LAE064 (3)	84	1		Passed 2.0	kV	
Latch Up	125°C, ±100 mA	LAE064 (3)	6	1		Passed		
	–40°C, 3.6V	LAE064 (3)	64	1	0	0.00	10k cycles	
Endurance (10k)	90°C, 3.6V	LAE064 (3)	128	1	0	0.00	10k cycles	
	105°C, 3.6V	TS056 (4)	240	3	0	0.00	10k cycles	
	G	eneric Reference D	ata					
Preconditioning	PC9/260°C, +0°C / -5°C	LAE064 (5)	230	1	Pass	ed Jedec L3	3 (Accel.)	
Freconditioning	PC9/260°C, +0°C / -5°C	TS056 (6)	77	1	Pass	ed Jedec L3	8 (Accel.)	
Preconditioning + Temp	PC9/260°C, -40°C / 150°C	LAE064 (5)	77	1	0	0.00	1000 cycles	
Cycle	PC9/260°C, -40°C / 150°C	TS056 (6)	77	1	0	0.00	1000 cycles	
Preconditioning + HAST	PC9/260°C, Biased, 110°C / 85% RH	LAE064 (5)	77	1	0	0.00	264 hrs	
Preconditioning + uHAST	PC9/260°C, Unbiased, 130°C / 85% RH	LAE064 (5)	76	1	0	0.00	96 hrs	

Notes:

1. Results from Qual Q100125, S29GL512S, 512M 65 nm MirrorBit Eclipse in 56 Lead TSOP (18.4 x 14 x 1 mm).

2. Results from Qual Q100226, S29GL512S, 512M CS239LS (65 nm) MirrorBit Eclipse in 64 Ball fFBGA (13 x 11 x 1.4 mm).

3. Results from Qual Q100156, S29GL512S, 512M CS239LS (65 nm) MirrorBit Eclipse in 64 Ball fFBGA (9 x 9 x 1.4 mm).

4. Results from QTP#184906, S29GL01GS in 56 Lead TSOP (18.4 x 14 x 1 mm) - Same TS056 Package, Same Product and Process Technology at Fab25.

5. Results from Qual Q100127, S29GL01GS in 64 Ball fFBGA (9 x 9 x 1.4 mm) - Same LAE064 package, Same Process Technology, Same Fab Location, Similar Product.

6. Results from Qual Q99990, S29GL512S in 56 Lead TSOP (18.4 x 14 x 1 mm) - Same TS056 package, Same Process Technology and Product from Fab25.

Preconditioning Flows

PC9 (Accelerated JEDEC L3 / JEITA Rank E): Bake 125°C, 24hr --> Soak @ 60°C/70%RH, 72hr => 3x Reflow.



12. Characterization Test Results

The data is pattern is "Random pattern" unless otherwise indicated.

12.1 DC Parameter Summary, 25°C

Room Temperature, 25°C, 3V, V_{CC} Summary

Data Shaat Baramatara		Spec		Average	Min	Max	Sigmo	Cok
Data Sneet Parameters	Тур	Мах	Unit	Average	WIIN	wax	Sigma	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	92.01	86.17	96.34	1.82	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	48.87	46.53	50.68	0.78	> 5
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.72	5.26	6.17	0.15	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.77	5.32	6.16	0.15	
I _{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.83	5.38	6.25	0.15	
I_{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.90	5.43	6.33	0.15	> 5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	45.64	42.17	49.41	1.23	> 5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	40.76	36.41	45.96	1.99	> 5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	17.70	9.44	56.77	7.62	3.6
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.02	0.01	0.06	0.01	> 5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μA	17.65	9.46	56.53	7.61	> 5
I _{LI} (Input Leakage Current)	0.02	±1	μA	0.000	-0.013	0.012	0.0	> 5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.001	-0.010	0.011	0.0	> 5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	261.3	173.0	616.0	32.8	> 5
Buffer Program Time (256 word)	340	750	μs	355.1	200.0	468.0	29.2	4.5
Buffer Program Time (128 word)	239	750	μs	281.4	226.0	387.0	24.2	> 5
Buffer Program Time (64 word)	198	750	μs	243.4	198.0	336.0	21.1	> 5
Buffer Program Time (32 word)	175	750	μs	233.0	179.0	309.0	31.3	> 5
Buffer Program Time (16 word)	160	750	μs	231.7	166.0	302.0	36.5	> 5
Single Word Program Time (1 word)	150	400	μs	183.0	150.0	279.0	25.2	> 5

Notes:

1. Data was collected from 300 units.

2. Sector Erase excludes Random data pattern programming prior to erasure.



12.2 DC Parameter Summary, 85°C

Hot Temperature, 85°C, 3V, V_{CC} Summary

Data Shoot Paramotors		Spec		Avorago	Min	Мах	Sigma	Cnk
Data Sheet Parameters	Тур	Мах	Unit	Average	IAILL	IVIAX	Sigina	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	96.9	52.9	102.3	3.1	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	51.3	40.5	53.9	1.0	> 5
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	6.100	5.570	6.340	1.270	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	6.130	5.620	6.400	1.220	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	6.210	5.720	6.460	1.220	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	6.280	5.750	6.540	1.210	> 5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	48.4	0.5	51.9	3.0	> 5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	42.8	10.0	48.2	2.8	> 5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	55.7	32.1	90.3	12.0	1.2
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.06	0.03	0.09	0.01	> 5
I_{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μA	55.1	31.7	91.0	12.0	> 5
I _{LI} (Input Leakage Current)	0.02	±1	μA	0.000	-0.015	0.012	0.0	> 5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.000	-0.008	0.011	0.0	> 5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	193.4	136.0	339.0	18.2	> 5
Buffer Program Time (256 word)	340	750	μs	328.0	191.0	437.0	24.1	> 5
Buffer Program Time (128 word)	239	750	μs	263.3	212.0	337.0	20.3	> 5
Buffer Program Time (64 word)	198	750	μs	223.6	185.0	285.0	16.9	> 5
Buffer Program Time (32 word)	175	750	μs	217.9	164.0	286.0	23.4	> 5
Buffer Program Time (16 word)	160	750	μs	210.3	154.0	267.0	25.3	> 5
Single Word Program Time (1 word)	150	400	μs	165.0	139.0	273.0	14.8	5.3

Notes:

1. Data was collected from 300 units.

2. Sector Erase excludes Random data pattern programming prior to erasure.



12.3 DC Parameter Summary, 105°C

Hot Temperature, 105°C, 3V, $V_{CC} = V_{IO}$ Summary

Data Shaat Baramatara		Spec			Ave	rage		Average	Min	Мох	Sigmo	Cnk
Data Sheet Parameters	Тур	Мах	Unit	-40	25	85	105	Average	IAIILI	Max	Sigina	Срк
			DC	Parame	eters							
I_{CC1} (V _{CC} Active Read Current) 10 MHz			mA	91.4	92.0	96.9	93.7	93.7	89.2	99.3	2.0	
I_{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	48.0	48.9	51.3	49.1	49.1	46.8	52.1	1.1	3.3
I_{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.5	5.7	6.1	6.1	6.1	5.5	6.8	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.6	5.8	6.1	6.0	6.0	5.4	6.7	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.6	5.8	6.2	5.9	5.9	5.4	6.6	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.7	5.9	6.3	5.9	5.9	5.3	6.6	0.2	> 5
I_{CC3} (V _{CC} Active Erase Current)	45	100	mA	42.2	45.6	48.4	51.4	51.4	49.2	54.3	1.1	> 5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	37.6	40.8	42.8	46.7	46.7	42.3	49.9	1.7	> 5
I _{CC4} (V _{CC} Standby Current)	70	200	μA	15.2	17.7	55.7	63.0	63.0	29.8	195.9	24.3	1.9
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.0	0.0	0.1	0.1	0.063	0.030	0.192	0.024	> 5
I_{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	15.1	17.7	55.1	61.6	61.6	29.9	110.5	19.6	2.4
I _{LI} (Input Leakage Current)	0.02	±1	μA	0.0	0.0	0.0	0.0	0.005	-0.008	0.244	0.021	> 5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	0.0	0.0	0.0	0.0	0.002	-0.009	0.156	0.004	> 5
	Ave	erage Sec	tor Er	ase/Pre	-progra	mming '	Time					
Sector Erase Time (64 kword sector)	275	1100	ms					189.5	136.0	264.0	14.2	> 5
Buffer Program Time (256 word)	420	1050	μs					333.1	281.0	394.0	19.1	> 5
Buffer Program Time (128 word)	320	1050	μs					272.2	233.0	324.0	14.0	> 5
Buffer Program Time (64 word)	250	1050	μs					231.7	200.0	267.0	10.8	> 5
Buffer Program Time (32 word)	220	1050	μs					205.6	181.0	234.0	9.2	> 5
Buffer Program Time (16 word)	200	1050	μs					185.1	165.0	209.0	7.7	> 5
Single Word Program Time (1 word)	125	400	μs					183.0	163.0	211.0	8.0	> 5

Notes:

1. Data was collected from 70 units from lots 5877960 and 5877980 (wflot : LDU6301, wf5, wflot : LDU6301, wf13).

2. Sector Erase data excludes Random data pattern programming prior to erasure.



12.4 DC Parameter Summary, -40°C

Cold Temperature, -40°C, 3V, V_{CC} Summary

Data Shaat Baramatara		Spec		Average	Min	Мах	Sigmo	Cak
Data Sheet Parameters	Тур	Мах	Unit	Average	IVIITI	IVIAX	Sigina	Срк
		DC Pa	arameters					
I_{CC1} (V _{CC} Active Read Current) 10 MHz			mA	91.40	86.59	96.76	1.84	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	48.02	45.64	50.63	0.89	> 5
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.52	4.94	5.91	0.16	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.58	4.99	5.98	0.16	
I _{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.63	5.03	6.01	0.16	
I_{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.70	5.13	6.09	0.17	> 5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	42.19	38.69	45.26	1.17	> 5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	37.61	33.41	42.89	1.87	> 5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	15.18	8.69	55.86	6.97	4.1
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.02	0.01	0.06	0.01	> 5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μA	15.06	8.59	56.63	7.00	> 5
I _{LI} (Input Leakage Current)	0.02	±1	μA	0.000	-0.013	0.011	0.0	> 5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.001	-0.011	0.013	0.0	> 5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	309.6	209.0	618.0	36.4	> 5
Buffer Program Time (256 word)	340	750	μs	344.5	204.0	485.0	27.0	> 5
Buffer Program Time (128 word)	239	750	μs	270.2	154.0	380.0	20.8	> 5
Buffer Program Time (64 word)	198	750	μs	231.2	155.0	305.0	15.5	> 5
Buffer Program Time (32 word)	175	750	μs	207.7	143.0	272.0	15.3	> 5
Buffer Program Time (16 word)	160	750	μs	192.0	131.0	265.0	12.8	> 5
Single Word Program Time (1 word)	150	400	μs	169.8	144.0	227.0	9.5	> 5

Notes:

1. Data was collected from 300 units.

2. Sector Erase excludes Random data pattern programming prior to erasure.



13. DC Device Characterization Data

ICC1 (Asynchronous Read) vs. Temperature



ICC2 (Page Read) vs. Temperature



ICC5 (Reset Current) vs. Temperature



ICC3 (Active Write) vs. Temperature



ICC6 (CMOSASM) vs. Temperature



ICC4 (Standby Current) vs. Temperature



14. AC Device Characterization Data

tACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)













tPACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tDF vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tOH vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



CONFIDENTIAL Qualification Database



Cumulative Erase Times per Sector at 105°C (VCC 3V)















Cumulative WB Program Times per Sector at 105°C (VCC 3V)

















Cumulative WB 256 Program Times per Buffer at 105°C (VCC 3V)

















Cumulative WB 128 Program Times per Buffer at 105°C (VCC 3V)















Cumulative WB 64 Program Times per Buffer at 105°C (VCC 3V)

















Cumulative WB 32 Program Times per Buffer at 105°C (VCC 3V)

















Cumulative WB 16 Program Times per Buffer at 105°C (VCC 3V)















Cumulative Single Word Program Times per Buffer at 105°C (VCC 3V)

















15. Shmoo Plots

 t_{ACC} vs. V_{CC} = V_{IO} @ 25°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	-+,	-+,	+		
3.650		* * * * *	******	* * *	94.0	
3.600		* * * * *	******	***	94.0	
3.550		* * * * *	******	***	94.0	
3.500		* * * * *	******	* * *	94.0	
3.450		* * * * *	******	* * *	94.0	
3.400		* * * * *	******	* * *	94.0	
3.350		* * * * *	******	* * *	94.0	
3.300		* * * * *	******	* * *	94.0	
3.250		* * * * *	******	* * *	94.0	
3.200		* * * * *	******	* * *	94.0	
3.150		* * * * *	******	* * *	94.0	
3.100		* * * * *	******	* * *	94.0	
3.050		* * * * *	******	* * *	94.0	
3.000		* * * * *	******	* * *	94.0	
2.950		* * * * *	******	* * *	94.0	
2.900		* * * * *	* * * * * * * * * *	***	94.0	
2.850		* * * * *	* * * * * * * * * *	***	94.0	
2.800		* * * * *	* * * * * * * * * *	***	94.0	
2.750		* * * * *	*******	***	94.0	
2.700		* * * * *	* * * * * * * * * *	* * *	94.0	
2.650		* * * * *	* * * * * * * * * *	***	94.0	
	+,	-+,	-+,	+		
	80.0	90.0	100.0	110.0		

t_{ACC} vs. V_{CC}=V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650	1	* * * * *	* * * * * * * * * *	**	94.0
3,600	İ	* * * * *	******	**	94.0
3.550	1	* * * * *	*******	**	94.0
3,500	1	* * * * *	******	**	94.0
3,450	1	* * * * *	******	**	94.0
3.400		*****	*******	**	94.0
3.350		* * * * *	******	**	94.0
3.300	1	* * * * *	******	**	94.0
3.250		* * * * *	*******	**	94.0
3.200		* * * *	******	**	95.0
3.150		* * * *	******	**	95.0
3.100		* * * *	* * * * * * * * * *	**	95.0
3.050		* * * *	******	**	95.0
3.000		* * * *	******	**	95.0
2.950	1	* * * *	******	**	95.0
2.900		* * * *	******	**	95.0
2.850		* * * *	* * * * * * * * * *	**	95.0
2.800		* * * *	******	**	95.0
2.750		* * * *	******	**	95.0
2.700		* * * *	* * * * * * * * * *	**	95.0
2.650		* * * *	******	**	95.0
	+,	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{CC}=V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first pass data
	+;	-+;	-+;	· - +	
3.500		* * * * *	*********	***	94.0
3.600		* * * * *	*********	***	94.0
3.550		* * * * *	*********	***	94.0
3.500		* * * * *	*********	***	94.0
3.450		* * * * *	*********	***	94.0
3.400		* * * * *	*********	***	94.0
3.350		* * * * *	*********	***	94.0
3.300		* * * * *	*********	***	94.0
3.250		* * * * *	*********	***	94.0
3.200		* * * * *	*********	***	94.0
3.150	1	* * * * *	*********	***	94.0
3.100		* * * * *	*********	***	94.0
3.050		* * * * *	*********	***	94.0
3.000		* * * * *	*********	***	94.0
2.950	1	* * * * *	*********	***	94.0
2.900		* * * * *	*********	***	94.0
2.850		* * * *	*********	***	95.0
2.800		* * * *	*********	***	95.0
2.750		* * * *	*********	***	95.0
2.700		* * * *	*********	***	95.0
2.650	1	* * * *	*********	***	95.0
	+;	-+;	- + ;	· - +	
	80.0	90.0	100.0	110.0	

t_{ACC} vs. V_{CC} = V_{IO} @ -40°C

	80.0	90.0	100.0	110.0	first pass	data
	+	-+,	-+,	-+		
3.650		* * * * *	******	**	94.0	
3.600		* * * * *	******	**	94.0	
3.550		* * * *	******	**	95.0	
3.500		* * * * *	******	**	94.0	
3.450		* * * * *	******	**	94.0	
3.400		* * * * *	******	**	94.0	
3.350		* * * * *	******	**	94.0	
3.300		* * * * *	*******	**	94.0	
3.250		* * * *	******	**	95.0	
3.200		* * * *	*******	**	95.0	
3.150		* * * *	*******	**	95.0	
3.100		* * * *	*******	**	95.0	
3.050		* * * *	*******	**	95.0	
3.000		* * * *	*******	**	95.0	
2.950	1	* * * *	******	**	95.0	
2.900		* * * *	******	**	95.0	
2.850		* * * *	*******	**	95.0	
2.800		* * * *	******	**	95.0	
2.750		* * * *	******	**	95.0	
2.700		* * * *	******	**	95.0	
2.650		* * * *	******	**	95.0	
	+,	-+,	-+,	- +		
	80.0	90.0	100.0	110.0		



t_{ACC} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass	data
	+,	+ ,	+,	· +		
3.000		* * * *	********	***	94.0	
2.950		* * * * *	********	***	94.0	
2.900		* * * * *	********	***	94.0	
2.850		* * * * *	* * * * * * * * * *	****	94.0	
2.800		* * * * *	********	****	94.0	
2.750		* * * * *	* * * * * * * * * *	****	94.0	
2.700		* * * * *	* * * * * * * * * *	****	94.0	
2.650		* * * * *	********	****	94.0	
2.600		* * * * *	* * * * * * * * * *	* * * *	94.0	
2.550		* * * * *	* * * * * * * * * *	* * * *	94.0	
2.500		* * * * *	********	****	94.0	
2.450		* * * * *	* * * * * * * * * *	***	94.0	
2.400		* * * * *	* * * * * * * * * *	****	94.0	
2.350		* * * * *	********	****	94.0	
2.300		* * * * *	* * * * * * * * * *	***	94.0	
2.250		* * * * *	* * * * * * * * * *	* * * *	94.0	
2.200		* * * *	* * * * * * * * * *	****	95.0	
2.150		* * * *	* * * * * * * * * *	***	95.0	
2.100		* * * *	* * * * * * * * * *	****	95.0	
2.050		* * * *	* * * * * * * * * *	****	95.0	
2.000		* * * *	* * * * * * * * * *	***	95.0	
1.950	1	* * * *	*******	***	95.0	
1.900	1	* * * *	*******	***	95.0	
1.850		* * * *	*******	***	95.0	
1.800	1	* * *	*******	****	96.0	
1.750	1	* * *	*******	****	96.0	
1.700	1	* * *	* * * * * * * * *	***	96.0	
1.650		* *	********	* * * *	97.0	
	+,	+,	+,	·+		
	80.0	90.0	100.0	110.0		

 t_{ACC} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	+,	+	
3.000		* * *	*******	***	95.0
2.950		* * *	* * * * * * * * * *	***	95.0
2.900		* * *	* * * * * * * * * *	***	95.0
2.850		* * *	********	***	95.0
2.800		* * *	* * * * * * * * * *	***	95.0
2.750		* * *	********	***	95.0
2.700		* * *	*******	***	95.0
2.650		* * *	* * * * * * * * * *	***	95.0
2.600		* * *	*******	***	95.0
2.550		* * *	*******	***	95.0
2.500		* * *	********	***	95.0
2.450		* * *	*******	***	95.0
2.400		* * *	*******	***	95.0
2.350		* * *	*******	***	95.0
2.300		* * *	*******	***	95.0
2.250		* * *	*******	***	95.0
2.200		* * *	*******	***	95.0
2.150		* *	*******	***	96.0
2.100		* *	*******	***	96.0
2.050		* *	********	***	96.0
2.000		* *	*******	***	96.0
1.950		* *	*******	***	96.0
1.900		* *	*******	***	96.0
1.850		* *	*******	***	96.0
1.800		*	*******	***	97.0
1.750		*	*******	***	97.0
1.700		*	* * * * * * * * * *	***	97.0
1.650		*	*******	***	97.0
	+,	-+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass	data
	+;	+;	+;-	+		
3.000		* * * * *	* * * * * * * * * *	* * * *	94.0	
2.950		* * * *	* * * * * * * * * *	* * * *	94.0	
2.900		* * * *	* * * * * * * * * *	* * * *	94.0	
2.850		* * * *	* * * * * * * * * *	* * * *	94.0	
2.800		* * * *	* * * * * * * * * *	****	94.0	
2.750		* * * *	* * * * * * * * * *	****	94.0	
2.700		* * * *	* * * * * * * * * *	* * * *	95.0	
2.650		* * * *	* * * * * * * * * *	****	95.0	
2.600		* * * *	* * * * * * * * * *	****	95.0	
2.550		* * * *	* * * * * * * * * *	* * * *	95.0	
2.500		* * * *	* * * * * * * * * *	****	95.0	
2.450		* * * *	* * * * * * * * * *	****	95.0	
2.400		* * * *	* * * * * * * * * *	* * * *	95.0	
2.350		* * * *	* * * * * * * * * *	****	95.0	
2.300		* * * *	* * * * * * * * * *	****	95.0	
2.250		* * * *	* * * * * * * * * *	* * * *	95.0	
2.200		* * * *	* * * * * * * * * *	****	95.0	
2.150		* * * *	* * * * * * * * * *	****	95.0	
2.100		* * * *	* * * * * * * * * *	* * * *	95.0	
2.050		* * * *	* * * * * * * * * *	****	95.0	
2.000		* * :	* * * * * * * * * *	****	96.0	
1.950		* * *	* * * * * * * * *	* * * *	96.0	
1.900		* * :	* * * * * * * * *	****	96.0	
1.850		* * *	* * * * * * * * * *	* * * *	96.0	
1.800		* * *	* * * * * * * * *	* * * *	96.0	
1.750		* * :	* * * * * * * * *	****	96.0	
1.700		*	* * * * * * * * *	****	97.0	
1.650		* :	* * * * * * * * * *	* * * *	97.0	
	+;	+;	+;-	+		
	80.0	90.0	100.0	110.0		

 t_{ACC} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.000		* * *	*******	****	95.0
2.950		* * *	******	****	95.0
2.900		* * *	*******	****	95.0
2.850		* * *	*******	****	95.0
2.800		* * *	******	****	95.0
2.750		* * *	******	****	95.0
2.700		* * *	*******	****	95.0
2.650		* * *	******	****	95.0
2.600		* * *	******	****	95.0
2.550		* * *	*******	****	95.0
2.500		* * *	*******	****	95.0
2.450		* * *	******	****	95.0
2.400		* * *	******	****	95.0
2.350		* * *	******	****	95.0
2.300		* * *	******	****	95.0
2.250		* * *	******	****	95.0
2.200		* * *	******	****	95.0
2.150		* *	******	****	96.0
2.100		* *	******	****	96.0
2.050		* *	******	****	96.0
2.000		* *	******	****	96.0
1.950		* *	******	****	96.0
1.900		* *	*******	****	96.0
1.850		* *	******	****	96.0
1.800		*	******	****	97.0
1.750		*	*******	****	97.0
1.700		*	*******	****	97.0
1.650			*******	****	98.0
	+,	+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. $V_{CC}\text{=}V_{IO} \textcircled{@} 25^\circ\text{C}$

	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.650		* * * *	* * * * * * * * * *	* * *	94.0
3.600		* * * *	******	***	94.0
3.550		* * * *	******	***	94.0
3.500		* * * *	* * * * * * * * * *	* * *	94.0
3.450		* * * *	******	***	94.0
3.400		* * * *	******	* * *	94.0
3.350		* * * *	******	* * *	94.0
3.300	1	* * * *	******	* * *	94.0
3.250		* * * *	******	* * *	94.0
3.200		* * *	******	* * *	95.0
3.150	1	* * *	******	* * *	95.0
3.100		* * *	* * * * * * * * * *	* * *	95.0
3.050		* * *	******	* * *	95.0
3.000	1	* * *	******	* * *	95.0
2.950	1	* * *	* * * * * * * * * *	* * *	95.0
2.900		* * *	* * * * * * * * * *	* * *	95.0
2.850	1	* * *	*******	* * *	95.0
2.800		* * *	* * * * * * * * * *	* * *	95.0
2.750		* * *	* * * * * * * * * *	* * *	95.0
2.700	1	* * *	******	* * *	95.0
2.650		* * *	* * * * * * * * * *	* * *	95.0
	+,	+,	+,	+	
	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{CC}=V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650		* * * *	******	**	95.0
3.600		* * * *	*******	**	95.0
3.550		* * * *	******	**	95.0
3.500		* * * *	*******	**	95.0
3.450		* * * *	*******	**	95.0
3.400		* * * *	******	**	95.0
3.350		* * * *	*******	**	95.0
3.300		* * * *	*******	**	95.0
3.250		* * * *	******	**	95.0
3.200		* * * *	*******	**	95.0
3.150		* * * *	*******	**	95.0
3.100		* * *	*******	**	96.0
3.050		* * *	*******	**	96.0
3.000		* * *	*******	**	96.0
2.950	1	* * *	* * * * * * * * * *	**	96.0
2.900		* * *	*******	**	96.0
2.850		* * *	*******	**	96.0
2.800		* * *	* * * * * * * * * *	**	96.0
2.750		* * *	*******	**	96.0
2.700		* * *	*******	**	96.0
2.650		* * *	* * * * * * * * * *	**	96.0
	+,	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{CC}=V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first	pass	data
	+;	- + ;	-+;	+			
3.650		* * * * * *	*******	***	93.0		
3.600		* * * * * *	*******	****	93.0		
3.550		* * * * * *	*******	***	93.0		
3.500		* * * * * *	*******	***	93.0		
3.450		* * * * * *	*******	****	93.0		
3.400		* * * * * *	*******	***	93.0		
3.350		* * * * * *	*******	****	93.0		
3.300		* * * * * *	*******	****	93.0		
3.250		* * * * * *	*******	****	93.0		
3.200		* * * * * *	*******	****	93.0		
3.150		* * * * * *	*******	****	93.0		
3.100		* * * * * *	*******	****	93.0		
3.050		* * * * * *	*******	****	93.0		
3.000		* * * * * *	*******	****	93.0		
2.950		* * * * * *	*******	****	93.0		
2.900		* * * * * *	*******	****	93.0		
2.850		* * * * *	*******	****	93.0		
2.800		* * * * *	*******	****	94.0		
2.750		* * * * *	*******	****	94.0		
2.700		* * * * *	*******	****	94.0		
2.650		* * * * *	*******	****	94.0		
	+;	- + ;	-+;	+			
	80.0	90.0	100.0	110.0			

t_{CE} vs. V_{CC}=V_{IO} @ -40°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650		* * * *	* * * * * * * * * *	**	95.0
3.600		* * * *	*******	**	95.0
3.550		* * * *	* * * * * * * * * *	**	95.0
3.500		* * * *	*******	**	95.0
3.450		* * * *	*******	**	95.0
3.400		* * *	*******	**	96.0
3.350		* * *	*******	**	96.0
3.300		* * *	*******	**	96.0
3.250		* * *	*******	**	96.0
3.200		* * *	*******	**	96.0
3.150		* * *	*******	**	96.0
3.100		* * *	*******	**	96.0
3.050		* * *	*******	**	96.0
3.000		* * *	*******	**	96.0
2.950	1	* * *	* * * * * * * * * *	**	96.0
2.900		* * *	* * * * * * * * * *	**	96.0
2.850		* * *	*******	**	96.0
2.800		* * *	* * * * * * * * * *	**	96.0
2.750		* * *	* * * * * * * * * *	**	96.0
2.700		* * *	*******	**	96.0
2.650		* * *	* * * * * * * * * *	**	96.0
	+,	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass	data
	+,	+ ,	+,	+		
3.000		* * * *	*******	***	95.0	
2.950		* * * *	******	* * *	95.0	
2.900		* * * *	*******	* * *	95.0	
2.850		* * * *	* * * * * * * * * *	* * *	95.0	
2.800		* * * *	* * * * * * * * * *	***	95.0	
2.750		* * * *	* * * * * * * * * *	* * *	95.0	
2.700		* * * *	* * * * * * * * * *	* * *	95.0	
2.650	1	* * * *	* * * * * * * * * *	***	95.0	
2.600		* * * *	* * * * * * * * * *	***	95.0	
2.550		* * * *	* * * * * * * * * *	***	95.0	
2.500		* * * *	* * * * * * * * * *	***	95.0	
2.450		* * * *	* * * * * * * * * *	***	95.0	
2.400		* * * *	* * * * * * * * * *	***	95.0	
2.350		* * * *	*******	***	95.0	
2.300	1	* * * *	* * * * * * * * * *	***	95.0	
2.250		* * * *	* * * * * * * * * *	***	95.0	
2.200		* * * *	******	***	95.0	
2.150	1	* * * *	* * * * * * * * * *	***	95.0	
2.100		* * * *	* * * * * * * * * *	***	95.0	
2.050		* * * *	******	***	95.0	
2.000	1	* * *	* * * * * * * * * *	***	96.0	
1.950	1	* * *	******	***	96.0	
1.900	1	* * *	*******	***	96.0	
1.850		* * *	******	***	96.0	
1.800		* *	*******	***	97.0	
1.750	1	* *	*******	***	97.0	
1.700	1	,	*******	* * *	98.0	
1.650	1	,	*******	* * *	98.0	
	+,	+,	+,	+		
	80.0	90.0	100.0	110.0		

t_{CE} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	-+,	+	
3.000		* * *	*******	* * *	96.0
2.950		* * *	******	***	96.0
2.900		* * *	*******	***	96.0
2.850		* * *	*******	***	96.0
2.800		* * *	******	***	96.0
2.750		* * *	*******	***	96.0
2.700		* * *	*******	***	96.0
2.650		* * *	******	***	96.0
2.600		* * *	*******	***	96.0
2.550		* * *	*******	***	96.0
2.500		* * *	******	***	96.0
2.450		* * *	******	* * *	96.0
2.400		* * *	*******	* * *	96.0
2.350		* * *	******	***	96.0
2.300		* * *	******	* * *	96.0
2.250		* * *	*******	* * *	96.0
2.200		* * *	******	***	96.0
2.150		* * *	*******	* * *	96.0
2.100		* *	*******	* * *	97.0
2.050		* *	******	***	97.0
2.000		* *	*******	***	97.0
1.950		* *	*******	* * *	97.0
1.900		* *	******	***	97.0
1.850		* *	*******	***	97.0
1.800		*	*******	***	98.0
1.750		*	******	***	98.0
1.700			*******	***	99.0
1.650			******	***	99.0
	+,	-+,	-+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first	pass	data
	+;	-+;	-+;	+			
3.000		* * * * *	********	* * *	93.0		
2.950		* * * * * *	********	* * *	93.0		
2.900		* * * * *	* * * * * * * * * *	* * *	93.0		
2.850		* * * * *	* * * * * * * * * *	* * *	93.0		
2.800		* * * * *	* * * * * * * * * *	***	93.0		
2.750		* * * * *	* * * * * * * * * *	* * *	94.0		
2.700		* * * * *	* * * * * * * * * *	* * *	94.0		
2.650		* * * * *	********	* * *	94.0		
2.600		* * * * *	* * * * * * * * * *	* * *	94.0		
2.550		* * * * *	* * * * * * * * * *	* * *	94.0		
2.500		* * * * *	* * * * * * * * * *	***	94.0		
2.450		* * * * *	* * * * * * * * * *	* * *	94.0		
2.400		* * * * *	* * * * * * * * * *	* * *	94.0		
2.350		* * * * *	********	* * *	94.0		
2.300		* * * * *	* * * * * * * * * *	* * *	94.0		
2.250		* * * * *	* * * * * * * * * *	* * *	94.0		
2.200		* * * * *	* * * * * * * * * *	***	94.0		
2.150		* * * * *	* * * * * * * * * *	* * *	94.0		
2.100		* * * * *	* * * * * * * * * *	* * *	94.0		
2.050		* * * *	* * * * * * * * *	* * *	95.0		
2.000		* * * *	* * * * * * * * *	* * *	95.0		
1.950		* * * *	* * * * * * * * *	***	95.0		
1.900		* * * *	*******	* * *	95.0		
1.850		* * *	* * * * * * * * *	* * *	96.0		
1.800		* * *	* * * * * * * * *	* * *	96.0		
1.750		* * *	*******	***	96.0		
1.700		* *	* * * * * * * * *	* * *	97.0		
1.650		* *	* * * * * * * * *	***	97.0		
	+;	-+;	-+;;	+İ			
	80.0	90.0	100.0	110.0			

 t_{CE} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	+,	- +	
3.000		* * *	*******	***	96.0
2.950		* *	*******	* * *	96.0
2.900		* * :	*******	***	96.0
2.850		* * :	*******	***	96.0
2.800		* *	*******	* * *	96.0
2.750		* * :	*******	***	96.0
2.700		* * :	*******	***	96.0
2.650		* *	******	***	96.0
2.600		* * :	******	***	96.0
2.550		* * :	*******	***	96.0
2.500		* *	******	***	96.0
2.450		* * :	*******	***	96.0
2.400		* * :	******	***	96.0
2.350		* *	******	***	96.0
2.300		* * :	*******	***	96.0
2.250		*	*******	***	97.0
2.200		*	******	***	97.0
2.150		*	*******	***	97.0
2.100		*	*******	***	97.0
2.050	1	*	*******	***	97.0
2.000		*	*******	***	97.0
1.950		* :	*******	***	97.0
1.900	1		******	***	98.0
1.850			******	***	98.0
1.800			******	***	98.0
1.750	1		*******	***	98.0
1.700	1		.********	***	99.0
1.650			. * * * * * * * * * *	***	99.0
	+,	-+,	+,	+ İ	
	80.0	90.0	100.0	110.0	

first pass data

6.0 6.0

6.0 6.0 6.0 6.0

6.0 6.0 6.0



t_{OE} vs. V_{CC}=V_{IO} @ 25°C

	0.0	10.0	20.0
	+	-+,	-+
3.650	* * *	* * * * * * * * * *	**
3.600	***	* * * * * * * * * *	**
3.550	***	* * * * * * * * * *	**
3.500	* * *	* * * * * * * * * *	**
3.450	* * *	* * * * * * * * * *	**
3.400	* * *	* * * * * * * * * *	**
3.350	* * *	* * * * * * * * * *	**
3.300	* * *	* * * * * * * * * *	**
3.250	* * *	* * * * * * * * * *	**
3.200	***	* * * * * * * * * *	**
3.150	* * *	* * * * * * * * * *	**
3.100	***	* * * * * * * * * *	**
3.050	***	* * * * * * * * * *	**
3.000	* * *	* * * * * * * * * *	**
2.950	***	* * * * * * * * * *	**
2.900	***	* * * * * * * * * *	**
2.850	* * *	* * * * * * * * * *	**
2.800	***	* * * * * * * * * *	**
2.750	***	* * * * * * * * * *	**
2.700	* * *	* * * * * * * * * *	**
2.650	***	* * * * * * * * * *	**
	+,	-+,	-+
	0.0	10.0	20.0

t_{OE} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0	first j	pass	data
	+,	-+,	-+			
3.650	***	* * * * * * * * * *	**	6.0		
3.600	***	* * * * * * * * * *	**	6.0		
3.550	***	* * * * * * * * * *	**	6.0		
3.500	***	* * * * * * * * * *	**	6.0		
3.450	***	* * * * * * * * * *	**	6.0		
3.400	***	* * * * * * * * * *	**	6.0		
3.350	***	* * * * * * * * * *	**	6.0		
3.300	***	* * * * * * * * * *	**	6.0		
3.250	***	* * * * * * * * * *	**	6.0		
3.200	***	* * * * * * * * * *	**	6.0		
3.150	***	* * * * * * * * * *	**	6.0		
3.100	***	* * * * * * * * * *	**	6.0		
3.050	***	* * * * * * * * * *	**	6.0		
3.000	**	* * * * * * * * * *	**	7.0		
2.950	* *	* * * * * * * * * *	**	7.0		
2.900	**	* * * * * * * * * *	**	7.0		
2.850	**	* * * * * * * * * *	**	7.0		
2.800	* *	* * * * * * * * * *	**	7.0		
2.750	**	* * * * * * * * * *	**	7.0		
2.700	**	* * * * * * * * * *	**	7.0		
2.650	**	* * * * * * * * * *	**	7.0		
	+,	-+,	-+			
	0.0	10.0	20.0			



t_{OE} vs. V_{CC}=V_{IO} @ 105°C

	0.0	10.0	20.0
	+;	+ ;	-+;
3.650	*	* * * * * * * * * * *	******
3.600	*	*******	******
3.550	*	* * * * * * * * * * *	******
3.500	*	* * * * * * * * * * *	******
3.450	*	* * * * * * * * * * *	******
3.400	*	* * * * * * * * * * *	******
3.350	*	* * * * * * * * * * *	******
3.300	*	* * * * * * * * * * *	******
3.250	*	* * * * * * * * * * *	******
3.200	*	* * * * * * * * * * *	******
3.150	*	* * * * * * * * * * *	******
3.100	*	* * * * * * * * * * *	******
3.050		* * * * * * * * * * *	******
3.000		* * * * * * * * * * *	******
2.950	'	* * * * * * * * * * *	******
2.900	'	* * * * * * * * * * *	******
2.850		* * * * * * * * * * *	******
2.800		* * * * * * * * * * *	******
2.750	'	* * * * * * * * * * *	******
2.700		* * * * * * * * * * *	******
2.650	'	* * * * * * * * * * *	******
	+;	+;	-+;
	0.0	10.0	20.0

first pass data

7.0

t_{OE} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first	pass	data
	+	-+,	-+			
3.650	***	* * * * * * * * * *	**	6.0		
3.600	***	* * * * * * * * * *	**	6.0		
3.550	***	* * * * * * * * * *	**	6.0		
3.500	***	* * * * * * * * * *	**	6.0		
3.450	***	* * * * * * * * * *	**	6.0		
3.400	***	* * * * * * * * * *	**	6.0		
3.350	***	* * * * * * * * * *	**	6.0		
3.300	* * *	* * * * * * * * * *	**	6.0		
3.250	***	* * * * * * * * * *	**	6.0		
3.200	***	* * * * * * * * * *	**	6.0		
3.150	***	* * * * * * * * * *	**	6.0		
3.100	***	* * * * * * * * * *	**	6.0		
3.050	***	* * * * * * * * * *	**	6.0		
3.000	***	* * * * * * * * * *	**	6.0		
2.950	***	* * * * * * * * * *	**	6.0		
2.900	* * *	* * * * * * * * * *	**	6.0		
2.850	***	* * * * * * * * * *	**	6.0		
2.800		* * * * * * * * * *	**	6.0		
2.750	* * *	* * * * * * * * * *	**	6.0		
2.700	* * *	* * * * * * * * * *	**	6.0		
2.650	***	* * * * * * * * * *	**	6.0		
	+	-+,	-+			
	0.0	10.0	20.0			

first pass data

6.06.06.06.06.06.06.06.06.06.07.0

7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0

8.0 8.0 8.0 8.0 9.0 9.0



t_{OE} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	0.0	10.0	20.0
	+,-	+, -	+
3.000	*	*********	* * * *
2.950	1 *	*********	****
2.900	*	*********	* * * * *
2.850	*	*********	* * * *
2.800	*	*********	****
2.750	1 *	*********	****
2.700	*	*********	* * * * *
2.650	1 *	********	****
2.600	1 *	*********	****
2.550	1 *	*********	****
2.500	1 *	********	****
2.450		********	****
2.400		. * * * * * * * * * *	* * * * *
2.350		********	****
2.300		. * * * * * * * * * *	* * * * *
2.250		. * * * * * * * * * *	* * * * *
2.200		********	****
2.150		********	****
2.100		. * * * * * * * * * *	* * * * *
2.050		********	****
2.000		********	****
1.950		* * * * * * * * *	****
1.900		* * * * * * * * *	****
1.850		* * * * * * * * *	****
1.800		* * * * * * * * *	* * * *
1.750		* * * * * * * * *	****
1.700		* * * * * * * *	****
1.650		* * * * * * * *	****
	+,-	+, -	+
	0.0	10.0	20.0

t_{OE} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	0.0	10.0	20.0	first	pass	data
	+,	+,	+			
3.000	*	********	***	7.0		
2.950	*	* * * * * * * * * *	***	7.0		
2.900	*	*******	* * *	7.0		
2.850	*	*******	***	7.0		
2.800	*	* * * * * * * * * *	***	7.0		
2.750	*	*******	* * *	7.0		
2.700	*	*******	* * *	7.0		
2.650	*	* * * * * * * * * *	***	7.0		
2.600	*	*******	* * *	7.0		
2.550	*	*******	* * *	7.0		
2.500	*	* * * * * * * * * *	***	7.0		
2.450	*	*******	* * *	7.0		
2.400	*	*******	* * *	7.0		
2.350	*	* * * * * * * * * *	***	7.0		
2.300	*	* * * * * * * * * *	* * *	7.0		
2.250	*	*******	***	7.0		
2.200	*	* * * * * * * * * *	***	7.0		
2.150	*	* * * * * * * * * *	* * *	7.0		
2.100	*	*******	***	7.0		
2.050		* * * * * * * * * *	***	8.0		
2.000		*******	* * *	8.0		
1.950		********	***	8.0		
1.900	1	********	***	8.0		
1.850		********	* * *	8.0		
1.800		********	***	8.0		
1.750	1	. * * * * * * * * *	***	9.0		
1.700		.*******	* * *	9.0		
1.650		. * * * * * * * * *	* * *	9.0		
	+,	+,	+			
	0.0	10.0	20.0			



t_{OE} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	0.0	10.0	20.0
	+;	- + ;	-+;
3.000	*	********	*****
2.950	*	*********	******
2.900	*	*********	******
2.850	*	*********	******
2.800		********	******
2.750	1	********	******
2.700	1	********	******
2.650	1	********	******
2.600	1	*******	******
2.550	1	********	******
2.500	1	********	******
2.450	1	* * * * * * * * * * *	******
2.400	1	*******	******
2.350	1	********	******
2.300	1	* * * * * * * * * * *	******
2.250	1	* * * * * * * * * * *	******
2.200	1	********	******
2.150	1	* * * * * * * * * * *	******
2.100		********	******
2.050	1	*******	******
2.000		********	******
1.950	1	*******	******
1.900	1	*******	******
1.850	1	*******	******
1.800		. * * * * * * * * *	******
1.750	1	. * * * * * * * * *	******
1.700	1	. * * * * * * * * *	******
1.650		. * * * * * * * * *	******
	+;	- + ;	-+;
	0.0	10.0	20.0

 t_{OE} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	0.0	10.0	20.0	first	pass	data
	+,	-+,	+			
3.000	***	*********	***	6.0		
2.950	* * *	*********	* * *	6.0		
2.900	***	*********	* * *	6.0		
2.850	* * *	*********	* * *	6.0		
2.800	* * *	*********	* * *	6.0		
2.750	***	*********	* * *	6.0		
2.700	* * *	*********	* * *	6.0		
2.650	* * *	********	* * *	6.0		
2.600	***	*********	* * *	6.0		
2.550	* * *	*********	* * *	6.0		
2.500	***	********	* * *	6.0		
2.450	***	*********	* * *	6.0		
2.400	* * *	*********	* * *	6.0		
2.350	* * *	********	* * *	6.0		
2.300	***	*********	* * *	6.0		
2.250	* * *	*********	* * *	6.0		
2.200	* * *	*********	* * *	6.0		
2.150	**	*********	* * *	7.0		
2.100	**	*********	* * *	7.0		
2.050	**	********	* * *	7.0		
2.000	**	*********	* * *	7.0		
1.950	**	*********	***	7.0		
1.900	**	* * * * * * * * * * *	***	7.0		
1.850	*	* * * * * * * * * * *	***	8.0		
1.800	*	*********	***	8.0		
1.750	*	* * * * * * * * * * *	***	8.0		
1.700	*	* * * * * * * * * * *	***	8.0		
1.650		* * * * * * * * * *	***	9.0		
	+,	-+,	+ İ			
	0.0	10.0	20.0			

8.0 8.0 8.0 8.0



t_{PACC} vs. V_{CC} = V_{IO} @ 25°C

	0.0	10.0	20.0	first pas	s data
	+,	-+,	- +		
3.650		. * * * * * * * * *	**	10.0	
3.600		. * * * * * * * * *	**	10.0	
3.550		. * * * * * * * * *	**	10.0	
3.500		. * * * * * * * * *	**	10.0	
3.450		. * * * * * * * * *	**	10.0	
3.400		. * * * * * * * * *	**	10.0	
3.350		. * * * * * * * * *	**	10.0	
3.300		. * * * * * * * * *	**	10.0	
3.250		. * * * * * * * * *	**	10.0	
3.200		. * * * * * * * * *	**	10.0	
3.150		. * * * * * * * * *	**	10.0	
3.100		. * * * * * * * * *	**	10.0	
3.050		. * * * * * * * * *	**	10.0	
3.000		. * * * * * * * * *	**	10.0	
2.950		. * * * * * * * * *	**	10.0	
2.900		. * * * * * * * * *	**	10.0	
2.850		. * * * * * * * * *	**	10.0	
2.800		. * * * * * * * * *	**	10.0	
2.750		. * * * * * * * * *	**	10.0	
2.700		. * * * * * * * * *	**	10.0	
2.650		. * * * * * * * * *	**	10.0	
	+,	-+,	- +		
	0.0	10.0	20.0		

t_{PACC} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0	first pass	data
	+,	-+,	-+		
3.650		. * * * * * * * * * *	**	10.0	
3.600		. * * * * * * * * * * *	**	10.0	
3.550		********	**	10.0	
3.500		********	**	10.0	
3.450		********	**	10.0	
3.400		. * * * * * * * * * *	**	10.0	
3.350		. * * * * * * * * * *	**	10.0	
3.300		. * * * * * * * * * *	**	10.0	
3.250		. * * * * * * * * * *	**	10.0	
3.200		. * * * * * * * * * *	**	10.0	
3.150		. * * * * * * * * * *	**	10.0	
3.100		. * * * * * * * * * *	**	10.0	
3.050		. * * * * * * * * * *	**	10.0	
3.000		. * * * * * * * * * *	**	10.0	
2.950		. * * * * * * * * * *	**	10.0	
2.900		. * * * * * * * * * *	**	10.0	
2.850		. * * * * * * * * * *	**	10.0	
2.800		. * * * * * * * * * *	**	10.0	
2.750		. * * * * * * * * * *	**	10.0	
2.700		. * * * * * * * * * *	**	10.0	
2.650		. * * * * * * * * * *	**	10.0	
	+,	-+,	-+		
	0.0	10.0	20.0		



t_{PACC} vs. V_{CC} = V_{IO} @ 105°C

	0.0	10.0	20.0	first	pass	data
	+;	-+;	-+			
3.650		* * * * * * *	**	12.0		
3.600		* * * * * * *	**	12.0		
3.550		* * * * * *	**	12.0		
3.500		* * * * * *	**	12.0		
3.450		* * * * * *	**	12.0		
3.400		* * * * * *	**	12.0		
3.350		* * * * * *	**	12.0		
3.300		* * * * * *	**	12.0		
3.250		* * * * * *	**	12.0		
3.200		* * * * * *	**	12.0		
3.150		* * * * * * *	**	12.0		
3.100		* * * * * *	**	12.0		
3.050		* * * * * *	**	12.0		
3.000		* * * * * *	**	12.0		
2.950		* * * * * * *	**	12.0		
2.900		* * * * * * *	**	12.0		
2.850		* * * * * *	**	12.0		
2.800		* * * * * *	**	12.0		
2.750		* * * * * * *	**	12.0		
2.700		* * * * * *	**	12.0		
2.650		* * * * * *	**	12.0		
	+;	-+;	-+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first pass	data
	+,	. + ,	-+		
3.650		******	**	9.0	
3.600	[,]	*******	**	9.0	
3,550	¹	********	**	9.0	
3.500		*******	* *	9.0	
3.450		********	**	9.0	
3,400		*******	**	9.0	
3.350		********	**	9.0	
3.300		*******	**	9.0	
3.250		********	* *	9.0	
3.200		********	**	9.0	
3.150	[,]	*******	**	9.0	
3.100		********	**	9.0	
3.050		********	**	9.0	
3.000	[,]	*******	**	9.0	
2.950		* * * * * * * * * * *	**	9.0	
2.900		* * * * * * * * * *	**	9.0	
2.850		* * * * * * * * * *	* *	9.0	
2.800		* * * * * * * * * * *	**	9.0	
2.750		*******	**	10.0	
2.700		*******	**	10.0	
2.650		*******	**	10.0	
	+,	-+,	-+		
	0.0	10.0	20.0		

first pass data

10.0 10.0 10.0 10.0

10.0 10.0 10.0

10.0 11.0 11.0 11.0 11.0 12.0 12.0 12.0



t_{PACC} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	0.0	10.0	20.0
	+,	+,	+
3.000		* * * * * * * *	***
2.950		* * * * * * * *	***
2.900		* * * * * * * *	***
2.850		* * * * * * * *	***
2.800		* * * * * * * *	***
2.750		* * * * * * * *	***
2.700		* * * * * * * *	***
2.650		* * * * * * * *	***
2.600		* * * * * * * *	***
2.550		* * * * * * * *	***
2.500		* * * * * * * *	***
2.450		* * * * * * * *	***
2.400		* * * * * * * *	***
2.350		* * * * * * * *	***
2.300		* * * * * * * *	***
2.250		* * * * * * * *	***
2.200		* * * * * * * *	***
2.150		* * * * * * * *	***
2.100		* * * * * * * *	***
2.050		* * * * * * * *	***
2.000		* * * * * * * *	***
1.950		* * * * * * *	***
1.900		* * * * * * *	***
1.850		* * * * * * *	***
1.800		* * * * * * *	***
1.750		* * * * * *	***
1.700		* * * * * *	***
1.650		* * * * * *	***
	+,	+,	+
	0.0	10.0	20.0

 t_{PACC} vs. $V_{IO} @ 85^{\circ}C (V_{CC} = 3V)$

	0.0	10.0	20.0	first	pass	data
	+,	-+,	- +			
3.000		. * * * * * * * * *	**	10.0		
2.950		. * * * * * * * * *	**	10.0		
2.900		. * * * * * * * * *	**	10.0		
2.850		. * * * * * * * * *	**	10.0		
2.800		. * * * * * * * * *	**	10.0		
2.750		. * * * * * * * * *	**	10.0		
2.700		. * * * * * * * * *	**	10.0		
2.650		. * * * * * * * * *	**	10.0		
2.600		. * * * * * * * * *	**	10.0		
2.550		. * * * * * * * * *	**	10.0		
2.500		. * * * * * * * * *	**	10.0		
2.450		. * * * * * * * * *	**	10.0		
2.400		* * * * * * * *	**	11.0		
2.350		* * * * * * * *	**	11.0		
2.300		* * * * * * * *	**	11.0		
2.250		* * * * * * * *	**	11.0		
2.200		* * * * * * * *	**	11.0		
2.150		* * * * * * * *	**	11.0		
2.100		* * * * * * * *	**	11.0		
2.050		* * * * * * * *	**	11.0		
2.000		* * * * * * * *	**	11.0		
1.950		* * * * * * * *	**	11.0		
1.900		* * * * * * * *	**	11.0		
1.850		* * * * * * *	**	12.0		
1.800		* * * * * * *	**	12.0		
1.750		* * * * * * *	**	12.0		
1.700		* * * * * * *	**	12.0		
1.650		* * * * * * *	**	12.0		
		-+,	-+İ			
	0.0	10.0	20.0			



t_{PACC} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	0.0	10.0	20.0	first	pass	data
	+;	- + ;	-+			
3.000		* * * * * * *	***	12.0		
2.950		* * * * * * *	**	12.0		
2.900		* * * * * * *	***	12.0		
2.850		* * * * * * *	***	12.0		
2.800		* * * * * * *	**	12.0		
2.750		* * * * * * *	**	12.0		
2.700		* * * * * * *	***	12.0		
2.650		* * * * * * *	**	12.0		
2.600		* * * * * * *	**	12.0		
2.550		* * * * * * *	**	12.0		
2.500		* * * * * * *	**	12.0		
2.450		* * * * * * *	**	12.0		
2.400		* * * * * * *	**	12.0		
2.350		* * * * * * *	**	12.0		
2.300		* * * * * *	**	13.0		
2.250		* * * * * *	**	13.0		
2.200		* * * * * *	**	13.0		
2.150		* * * * * *	**	13.0		
2.100		* * * * * *	**	13.0		
2.050		* * * * * *	**	13.0		
2.000		* * * * * *	**	13.0		
1.950		* * * * * *	**	13.0		
1.900		* * * * * *	**	13.0		
1.850		* * * * * *	**	13.0		
1.800		* * * * * *	**	13.0		
1.750		* * * * *	**	14.0		
1.700		* * * * *	***	14.0		
1.650		* * * * *	***	14.0		
	+;	- + ;	· - +			
	0.0	10.0	20.0			

 t_{PACC} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	0.0	10.0	20.0	first	pass	data
	+,	-+,	-+			
3.000		* * * * * * * * * *	**	9.0		
2.950		* * * * * * * * * *	**	9.0		
2.900		* * * * * * * * * *	***	9.0		
2.850		* * * * * * * * * *	**	9.0		
2.800		* * * * * * * * * *	**	9.0		
2.750		* * * * * * * * * *	***	9.0		
2.700		* * * * * * * * * *	***	9.0		
2.650		* * * * * * * * * *	**	9.0		
2.600		* * * * * * * * * *	***	9.0		
2.550		. * * * * * * * * *	**	10.0		
2.500		.*******	**	10.0		
2.450		.*******	**	10.0		
2.400		.*******	**	10.0		
2.350		.*******	**	10.0		
2.300		.*******	**	10.0		
2.250		.*******	**	10.0		
2.200		.*******	**	10.0		
2.150		.*******	**	10.0		
2.100		.*******	**	10.0		
2.050		.*******	**	10.0		
2.000		.*******	**	10.0		
1.950		. * * * * * * * * *	**	10.0		
1.900		* * * * * * * *	**	11.0		
1.850		* * * * * * * *	**	11.0		
1.800		* * * * * * * *	**	11.0		
1.750		******	**	12.0		
1.700		******	**	12.0		
1.650		******	**	12.0		
	+,	-+,	· - +			
	0.0	10.0	20.0			



V_{IH} vs. $V_{\text{CC}}\text{=}V_{\text{IO}}$ @ 25°C

	1.000	1.500	2.000	2.500	3.000	first pass da	ita
	+,	+,	+,	+,	+		
3.650			* * * * *	* * * * * * * * * *	***	2.150	
3.600			* * * * * *	* * * * * * * * * *	***	2.100	
3.550			* * * * * *	* * * * * * * * * *	***	2.100	
3.500			* * * * * *	* * * * * * * * * *	***	2.050	
3.450			* * * * * * * *	* * * * * * * * * *	***	2.000	
3.400			* * * * * * * *	* * * * * * * * * *	***	2.000	
3.350			. * * * * * * * * *	* * * * * * * * * *	***	1.950	
3.300			*******	* * * * * * * * * *	***	1.900	
3.250			******	* * * * * * * * * *	* * * *	1.900	
3.200		*	*******	* * * * * * * * * *	***	1.850	
3.150	1	*	******	* * * * * * * * * *	***	1.850	
3.100		* *	*******	* * * * * * * * * *	***	1.800	
3.050		* *	* * * * * * * * * *	* * * * * * * * * *	***	1.800	
3.000		* * *	*******	* * * * * * * * * *	***	1.750	
2.950		* * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.700	
2.900		* * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.700	
2.850		* * * * *	******	* * * * * * * * * *	***	1.650	
2.800		* * * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.650	
2.750		* * * * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.600	
2.700		* * * * * *	******	* * * * * * * * * *	***	1.600	
2.650		* * * * * * *	******	* * * * * * * * *	***	1.550	
	+,	+,	+,	+,	· +		
	1.000	1.500	2.000	2.500	3.000		

V_{IH} vs. V_{CC}=V_{IO} @ 85°C

	1.000	1.500	2.000	2.500	3.000	first	pass	data
	+	-+,	+,	+,	+			
3.650			* * * * *	* * * * * * * * * *	***	2.150		
3.600			* * * * * *	* * * * * * * * * *	***	2.100		
3.550	1		* * * * * * *	* * * * * * * * * *	***	2.050		
3.500	1		* * * * * * *	* * * * * * * * * *	***	2.050		
3,450			*******	* * * * * * * * * *	***	2.000		
3 400			*******	* * * * * * * * * *	***	2 000		
3 350			********	* * * * * * * * * *	***	1 950		
3 300			* * * * * * * * * * * *	* * * * * * * * * *	***	1 900		
3 250			*******	* * * * * * * * * *	***	1 900		
3 200		**	********	* * * * * * * * * *	***	1 950		
3 150		**	*******	* * * * * * * * * *	***	1 950		
2 100		***	*********	* * * * * * * * * *	***	1 000		
2 050		***	*******	* * * * * * * * * * *	***	1 000		
3.030	• • • • • • • • •				+++	1 750		
3.000					***	1.750		
2.950					***	1.700		
2.900					***	1.700		
2.850			* * * * * * * * * * *	* * * * * * * * * * *	***	1.650		
2.800		*****	*******	* * * * * * * * * *	***	1.650		
2.750		*****	********	* * * * * * * * * *	***	1.600		
2.700		* * * * * * * *	*********	* * * * * * * * * *	***	1.550		
2.650		* * * * * * * *	*******	* * * * * * * * * *	***	1.550		
	+,	-+,	+,	+,	+			
	1.000	1.500	2.000	2.500	3.000			



V_{IH} vs. V_{CC}=V_{IO} @ 105°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+;	+;	+;	+;	+	
3.650			.*******	*******	****	1.950
3.600			.******	*******	****	1.950
3.550	1		******	*******	****	1.900
3.500		*	*******	*******	****	1.850
3.450		*	******	*******	****	1.850
3.400	1	*	******	*******	****	1.850
3.350		* *	******	*******	****	1.800
3.300		* *	******	*******	****	1.800
3.250		* * *	*******	*******	****	1.750
3.200		* * * *	*******	*******	****	1.700
3.150		* * * *	******	*******	****	1.700
3.100		* * * * *	*******	*******	****	1.650
3.050		* * * * *	*******	*******	****	1.650
3.000	1	* * * * * *	*******	*******	****	1.600
2.950		* * * * * *	*******	*******	****	1.600
2.900		* * * * * *	*******	*******	****	1.550
2.850		* * * * * * *	*******	*******	* * * *	1.550
2.800		* * * * * * * *	*******	*******	****	1.500
2.750		* * * * * * * *	*******	*******	* * * *	1.500
2.700		.*******	*******	*******	* * * *	1.450
2.650		. * * * * * * * * *	*******	*******	* * * *	1.450
	+;	+;	+;	+;	+	
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. V_{CC}=V_{IO} @ -40°C

lata



V_{IL} vs. V_{CC} = V_{IO} @ 25°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+,	+,	+,	+ ,	+			
3.650	*******	********	* * * * * * * * * * *	**		1.450		
3.600	*******	*******	* * * * * * * * * * *	*		1.400		
3.550	******	*******	*******	*		1.400		
3.500	******	*******	* * * * * * * * * *	*		1.400		
3.450	*******	*******	*******			1.350		
3.400	******	*******	*******			1.350		
3.350	******	*******	*******			1.350		
3.300	*******	*******	*********			1.300		
3.250	*******	*******	*********			1.300		
3.200	******	*******	********			1.300		
3.150	*******	*******	*********			1.300		
3.100	******	*******	*******			1.250		
3.050	******	*******	*******			1.250		
3.000	*******	*******	*******			1.250		
2.950	******	*******	******			1.200		
2.900	******	*******	******			1.200		
2.850	******	*******	*****			1.150		
2.800	******	*******	*****			1.150		
2.750	******	*******	*****			1.150		
2.700	******	*******	*****			1.100		
2.650	******	* * * * * * * * * *	*****			1.100		
	+,	+,	+,	+,	+			
	0.000	0.500	1.000	1.500	2.000			

V_{IL} vs. V_{CC} =V_{IO} @ 85°C

	0.000	0.500	1.000	1.500	2.000	first pass da	ata
	+,	+,	+,	+,	+		
3.650	*******	*******	*******	***		1.450	
3.600	******	*******	*******	**		1.400	
3.550	******	* * * * * * * * * *	*******	**		1.400	
3.500	*******	* * * * * * * * * *	*******	**		1.400	
3.450	*******	* * * * * * * * * *	*******	*		1.350	
3.400	******	* * * * * * * * * *	*******	•		1.350	
3.350	******	* * * * * * * * * *	********			1.300	
3.300	******	* * * * * * * * * *	********			1.300	
3.250	******	* * * * * * * * * *	******			1.300	
3.200	******	* * * * * * * * * *	*******			1.300	
3.150	*******	* * * * * * * * * *	*******			1.250	
3.100	******	* * * * * * * * * *	*******			1.250	
3.050	******	* * * * * * * * * *	******			1.200	
3.000	******	* * * * * * * * * *	******			1.200	
2.950	******	* * * * * * * * * *	*****			1.150	
2.900	******	* * * * * * * * * *	******			1.200	
2.850	******	* * * * * * * * * *	*****			1.150	
2.800	******	*******	*****			1.150	
2.750	******	* * * * * * * * * *	****			1.100	
2.700	******	* * * * * * * * * *	****			1.100	
2.650	******	******	****			1.100	
	+,	+,	+,	+,	+		
	0.000	0.500	1.000	1.500	2.000		


$V_{IL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	1.500	2.000	first pass data
	+;	+ ;	+;	+ ;	· +	
3.650	*******	* * * * * * * * * *	*******	***		1.450
3.600	*******	* * * * * * * * * *	********	***		1.450
3.550	*******	* * * * * * * * * *	********	***		1.450
3.500	*******	* * * * * * * * * *	*******	**		1.400
3.450	*******	* * * * * * * * * *	********	**		1.400
3.400	*******	* * * * * * * * * *	********	**		1.400
3.350	*******	* * * * * * * * * *	********	*		1.350
3.300	******	* * * * * * * * * *	********	*		1.350
3.250	*******	* * * * * * * * * *	********	*		1.350
3.200	*******	* * * * * * * * * *	*******			1.300
3.150	*******	* * * * * * * * * *	*******			1.300
3.100	*******	* * * * * * * * * *	*******			1.300
3.050	******	* * * * * * * * * *	*********		[1.250
3.000	*******	* * * * * * * * * *	********			1.250
2.950	*******	* * * * * * * * * *	********			1.250
2.900	*******	* * * * * * * * * *	*******			1.200
2.850	*******	* * * * * * * * * *	*******			1.200
2.800	******	* * * * * * * * * *	*******			1.200
2.750	*******	* * * * * * * * * *	******			1.150
2.700	*******	* * * * * * * * * *	******			1.150
2.650	******	* * * * * * * * * *	******			1.150
	+;;	+;	+;	+;	· + İ	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	+,	+,	+	
3.650	*******	*******	*******	***		1.450
3.600	*******	*******	*******	**		1.400
3.550	******	********	********	**		1.400
3.500	******	********	********	**		1.400
3.450	******	********	********	**		1.400
3.400	******	* * * * * * * * * *	*******	**		1.400
3.350	******	* * * * * * * * * *	*******	*		1.350
3.300	******	* * * * * * * * * *	*******	*		1.350
3.250	******	* * * * * * * * * *	*******	*		1.350
3.200	******	* * * * * * * * * *	*******			1.300
3.150	******	* * * * * * * * * *	*******			1.300
3.100	******	* * * * * * * * * *	********			1.250
3.050	******	********	********			1.250
3.000	******	********	********			1.250
2.950	******	* * * * * * * * *	********			1.250
2.900	******	*******	*******			1.200
2.850	******	*******	*******			1.200
2.800	******	* * * * * * * * * *	*******			1.200
2.750	******	* * * * * * * * * *	******			1.150
2.700	******	*******	******			1.150
2.650	* * * * * * * *	* * * * * * * * * *	*****			1.100
	+,	+,	+ ,	+,	+	
	0.000	0.500	1.000	1.500	2.000	



$V_{OH}\,vs.~V_{CC}{=}V_{IO} \textcircled{0}{25}{}^\circ C$

	2.000	2.500	3.000	3.500	4.000	first pas	s data
	+,	-+,	-+,	+,	+		
3.650	*******	* * * * * * * * * *	********	****		3.550	
3.600	*******	*******	********	***		3.500	
3.550	*******	* * * * * * * * * *	********	**		3.450	
3.500	*******	* * * * * * * * * *	********	*		3.400	
3.450	*******	* * * * * * * * * *	*********	*		3.400	
3.400	*******	* * * * * * * * * *	********			3.300	
3.350	*******	* * * * * * * * * *	*******			3.250	
3.300	*******	********	******			3.200	
3.250	*******	* * * * * * * * * *	*****			3.150	
3.200	*******	* * * * * * * * * *	****			3.100	
3.150	*******	*******	****			3.050	
3.100	*******	* * * * * * * * * *	****			3.050	
3.050	*******	* * * * * * * * * *	***			3.000	
3.000	*******	*******	**			2.950	
2.950	*******	* * * * * * * * * *	•			2.900	
2.900	*******	********				2.850	
2.850	*******	*******				2.800	
2.800	*******	******				2.750	
2.750	*******	*****				2.700	
2.700	*******	****				2.650	
2.650	*******	****				2,600	
	+	-+	-+	+	+		
	2.000	2.500	3.000	3.500	4.000		

V_{OH} vs. V_{CC}=V_{IO} @ 85°C

2.000	2.500	3.000	3.500	4.000	first pas	s data
+,	+,	+ ,	+ ,	+		
*******	*******	*********	****		3.600	
*******	*******	*********	***		3.500	
*******	********	*********	**		3.450	
*******	********	*********	*		3.400	
*******	********	*********			3.350	
******	* * * * * * * * * * *	*********			3.350	
*******	********	********			3.300	
*******	********	*******			3.250	
******	* * * * * * * * * * *	******			3.200	
*******	********	*****			3.150	
*******	********	*****			3.100	
******	* * * * * * * * * * *	****			3.050	
*******	********	***			3.000	
*******	********	**			2.950	
******	* * * * * * * * * * *	*			2.900	
*******	*******				2.850	
*******	*********				2.800	
******	*******				2.750	
******	******				2.700	
*******	*****				2.650	
*******	*****				2.600	
+,	+,	+,	+ ,	+		
2.000	2.500	3.000	3.500	4.000		
	2.000 +, ******** **********************	2.000 2.500 +,+,,,,,,	2.000 2.500 3.000 ************************************	2.000 2.500 3.000 3.500 +***********************************	2.000 2.500 3.000 3.500 4.000 ************************************	2.000 2.500 3.000 3.500 4.000 first pas ************************************



$V_{OH}\,vs.\,V_{CC}\text{=}V_{IO}\,\textcircled{0}$ 105°C

	2.000	2.500	3.000	3.500	4.000	first pass data
	+;	- + ;	+;	+ ;	+	
3.650	*******	*******	* * * * * * * * * *	* * * *		3.550
3.600	*******	*******	*******	* * *		3.500
3.550	* * * * * * * * *	* * * * * * * * * *	*******	**		3.450
3.500	* * * * * * * * *	* * * * * * * * * *	*******	*		3.400
3.450	*******	*******	*******			3.350
3.400	*******	*******	********			3.300
3.350	*******	*******	*******			3.250
3,300	*******	*******	******			3,200
3.250	*******	*******	*****			3.150
3.200	*******	*******	****			3.100
3,150	*******	*******	****			3,050
3.100	*******	*******	***			3.000
3.050	*******	*******	**			2,950
3.000	 * * * * * * * * *	*******	*			2,900
2,950		*******				2.850
2,900	*******	********				2.800
2.850	*******	*******				2.750
2.800	 * * * * * * * * * *	******				2.700
2.750	*******	*****				2.650
2 700	* * * * * * * * *	****				2 600
2.700	 * * * * * * * * * *	****				2.000
2.030	4	····				2.000
	2 000	2 500	3 000	3 500	1 000	
	2.000	4.500	5.000	5.500	4.000	

V_{OH} vs. V_{CC}=V_{IO} @ -40°C

	2.000	2.500	3.000	3.500	4.000	first	pass	data
	+,	- + ,	-+,	-+,	-+			
3.650	*******	*********	*******	***		3.550		
3.600	*******	*********	*******	**		3.500		
3.550	*******	********	*******	*		3.450		
3.500	*******	********	*******			3.400		
3.450	*******	********	*********			3.350		
3.400	*******	********	********			3.300		
3.350	*******	********	*******			3.250		
3.300	*******	********	*******			3.250		
3.250	*******	* * * * * * * * * * *	*****			3.150		
3.200	*******	********	*****			3.150		
3.150	*******	********	***			3.050		
3.100	*******	* * * * * * * * * * *	***			3.050		
3.050	*******	********	**			3.000		
3.000	*******	********	*			2.950		
2.950	*******	*********	•			2.900		
2.900	*******	**********				2.850		
2.850	*******	********				2.800		
2.800	*******	*******				2.750		
2.750	*******	******				2.700		
2.700	*******	*****				2.650		
2.650	*******	****				2.600		
	+,	-+,	-+,	-+,	-+			
	2.000	2.500	3.000	3.500	4.000			



$V_{OL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 25^{\circ}\text{C}$

	0.000	0.500	1.000	first pass	data
	+,	+,	+		
3.650	.******	*******	* * * *	0.050	
3.600	.******	******	* * * *	0.050	
3.550	.******	*******	* * * *	0.050	
3.500	.******	*******	* * * *	0.050	
3.450	.******	******	* * * *	0.050	
3.400	.******	*******	* * * *	0.050	
3.350	.******	*******	* * * *	0.050	
3.300	.******	******	* * * *	0.050	
3.250	.******	*******	* * * *	0.050	
3.200	.******	*******	* * * *	0.050	
3.150	.******	******	* * * *	0.050	
3.100	.******	*******	* * * *	0.050	
3.050	.******	*******	* * * *	0.050	
3.000	.******	******	* * * *	0.050	
2.950	.******	*******	* * * *	0.050	
2.900	.******	*******	* * * *	0.050	
2.850	.******	******	* * * *	0.050	
2.800	.******	******	* * * *	0.050	
2.750	.******	*******	* * * *	0.050	
2.700	.******	******	* * * *	0.050	
2.650	.******	******	* * * *	0.050	
	+,	+,	+		
	0.000	0.500	1.000		

V_{OL} vs. V_{CC}=V_{IO} @ 85°C

	0.000	0.500	1.000	first pass 🛛	data
	+,	+,	+		
3.650	.****	* * * * * * * * * * *	****	0.050	
3.600	.****	* * * * * * * * * * *	****	0.050	
3.550	.****	*******	****	0.050	
3.500	.****	* * * * * * * * * * *	****	0.050	
3.450	.****	* * * * * * * * * * *	****	0.050	
3.400	.****	* * * * * * * * * * *	****	0.050	
3.350	.****	* * * * * * * * * * *	****	0.050	
3.300	.****	* * * * * * * * * * *	****	0.050	
3.250	.****	* * * * * * * * * * *	****	0.050	
3.200	.****	* * * * * * * * * * *	****	0.050	
3.150	.****	* * * * * * * * * * *	****	0.050	
3.100	.****	* * * * * * * * * * *	****	0.050	
3.050	.****	* * * * * * * * * * *	****	0.050	
3.000	.****	*******	****	0.050	
2.950	.****	* * * * * * * * * * *	****	0.050	
2.900	.****	* * * * * * * * * * *	* * * * *	0.050	
2.850	.****	*******	****	0.050	
2.800	.****	* * * * * * * * * * *	* * * * *	0.050	
2.750	.****	* * * * * * * * * * *	* * * * *	0.050	
2.700	.****	*******	****	0.050	
2.650	.****	* * * * * * * * * * *	* * * * *	0.050	
	+,	,	+		
	0.000	0.500	1.000		



$V_{OL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	first pa	ss data
	+;	-+;	+		
3.650	.******	* * * * * * * * * *	***	0.050	
3.600	.******	* * * * * * * * *	***	0.050	
3.550	.*******	* * * * * * * * * *	***	0.050	
3.500	.*******	* * * * * * * * * *	***	0.050	
3.450	.*******	* * * * * * * * * *	***	0.050	
3.400	.*******	* * * * * * * * * *	***	0.050	
3.350	.*******	* * * * * * * * * *	***	0.050	
3.300	.*******	* * * * * * * * * *	***	0.050	
3.250	.*******	* * * * * * * * * *	***	0.050	
3.200	.*******	* * * * * * * * * *	***	0.050	
3.150	.******	* * * * * * * * *	***	0.050	
3.100	. * * * * * * * *	* * * * * * * * *	* * *	0.050	
3.050	.*******	* * * * * * * * * *	***	0.050	
3.000	.*******	* * * * * * * * * *	***	0.050	
2.950	. * * * * * * * *	* * * * * * * * *	***	0.050	
2.900	. * * * * * * * *	* * * * * * * * *	***	0.050	
2.850	.******	* * * * * * * * *	***	0.050	
2.800	. * * * * * * * *	* * * * * * * * *	***	0.050	
2.750	. * * * * * * * *	* * * * * * * * *	***	0.050	
2.700	.******	* * * * * * * * *	***	0.050	
2.650	.******	* * * * * * * * *	***	0.050	
	+;	-+;	+		
	0.000	0.500	1.000		

V_{OL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	first	pass	data
	+	-+,	-+			
3.650	*******	*******	**	0.050		
3.600	.*******	* * * * * * * * * *	**	0.050		
3.550	.*******	******	**	0,050		
3.500	*******	* * * * * * * * * *	**	0.050		
3.450	*******	* * * * * * * * * *	**	0.050		
3.400	.*******	******	**	0,050		
3.350	.*******	* * * * * * * * * *	**	0.050		
3.300	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.250	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.200	.*******	* * * * * * * * * *	**	0.050		
3.150	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.100	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.050	.*******	* * * * * * * * * *	**	0.050		
3.000	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.950	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.900	.******	* * * * * * * * * *	**	0.050		
2.850	.******	* * * * * * * * * *	**	0.050		
2.800	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.750	.*******	* * * * * * * * * *	**	0.050		
2.700	.******	* * * * * * * * * *	**	0.050		
2.650	.******	* * * * * * * * * *	**	0.050		
	+,	-+,	-+			
	0.000	0.500	1.000			



V_{IH} vs. V_{IO} @ 25°C

	0.500	1.000	1.500	2.000	first pass	data
	+,	+,	+,	· +		
3.000			* * *	****	1.750	
2.950			* * * *	****	1.700	
2.900			* * * *	****	1.700	
2.850			* * * * *	***	1.650	
2.800			* * * * *	***	1.650	
2.750			* * * * *	****	1.600	
2.700			* * * * *	****	1.600	
2.650			* * * * * *	****	1.550	
2.600	1		* * * * * * * *	****	1.500	
2.550	1		* * * * * * * *	****	1.500	
2.500	1		* * * * * * * * *	****	1.450	
2.450			* * * * * * * * *	****	1.450	
2.400			********	****	1.400	
2.350	1		*******	****	1.400	
2.300		,	********	****	1.350	
2.250		,	********	****	1.350	
2.200	1	* *	********	****	1.300	
2.150		* * *	********	****	1.250	
2.100		* * *	********	****	1.250	
2.050	1	* * * *	********	****	1.200	
2.000	1	* * * *	*******	****	1.200	
1.950		* * * * *	* * * * * * * * * *	****	1.150	
1.900	1	* * * * * *	*********	****	1.100	
1.850	1	* * * * * *	* * * * * * * * * *	****	1.100	
1.800	1	* * * * * * *	* * * * * * * * * *	****	1.050	
1.750	1	* * * * * * *	*********	****	1.050	
1.700		* * * * * * * *	********	****	1.000	
1.650	1	. * * * * * * * * *	********	****	0.950	
	+	+,	+,	+		
	0.500	1.000	1.500	2.000		



	0.500	1.000	1.500	2.000	2.500	first pass data
	+,	-+,	-+,	-+,	+	
3.000			* * * *	******	***	1.750
2.950			* * * * *	*******	***	1.700
2.900			*****	*******	***	1.700
2.850			*****	*******	***	1.650
2.800			* * * * * *	******	***	1.650
2.750			* * * * * *	******	***	1.600
2.700			* * * * * * * *	*******	***	1.550
2.650			* * * * * * * *	*******	***	1.550
2.600			.*******	******	***	1.500
2.550			. * * * * * * * * *	*******	***	1.500
2.500			*******	*******	***	1.450
2.450			* * * * * * * * * *	******	***	1.450
2.400		*	******	*******	***	1.400
2.350		*	******	*******	***	1.400
2.300		* *	******	******	***	1.350
2.250		***	******	*******	***	1.300
2.200		* * *	******	******	***	1.300
2.150		* * * *	******	******	***	1.250
2.100		* * * *	******	*******	***	1.250
2.050		* * * * *	******	*******	***	1.200
2.000		* * * * *	******	******	***	1.200
1.950		* * * * * *	* * * * * * * * * *	*******	***	1.150
1.900		* * * * * * *	*******	******	***	1.100
1.850		* * * * * *	* * * * * * * * * *	*******	***	1.100
1.800		* * * * * * * *	* * * * * * * * * *	*******	***	1.050
1.750		* * * * * * * *	*******	*******	***	1.050
1.700		. * * * * * * * * *	* * * * * * * * * *	*****	***	1.000
1.650		* * * * * * * * * *	*******	******	***	0.950
	+,	-+,	-+,	-+,	+	
	0.500	1.000	1.500	2.000	2.500	



V_{IH} vs. V_{IO} @ 105°C

	0.500	1.000	1.500	2.000	2.500	first pass data
	+;	+;	;-;	+;	+	
3.000			* * * * *	* * * * * * * * * * *	* * * *	1.600
2.950			* * * * *	********	* * * *	1.600
2.900			• • • • * * * * * * *	* * * * * * * * * * *	* * * *	1.550
2.850			• • • • * * * * * * *	* * * * * * * * * * *	* * * *	1.550
2.800			* * * * * * *	*******	* * * *	1.500
2.750			* * * * * * *	* * * * * * * * * * *	* * * *	1.500
2.700			* * * * * * * * *	* * * * * * * * * * *	* * * *	1.450
2.650			* * * * * * * * *	********	* * * *	1.450
2.600			. * * * * * * * * * *	* * * * * * * * * * * *	* * * *	1.400
2.550			. * * * * * * * * * *	* * * * * * * * * * * *	* * * *	1.400
2.500		'	* * * * * * * * * * *	********	* * * *	1.350
2.450		* '	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.300
2.400		* '	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.300
2.350		* '	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.300
2.300		* * '	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.250
2.250		* * * *	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.200
2.200		* * * *	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.200
2.150		* * * *	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.200
2.100		* * * * *	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.150
2.050		* * * * *	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.150
2.000		* * * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.100
1.950		* * * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.100
1.900		* * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.050
1.850		* * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.050
1.800		* * * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.000
1.750		* * * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.000
1.700		* * * * * * * *	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.000
1.650		* * * * * * * * *	* * * * * * * * * *	* * * * * * * * * *	* * * *	0.950
	+;	;;	;-;-	;;;	+	
	0.500	1.000	1.500	2.000	2.500	



	0.500	1.000	1.500	2.000	2.500	first pass data
	+,	-+,	+,	+ ,	+	
3.000			* * * '	********	***	1.750
2.950			* * * *	* * * * * * * * * *	***	1.750
2.900			* * * * *	* * * * * * * * * *	***	1.700
2.850			* * * * *	* * * * * * * * * *	***	1.700
2.800			* * * * *	*******	***	1.650
2.750			* * * * * * *	* * * * * * * * * *	***	1.600
2.700			* * * * * * *	*******	***	1.600
2.650	1		* * * * * * * *	* * * * * * * * * *	***	1.550
2.600			* * * * * * * *	* * * * * * * * * *	***	1.550
2.550			* * * * * * * * *	*******	***	1.500
2.500	1		* * * * * * * * *	* * * * * * * * * *	***	1.500
2.450			********	* * * * * * * * * *	***	1.450
2.400		*	********	* * * * * * * * * *	***	1.400
2.350	1	,	********	* * * * * * * * * *	***	1.400
2.300		* *	********	* * * * * * * * * *	***	1.350
2.250		* *	********	* * * * * * * * * *	***	1.350
2.200	1	* * *	********	* * * * * * * * * *	***	1.300
2.150		* * *	********	* * * * * * * * * *	***	1.300
2.100		* * * *	********	* * * * * * * * * *	***	1.250
2.050	1	* * * * *	********	* * * * * * * * * *	***	1.200
2.000		* * * * *	*******	* * * * * * * * * *	***	1.200
1.950		* * * * * *	*********	*******	***	1.150
1.900	1	* * * * * *	********	********	***	1.150
1.850	1	* * * * * * *	********	* * * * * * * * * *	***	1.100
1.800	1	* * * * * * * *	********	* * * * * * * * * *	***	1.050
1.750	1	. * * * * * * * * *	********	*******	***	1.000
1.700		*******	********	*******	***	1.000
1,650		*******	********	*******	***	0,950
	+	-+	-+	+	+	
	0.500	1.000	1.500	2.000	2.500	



V_{IL} vs. V_{IO} @ 25°C

	0.000	0.500	1.000	1.500	2.000	first pass data
3 000	+, ******	********	+,-	+,	+	1 250
3.000	+ + + + + + + + + + + + + + + + + + +		*********	•••••	• • • •	1.250
2.950	+ + + + + + + + + + + + + + + + + + +				• • • •	1,250
2.900	++++++++				• • • •	1.200
2.830			*******	• • • • • • • • • • •	• • • •	1.200
2.800	+ + + + + + + + + + + + + + + + + + +				• • • •	1,150
2.750	+ + + + + + + + + + + + + + + + + + +		· · · · · · · · · · · · · · · · · · ·		• • • •	1.150
2.700					• • • •	1.100
2.650			* * * * * * * * * * * * * * * * * * * *			1.100
2.600			* * * * * * * • • • • •			1.100
2.550			* * * * * *			1.050
2.500			* * * * * *			1.050
2.450	*******	********	* * * * *			1.050
2.400	*******	*******	* * * *			1.000
2.350	*******	******	* * * *			1.000
2.300	******	*******	* * * *			1.000
2.250	*******	*******	* * * * • • • • • • •			1.000
2.200	*******	********	* * *			0.950
2.150	*******	********	* * *			0.950
2.100	*******	********	* *			0.900
2.050	*******	*******	* *			0.900
2.000	******	*******	* *			0.900
1.950	******	********	*			0.850
1.900	******	********	*			0.850
1.850	******	*******	*			0.850
1.800	******	********	*			0.850
1.750	******	*******	*			0.850
1.700	******	*******				0.800
1.650	******	*******				0.800
	+,	+,	+,-	+,	+	
	0.000	0.500	1.000	1.500	2.000	



	0.000	0.500	1.000	1.500	2.000	first pass dat	a
	+,	+,	+,	-+,	+		
3.000	*******	*******	*******			1.200	
2.950	*******	* * * * * * * * * * *	* * * * * * *			1.200	
2.900	*******	* * * * * * * * * * *	******			1.200	
2.850	*******	* * * * * * * * * * *	*****			1.150	
2.800	******	* * * * * * * * * * *	*****			1.150	
2.750	******	* * * * * * * * * * *	*****			1.150	
2.700	*******	* * * * * * * * * * *	*****			1.100	
2.650	******	* * * * * * * * * * *	*****			1.100	
2.600	******	* * * * * * * * * * *	****			1.050	
2.550	*******	* * * * * * * * * * *	****			1.050	
2.500	******	* * * * * * * * * * *	* * * *			1.050	
2.450	******	* * * * * * * * * * *	****			1.050	
2.400	******	* * * * * * * * * * *	***			1.000	
2.350	******	* * * * * * * * * * *	***			1.000	
2.300	******	* * * * * * * * * * *	***			1.000	
2.250	*******	* * * * * * * * * * *	**			0.950	
2.200	******	* * * * * * * * * * *	**			0.950	
2.150	******	* * * * * * * * * * *	**			0.950	
2.100	*******	* * * * * * * * * * *	*			0.900	
2.050	******	* * * * * * * * * * *	*			0.900	
2.000	******	* * * * * * * * * * *	*			0.900	
1.950	*******	* * * * * * * * * * *	*			0.900	
1.900	******	*******				0.850	
1.850	*******	********				0.850	
1.800	*******	*******				0.850	
1.750	* * * * * * * * * *	*******				0.850	
1.700	*******	********				0.800	
1.650	******	********				0.800	
	+,	+,	+,	-+,	+		
	0.000	0.500	1.000	1.500	2.000		



V_{IL} vs. V_{IO} @ 105°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+;	+;	;-	+;	+	1 050
3.000		* * * * * * * * * * * *	* * * * * * * * * * *	•••••		1.250
2.950	*******	* * * * * * * * * * *	* * * * * * * * * * .			1.250
2.900	*******	* * * * * * * * * * *	* * * * * * * * *			1.200
2.850	*******	* * * * * * * * * * *	* * * * * * * * *			1.200
2.800	*******	* * * * * * * * * * *	* * * * * * * * *			1.200
2.750	*******	* * * * * * * * * * *	* * * * * * * *		• • • •	1.150
2.700	*******	******	* * * * * * *		• • • •	1.150
2.650	*******	*******	* * * * * * * *			1.150
2.600	*******	*******	* * * * * *			1.100
2.550	*******	*******	* * * * * * • • • • •			1.100
2.500	*******	********	* * * * * *			1.100
2.450	*******	********	* * * * *			1.050
2.400	*******	********	* * * * *			1.050
2.350	*******	*******	* * * * *			1.050
2.300	*******	*******	* * * *			1.000
2.250	*******	*******	* * * *			1.000
2.200	******	*******	* * * *			1.000
2.150	******	*******	* * *			0.950
2.100	******	*******	* * *			0.950
2.050	******	********	* * *			0.950
2.000	******	********	* *			0.900
1.950	******	********	* *			0.900
1.900	******	********	* *			0.900
1.850	*******	*********	*			0.850
1.800	******	********	*			0.850
1.750	******	********	*			0.850
1.700	******	********				0.800
1.650	* * * * * * * *	********				0.800
	+;	;;	+;-	+;	+	
	0.000	0.500	1.000	1.500	2.000	



	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	+,	-+,	+	
3.000	*******	*******	********			1.250
2.950	*******	*******	*******			1.250
2.900	******	*******	******			1.200
2.850	*******	*******	******			1.200
2.800	*******	******	******			1.200
2.750	******	*******	*****			1.150
2.700	*******	*******	*****			1.150
2.650	*******	******	*****			1.150
2.600	******	*******	*****			1.100
2.550	******	*******	*****			1.100
2.500	*******	******	*****			1.100
2.450	******	*******	****			1.050
2.400	******	*******	****			1.050
2.350	******	******	****			1.050
2.300	******	*******	***			1.000
2.250	******	*******	***			1.000
2.200	******	*******	***			1.000
2.150	******	* * * * * * * * * *	**			0.950
2.100	******	*******	**			0.950
2.050	******	*******	*			0.900
2.000	******	*******	*			0.900
1.950	*******	*******	*			0.900
1.900	*******	********	*			0.900
1.850	******	*******				0.850
1.800	*******	*******				0.850
1.750	*******	*******				0.850
1.700	*******	********				0.800
1.650	*******	********				0.800
	+,	+,	+,	-+,	+	
	0.000	0.500	1.000	1.500	2.000	



V_{OH} vs. V_{IO} @ 25°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+,	+,-	+,-	+,-	+	
3.000	******	* * * * * * * * * * *	* * * * * * * * * * *	***		2.950
2.950	******	* * * * * * * * * * *	* * * * * * * * * * *	**		2.900
2.900	******	* * * * * * * * * * *	* * * * * * * * * *	*		2.850
2.850	******	* * * * * * * * * * *	* * * * * * * * * *			2.800
2.800	******	* * * * * * * * * *	* * * * * * * * * * .			2.750
2.750	******	* * * * * * * * * * *	* * * * * * * * * • •			2.700
2.700	******	* * * * * * * * * * *	* * * * * * * * • • •			2.650
2.650	******	* * * * * * * * * * *	* * * * * *			2.600
2.600	******	* * * * * * * * * * *	* * * * *			2.550
2.550	******	* * * * * * * * * * *	* * * *			2.500
2.500	******	* * * * * * * * * * *	* * *			2.450
2.450	******	* * * * * * * * * * *	* *			2.400
2.400	******	* * * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *				2.300
2.300	******	* * * * * * * * * .				2.250
2.250	******	* * * * * * * *				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	* * * * *				2.050
2.050	******	* * * *				2.000
2.000	******	* * *				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******					1.750
1,750	*****				İ	1,700
1.700	****					1,650
1.650	***					1,600
	+	+	+	+	+	
	1.500	2.000	2.500	3.000	3.500	



	1.500	2.000	2.500	3.000	3.500	first pass data
2 000	+,-	+,-	+, -	· + , -	+	2 050
3.000				· · · · · · · · · · · · · · · · · · ·		2.930
2.950	+++++++	*********	* * * * * * * * * * * *	· ^ ^		2.900
2.900	+++++++			° ° · · · · · · · · · · ·		2.850
2.850				••••••		2.800
2.800	******	********	* * * * * * * * * * .			2.750
2.750	******	*********	* * * * * * * * *			2.700
2.700	******	* * * * * * * * * * *	* * * * * * * *			2.650
2.650	******	******	* * * * * *			2.600
2.600	******	******	* * * * *			2.550
2.550	******	******	* * * *			2.500
2.500	******	* * * * * * * * * *	* * *			2.450
2.450	******	* * * * * * * * * *	* *			2.400
2.400	******	* * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *				2.300
2.300	******	********				2.250
2.250	******	*******				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	*****				2.050
2.050	******	****				2.000
2.000	******	***				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******					1.750
1.750	*****				İ	1.700
1.700	****					1.650
1.650	***					1,600
	+	+	+	+	+	
	1.500	2.000	2.500	3.000	3.500	



V_{OH} vs. V_{IO} @ 105°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+;;	;-	+ ; -	;-	+	
3.000	******	* * * * * * * * * *	* * * * * * * * * *	**		2.900
2.950	******	* * * * * * * * * *	* * * * * * * * * *	*		2.850
2.900	******	* * * * * * * * * *	* * * * * * * * * *	• • • • • • • • • • •		2.800
2.850	******	* * * * * * * * * *	* * * * * * * * * .			2.750
2.800	******	* * * * * * * * * *	* * * * * * * *			2.700
2.750	******	* * * * * * * * * *	* * * * * * *			2.650
2.700	******	* * * * * * * * * *	* * * * * *			2.600
2.650	******	* * * * * * * * * *	* * * * *			2.550
2.600	******	* * * * * * * * * *	* * * *			2.500
2.550	******	* * * * * * * * * *	* * *			2.450
2.500	******	* * * * * * * * * *	**			2.400
2.450	******	* * * * * * * * * *	*			2.350
2.400	******	* * * * * * * * * *				2.300
2.350	******	*********				2.250
2.300	******	*******				2.200
2.250	******	* * * * * * *				2.150
2.200	******	* * * * * *				2.100
2.150	******	* * * * *				2.050
2.100	******	* * * *				2.000
2.050	******	* * *				1.950
2.000	******	* *				1.900
1.950	******	*				1.850
1.900	******	*				1.850
1.850	*****				[1.750
1.800	*****					1.700
1.750	****					1.650
1.700	****					1.650
1.650	***					1.600
	+;	+;-	+;-	;-	·+	
	1.500	2.000	2.500	3.000	3.500	



	1.500	2.000	2.500	3.000	3.500	first pass data
	+,-	+, -	+, -	, -	+	
3.000	******	* * * * * * * * * *	* * * * * * * * * *	****		2.950
2.950	******	* * * * * * * * * *	* * * * * * * * * *	**		2.900
2.900	******	* * * * * * * * * *	* * * * * * * * * *	**		2.850
2.850	******	*******	* * * * * * * * * *	•		2.800
2.800	******	* * * * * * * * * *	*********			2.750
2.750	******	* * * * * * * * * *	*******			2.700
2.700	******	* * * * * * * * * *	******			2.650
2.650	******	* * * * * * * * * *	* * * * * *			2.600
2.600	******	* * * * * * * * * *	* * * * *			2.550
2.550	******	* * * * * * * * * *	* * * *			2.500
2.500	******	* * * * * * * * * *	* * *			2.450
2.450	******	* * * * * * * * * *	**			2.400
2.400	******	* * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *				2.300
2.300	******	*********				2.250
2.250	******	********				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	*****				2.050
2.050	******	****]	2.000
2.000	******	* * *				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******					1.750
1.750	*****				[1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+,-	+,-		· + İ	
	1.500	2.000	2.500	3.000	3.500	



V_{OL} vs. V_{IO} @ 25°C

	0.000	0.500	1.000	first pass data
	+,-	+, -	+	
3.000	.*****	********	****	0.050
2.950	.*****	********	****	0.050
2.900	. * * * * * *	********	****	0.050
2.850	.*****	********	****	0.050
2.800	.*****	********	****	0.050
2.750	.*****	*******	****	0.050
2.700	.*****	*******	****	0.050
2.650	.*****	********	****	0.050
2.600	.*****	*******	****	0.050
2.550	.*****	*******	****	0.050
2.500	.*****	*******	****	0.050
2.450	.*****	*******	****	0.050
2.400	.*****	*******	****	0.050
2.350	.****	********	****	0.050
2.300	.*****	********	****	0.050
2.250	.*****	*******	****	0.050
2.200	.*****	********	****	0.050
2.150	.*****	********	****	0.050
2.100	.*****	*******	****	0.050
2.050	.*****	********	****	0.050
2.000	.*****	********	****	0.050
1.950	.*****	*******	****	0.050
1.900	.*****	*******	****	0.050
1.850	.*****	*******	****	0.050
1.800	.*****	********	****	0.050
1.750	.*****	********	****	0.050
1.700	.*****	********	****	0.050
1.650	.*****	********	****	0.050
	+,-	, -	+	
	0.000	0.500	1.000	

V_{OL} vs. V_{IO} @ 85°C

	0.000	0.500	1.000	first pas	s data
	+,	+,	+		
3.000	.******	*******	***	0.050	
2.950	.******	******	***	0.050	
2.900	.******	* * * * * * * * * *	***	0.050	
2.850	.******	* * * * * * * * * *	***	0.050	
2.800	.******	******	***	0.050	
2.750	.******	* * * * * * * * * *	***	0.050	
2.700	.******	* * * * * * * * * *	***	0.050	
2.650	.******	******	***	0.050	
2.600	.******	* * * * * * * * * *	***	0.050	
2.550	.******	* * * * * * * * * *	***	0.050	
2.500	.******	******	***	0.050	
2.450	.******	* * * * * * * * * *	***	0.050	
2.400	.******	******	***	0.050	
2.350	.******	******	***	0.050	
2.300	.******	* * * * * * * * * *	***	0.050	
2.250	.******	******	***	0.050	
2.200	.******	******	***	0.050	
2.150	.******	* * * * * * * * * *	***	0.050	
2.100	.******	******	***	0.050	
2.050	.******	******	***	0.050	
2.000	.******	* * * * * * * * * *	***	0.050	
1.950	.******	******	***	0.050	
1.900	.******	******	***	0.050	
1.850	.******	*******	***	0.050	
1.800	.******	******	***	0.050	
1.750	.******	******	***	0.050	
1.700	.******	* * * * * * * * * *	***	0.050	
1.650	.******	******	***	0.050	
	+,	+,	+		
	0.000	0.500	1.000		



V_{OL} vs. V_{IO} @ 105°C

	0.000	0.500	1.00	0 first	pass	data
	+;	+; -	+			
3.000	. * * * * * * *	******	* * * *	0.050		
2.950	.******	******	* * * *	0.050		
2.900	. * * * * * * *	******	* * * *	0.050		
2.850	. * * * * * * *	******	* * * *	0.050		
2.800	. * * * * * * *	*******	* * * *	0.050		
2.750	. * * * * * * *	*******	* * * *	0.050		
2.700	. * * * * * * *	*******	* * * *	0.050		
2.650	. * * * * * * *	******	* * * *	0.050		
2.600	. * * * * * * *	*******	****	0.050		
2.550	. * * * * * * *	*******	****	0.050		
2.500	.******	*******	* * * *	0.050		
2.450	.******	*******	* * * *	0.050		
2.400	.******	*******	* * * *	0.050		
2.350	.******	*******	* * * *	0.050		
2.300	.******	*******	* * * *	0.050		
2.250	.******	*******	* * * *	0.050		
2.200	.******	******	* * * *	0.050		
2.150	.******	*******	* * * *	0.050		
2.100	.******	*******	* * * *	0.050		
2.050	.******	******	* * * *	0.050		
2.000	.******	*******	* * * *	0.050		
1.950	. * * * * * * *	*******	* * * *	0.050		
1.900	.******	*******	* * * *	0,050		
1.850	******	*******	* * * *	0.050		
1.800	******	*******	* * * *	0.050		
1.750	******	*******	* * * *	0.050		
1.700	******	*******	* * * *	0.050		
1.650	******	*******	* * * *	0.050		
	+:	+:-	+	0.000		
	0.000	0.500	1.00	0		

V_{OL} vs. V_{IO} @ -40°C

	0.000	0.500	1.000	first	pass	data
	+,	+,	+			
3.000	.******	*******	***	0.050		
2.950	. * * * * * * *	* * * * * * * * * *	***	0.050		
2.900	.******	******	***	0.050		
2.850	.******	******	***	0.050		
2.800	.******	******	***	0.050		
2.750	.******	******	***	0.050		
2.700	.******	******	***	0.050		
2.650	.******	******	***	0.050		
2.600	.******	******	***	0.050		
2.550	.******	*******	***	0.050		
2.500	.******	******	***	0.050		
2.450	.******	*******	***	0.050		
2.400	.******	*******	***	0.050		
2.350	.******	******	***	0.050		
2.300	.******	* * * * * * * * * *	***	0.050		
2.250	.******	*******	***	0.050		
2.200	.******	* * * * * * * * * *	***	0.050		
2.150	.******	*******	***	0.050		
2.100	.******	*******	***	0.050		
2.050	.******	* * * * * * * * * *	***	0.050		
2.000	.******	*******	***	0.050		
1.950	.******	*******	***	0.050		
1.900	.******	* * * * * * * * * *	***	0.050		
1.850	.******	*******	***	0.050		
1.800	.******	*******	***	0.050		
1.750	. * * * * * * *	******	***	0.050		
1.700	. * * * * * * *	* * * * * * * * * *	***	0.050		
1.650	.******	*******	***	0.050		
	+,	+,	+			
	0.000	0.500	1.000			



16. Quality Assurance Guidelines

Cypress is totally committed to shipping the highest quality product to its customers.

To assure this quality commitment, each commercial manufacturing lot must meet the requirements defined in all of the specifications listed below:

Procedure	Test Method	Quality Test
Electrical Classification Tests	Guard banded to Data Sheet Specification	100%
Mark	Cypress F16-018	100%
Lead Scan / Straighten	Cypress F16-049	100%
Visual / Mechanical Inspection	Cypress F16-049	100%
QA Documentation / Test verification	Cypress F06-027	100%
QA - Visual / Mechanical	Cypress F06-027	Sample
Excelsior Monitor (See Below)	Cypress F00-006	Sample
Qualification Maintenance Program	Cypress F01-002.18	Sample

16.1 Excelsior Quality Monitor

Cypress's Excelsior Quality Program is an in-line monitor of electrical, visual/mechanical, solderability and marking permanency quality. Data from Excelsior Electrical Monitor may be made available to customers on request. Samples are selected from production lots and subjected to data sheet electrical temperature requirements. Any failures are analyzed by product engineering and appropriate corrective action is implemented. The excelsior quality levels are summarized by each product line on a monthly basis. This monitor has proven to be instrumental in Cypress's drive to attain the highest quality levels in the industry.

16.2 Advance Change Notification

The Cypress Advance Change Notification System aims to notify the customer of major product changes 90 days prior to the implementation of that change. A change is considered to be major if it affects the application, performance, quality, reliability, parameter distribution, form, fit or function of the product. In addition we may also notify changes such as relocation of manufacturing sites, certain Data Sheet items, or other changes that may affect use or acceptance of the product.

It should be noted that all changes are fully evaluated and qualified in accordance with well established and rigorous procedures. The changed product is not released for production or shipment until satisfactory qualification results, consistent with stable processes, predictable distributions and satisfactory and expected reliability figures and yields are achieved. Often shipment is recommended before the formal qualification report is available. The actual qualification tests, however, are completed and approved prior to shipment.

16.3 Customer Corrective Action Request

Cypress's Customer Corrective Action Request (CCAR) system provides a means for submitting customer perceived product problems to Cypress's factory for analysis. The analysis may be comprised of several stages, usually an initial analysis and follow-up analysis. A summary of Cypress's findings are issued. These may include corrective actions, requests for additional information or detailed failure analysis results.



17. Qualification Maintenance Program

The Cypress Qualification Maintenance Program (QMP) is used to measure the reliability of all process families on a regular basis. As it is not feasible to monitor the reliability of each of the literally hundreds of device types that Cypress produces, devices representative of the wafer fabrication process and the generic device grouping are selected on the basis of complexity, production volume, and strategic importance. These samples are subjected to the typical accelerated stress tests listed below on a monthly basis. Any failures encountered are analyzed by product engineering and appropriate corrective action is implemented. The results of this testing are summarized in the Cypress Quarterly Reliability Report (QRR).

17.1 Types of Stress

Several different process technology groups have been identified based on similarity of process parameters. Representative product types for each of these groups are listed in the Cypress QRR. Failure rates are tabulated for defective sub-populations and competing failure mechanisms. Two common measures of failure rates are early life failure rate (EL) and inherent life failure rate (IL). The early life period corresponds to approximately the first 4,000 hours at field use conditions. The inherent life corresponds to the useful life beyond the first 4000 of field operation. For these calculations, device operation temperature is assumed to be 55°C ambient unless otherwise noted. Voltage acceleration factors are used in the analysis wherever noted.

17.2 Reliability Monitor Stress Conditions

Stress	Package Typical Duration		Target Sample Size	Typical Conditions
Early Life	All	24, 168 hours	350	125°C or 150°C, V _{CC} max
Inherent Life	All	1000 hours	120	125°C or 150°C, V _{CC} max
Endurance Cycling	All	10000 cycles	64	90°C
Data Retention Bake	All	1000 hours	64	150°C
Preconditioning (PC)	All	216 hours	231	30°C/70% RH Soak, 3X Reflow @ 260°C
PC + Temperature	Discrete, 2 die MCP	1000 cycles	77	–40°C to 150°C
Cycle	> 2 die MCP	1000 cycles	77	–55°C to 125°C
	BGA	264 hours	77	110°C, 85% RH, V _{CC} max alt. bias
FC + blased HAST	Lead Frame	96 hours	77	130°C, 85% RH, V_{CC} max alt. bias
PC + Unbiased HAST	All	96 hours	77	110°C, 85% RH, no bias



18. Statistical Process Management

Statistical Process Management is used extensively throughout manufacturing and engineering areas in Cypress to help in reducing process variation and optimizing product/process performance. Examples of the tools used are Statistical Process Control (SPC), Process Capability Studies, Design of Experiments, Measurement Systems Analysis, Systematic Problem Solving, Structured project management, and statistical yield analysis, etc.

Some highlights of our SPC program include:

- Ubiquitous and intelligent use of problem solving methodologies
- SPC is 100% automated in all manufacturing areas using both statistically and economically derived Control Limits
- Out of Control Trouble Shooting Guides
- Statistical Equipment Control, (monitoring and control of input variables)
- Advanced Process Control (model based, active run-to-run control of processes during wafer fabrication)
- Suppliers are encouraged to implement SPC
- Six-Sigma target for critical processes

18.1 Kaizen + Program

All the training of statistical analysis tools, as well as other hard and soft improvement skills such as FMEA, Lean, Error Proofing, Structured Teamwork, are provided to employees as a part of Cypress's Kaizen+ (continuous improvement) program. The program involves all functional groups by establishing a structure that consists of a Champion, internal/external certified Black, Brown, Green and Yellow Belts in each organization to drive for improvement projects. The results are shared in a Project Sharing Conference twice per year. Statistical thinking and use of statistical methods are a part of Cypress's Kaizen+ culture.



19. Document History

Document Document	Document Title: S29GL512S (XMC 85C 105C) Qualification Database Document Number: 002-00479								
Revision	ECN	Orig. of Change	Submission Date	Description of Change					
**	_	-	12/21/2011	Initial release.					
*A	-	-	01/27/2012	Characterization Test Results: Typical Program Time, ${\sf I}_{LI},~{\sf I}_{LO}$ and ${\sf I}_{CC2}$ values updated.					
*B	-	-	01/27/2015	CS239/L Life Test Failure Rate Calculation: Summary of Stress Test Results table: corrected 'Number of Fails' and 'Failure Rate %' for Endurance (10k) at 90°C.					
*C	6070150	CNSO	02/22/2018	Updated Assembly Packaging Summary: Updated LAE064: Updated details under "Theta Ja / Psi Jt" and "Assembly Location". Updated TS056: Updated details under "Theta Ja / Psi Jt" and "Assembly Location". Updated LAA064: Updated details under "Theta Ja / Psi Jt" and "Assembly Location". Updated details under "Theta Ja / Psi Jt" and "Assembly Location". Updated Test Methodology: Replaced "Class Test (Bangkok, Thailand; Kuala Lumpur, Malaysia)" with "Class Test (Bangkok, Thailand)". Updated to Cypress template.					
*D	6609547	CNSO	08/02/2019	Updated Document Title to read as "S29GL512S (XMC 85C 105C) Qualification Database". Added 105°C Temperature Range related information in all instances across the document. Updated to new template.					



20. Non-Disclosure Agreement

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Qualification Database

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Additionally, the package details (material set, assembly location, etc.) are specific to the qualification vehicle used. Alternate material sets and assembly locations may be qualified for the product. Production material can be assembled with any qualified material set and at any qualified assembly location.

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 Revised Tuesday, June 12, 2018



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1. Introduction

The Cypress[®] S29GL256S flash memory device has a die size of 4.589×5.104 mm.

2. Die Photograph

Figure 2.1 Die Photograph



Pad Number 1

Note:

1. X in the diagram is pad #1. Count counter clockwise.



Qualification Database

3. Pad Definition Table

Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA	Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA
1	VSS	33,52	H7	37	VCC	43	G5
2	VCC	43	G5	38	VSS	33,52	H7
3	A23	1	C8	39	VCC	43	G5
4	A22	2	B8	40	VSS	33, 52	H7
5	A15	3	D7	41	A0	31	E2
6	A14	4	C7	42	CE#	32	F2
7	A13	5	A7	43	OE#	34	G2
8	VSS	33, 52	H7	44	DQ0	35	E3
9	VCC	43	G5	45	DQ8	36	F3
10	A12	6	B7	46	DQ1	37	H3
11	A11	7	D6	47	DQ9	38	G3
12	A10	8	C6	48	VSS	33, 52	H2, E8
13	A9	9	A6	49	VIO	29	F1, D8
14	A8	10	B6	50	DQ2	39	E4
15	A19	11	D5	51	DQ10	40	F4
16	A20	12	D4	52	DQ3	41	H4
17	WE#	13	A5	53	DQ11	42	G4
18	NC			54	VCC	43	G5
19	RESET#	14	B5	55	VSS	33, 52	H7
20	A21	15	C5	56	DQ4	44	H5
21	WP#	16	B4	57	DQ12	45	F5
22	RY/BY#	17	A4	58	DQ5	46	E5
23	VIO	29	D8, F1	59	VSS	33, 52	H7
24	VSS	33, 52	H7	60	VCC	43	G5
25	A18	18	C4	61	DQ13	47	G6
26	A17	19	B3	62	NC		
27	A7	20	A3	63	VSS	33, 52	E8, H2
28	A6	21	C3	64	VIO	29	D8, F1
29	A5	22	D3	65	DQ6	48	H6
30	A4	23	B2	66	DQ14	49	F6
31	A3	24	A2	67	DQ7	50	E6
32	A2	25	C2	68	DQ15	51	G7
33	A1	26	D2	69	VCC	43	G5
34	DNU	28	E1	70	VSS	33, 52	H7
35	VCC	43	G5	71	A16	54	E7
36	VSS	33, 52	H7				



4. Physical Sector Layout

Internal Use Row (33)	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use
Internal Use Row (32)					Internal Use	Internal Use	Internal Use	Internal Use
Row 31	248	249	250	251	252	253	254	255
Row 30	240	241	242	243	244	245	246	247
Row 3	24	25	26	27	28	29	30	31
Row 2	16	17	18	19	20	21	22	23
Row 1	8	9	10	11	12	13	14	15
Row 0	0	1	2	3	4	5	6	7
VerticalBank	0	1	2	3	0	1	2	3
Bank		()			1		

Figure 4.1 Physical Sector Layout



Qualification Database

5. Sector Enlargement

Figure 5.1 Sector Enlargement

	Internal Use	0	1	2	3	4	5	6	7	8	9	10
M3BL	0-7	0-63	64-127	128-191	192-255	256-319	320-383	384-447	448-511	512-575	576-639	640-703
M1BL	8-15	0-127	128-255	256-383	384-511	512-639	640-767	768-895	896-1023	1024-1151	1152-1279	1280-1407

	11	12	13	14	15	Internal Use	Internal Use	Internal Use	Internal Use
M3BL	704-767	768-831	832-895	896-959	960-1023	1024-1063	1064-1071	1072-1079	0-7
M1BL	1408-1535	1536-1663	1664-1791	1792-1919	1920-2047	2048-2127	2128-2143	2144-2159	0-7



6. Die Processing Summary

The Cypress S29GL256S flash memory device is manufactured using the 65 nm MirrorBit[®] Eclipse[™] process technology.

The device is processed at WXIC, a 12-inch CMOS manufacturing facility located in Wuhan, China.

The device is manufactured on the highly reliable CS239LS process.





PERIPHERY

Qualification Database

6.1 Key Features of the 65 nm MirrorBit Eclipse Process Technology

A. Technology

- CMOS Triple-well process
- Proven reliable Flash MirrorBit Eclipse Technology

B. Transistor Types

- n-channel enhancement
- n-channel intrinsic
- p-channel enhancement
- MirrorBit Eclipse core cell

C. Process Features

- ONO (oxide nitride oxide) gate dielectric
- Silicon Nitride (SiN) data storage layer

D. Cypress Highlights

- Volume Production Fab
- Solely dedicated to Non-Volatile Memories
- Ongoing Statistical Process Control program



7. Assembly Packaging Summary

7.1 LAE064

Product Description:	S29GL256S				
· · · · · · · · · · · · · · · · · · ·	256-Mb, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse Process Technology				
Package:	LAE064 Qualification:		Q100199		
Description:	(9 x 9 x 1.4 mm) 64-ball, Fortifie				
Theta Ja:	33°C/W	Psi Jt:	0.07°C/W		
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin		
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste		
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres	Bond Wire:	Copper		
Comments:					
Est. Field Temperature:	55°C	Life Test Temperature:	125°C		
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA		
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V		
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts		
Est. Field Delta Tj:	57.9°C	Est. Stress Delta Tj:	126.4°C		
Die:	98223B	Die Size:	4.58 x 5.10 mm		
Process:	CS239LS (65 nm)	Fab:	WXIC		
Туре:	MirrorBit Eclipse	Density:	256M		

7.2 LAA064

Product Description:	S29GL256S 256-Mb_3.0 Volt-Only Page Mode Elash Memory featuring 65 nm MirrorBit Eclinse Process Technology			
Package:	LAA064 Qualification:		Q100227	
Description:	(13.0 x 11.0 x 1.4 mm) 64-ball, F	BGA)		
Theta Ja:	24.1°C/W Psi Jt		0.07°C/W	
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin	
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste	
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres Bond Wire:		Copper	
Comments:				
Est. Field Temperature:	55°C	Life Test Temperature:	125°C	
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA	
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V	
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts	
Est. Field Delta Tj:	57.9°C	Est. Stress Delta Tj:	126.4°C	
Die:	98223B	Die Size:	4.58 x 5.10 mm	
Process:	CS239LS (65 nm)	Fab:	WXIC	
Туре:	MirrorBit Eclipse	Density:	256M	



Qualification Database

7.3 TS056

Product Description:	S29GL256S				
r router bescription.	256-Mb, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse Process Technology				
Package:	TS056 Qualification:		Q100239		
Description:	(18.4 x 14.0 x 1.0 mm) 56-lead, Thin Small Outline Package (TSOP)				
Theta Ja:	46°C/W	Psi Jt:	0.21°C/W		
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin		
Substrate/Leadframe:	Copper Leadframe	Die Attachment:	Paste		
Lead Finish:	100% Matte Sn Plating	Bond Wire:	Copper		
Comments:					
Est. Field Temperature:	55°C	Life Test Temperature:	125°C		
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA		
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V		
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts		
Est. Field Delta Tj:	58.0°C	Est. Stress Delta Tj:	126.4°C		
Die:	98223B	Die Size:	4.58 x 5.10 mm		
Process:	CS239LS (65 nm)	Fab:	WXIC		
Туре:	MirrorBit Eclipse	Density:	256M		

7.4 VBU056

Product Description:	S29GL256S 256-Mb, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse Process Technology				
Package:	VBU056 Qualification:		Q100373		
Description:	(9.0 x 7.0 x 1.0 mm) 56-ball, Ver	y Thin Fine Pitch Ball Grid Array Pa	ine Pitch Ball Grid Array Package (FBGA)		
Theta Ja:	34.5°C/W		0.10°C/W		
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin		
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste		
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres	Bond Wire:	Copper		
Comments:					
Est. Field Temperature:	55°C	Life Test Temperature:	125°C		
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA		
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V		
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts		
Est. Field Delta Tj:	57.9°C	Est. Stress Delta Tj:	126.4°C		
Die:	98223B	Die Size:	4.58 x 5.10 mm		
Process:	CS239LS (65 nm)	Fab:	WXIC		
Туре:	MirrorBit Eclipse	Density:	256M		



8. Assembly Bonding Diagram

8.1 TS056 Package

VCC VCC VCC VSS VSS VCC Vio Vio ľ 56 55 54 I Щ Ш Ĩ I Ĩ 1 2 3 4 5 6 7 8 9 10 ГŤ Г Π 53 52 51 50 49 48 П 47 11 12 13 L . 46 ₫**Г** 45 語が 44 1995 2 5821 2 1993 1993 14 15 43 42 and 2 1 Vill street Ē 16 41 жų. 17 18 19 40 100 ſ 39 38 20 21 22 П 37 T 36 Ī 35 Œ 23 34 Г 24 25 26 27 28 33 32 31 Π 30 29 ħ Vio Vio

Figure 8.1 56-Pin — TS056 Package

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Qualification Database

8.2 LAE064 Package

Figure 8.2 64-Ball — LAE064 Package





CONFIDENTIAL Qualification Database

8.3 LAA064 Package







8.4 VBU056 Package

Figure 8.4 56-Ball — VBU056 Package







9. Test Methodology

Testing includes

- 4 hour, 250°C Data Retention Bake (in wafer form)
- Special test mode for extended life operation
- Proprietary screens for endurance

Wafer Sort (Austin, Texas, USA)

At Wafer Sort, all die experience 100% testing for:

- DC Parametrics
- AC Functionality
- Programmability
- Erasability

Class Test (Bangkok, Thailand)

At Class Test, all devices are tested for:

- DC Parametrics
- AC Functionality
- AC Speed
- Programmability
- Erasability

Test Coverage

All parameters specified in the data sheet are 100% tested in production unless otherwise specified. Those parameters not tested in production are guaranteed by characterization or correlation to other tests. AC speed testing is performed at class test.

Test Correlation and Guard Banding

Tester correlation to bench set-up has been completed for all tested parameters. Tester repeatability studies have been run. These results have been evaluated and incorporated into the tester guard band strategy. Guard bands have been implemented which demonstrate acceptable yield, quality assurance and customer satisfaction.

Test Flow

See the generalized Test Flow for the S29GL256S in Section 10.



10. Generalized Test Flow

The S29GL256S Generalized Test Flow for Industrial Temperature Range:




11. Quality and Reliability Data

11.1 S29GL256S High Temperature Operating Life Test Configuration

Pin/Pad #	Function	Resistor	Bias/CLK
1	A23	2.7K	CLK23
2	A22	2.7K	CLK22
3	A15	2.7K	CLK15
4	A14	2.7K	CLK14
5	A13	10K	CLK13
6	A12	2.7K	CLK12
7	A11	2.7K	CLK11
8	A10	2.7K	CLK10
9	A9	2.7K	CLK9
10	A8	2.7K	CLK8
11	A19	2.7K	CLK19
12	A20	2.7K	CLK20
13	WE#	2.7K	VCC
14	RESET#	2.7K	VCC
15	A21	2.7K	CLK21
16	WP#	2.7K	VCC
17	RY/BY#	2.7K	VCC
18	A18	2.7K	CLK18
19	A17	2.7K	CLK17
20	A7	2.7K	CLK7
21	A6	2.7K	CLK6
22	A5	2.7K	CLK5
23	A4	2.7K	CLK4
24	A3	2.7K	CLK3
25	A2	2.7K	CLK2
26	A1	2.7K	CLK1
27	RFU		NC
28	RFU		NC

Pin/Pad #	Function	Resistor	Bias/CLK
56	NC		
55	NC		
54	A16	2.7K	CLK16
53	RFU		NC
52	VSS		GND
51	DQ15	2.7K	VCC
50	DQ7	2.7K	VCC
49	DQ14	2.7K	VCC
48	DQ6	2.7K	VCC
47	DQ13	2.7K	VCC
46	DQ5	2.7K	VCC
45	DQ12	2.7K	VCC
44	DQ4	2.7K	VCC
43	VCC		VCC
42	DQ11	2.7K	VCC
41	DQ3	2.7K	VCC
40	DQ10	2.7K	VCC
39	DQ2	2.7K	VCC
38	DQ9	2.7K	VCC
37	DQ1	2.7K	VCC
36	DQ8	2.7K	VCC
35	DQ0	2.7K	VCC
34	OE#	2.7K	VCC
33	VSS		GND
32	CE#	2.7K	GND
31	A0	2.7K	CLK0
30	RFU		NC
29	VIO	2.7K	VCC



11.2 CS239/L Life Test Failure Rate Calculation

HTOL Stress Temperature @ 125°C

	Re	Read Points / Test Results			Modeling Parameters @ 55°C				Average Failure Rate FITS @ 55°C, 60% Conf.	
Failure Mechanisms	24 hrs	168 hrs	1000 hrs	Ea eV	TAF	VAF	OAF	MTTF (yrs)	Early Life	Inherent Life
PLASTIC										
Sample Size	4950	4615	842							
Zero fails, Process ave. Ea	0	0 (1)	0	0.66	53	1	53		48	11
Totals	0	0	0					10378	48	11

Note:

1. Contributes to Early Life FITS.

Data Retention Bake @ 150°C

Reliability Stress	Number of Rejects	Sample Size	Failure Rate %	Failure Mechanism
500 hrs	0	1735	0.00	No Failures
1000 hrs	0	1208	0.00	No Failures



CONFIDENTIAL Qualification Database

Table 11.1 Summary of Stress Test Results

Stress Test	Condition	Package Type	Samples Size	Num. of Lots	Number of Fails	Failure Rate %	Comments	
	Data From Quali	fication Q100227, Q	100239, Q1	00199:				
HTOL (EL)	3.6V, 125°C	LAE064 (3)	154	2	0	0.00	168 hrs	
HTOL (IL)	3.6V, 125°C	LAE064 (3)	154	2	0	0.00	504 hrs	
	N/A	LAA064 (1)	15	1		Passed 1.0 kV		
ESD CDM	N/A	TS056 (2)	15	1		Passed 1.0	kV	
	N/A	LAE064 (3)	15			Passed 1.0	kV	
ESD HBM	(100 pF, 1500 Ohms)	LAE064 (3)	84	1		Passed 2.0	kV	
Latch Up	±100 mA	LAE064 (3)	10	1		Passed		
	105°C, 3.6V	LAE064 (3)	64	1	0	0.00	10k cycles	
Endurance (10k)	–40°C, 3.6V	LAE064 (3)	64	1	0	0.00	10k cycles	
	90°C, 3.6V	LAE064 (3)	64	1	0	0.00	10k cycles	
	G	eneric Reference Da	ata					
ESD CDM	N/A	VBU056 (4)	15	1		Passed 1.0	kV	
	PC9/260°C, +0°C / -5°C	VBU056 (4)	77	1	Passed .	Passed Jedec L3 / Jeita Rank E		
Preconditioning	PC1/260°C, +0°C / _5°C	LAE064 (5)	231	1	Passed	Jedec L3 / J	leita Rank E	
	PC9/260°C, +0°C / -5°C	TS056 (6)	164	1	Passed	Jedec L3 / J	leita Rank E	
	PC9/260°C, -40°C / 150°C	VBU056 (4)	77	1	0	0.00	1000 cycles	
Preconditioning + Temp Cvcle	PC1/260°C, -40°C / 150°C	LAE064 (5)	77	1	0	0.00	1000 cycles	
	PC9/260°C, -40°C / 150°C	TS056 (6)	87	1	0	0.00	500 cycles	
Preconditioning + HAST	PC1/260°C, Biased, 110°C / 85% RH	LAE064 (5)	77	1	0	0.00	264 hrs	
Freconditioning + HAST	PC9/260°C, Biased, 130°C / 85% RH	TS056 (6)	TS056 (6) 77 1 0		0.00	96 hrs		
Preconditioning + uHAST	PC1/260°C, Unbiased, 130°C / 85% RH	LAE064 (5)	76	1	0	0.00	96 hrs	

Notes:

1. Results from Qual Q100227, S29GL256S, 256M CS239LS (65 nm) MirrorBit Eclipse in 64-Ball fFBGA (13 x 11 x 1.4 mm).

2. Results from Qual Q100239, S29GL256S, 256M CS239LS (65 nm) MirrorBit Eclipse in 56-Lead TSOP (18.4 x 14 x 1 mm).

3. Results from Qual Q100199, S29GL256S, 256M CS239LS (65 nm) MirrorBit Eclipse in 64-Ball fFBGA (9 x 9 x 1.4 mm).

4. Results from Qual Q100333, S29GL512S in 56-Ball vFBGA (9 x 7 x 1 mm) - Same VBU056 Package and Technology.

 Results from Qual Q100167, S29GL01GS in 64-Ball fFBGA (9 x 9 x 1.4 mm) - Same LAE064 Package (Similar to LAA064), Technology and Fab location (WXIC).

6. Results from Qual Q100013, S29GL256S in 56-Lead TSOP (18.4 x 14 x 1 mm) - Same TSOP package and Technology, Same die from a different fab.

Preconditioning Flows

PC1 (Exceeds JEDEC L3 and JEITA Rank E): Bake 125°C, 24hr --> Soak @ 30°C/70%RH, 216hr => 3x Reflow. PC9 (Accelerated JEDEC L3 / JEITA Rank E): Bake 125°C, 24hr --> Soak @ 60°C/70%RH, 72hr => 3x Reflow.



12. Characterization Test Results

The data is pattern is "Random pattern" unless otherwise indicated.

12.1 DC Parameter Summary, 105°C

Hot Temperature, 105°C, 3V, V_{CC} Summary

Data Shaat Baramatara		Spec		Average	Min	Мах	Sigmo	Cink
Data Sheet Parameters	Тур	Мах	Unit	Average	WIIN	wax	Sigma	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	93.74	89.65	97.56	1.28	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	49.20	47.00	51.01	0.67	>5
I_{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	15.13	14.53	15.70	0.22	
I _{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	16.45	15.98	16.91	0.21	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	18.13	17.70	18.53	0.19	
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	19.19	17.00	20.33	0.82	>5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	50.97	45.72	55.07	1.83	>5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	42.26	37.12	46.95	1.78	>5
I _{CC4} (V _{CC} Standby Current)	70	200	μA	64.72	50.35	102.89	9.56	1.2
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.06	0.05	0.10	0.01	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	64.35	49.51	100.66	9.55	>5
I _{LI} (Input Leakage Current)	0.02	±1	μΑ	-0.010	-0.010	0.220	0.030	>5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	-0.020	-0.020	0.010	0.000	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64-kword sector)	275	1100	ms	187.54	115.00	323.00	12.45	>5
Buffer Program Time (256 word)	420	1050	μs	329.39	271.00	410.00	19.80	>5
Buffer Program Time (128 word)	320	1050	μs	257.11	220.00	291.00	13.87	>5
Buffer Program Time (64 word)	250	1050	μs	218.31	189.00	246.00	11.57	>5
Buffer Program Time (32 word)	220	1050	μs	194.13	169.00	218.00	10.15	>5
Buffer Program Time (16 word)	200	1050	μs	173.97	154.00	200.00	7.81	>5
Single Word Program Time (1 word)	125	400	μs	321.41	167.00	405.00	20.03	1.3

Notes:

1. Data were collected from 300 units (LD10133, #23), lot no. 5824180 LAA064.



12.2 DC Parameter Summary, 85°C

Hot Temperature, 85°C, 3V, V_{CC} Summary

Data Shoot Parameters		Spec		Average	Min	Max	Sigma	Cpk
Data Sheet Parameters	Тур	Max	Unit	Average	IVIIII	IVIAX	Sigina	
		DC Pa	arameters					
I_{CC1} (V _{CC} Active Read Current) 10 MHz			mA	92.24	87.96	95.94	1.30	
I_{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	48.37	46.16	50.28	0.68	>5
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	14.71	14.14	15.16	0.23	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	16.00	15.55	16.37	0.18	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	17.66	17.21	18.32	0.16	
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	18.60	16.57	20.23	0.83	>5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	51.23	48.48	54.29	0.83	>5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	41.83	37.68	46.63	1.89	>5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	39.94	30.00	74.59	8.84	2.3
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.04	0.03	0.07	0.01	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μΑ	39.71	30.10	74.22	8.92	>5
I _{LI} (Input Leakage Current)	0.02	±1	μΑ	-0.010	-0.010	0.220	0.030	>5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	-0.010	-0.010	0.010	0.000	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64-kword sector)	275	1100	ms	197.40	134.00	302.00	15.45	>5
Buffer Program Time (256 word)	340	750	μs	343.14	297.00	414.00	23.33	>5
Buffer Program Time (128 word)	239	750	μs	272.21	241.00	326.00	18.33	>5
Buffer Program Time (64 word)	198	750	μs	230.01	205.00	270.00	14.67	>5
Buffer Program Time (32 word)	175	750	μs	204.37	182.00	240.00	12.57	>5
Buffer Program Time (16 word)	160	750	μs	180.53	161.00	207.00	10.17	>5
Single Word Program Time (1 word)	125	400	μs	334.05	180.00	409.00	23.54	0.9

Notes:

1. Data were collected from 300 units (LD10133, #23), lot no. 5824180 LAA064.



12.3 DC Parameter Summary, 25°C

Room Temperature, 25°C, 3V, V_{CC} Summary

Data Shoot Paramotoro		Spec		Average	Min	Max	Sigma	Cpk
Data Sheet Parameters	Тур	Max	Unit	Average	IAIILI	IVIAX	Sigina	
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	88.66	84.26	92.43	1.38	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	46.41	44.16	48.26	0.70	>5
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	14.22	13.75	14.77	0.20	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	15.54	14.77	15.94	0.19	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	17.12	16.77	17.50	0.15	
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	17.94	15.94	19.11	0.64	>5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	48.06	44.54	50.47	1.07	>5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	40.16	35.86	44.19	2.03	>5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	16.06	9.11	46.29	7.62	3.7
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.02	0.01	0.05	0.01	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μΑ	16.20	9.04	54.64	7.67	>5
I _{LI} (Input Leakage Current)	0.02	±1	μA	-0.010	-0.010	0.290	0.030	>5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	-0.010	-0.010	0.010	0.000	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64-kword sector)	275	1100	ms	261.11	176.00	411.00	22.91	>5
Buffer Program Time (256 word)	340	750	μs	393.35	345.00	467.00	16.19	>5
Buffer Program Time (128 word)	239	750	μs	305.97	272.00	354.00	13.57	>5
Buffer Program Time (64 word)	198	750	μs	256.35	228.00	290.00	11.04	>5
Buffer Program Time (32 word)	175	750	μs	226.15	203.00	254.00	9.49	>5
Buffer Program Time (16 word)	160	750	μs	198.89	180.00	222.00	7.74	>5
Single Word Program Time (1 word)	125	400	μs	381.81	70.00	448.00	19.53	0.3

Notes:

1. Data were collected from 300 units (LD10133, #23), lot no. 5824180 LAA064.



12.4 DC Parameter Summary, –40°C

Cold Temperature, –40°C, 3V, $V_{CC}\,Summary$

Data Shoot Paramotors		Spec		Average	Min	Max	Sigma	Cpk
Data Sheet Parameters	Тур	Мах	Unit	Average	IAILL	IVIAX	Sigina	
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	86.85	81.15	92.90	1.92	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	45.76	43.04	51.24	0.93	>5
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	13.89	13.41	14.43	0.20	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	15.10	14.58	15.50	0.18	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	16.67	16.14	17.01	0.17	
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	17.27	15.30	18.53	0.77	>5
I _{CC3} (V _{CC} Active Erase Current)	45	100	mA	43.11	39.88	46.03	1.01	>5
I _{CC3} (V _{CC} Active Program Current)	45	100	mA	35.87	32.09	40.50	1.83	>5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	13.73	7.96	42.98	6.59	4.4
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.01	0.01	0.04	0.01	>5
I_{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μΑ	13.85	7.96	50.95	6.74	>5
I _{LI} (Input Leakage Current)	0.02	±1	μA	-0.010	-0.010	0.270	0.040	>5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	-0.010	-0.010	0.010	0.000	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64-kword sector)	275	1100	ms	353.77	219.00	605.00	42.59	>5
Buffer Program Time (256 word)	340	750	μs	390.67	319.00	471.00	23.80	5.0
Buffer Program Time (128 word)	239	750	μs	303.91	250.00	353.00	18.25	>5
Buffer Program Time (64 word)	198	750	μs	253.69	208.00	295.00	14.70	>5
Buffer Program Time (32 word)	175	750	μs	224.48	185.00	258.00	12.51	>5
Buffer Program Time (16 word)	160	750	μs	201.72	166.00	236.00	10.74	>5
Single Word Program Time (1 word)	125	400	μs	390.44	196.00	476.00	26.37	0.1

Notes:

1. Data were collected from 300 units (LD10133, #23), lot no. 5824180 LAA064.

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Qualification Database

13. DC Device Characterization Data

ICC1 (Asynchronous Read) vs. Temperature







ICC3 (Active Write) vs. Temperature





ICC4 (Standby Current) vs. Temperature













14. AC Device Characterization Data

tACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tCE vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tOE vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)





tPACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tDF vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)







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Qualification Database



Cumulative Erase Times per Sector at 105°C (VCC 3V)

Cumulative Erase Times per Sector at 85°C (VCC 3V)



Cumulative Erase Times per Sector at 25°C (VCC 3V)

Cumulative Erase Times per Sector at -40°C (VCC 3V)





Cumulative WB Program Times per Sector at 105°C (VCC 3V)

Cumulative WB Program Times per Sector at 85°C (VCC 3V)









Cumulative WB 256 Program Times per Buffer at 105°C (VCC 3V)

Cumulative WB 256 Program Times per Buffer at 85°C (VCC 3V)





Cumulative WB 256 Program Times per Buffer at 25°C (VCC 3V)

Cumulative WB 256 Program Times per Buffer at -40°C (VCC 3V)





Cumulative WB 128 Program Times per Buffer at 105°C (VCC 3V) Cumulative WB 128 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 128 Program Times per Buffer at 25°C (VCC 3V) Cumulative WB 128 Program Times per Buffer at -40°C (VCC 3V)



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Qualification Database

Cumulative WB 64 Program Times per Buffer at 105°C (VCC 3V) Cumulative WB 64 Program Times per Buffer at 85°C (VCC 3V)







Cumulative WB 32 Program Times per Buffer at 105°C (VCC 3V) Cumulative WB 32 Program Times per Buffer at 85°C (VCC 3V)









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Qualification Database

Cumulative WB 16 Program Times per Buffer at 105°C (VCC 3V) Cumulative WB 16 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 16 Program Times per Buffer at 25°C (VCC 3V) C

Cumulative WB 16 Program Times per Buffer at -40°C (VCC 3V)





Cumulative Single Word Program Times per Buffer at 105°C (VCC 3V) Cumulative Single Word Program Times per Buffer at 85°C (VCC 3V)





Cumulative Single Word Program Times per Buffer at 25°C (VCC 3V) Cumulative Single Word Program Times per Buffer at -40°C (VCC 3V)







15. Shmoo Plots

t_{ACC} vs. V_{CC}=V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	-+,	-+,	+		
3.650	****	* * * * * * * * * *	*******	***	85.0	
3.600	****	* * * * * * * * * *	*******	***	85.0	
3.550	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.500	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.450	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.400	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.350	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.300	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.250	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.200	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.150	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.100	****	* * * * * * * * * *	*******	***	85.0	
3.050	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
3.000	****	* * * * * * * * * *	* * * * * * * * *	***	85.0	
2.950	****	* * * * * * * * * *	******	***	85.0	
2.900	****	* * * * * * * * * *	******	***	85.0	
2.850	****	* * * * * * * * * *	*******	***	85.0	
2.800	***	* * * * * * * * * *	*******	***	86.0	
2.750	***	* * * * * * * * * *	*******	***	86.0	
2.700	* * *	* * * * * * * * * *	*******	***	86.0	
2.650	***	* * * * * * * * * *	*******	***	86.0	
	İ+,	-+,	-+,	+		
	80.0	90.0	100.0	110.0		

t_{ACC} vs. V_{CC}=V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650	*****	* * * * * * * * * *	******	**	84.0
3.600	*****	* * * * * * * * * *	******	**	84.0
3.550	****	* * * * * * * * * *	******	**	84.0
3.500	****	* * * * * * * * * *	******	**	84.0
3.450	*****	* * * * * * * * * *	******	**	84.0
3.400	****	* * * * * * * * * *	******	**	84.0
3.350	****	* * * * * * * * * *	******	**	84.0
3.300	*****	* * * * * * * * * *	******	**	84.0
3.250	****	* * * * * * * * * *	******	**	84.0
3.200	****	* * * * * * * * * *	******	**	84.0
3.150	*****	* * * * * * * * * *	******	**	84.0
3.100	****	* * * * * * * * * *	******	**	84.0
3.050	****	* * * * * * * * * *	******	**	84.0
3.000	*****	* * * * * * * * * *	******	**	84.0
2.950	****	* * * * * * * * * *	******	**	84.0
2.900	*****	* * * * * * * * * *	******	**	84.0
2.850	****	* * * * * * * * * *	******	**	84.0
2.800	****	* * * * * * * * * *	******	**	84.0
2.750	*****	* * * * * * * * * *	******	**	84.0
2.700	****	* * * * * * * * * *	******	**	85.0
2.650	****	* * * * * * * * * *	******	**	85.0
	+,	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{CC} = V_{IO} @ 25°C

1 3.650 ********************************		80.0	90.0	100.0	110.0	first pass data
3.650 ********************************		+,	+,	+,	+	
3.600 ********************************	3.650	****	*******	* * * * * * * * * *	* * *	84.0
3.550 ********************************	3.600	*****	*******	******	***	84.0
3.500 ********************************	3.550	*****	*******	*******	* * *	84.0
3.450 *********************************	3.500	*****	*******	******	* * *	84.0
3.400 *********************************	3.450	*****	*******	******	***	84.0
3.350 *********************************	3.400	*****	*******	*******	* * *	84.0
3.300 *********************************	3.350	*****	*******	******	* * *	84.0
3.250 *********************************	3.300	*****	*******	******	***	84.0
3.200 *********************************	3.250	*****	*******	******	* * *	84.0
3.150 *********************************	3.200	****	*******	* * * * * * * * * *	* * *	84.0
3.100 *********************************	3.150	*****	*******	******	* * *	84.0
3.050 *********************************	3.100	* * * * *	*******	* * * * * * * * * *	* * *	84.0
3.000 *********************************	3.050	****	*******	* * * * * * * * * *	* * *	84.0
2.950 *********************************	3.000	*****	*******	******	* * *	84.0
2.900 *********************************	2.950	****	*******	* * * * * * * * * *	***	84.0
2.850 *********************************	2.900	****	* * * * * * * * * * *	* * * * * * * * * *	***	84.0
2.800 *********************************	2.850	****	*******	******	***	84.0
2.750 *********************************	2.800	****	*******	* * * * * * * * * *	***	84.0
2.700 ********************************	2.750	****	* * * * * * * * * * *	* * * * * * * * * *	***	84.0
2.650	2.700	****	*******	******	***	84.0
+,+,+	2.650	****	*******	* * * * * * * * * *	***	84.0
		+,	+,	+,	+	
80.0 90.0 100.0 110.0		80.0	90.0	100.0	110.0	

t_{ACC} vs. V_{CC}=V_{IO} @ -40°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650	***	********	*******	**	86.0
3.600	***	* * * * * * * * * *	*******	**	86.0
3.550	***	* * * * * * * * * *	*******	**	86.0
3.500	***	* * * * * * * * * *	*******	**	86.0
3.450	***	********	*******	**	86.0
3.400	***	* * * * * * * * * *	*******	**	86.0
3.350	***	* * * * * * * * * *	*******	**	86.0
3.300	***	********	*******	**	86.0
3.250	***	* * * * * * * * * *	******	**	86.0
3.200	***	* * * * * * * * * *	*******	**	86.0
3.150	***	* * * * * * * * * *	*******	**	86.0
3.100	***	* * * * * * * * * *	*******	**	86.0
3.050	***	* * * * * * * * * *	*******	**	86.0
3.000	***	* * * * * * * * * *	*******	**	86.0
2.950	***	* * * * * * * * * *	*******	**	86.0
2.900	***	* * * * * * * * * *	*******	**	86.0
2.850	***	* * * * * * * * * *	*******	**	86.0
2.800	* * *	********	*******	**	86.0
2.750	* * *	* * * * * * * * * *	*******	**	86.0
2.700	İ**	* * * * * * * * * *	*******	**	87.0
2.650	**	*******	*******	**	87.0
	+	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	+,	+,	+		
3.000	**	* * * * * * * * * *	********	****	86.0	
2.950	* * :	* * * * * * * * * *	********	****	86.0	
2.900	* * :	* * * * * * * * * *	* * * * * * * * * *	* * * *	86.0	
2.850	**	* * * * * * * * * *	* * * * * * * * * *	* * * *	86.0	
2.800	**	* * * * * * * * * *	* * * * * * * * * *	****	86.0	
2.750	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.700	**	* * * * * * * * * *	* * * * * * * * * *	* * * *	86.0	
2.650	**	* * * * * * * * * *	* * * * * * * * * *	****	86.0	
2.600	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.550	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.500	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.450	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.400	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.350	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.300	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.250	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.200	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.150	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.100	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
2.050	**	* * * * * * * * * *	* * * * * * * * * *	****	86.0	
2.000	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
1.950	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
1.900	*	******	* * * * * * * * * *	***	87.0	
1.850	*·	* * * * * * * * * *	* * * * * * * * * *	****	87.0	
1.800	*·	* * * * * * * * * *	* * * * * * * * * *	****	87.0	
1.750	*	******	* * * * * * * * * *	***	87.0	
1.700	*·	* * * * * * * * * *	* * * * * * * * * *	****	87.0	
1.650	*	* * * * * * * * * *	* * * * * * * * * *	***	87.0	
	+,	+,	+,	· +		
	80.0	90.0	100.0	110.0		



	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	+,	+	
3.000	****	********	* * * * * * * * * * *	* * *	85.0
2.950	****	*******	* * * * * * * * * *	* * *	85.0
2.900	****	********	* * * * * * * * * * *	* * *	85.0
2.850	* * * *	********	* * * * * * * * * * *	* * *	85.0
2.800	* * * *	*******	* * * * * * * * * *	* * *	85.0
2.750	****	********	* * * * * * * * * * *	* * *	85.0
2.700	* * * *	********	*******	* * *	85.0
2.650	****	*******	* * * * * * * * * *	* * *	85.0
2.600	****	*******	*******	* * *	85.0
2.550	* * * *	********	*******	* * *	85.0
2.500	****	*******	* * * * * * * * * *	* * *	85.0
2.450	****	*******	*******	* * *	85.0
2.400	****	********	******	* * *	85.0
2.350	****	********	* * * * * * * * * * *	* * *	85.0
2.300	****	*******	*******	* * *	85.0
2.250	****	********	*******	* * *	85.0
2.200	****	********	* * * * * * * * * * *	* * *	85.0
2.150	***	*******	*******	* * *	86.0
2.100	***	********	*******	* * *	86.0
2.050	* * *	********	* * * * * * * * * * *	* * *	86.0
2.000	***	*******	*******	* * *	86.0
1.950	***	********	*******	* * *	86.0
1.900	***	* * * * * * * * * * *	* * * * * * * * * * *	* * *	86.0
1.850	***	*******	* * * * * * * * * * *	* * *	86.0
1.800	***	*******	*******	* * *	86.0
1.750	***	* * * * * * * * * * *	* * * * * * * * * * *	* * *	86.0
1.700	***	*******	* * * * * * * * * * *	* * *	86.0
1.650	**	*******	*******	* * *	87.0
	+,	-+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} @ 25°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	+,	+,	+		
3.000	****	******	* * * * * * * * * * *	* * *	84.0	
2.950	***	******	* * * * * * * * * * *	***	85.0	
2.900	***	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.850	***	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.800	***	* * * * * * * * * *	* * * * * * * * * * *	***	85.0	
2.750	***	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.700	***	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.650	***	* * * * * * * * * *	* * * * * * * * * * *	***	85.0	
2.600	***	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.550	***	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.500	***	*******	* * * * * * * * * * *	* * *	85.0	
2.450	* * * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.400	* * * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.350	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.300	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.250	* * * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.200	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.150	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.100	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.050	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
2.000	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * *	85.0	
1.950	**	* * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
1.900	**	*******	* * * * * * * * * * *	* * *	86.0	
1.850	**	*******	* * * * * * * * * * *	* * *	86.0	
1.800	**	*******	* * * * * * * * * * *	* * *	86.0	
1.750	**	*******	* * * * * * * * * * *	***	86.0	
1.700	**	*******	* * * * * * * * * * *	* * *	86.0	
1.650	*	*******	* * * * * * * * * * *	* * *	87.0	
	+,	+,	+,	+		
	80.0	90.0	100.0	110.0		



	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.000	*	*******	*******	* * *	87.0
2.950	1*	* * * * * * * * * *	********	* * *	87.0
2.900	*	* * * * * * * * * *	*******	* * *	87.0
2.850	*	******	*******	* * *	87.0
2.800		* * * * * * * * * *	*******	* * *	87.0
2.750	*	* * * * * * * * * *	*******	* * *	87.0
2.700	*	* * * * * * * * * *	*******	* * *	87.0
2.650	1	******	* * * * * * * * * *	* * *	88.0
2.600		* * * * * * * * * *	*******	* * *	88.0
2.550		* * * * * * * * * *	*******	* * *	88.0
2.500		* * * * * * * * * *	*******	* * *	88.0
2.450		* * * * * * * * * *	*******	* * *	88.0
2.400		* * * * * * * * * *	*******	* * *	88.0
2.350		* * * * * * * * * *	*******	* * *	88.0
2.300		* * * * * * * * * *	*******	* * *	88.0
2.250		* * * * * * * * * *	*******	* * *	88.0
2.200		* * * * * * * * * *	*******	* * *	88.0
2.150		* * * * * * * * * *	*******	* * *	88.0
2.100		* * * * * * * * * *	*******	* * *	88.0
2.050		* * * * * * * * * *	*******	* * *	88.0
2.000		* * * * * * * * * *	*******	* * *	88.0
1.950		*******	*******	* * *	88.0
1.900		* * * * * * * * * * *	********	* * *	88.0
1.850		. * * * * * * * * * *	********	* * *	89.0
1.800		. * * * * * * * * * *	********	* * *	89.0
1.750	1	********	* * * * * * * * * *	* * *	89.0
1.700		. * * * * * * * * * *	*******	* * *	89.0
1.650		* * * * * * * * *	********	* * *	90.0
	+,	+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. $V_{CC}\text{=}V_{IO} \textcircled{@} 105^\circ\text{C}$

	80.0	90.0	100.0	110.0	first pass	data
	+,	· + , - ·	+,	+		
3.650	**	*******	* * * * * * * * * * *	***	86.0	
3.600	**	*******	* * * * * * * * * * *	***	86.0	
3.550	**	* * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
3.500	**	* * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
3.450	1**	*******	* * * * * * * * * * *	***	86.0	
3.400	**	*******	* * * * * * * * * * *	***	86.0	
3.350	**	* * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
3.300	1**	*******	* * * * * * * * * * *	***	86.0	
3.250	**	*******	* * * * * * * * * * *	***	86.0	
3.200	**	* * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
3.150	**	*******	* * * * * * * * * * *	***	86.0	
3.100	**	* * * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
3.050	**	* * * * * * * * * * *	* * * * * * * * * * *	* * *	86.0	
3.000	**	*******	* * * * * * * * * * *	***	86.0	
2.950	**	*******	* * * * * * * * * * *	***	86.0	
2.900	**	*******	* * * * * * * * * * *	***	86.0	
2.850	* *	*******	* * * * * * * * * * *	***	86.0	
2.800	*	*******	* * * * * * * * * * *	***	87.0	
2.750	*	*******	* * * * * * * * * * *	***	87.0	
2.700	1	*******	* * * * * * * * * * *	***	87.0	
2.650	*	*******	* * * * * * * * * * *	* * *	87.0	
	+,	· + , - ·	+,	+		
	80.0	90.0	100.0	110.0		

t_{CE} vs. V_{CC}=V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650	****	* * * * * * * * * *	*******	**	85.0
3.600	****	* * * * * * * * * *	*******	**	85.0
3.550	****	* * * * * * * * * *	********	**	85.0
3.500	****	* * * * * * * * * *	********	**	85.0
3.450	****	* * * * * * * * * *	*******	**	85.0
3.400	****	* * * * * * * * * *	********	**	85.0
3.350	****	* * * * * * * * * *	******	**	85.0
3.300	****	* * * * * * * * * *	*******	**	85.0
3.250	****	* * * * * * * * * *	********	**	85.0
3.200	****	* * * * * * * * * *	******	**	85.0
3.150	****	* * * * * * * * * *	*******	**	85.0
3.100	***	* * * * * * * * * *	*******	**	86.0
3.050	***	* * * * * * * * * *	*******	**	86.0
3.000	***	* * * * * * * * * *	*******	**	86.0
2.950	***	* * * * * * * * * *	* * * * * * * * * *	**	86.0
2.900	***	* * * * * * * * * *	*******	**	86.0
2.850	***	* * * * * * * * * *	* * * * * * * * * *	**	86.0
2.800	* * *	* * * * * * * * * *	*******	**	86.0
2.750	***	* * * * * * * * * *	******	**	86.0
2.700	* * *	* * * * * * * * * *	* * * * * * * * * *	**	86.0
2.650	***	* * * * * * * * * *	*******	**	86.0
	+	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. $V_{CC}{=}V_{IO} @~25^\circ C$

	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.650	****	* * * * * * * * * *	*******	* * *	84.0
3.600	****	* * * * * * * * * *	******	***	84.0
3.550	i****	* * * * * * * * * *	*******	* * *	84.0
3.500	****	* * * * * * * * * *	******	* * *	84.0
3.450	****	* * * * * * * * * *	******	***	84.0
3.400	i****	* * * * * * * * * *	*******	* * *	84.0
3.350	****	* * * * * * * * * *	******	* * *	84.0
3.300	****	* * * * * * * * * *	******	***	84.0
3.250	***	* * * * * * * * * *	******	* * *	85.0
3.200	***	* * * * * * * * * *	*******	* * *	85.0
3.150	***	* * * * * * * * * *	******	* * *	85.0
3.100	***	* * * * * * * * * *	*******	* * *	85.0
3.050	***	* * * * * * * * * *	*******	* * *	85.0
3.000	***	* * * * * * * * * *	******	* * *	85.0
2.950	***	* * * * * * * * * *	* * * * * * * * * *	***	85.0
2.900	***	* * * * * * * * * *	* * * * * * * * * *	***	85.0
2.850	***	******	* * * * * * * * * *	***	85.0
2.800	***	* * * * * * * * * *	* * * * * * * * * *	***	85.0
2.750	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0
2.700	**	******	* * * * * * * * * *	***	86.0
2.650	**	* * * * * * * * * *	* * * * * * * * * *	***	86.0
	+,	+,	+,	+	
	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{CC}=V_{IO} @ -40°C

	80.0	90.0	100.0	110.0	first pass data
	+	-+,	-+,	-+	
3.650	**	******	******	**	87.0
3.600	**	* * * * * * * * * *	*******	**	87.0
3.550	**	* * * * * * * * * *	*******	**	87.0
3.500	**	* * * * * * * * * *	*******	**	87.0
3.450	**	* * * * * * * * * *	******	**	87.0
3.400	**	* * * * * * * * * *	*******	**	87.0
3.350	**	* * * * * * * * * *	******	**	87.0
3.300	**	* * * * * * * * * *	*******	**	87.0
3.250	**	* * * * * * * * * *	******	**	87.0
3.200	**	* * * * * * * * * *	*******	**	87.0
3.150	**	* * * * * * * * * *	*******	**	87.0
3.100	*	* * * * * * * * * *	******	**	88.0
3.050	*	* * * * * * * * * *	*******	**	88.0
3.000	*	* * * * * * * * * *	*******	**	88.0
2.950	*	* * * * * * * * * *	******	**	88.0
2.900	*	* * * * * * * * * *	*******	**	88.0
2.850	*	* * * * * * * * * *	*******	**	88.0
2.800	*	* * * * * * * * * *	*******	**	88.0
2.750		* * * * * * * * * *	*******	**	89.0
2.700		* * * * * * * * * *	*******	**	89.0
2.650		* * * * * * * * * *	******	**	89.0
	+,	-+,	-+,	-+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	-+,	-+,	+		
3.000	***	******	******	* * *	86.0	
2.950	***	* * * * * * * * * *	*******	* * *	86.0	
2.900	***	* * * * * * * * * *	*******	* * *	86.0	
2.850	***	* * * * * * * * * *	*******	* * *	86.0	
2.800	***	*******	*******	* * *	86.0	
2.750	***	* * * * * * * * * *	*******	* * *	86.0	
2.700	***	* * * * * * * * * *	*******	* * *	86.0	
2.650	***	*******	*******	* * *	86.0	
2.600	* * *	* * * * * * * * * *	* * * * * * * * * *	* * *	86.0	
2.550	* *	* * * * * * * * * *	*******	* * *	87.0	
2.500	* *	*******	*******	* * *	87.0	
2.450	**	* * * * * * * * * *	* * * * * * * * * *	* * *	87.0	
2.400	**	* * * * * * * * * *	* * * * * * * * * *	* * *	87.0	
2.350	**	* * * * * * * * * *	*******	***	87.0	
2.300	**	* * * * * * * * * *	* * * * * * * * * *	***	87.0	
2.250	**	* * * * * * * * * *	* * * * * * * * * *	* * *	87.0	
2.200	**	* * * * * * * * * *	*******	***	87.0	
2.150	**	* * * * * * * * * *	* * * * * * * * * *	***	87.0	
2.100	**	* * * * * * * * * *	* * * * * * * * * *	***	87.0	
2.050	**	* * * * * * * * * *	*******	***	87.0	
2.000	**	* * * * * * * * * *	*******	***	87.0	
1.950	*	* * * * * * * * * *	*******	***	88.0	
1.900	*	* * * * * * * * * *	*******	***	88.0	
1.850	*	* * * * * * * * * *	* * * * * * * * * *	***	88.0	
1.800	*	* * * * * * * * * *	* * * * * * * * * *	***	88.0	
1.750	*	* * * * * * * * * *	*******	***	88.0	
1.700		* * * * * * * * *	* * * * * * * * * *	* * *	89.0	
1.650		* * * * * * * * *	* * * * * * * * * *	* * *	89.0	
	+,	-+,	-+,	+		
	80.0	90.0	100.0	110.0		

t_{CE} vs. V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	+,	+	
3.000	***	*******	*******	* * *	86.0
2.950	***	********	********	* * *	86.0
2.900	***	********	*******	* * *	86.0
2.850	***	*******	*******	* * *	86.0
2.800	***	*******	*******	* * *	86.0
2.750	***	********	*******	* * *	86.0
2.700	***	*******	*******	* * *	86.0
2.650	***	*******	*******	* * *	86.0
2.600	***	********	*******	* * *	86.0
2.550	***	*******	*******	* * *	86.0
2.500	***	*******	* * * * * * * * * *	* * *	86.0
2.450	***	********	*******	* * *	86.0
2.400	***	*******	*******	* * *	86.0
2.350	***	*******	* * * * * * * * * *	* * *	86.0
2.300	***	********	*******	* * *	86.0
2.250	***	*******	*******	* * *	86.0
2.200	***	********	********	* * *	86.0
2.150	* * *	********	*******	* * *	86.0
2.100	***	*******	*******	* * *	86.0
2.050	***	********	********	* * *	86.0
2.000	***	********	*******	* * *	86.0
1.950	**	*******	* * * * * * * * * *	* * *	87.0
1.900	**	********	*********	* * *	87.0
1.850	**	*******	********	* * *	87.0
1.800	**	*******	* * * * * * * * * *	* * *	87.0
1.750	*	*******	* * * * * * * * * *	* * *	88.0
1.700	*	*******	*******	* * *	88.0
1.650	*	*******	*******	* * *	88.0
	+,	-+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} @ 25°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	-+,	+,	+		
3.000	* * * *	* * * * * * * * * * *	*******	* * *	85.0	
2.950	* * * *	*******	*******	***	85.0	
2.900	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.850	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.800	****	*******	* * * * * * * * * *	***	85.0	
2.750	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.700	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.650	****	*******	* * * * * * * * * *	***	85.0	
2.600	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.550	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.500	****	*******	* * * * * * * * * *	***	85.0	
2.450	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.400	****	*******	* * * * * * * * * *	* * *	85.0	
2.350	****	*******	* * * * * * * * * *	***	85.0	
2.300	* * * *	*******	* * * * * * * * * *	* * *	85.0	
2.250	****	*******	* * * * * * * * * *	* * *	85.0	
2.200	****	*******	* * * * * * * * * *	***	85.0	
2.150	***	*******	* * * * * * * * * *	* * *	86.0	
2.100	***	*******	* * * * * * * * * *	* * *	86.0	
2.050	***	*******	******	***	86.0	
2.000	***	* * * * * * * * * *	* * * * * * * * * *	***	86.0	
1.950	***	* * * * * * * * * *	* * * * * * * * * *	* * *	86.0	
1.900	***	* * * * * * * * * *	******	* * *	86.0	
1.850	***	* * * * * * * * * *	******	***	86.0	
1.800	**	* * * * * * * * * *	******	***	87.0	
1.750	**	* * * * * * * * * *	******	* * *	87.0	
1.700	**	* * * * * * * * * *	******	***	87.0	
1.650	*	* * * * * * * * * *	******	***	88.0	
	+,	-+,	+,	+		
	80.0	90.0	100.0	110.0		



	80.0	90.0	100.0	110.0	first pass	data
3 000	+,	+,	+, *******	+ ***	88 0	
2 950	1	*******	********	***	99 0	
2 900		*******	*********	* * *	88 0	
2 850		*******	********	* * *	88 0	
2 800		******	*******	***	88 0	
2 750		*******	*******	* * *	88 0	
2.700		*******	********	* * *	88.0	
2.650		*******	*******	* * *	88.0	
2.600		*******	********	* * *	88.0	
2.550		******	*******	* * *	88.0	
2.500		******	*******	* * *	88.0	
2.450		*******	* * * * * * * * * *	* * *	88.0	
2.400		*******	*******	* * *	88.0	
2.350		******	*******	* * *	88.0	
2.300		*******	* * * * * * * * * *	***	89.0	
2.250		*******	*******	* * *	89.0	
2.200	1	*******	*******	* * *	89.0	
2.150		. * * * * * * * * * *	* * * * * * * * * *	* * *	89.0	
2.100		.*******	* * * * * * * * * *	* * *	89.0	
2.050		. * * * * * * * * *	******	***	89.0	
2.000		.*******	* * * * * * * * * *	***	89.0	
1.950		. * * * * * * * * * *	* * * * * * * * * *	* * *	89.0	
1.900		. * * * * * * * * * *	* * * * * * * * * *	* * *	89.0	
1.850		. * * * * * * * * * *	* * * * * * * * * *	* * *	89.0	
1.800		* * * * * * * * *	* * * * * * * * * * *	* * *	90.0	
1.750		* * * * * * * * *	* * * * * * * * * *	* * *	90.0	
1.700		* * * * * * * * *	* * * * * * * * * * *	* * *	90.0	
1.650		* * * * * * * *	* * * * * * * * * * *	* * *	91.0	
	+,	+,	+,	+		
	80.0	90.0	100.0	110.0		



first pass data

data

t_{OE} vs. V_{CC}=V_{IO} @ 105°C

	0.0	10.0	20.0	firs
	+,-	+,	+	
3.650		. * * * * * * * * * *	* * * *	8.0
3.600		. * * * * * * * * * *	* * * *	8.0
3.550		. * * * * * * * * *	* * * *	8.0
3.500		. * * * * * * * * *	* * * *	8.0
3.450		. * * * * * * * * * *	* * * *	8.0
3.400		. * * * * * * * * *	* * * *	8.0
3.350		. * * * * * * * * * *	* * * *	8.0
3.300		. * * * * * * * * * *	* * * *	8.0
3.250		. * * * * * * * * * *	* * * *	8.0
3.200		. * * * * * * * * * *	* * * *	8.0
3.150		. * * * * * * * * * *	* * * *	8.0
3.100		. * * * * * * * * * *	* * * *	8.0
3.050		. * * * * * * * * * *	* * * *	8.0
3.000		. * * * * * * * * * *	* * * *	8.0
2.950		. * * * * * * * * * *	* * * *	8.0
2.900		. * * * * * * * * * *	* * * *	8.0
2.850		. * * * * * * * * * *	* * * *	8.0
2.800		. * * * * * * * * * *	* * * *	8.0
2.750		. * * * * * * * * * *	* * * *	8.0
2.700		. * * * * * * * * * *	* * * *	8.0
2.650		. * * * * * * * * * *	* * * *	8.0
	+,-	+,	+	
	0.0	10.0	20.0	

t_{OE} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0	first pass
	+,	-+,	+	
3.650	*	* * * * * * * * *	***	8.0
3.600	*	* * * * * * * * *	***	8.0
3.550	*	* * * * * * * * *	***	8.0
3.500	*	* * * * * * * * *	***	8.0
3.450	*	* * * * * * * * *	***	8.0
3.400	*	* * * * * * * * *	***	8.0
3.350	*	* * * * * * * * *	***	8.0
3.300	*	* * * * * * * * *	***	8.0
3.250	*	* * * * * * * * *	***	8.0
3.200	*	* * * * * * * * *	***	8.0
3.150	*	* * * * * * * * *	***	8.0
3.100	*	* * * * * * * * *	***	8.0
3.050	*	* * * * * * * * *	***	8.0
3.000	*	* * * * * * * * *	***	8.0
2.950	*	*******	***	8.0
2.900	*	******	***	8.0
2.850	*	* * * * * * * * *	***	8.0
2.800	*	*******	***	8.0
2.750	*	*******	***	8.0
2.700	*	* * * * * * * * *	***	8.0
2.650	*	*******	***	8.0
	+,	-+,	+	
	0.0	10.0	20.0	



first pass data

7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0

t_{OE} vs. V_{CC}=V_{IO} @ 25°C

	0.0	10.0	20.0
	+,	+,	+
3.650	*	* * * * * * * * * *	* * *
3.600	*	********	***
3.550	*	********	* * *
3.500	*	*******	* * *
3.450	*	*******	* * *
3.400	*	*******	* * *
3.350	*	*******	* * *
3.300	*	******	* * *
3.250	*	*******	* * *
3.200	*	******	* * *
3.150	*	*******	* * *
3.100	*	*******	* * *
3.050	*	*******	* * *
3.000	*	*******	* * *
2.950	*	* * * * * * * * * *	* * *
2.900	*	* * * * * * * * * *	* * *
2.850	*	*******	* * *
2.800	*	* * * * * * * * * *	* * *
2.750	*	* * * * * * * * * *	* * *
2.700	*	*******	* * *
2.650	*	* * * * * * * * * *	* * *
	+,	+,	+
	0.0	10.0	20.0

t_{OE} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first	pass	data
	+	-+,	-+			
3.650	**	* * * * * * * * * *	**	7.0		
3.600	**	* * * * * * * * * *	**	7.0		
3.550	**	* * * * * * * * * *	**	7.0		
3.500	**	* * * * * * * * * *	**	7.0		
3.450	* *	* * * * * * * * * *	**	7.0		
3.400	**	* * * * * * * * * *	**	7.0		
3.350	**	* * * * * * * * * *	**	7.0		
3.300	**	* * * * * * * * * *	**	7.0		
3.250	**	* * * * * * * * * *	**	7.0		
3.200	**	* * * * * * * * * *	**	7.0		
3.150	**	* * * * * * * * * *	**	7.0		
3.100	**	* * * * * * * * * *	**	7.0		
3.050	**	* * * * * * * * * *	**	7.0		
3.000	**	* * * * * * * * * *	**	7.0		
2.950	**	* * * * * * * * * *	**	7.0		
2.900	**	* * * * * * * * * *	**	7.0		
2.850	**	* * * * * * * * * *	**	7.0		
2.800	**	* * * * * * * * * *	**	7.0		
2.750	**	* * * * * * * * * *	**	7.0		
2.700	**	* * * * * * * * * *	**	7.0		
2.650	**	* * * * * * * * * *	**	7.0		
	+,	-+,	-+			
	0.0	10.0	20.0			



t_{OE} vs. V_{IO} @ 105°C

	0.0	10.0	20.0	first	pass	data
	+,	+,	+			
3.000		. * * * * * * * * * * *	***	8.0		
2.950		. * * * * * * * * * * *	***	8.0		
2.900		. * * * * * * * * * * *	***	8.0		
2.850		. * * * * * * * * * * *	***	8.0		
2.800		. * * * * * * * * * * *	***	8.0		
2.750		. * * * * * * * * * * *	***	8.0		
2.700		. * * * * * * * * * * *	***	8.0		
2.650		. * * * * * * * * * * *	***	8.0		
2.600		. * * * * * * * * * * *	***	8.0		
2.550		. * * * * * * * * * * *	***	8.0		
2.500		. * * * * * * * * * * *	***	8.0		
2.450		. * * * * * * * * * * *	***	8.0		
2.400		. * * * * * * * * * * *	***	8.0		
2.350		. * * * * * * * * * * *	***	8.0		
2.300		* * * * * * * * * *	***	9.0		
2.250		* * * * * * * * * *	***	9.0		
2.200		* * * * * * * * * *	***	9.0		
2.150		* * * * * * * * * *	***	9.0		
2.100		* * * * * * * * * *	***	9.0		
2.050		* * * * * * * * * *	***	9.0		
2.000		* * * * * * * * * *	***	9.0		
1.950		* * * * * * * * * *	***	9.0		
1.900		* * * * * * * * * *	***	9.0		
1.850		* * * * * * * * * *	***	9.0		
1.800		* * * * * * * * *	***	10.0		
1.750		* * * * * * * * *	***	10.0		
1.700		* * * * * * * * *	***	10.0		
1.650		* * * * * * * * *	***	10.0		
	+,	+,	+			
	0.0	10.0	20.0			



	0.0	10.0	20.0	first pass
	+, -	+, -	+	
3.000		. * * * * * * * * *	****	8.0
2.950		. * * * * * * * * *	****	8.0
2.900		. * * * * * * * * *	****	8.0
2.850		. * * * * * * * * *	****	8.0
2.800		. * * * * * * * * *	****	8.0
2.750		. * * * * * * * * *	****	8.0
2.700		. * * * * * * * * *	****	8.0
2.650		. * * * * * * * * *	****	8.0
2.600		. * * * * * * * * *	****	8.0
2.550		. * * * * * * * * *	****	8.0
2.500		. * * * * * * * * *	****	8.0
2.450		. * * * * * * * * *	****	8.0
2.400		. * * * * * * * * *	****	8.0
2.350		. * * * * * * * * *	****	8.0
2.300		. * * * * * * * * *	****	8.0
2.250		. * * * * * * * * *	****	8.0
2.200		. * * * * * * * * *	****	8.0
2.150		* * * * * * * *	****	9.0
2.100		* * * * * * * *	****	9.0
2.050		* * * * * * * *	****	9.0
2.000		* * * * * * * *	****	9.0
1.950		* * * * * * * *	****	9.0
1.900		* * * * * * * *	****	9.0
1.850		* * * * * * * *	****	9.0
1.800		* * * * * * * *	****	9.0
1.750		* * * * * * *	****	10.0
1.700		* * * * * * *	****	10.0
1.650		* * * * * * *	****	10.0
	+,-	+,-	+	
	0.0	10.0	20.0	

data



first pass data

first pass data

7.0 7.0 7.0

7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 9.0 9.0 9.0 9.0 9.0

7.0 7.0 7.0 7.0 7.0 7.0 7.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 8.0 9.0 9.0 9.0 9.0 9.0 10.0

t_{OE} vs. V_{IO} @ 25°C

	0.0	10.0	20.0
	+,-	+, -	+
3.000		* * * * * * * * * *	* * * *
2.950		* * * * * * * * * *	* * * *
2.900		* * * * * * * * * *	****
2.850		* * * * * * * * * *	* * * *
2.800		* * * * * * * * * *	* * * *
2.750		* * * * * * * * * *	****
2.700		* * * * * * * * * *	****
2.650		. * * * * * * * * *	****
2.600		. * * * * * * * * *	****
2.550		. * * * * * * * * *	* * * *
2.500		. * * * * * * * * *	* * * *
2.450		. * * * * * * * * *	* * * *
2.400		. * * * * * * * * *	* * * *
2.350		. * * * * * * * * *	* * * *
2.300		. * * * * * * * * *	* * * *
2.250		. * * * * * * * * *	* * * *
2.200		. * * * * * * * * *	* * * *
2.150		. * * * * * * * * *	* * * *
2.100		. * * * * * * * * *	* * * *
2.050		. * * * * * * * * *	* * * *
2.000		. * * * * * * * * *	* * * *
1.950		. * * * * * * * * *	****
1.900		* * * * * * * *	* * * *
1.850		* * * * * * * *	* * * *
1.800		* * * * * * * *	* * * *
1.750		* * * * * * * *	* * * *
1.700		* * * * * * * *	* * * *
1.650		* * * * * * *	* * * *
	+,-	+, -	+
	0.0	10.0	20.0

t_{OE} vs. V_{IO} @ -40°C

	0.0	10.0	20.0
	+	+,	+
3.000		********	***
2 950		* * * * * * * * * * * *	* * *
2.900		******	* * *
2.850		*****	* * *
2.800		*******	* * *
2.750		*****	* * *
2.700		*****	* * *
2.650		* * * * * * * * * * *	* * *
2.600		* * * * * * * * * * *	* * *
2.550		* * * * * * * * * * *	***
2.500		* * * * * * * * * * * *	* * *
2.450		* * * * * * * * * * * *	* * *
2.400		* * * * * * * * * * * *	* * *
2.350		* * * * * * * * * * * *	* * *
2.300		* * * * * * * * * * * *	* * *
2.250		* * * * * * * * * * * *	* * *
2.200		* * * * * * * * * * * *	* * *
2.150		.********	* * *
2.100		.********	* * *
2.050		.********	* * *
2.000		.********	* * *
1.950		.********	* * *
1.900		.********	* * *
1.850		.********	* * *
1.800		* * * * * * * * *	***
1.750		* * * * * * * * * *	* * *
1.700		* * * * * * * * * *	* * *
1.650		* * * * * * * * *	***
	+,-	+,	+
	0.0	10.0	20.0



t_{PACC} vs. V_{CC} = V_{IO} @ 105°C

	0.0	10.0	20.0	first pass	data
	+,	-+,	- +		
3.650		* * * * * * * * *	**	11.0	
3.600		* * * * * * * * *	**	11.0	
3.550		* * * * * * * *	**	11.0	
3.500		* * * * * * * *	**	11.0	
3.450		* * * * * * * *	**	11.0	
3.400		* * * * * * * *	**	11.0	
3.350		* * * * * * * *	**	11.0	
3.300		* * * * * * * *	**	11.0	
3.250		* * * * * * * *	**	11.0	
3.200		* * * * * * * *	**	11.0	
3.150		* * * * * * * *	**	11.0	
3.100		* * * * * * * *	**	11.0	
3.050		* * * * * * * * *	**	11.0	
3.000		* * * * * * * * *	**	11.0	
2.950		* * * * * * * *	**	11.0	
2.900		* * * * * * * *	**	11.0	
2.850		* * * * * * * *	**	11.0	
2.800		* * * * * * * *	**	11.0	
2.750		* * * * * * * *	**	11.0	
2.700		* * * * * * * *	**	11.0	
2.650		* * * * * * * *	**	11.0	
	+,	-+,	-+		
	0.0	10.0	20.0		

t_{PACC} vs. $V_{CC}=V_{IO}$ @ 85°C

	0.0	10.0	20.0	first pass	data
	+	-+,	-+		
3.650		* * * * * * * * *	**	11.0	
3.600		* * * * * * * * *	**	11.0	
3.550		* * * * * * * *	**	11.0	
3.500		* * * * * * * *	**	11.0	
3.450		* * * * * * * *	**	11.0	
3.400		* * * * * * * *	**	11.0	
3.350		* * * * * * * *	**	11.0	
3.300		* * * * * * * *	**	11.0	
3.250		* * * * * * * *	**	11.0	
3.200		* * * * * * * * *	**	11.0	
3.150		* * * * * * * * *	**	11.0	
3.100		* * * * * * * *	**	11.0	
3.050		* * * * * * * * *	**	11.0	
3.000		* * * * * * * * *	**	11.0	
2.950		* * * * * * * *	**	11.0	
2.900		* * * * * * * *	**	11.0	
2.850		* * * * * * * *	**	11.0	
2.800		* * * * * * * *	**	11.0	
2.750		* * * * * * * *	**	11.0	
2.700		* * * * * * * *	**	11.0	
2.650		* * * * * * * *	**	11.0	
	+,	-+,	-+		
	0.0	10.0	20.0		



first pass data

t_{PACC} vs. V_{CC} = V_{IO} @ 25°C

	0.0	10.0	20.0	first
	+,	-+,	-+	
3.650		. * * * * * * * * *	**	10.0
3.600		. * * * * * * * * *	**	10.0
3.550		. * * * * * * * * *	**	10.0
3.500		. * * * * * * * * *	**	10.0
3.450		. * * * * * * * * *	**	10.0
3.400		. * * * * * * * * *	**	10.0
3.350		. * * * * * * * * *	**	10.0
3.300		. * * * * * * * * *	**	10.0
3.250		. * * * * * * * * *	**	10.0
3.200		. * * * * * * * * *	**	10.0
3.150		. * * * * * * * * *	**	10.0
3.100		. * * * * * * * * *	**	10.0
3.050		. * * * * * * * * *	**	10.0
3.000		. * * * * * * * * *	**	10.0
2.950		. * * * * * * * * *	**	10.0
2.900		. * * * * * * * * *	**	10.0
2.850		. * * * * * * * * *	**	10.0
2.800		. * * * * * * * * *	**	10.0
2.750		. * * * * * * * * *	**	10.0
2.700		. * * * * * * * * *	**	10.0
2.650		. * * * * * * * * *	**	10.0
	+,	-+,	-+	
	0.0	10.0	20.0	

t_{PACC} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first pass	data
	+,	-+,	-+		
3.650		*******	**	10.0	
3.600		*******	**	10.0	
3.550		********	**	10.0	
3.500		*******	**	10.0	
3.450		*******	**	10.0	
3.400		********	**	10.0	
3.350		*******	**	10.0	
3.300		*******	**	10.0	
3.250		*******	**	10.0	
3.200		*******	**	10.0	
3.150		. * * * * * * * * * *	**	10.0	
3.100		********	**	10.0	
3.050		. * * * * * * * * * *	**	10.0	
3.000		. * * * * * * * * * *	**	10.0	
2.950		. * * * * * * * * * *	**	10.0	
2.900		. * * * * * * * * * *	* *	10.0	
2.850		. * * * * * * * * * *	**	10.0	
2.800		. * * * * * * * * * *	**	10.0	
2.750		. * * * * * * * * * *	* *	10.0	
2.700		. * * * * * * * * * *	**	10.0	
2.650		. * * * * * * * * * *	**	10.0	
	+,	-+,	-+		
	0.0	10.0	20.0		



t_{PACC} vs. V_{IO} @ 105°C

	0.0	10.0	20.0	first	pass	data
	+,	+,	+			
3.000		* * * * * * *	***	11.0		
2.950	1	* * * * * *	***	11.0		
2.900		* * * * * *	***	11.0		
2.850		* * * * * *	***	11.0		
2.800		* * * * * *	***	11.0		
2.750		* * * * * *	***	11.0		
2.700		* * * * * *	***	11.0		
2.650		* * * * * *	***	11.0		
2.600		* * * * * *	***	11.0		
2.550		* * * * *	***	12.0		
2.500		* * * * * *	***	12.0		
2.450		* * * * *	***	12.0		
2.400		* * * * * *	***	12.0		
2.350		* * * * * *	***	12.0		
2.300		* * * * *	***	12.0		
2.250		* * * * * *	***	12.0		
2.200		* * * * *	***	12.0		
2.150		* * * * *	***	12.0		
2.100		* * * * * *	***	12.0		
2.050		* * * * * *	***	12.0		
2.000		* * * * *	***	12.0		
1.950	1	* * * * * *	***	12.0		
1.900	1	* * * * * *	***	12.0		
1.850		* * * * *	***	12.0		
1.800		* * * * * *	***	12.0		
1.750	1	* * * * *	***	13.0		
1.700		* * * * *	***	13.0		
1.650		* * * * *	***	13.0		
	+,	+,	+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{IO} @ 85°C

	0.0	10.0	20.0	first	pass	data
	+,	-+,	-+			
3.000		* * * * * * * *	***	11.0		
2.950		* * * * * * * *	**	11.0		
2.900		* * * * * * * *	**	11.0		
2.850		* * * * * * * *	**	11.0		
2.800	1	* * * * * * * *	**	11.0		
2.750		* * * * * * * *	**	11.0		
2.700		* * * * * * * *	**	11.0		
2.650		* * * * * * * *	**	11.0		
2.600		* * * * * * * *	**	11.0		
2.550		* * * * * * * *	**	11.0		
2.500		* * * * * * * *	**	11.0		
2.450		* * * * * * * *	**	11.0		
2.400		* * * * * * * *	**	11.0		
2.350		* * * * * * * *	**	11.0		
2.300		* * * * * * * *	**	11.0		
2.250		* * * * * * * *	**	11.0		
2.200		* * * * * * *	**	12.0		
2.150		* * * * * * *	**	12.0		
2.100		* * * * * *	**	12.0		
2.050		* * * * * *	**	12.0		
2.000		* * * * * * *	**	12.0		
1.950		******	***	12.0		
1.900		* * * * * * *	**	12.0		
1.850		******	***	12.0		
1.800		******	***	12.0		
1.750		* * * * * * *	**	12.0		
1.700		******	**	12.0		
1.650		* * * * * *	**	13.0		
	+,	- + ,	-+			
	0.0	10.0	20.0			



first pass data

11.0 11.0 11.0 11.0 11.0

t_{PACC} vs. V_{IO} @ 25°C

	0.0	10.0	20.0
	+,	+,	+
3.000		* * * * * * * *	***
2.950		*******	***
2.900		*******	* * *
2.850		*******	***
2.800		*******	***
2.750		*******	***
2.700		* * * * * * * *	***
2.650		* * * * * * * *	***
2.600		*******	***
2.550		*******	***
2.500		* * * * * * * *	***
2.450		* * * * * * *	***
2.400		******	***
2.350		******	***
2.300		******	***
2.250		* * * * * * *	***
2.200		******	***
2.150		******	***
2.100		* * * * * * *	***
2.050		******	***
2.000		******	***
1.950		* * * * * * *	***
1.900		* * * * * * *	***
1.850		* * * * * * *	***
1.800		* * * * * *	***
1.750		* * * * * *	***
1.700		* * * * * *	***
1.650		* * * * * *	***
	+,	+,	+İ
	0.0	10.0	20.0

t_{PACC} vs. V_{IO} @ -40°C

	0.0	10.0	20.0	first	pass	data
3.000 2.950 2.850 2.750 2.650 2.650 2.550 2.450 2.400 2.350 2.400 2.350 2.200 2.200 2.150 2.100 2.150 2.100 2.000	0.0	10.0	20.0 -+ ** ** ** ** ** ** ** ** ** ** ** ** **	first 10.0 10.0 10.0 10.0 10.0 10.0 10.0 10.	pass	data
2.050	 	. * * * * * * * * * * * * * * * * * * *	**	10.0 10.0		
1.900 1.850		· · * * * * * * * * * * * * * * * * * *	** **	10.0 11.0 11.0		
1.800 1.750 1.700		· · * * * * * * * * * * * * * * * * * *	* * * * * *	11.0 11.0 11.0		
1.650	 +, 0.0	******** -+, 10.0	** -+ 20.0	12.0		



V_{IH} vs. $V_{CC}\text{=}V_{IO}$ @ 105°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+,	+,	+,	+,	+	
3.650			* * * * *	*******	* * * *	2.100
3.600			* * * * * *	* * * * * * * * * * *	* * * *	2.050
3.550			* * * * * *	* * * * * * * * * * *	* * * *	2.050
3.500			* * * * * * *	* * * * * * * * * * *	* * * *	2.000
3.450			* * * * * * * * *	* * * * * * * * * * *	****	1.950
3.400			* * * * * * * * *	* * * * * * * * * * *	****	1.950
3.350			********	* * * * * * * * * * *	****	1.900
3.300	1		********	* * * * * * * * * * *	* * * *	1.900
3.250	1		* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.850
3.200			* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.850
3.150	1	*:	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.800
3.100	1	* * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.750
3.050		* * :	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.750
3.000	1	* * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.700
2.950	1	* * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.700
2.900		* * * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.650
2,850	1	* * * * *	* * * * * * * * * *	******	* * * *	1,650
2.800	1	*****	* * * * * * * * * *	*******	* * * *	1,600
2.750		*****	* * * * * * * * * *	*******	* * * *	1,600
2.700		*****	* * * * * * * * * *	********	* * * *	1.550
2.650		******	* * * * * * * * * * *	********	* * * *	1.500
2.000	+	· · ·	+	+	+	2.000
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. V_{CC}=V_{IO} @ 85°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+,	+,	+,	+,	+	
3.650	1		*****	* * * * * * * * * * *	****	2.100
3.600			*****	* * * * * * * * * * *	****	2.050
3.550			*****	* * * * * * * * * * *	****	2.050
3.500	1		* * * * * * *	* * * * * * * * * * *	****	2.000
3.450			* * * * * * * *	* * * * * * * * * * *	****	2.000
3.400			.******	* * * * * * * * * * *	****	1.950
3.350	1		* * * * * * * * *	* * * * * * * * * * *	****	1.900
3.300			*******	* * * * * * * * * * *	****	1.900
3.250		*	*******	* * * * * * * * * * *	****	1.850
3.200	1	*	* * * * * * * * *	* * * * * * * * * * *	****	1.850
3.150		* *	*******	* * * * * * * * * * *	****	1.800
3.100		**	*******	* * * * * * * * * * *	****	1.800
3.050	1	* * *	* * * * * * * * *	* * * * * * * * * * *	****	1.750
3.000		* * * *	*******	* * * * * * * * * * *	****	1.700
2.950	1	* * * *	*******	* * * * * * * * * * *	****	1.700
2.900	1	* * * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.650
2.850		* * * * *	*******	* * * * * * * * * * *	****	1.650
2.800		* * * * * *	*******	* * * * * * * * * * *	****	1.600
2.750	1	* * * * * *	* * * * * * * * *	* * * * * * * * * * *	****	1.600
2.700		* * * * * * *	*******	* * * * * * * * * * *	****	1.550
2.650		* * * * * * * *	*******	* * * * * * * * * * *	****	1.500
	+,	+,	+,	+,	+	
	1.000	1.500	2.000	2.500	3.000	


V_{IH} vs. V_{CC}=V_{IO} @ 25°C

	1.000	1.500	2.000	2.500	3.000	first p	ass data
	+,	+,	+,-	+,	+		
3.650			* * * * *	* * * * * * * * * * *	****	2.100	
3.600			* * * * * *	* * * * * * * * * * *	****	2.050	
3.550			* * * * * * *	* * * * * * * * * * *	****	2.000	
3.500			* * * * * * *	* * * * * * * * * * *	****	2.000	
3.450	1		.*******	* * * * * * * * * * *	****	1.950	
3.400	1		.*******	* * * * * * * * * * *	****	1.950	
3.350	1		*******	* * * * * * * * * * *	****	1.900	
3.300	1		*******	*******	****	1.900	
3.250	1	*	*******	* * * * * * * * * * *	****	1.850	
3.200	1	* *	*******	* * * * * * * * * * *	****	1.800	
3.150	1	* *	*******	*******	****	1.800	
3.100	1	* * *	*******	* * * * * * * * * * *	****	1.750	
3.050	1	* * *	*******	* * * * * * * * * * *	****	1.750	
3,000	1	* * * *	*******	********	****	1,700	
2.950	1	* * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.700	
2.900		* * * * *	* * * * * * * * * *	* * * * * * * * * * *	****	1.650	
2,850	1	* * * * *	*******	********	****	1,650	
2.800		*****	*******	********	****	1.600	
2.750		*****	*******	********	****	1.600	
2.700		******	*******	********	****	1.550	
2.650		******	*******	********	****	1.500	
2.000	+	+	+	+	+	2.000	
	1.000	1.500	2.000	2.500	3.000		

V_{IH} vs. V_{CC}=V_{IO} @ -40°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+,	+,	+,	+,	+	
3.650			* * * * *	* * * * * * * * * *	* * * *	2.100
3.600			* * * * * *	*******	****	2.050
3.550			* * * * * *	*******	****	2.050
3.500			* * * * * * *	******	****	2.000
3.450			* * * * * * * *	* * * * * * * * * *	****	2.000
3.400			. * * * * * * * * *	*******	****	1.950
3.350			********	******	****	1.900
3.300			*******	* * * * * * * * * *	* * * *	1.900
3.250		,	********	*******	****	1.850
3.200		,	********	******	****	1.850
3.150		* *	********	* * * * * * * * * *	****	1.800
3.100		* *	********	*******	****	1.800
3.050		* * *	********	* * * * * * * * * * *	* * * *	1.750
3.000		* * * *	********	*******	****	1.700
2.950		* * * *	*******	*******	****	1.700
2.900		* * * * *	*******	*******	* * * *	1.650
2.850		* * * * *	*******	* * * * * * * * * * *	****	1.650
2.800		* * * * * *	*******	*******	****	1.600
2.750		* * * * * *	********	******	****	1.600
2.700		* * * * * * *	*******	* * * * * * * * * *	****	1.550
2.650			*******	* * * * * * * * * * *	* * * *	1.550
	+	+	+	+	+	
	1.000	1.500	2.000	2.500	3.000	



V_{IL} vs. V_{CC} = V_{IO} @ 105°C

	0.000	0.500	1.000	1.500	2.000	first pass	data
	+,	-+,	+,	+ ,	- +		
3.650	*******	* * * * * * * * * *	********	* *		1.450	
3.600	*******	*******	*******	**		1.450	
3.550	*******	*******	*******	*		1.400	
3.500	*******	* * * * * * * * * *	*******	*		1.400	
3.450	*******	* * * * * * * * * *	*******	*		1.400	
3.400	*******	* * * * * * * * * *	*******			1.350	
3.350	*******	* * * * * * * * * *	*******			1.350	
3.300	*******	* * * * * * * * * *	********			1.350	
3.250	*******	* * * * * * * * * *	*******			1.350	
3.200	*******	* * * * * * * * * *	********			1.300	
3.150	*******	* * * * * * * * * *	*********			1.300	
3.100	*******	* * * * * * * * * *	********			1.300	
3.050	*******	* * * * * * * * * *	*******			1.250	
3.000	*******	* * * * * * * * * *	*******			1.250	
2.950	* * * * * * * * *	* * * * * * * * * *	*******			1.250	
2.900	*******	* * * * * * * * * *	******			1.200	
2.850	*******	*******	******			1.200	
2.800	*******	* * * * * * * * * *	*****			1.150	
2.750	*******	* * * * * * * * * *	*****			1.150	
2.700	*******	*******	*****			1.100	
2.650	*******	* * * * * * * * * *	*****			1.150	
	+,	-+,	+,	+,	-+		
	0.000	0.500	1.000	1.500	2.000		

V_{IL} vs. V_{CC} =V_{IO} @ 85°C

	0.000	0.500	1.000	1.500	2.000	first pass dat	a
	+,	-+,	+,	+ ,	-+		
3.650	*******	* * * * * * * * * *	*********	***		1.500	
3.600	*******	* * * * * * * * * *	*********	**		1.450	
3.550	*******	* * * * * * * * * *	*********	**		1.450	
3.500	*******	* * * * * * * * * *	*********	**		1.450	
3.450	*******	* * * * * * * * * *	*********	•		1.400	
3.400	*******	* * * * * * * * * *	*********	•		1.400	
3.350	*******	* * * * * * * * * *	*********	•		1.400	
3.300	*******	* * * * * * * * * *	*********			1.350	
3.250	*******	* * * * * * * * * *	*********			1.350	
3.200	*******	* * * * * * * * * *	********			1.300	
3.150	*******	* * * * * * * * * *	********			1.300	
3.100	*******	* * * * * * * * * *	********			1.300	
3.050	*******	* * * * * * * * * *	********			1.300	
3.000	*******	* * * * * * * * * *	*******			1.250	
2.950	*******	* * * * * * * * * * *	******			1.200	
2.900	*******	* * * * * * * * * * *	******			1.200	
2.850	*******	* * * * * * * * * *	******			1.200	
2.800	*******	* * * * * * * * * * *	******			1.200	
2.750	*******	* * * * * * * * * * *	*****			1.150	
2.700	*******	* * * * * * * * * *	*****			1.150	
2.650	*******	* * * * * * * * * *	*****			1.150	
	+,	-+,	- + ,	-+,	-+		
	0.000	0.500	1.000	1.500	2.000		



V_{IL} vs. V_{CC} = V_{IO} @ 25°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	+,	+ ,	+	
3.650	******	*******	*******	***		1.500
3.600	*******	*******	*******	* * *		1.500
3.550	******	*******	*******	**		1.450
3.500	******	*******	*******	*		1.400
3.450	*******	*******	******	*		1.400
3.400	*******	*******	* * * * * * * * * *	*		1.400
3.350	*******	*******	* * * * * * * * * *			1.350
3.300	*******	*******	******	*		1.400
3.250	*******	*******	* * * * * * * * * *			1.350
3.200	*******	*******	********			1.300
3.150	*******	********	********			1.300
3.100	*******	*******	********			1.300
3.050	******	*******	********			1.300
3.000	*******	*******	*******			1.250
2.950	******	*******	*******			1.250
2.900	******	*******	*******			1.250
2.850	******	*******	*******			1.250
2.800	******	* * * * * * * * * *	******			1.200
2.750	******	*******	******			1.200
2.700	******	*******	*****			1.150
2.650	******	* * * * * * * * * *	*****			1.150
	+,	+,	+,	+,	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	-+,	-+,	-+,	-+	
3.650	*******	*******	* * * * * * * * * *	**		1.500
3.600	*******	*******	* * * * * * * * * *	**		1.500
3.550	*******	* * * * * * * * * * *	* * * * * * * * * *	*		1.450
3.500	*******	* * * * * * * * * * *	* * * * * * * * * *	*		1.450
3.450	*******	*******	* * * * * * * * * *	*		1.450
3.400	*******	* * * * * * * * * * *	* * * * * * * * * *	*		1.450
3.350	*******	* * * * * * * * * * *	* * * * * * * * * *			1.400
3.300	*******	*******	* * * * * * * * * *			1.400
3.250	*******	* * * * * * * * * * *	********			1.350
3.200	*******	*******	********			1.350
3.150	*******	*******	********			1.350
3.100	*******	*******	*******			1.300
3.050	*******	* * * * * * * * * * *	*******			1.300
3.000	*******	******	*******			1.300
2.950		*******	******			1.250
2.900	*******	*******	******			1.250
2.850	*******	*******	******			1.250
2.800	*******	*******	*****			1.200
2.750	*******	*******	*****			1.200
2.700	*******	*******	*****			1.200
2.650	*******	* * * * * * * * * * *	*****			1.150
	+,	-+,	-+,	-+,	-+	
	0.000	0.500	1.000	1.500	2.000	



Qualification Database

V_{OH} vs. V_{CC} = V_{IO} @ 105°C

	2.000	2.500	3.000	3.500	4.000	first pass data
	+,	-+,	+,	+,	+	
3.650	*******	* * * * * * * * * * *	*******	****		3.600
3.600	*******	* * * * * * * * * *	******	****		3.550
3.550	*******	* * * * * * * * * *	******	***		3.500
3.500	*******	* * * * * * * * * *	******	**		3.450
3.450	*******	* * * * * * * * * *	*******	*		3.400
3.400	*******	* * * * * * * * * *	*******			3.350
3.350	*******	* * * * * * * * * *	********			3.300
3.300	*******	* * * * * * * * * *	*******			3.250
3.250	*******	* * * * * * * * * *	******			3.200
3.200	*******	* * * * * * * * * *	*****			3.150
3.150	*******	* * * * * * * * * *	*****			3.100
3.100	*******	* * * * * * * * * *	****			3.050
3.050	*******	* * * * * * * * * *	***			3.000
3.000	*******	* * * * * * * * * *	**			2.950
2.950		* * * * * * * * * *	*			2.900
2.900	*******	********				2.850
2.850	*******	********				2.800
2.800	*******	******				2.750
2.750	*******	*****				2.700
2.700	*******	*****				2.650
2.650	*******	****				2.600
	+,	-+,	+,	+,	+	
	2.000	2.500	3.000	3.500	4.000	

V_{OH} vs. V_{CC}=V_{IO} @ 85°C

	2.000	2.500	3.000	3.500	4.000	first pass	data
	+,	+,	- + ,	-+,	-+		
3.650	********	*********	*********	****		3.600	
3.600	*******	*********	********	***		3.550	
3.550	* * * * * * * * * *	*********	********	**		3.500	
3.500	*******	*********	********	*		3.450	
3.450	*******	*********	*********			3.400	
3.400	*******	*********	*********			3.350	
3.350	*******	*********	********			3.300	
3.300	*******	*********	*******			3.250	
3.250	*******	*********	******			3.200	
3.200	*******	*********	*****			3.150	
3.150	*******	*********	****			3.100	
3.100	*******	*********	****			3.050	
3.050	*******	*********	***			3.000	
3.000	. * * * * * * * * *	*********	**			2.950	
2.950	* * * * * * * * *	* * * * * * * * * *	*			2.900	
2.900	*******	*********				2.850	
2.850	*******	********				2.800	
2.800	*******	*******				2.750	
2.750	*******	******				2.700	
2.700	* * * * * * * * *	*****				2.650	
2.650	* * * * * * * * *	*****				2.600	
	+,,	+,	-+,	-+,	- +		
	2.000	2.500	3.000	3.500	4.000		



V_{OH} vs. V_{CC}=V_{IO} @ 25°C

	2.000	2.500	3.000	3.500	4.000	first p	ass	data
	+,	-+,	+ ,	-+,	- +			
3.650	*******	* * * * * * * * * *	*******	****		3.600		
3.600	*******	* * * * * * * * * *	*******	***		3.550		
3.550	*******	* * * * * * * * * *	*******	**		3.500		
3.500	*******	* * * * * * * * * *	*******	*		3.450		
3.450	*******	* * * * * * * * * *	******			3.400		
3.400	*******	* * * * * * * * * *	*********			3.350		
3.350	*******	* * * * * * * * * *	********			3.300		
3.300	*******	* * * * * * * * * *	*******			3.250		
3.250	*******	* * * * * * * * * *	******			3.200		
3.200	*******	* * * * * * * * * *	*****			3.150		
3.150	*******	* * * * * * * * * *	*****			3.100		
3.100	*******	* * * * * * * * * *	****			3.050		
3.050	*******	* * * * * * * * * *	***			3.000		
3.000	*******	* * * * * * * * * *	**			2.950		
2.950	******	* * * * * * * * * *	*			2.900		
2.900	*******	*******				2.850		
2.850	*******	*******				2.800		
2.800	*******	******				2.750		
2.750	*******	*****				2.700		
2.700	*******	****				2,650		
2.650	******	****				2.600		
	+	-+	-+	-+	-+			
	2.000	2.500	3.000	3.500	4.000			

V_{OH} vs. V_{CC}=V_{IO} @ -40°C

	2.000	2.500	3.000	3.500	4.000	first pass data
3.650 3.500 3.550 3.450 3.400 3.350 3.250 3.200 3.250 3.200 3.150 3.150 3.050	2.000	2.500 	3.000 **********************************	3.500 ***** **** *** *** ***	4.000 + 	first pass data 3.600 3.550 3.500 3.400 3.400 3.350 3.300 3.250 3.200 3.150 3.100 3.050 3.000 2.950
3.100 3.050 3.000 2.950 2.900 2.850 2.800 2.750	**************************************	* * * * * * * * * * * * * * * * * * *	* * * *		· · · · · · · · · · · · · · · · · · ·	3.050 3.000 2.950 2.900 2.850 2.800 2.750 2.750
2.700 2.650	******** ********* +, 2.000	***** ***** +, 2.500		+, 3.500	···· ···-+ 4.000	2.650 2.600



Qualification Database

$V_{OL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	first	pass	data
	+,	-+,	+			
3.650	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
3.600	. * * * * * * * *	* * * * * * * * *	***	0.050		
3.550	.*******	* * * * * * * * * *	***	0.050		
3.500	.*******	* * * * * * * * * *	***	0.050		
3.450	.*******	* * * * * * * * *	***	0.050		
3.400	.*******	* * * * * * * * *	***	0.050		
3.350	.*******	* * * * * * * * * *	***	0.050		
3.300	.*******	* * * * * * * * * *	***	0.050		
3.250	.*******	* * * * * * * * *	***	0.050		
3.200	.*******	* * * * * * * * * *	***	0.050		
3.150	. * * * * * * * *	* * * * * * * * * *	***	0.050		
3.100	.*******	* * * * * * * * * *	***	0.050		
3.050	.*******	* * * * * * * * * *	* * *	0.050		
3.000	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.950	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.900	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.850	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.800	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.750	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.700	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.650	. * * * * * * * *	* * * * * * * * *	***	0.050		
	+,	-+,	+			
	0.000	0.500	1.000			

V_{OL} vs. V_{CC}=V_{IO} @ 85°C

	0.000	0.500	1.000	first pass dat	ta
	+,-	+, -	+		
3.650	. * * * * * *	* * * * * * * * * *	****	0.050	
3.600	.*****	* * * * * * * * * *	****	0.050	
3.550	.*****	* * * * * * * * * *	****	0.050	
3.500	.*****	* * * * * * * * * *	****	0.050	
3.450	.*****	* * * * * * * * * *	****	0.050	
3.400	.*****	* * * * * * * * * *	****	0.050	
3.350	. * * * * * *	* * * * * * * * * *	****	0.050	
3.300	.*****	* * * * * * * * * *	****	0.050	
3.250	. * * * * * *	* * * * * * * * * *	****	0.050	
3.200	. * * * * * *	* * * * * * * * * *	****	0.050	
3.150	.*****	* * * * * * * * * *	****	0.050	
3.100	. * * * * * *	* * * * * * * * * *	****	0.050	
3.050	. * * * * * *	* * * * * * * * * *	****	0.050	
3.000	.*****	* * * * * * * * * *	****	0.050	
2.950	. * * * * * *	* * * * * * * * * *	****	0.050	
2.900	. * * * * * *	* * * * * * * * * *	****	0.050	
2.850	. * * * * * *	* * * * * * * * * *	****	0.050	
2.800	. * * * * * *	* * * * * * * * * *	****	0.050	
2.750	. * * * * * *	* * * * * * * * * *	****	0.050	
2.700	. * * * * * *	* * * * * * * * * *	****	0.050	
2.650	. * * * * * *	* * * * * * * * * *	****	0.050	
	+,-	+, -	+		
	0.000	0.500	1.000		



first pass data

V_{OL} vs. V_{CC} = V_{IO} @ 25°C

	0.000	0.500	1.000	first
	+,	+,	+	
3.650	. * * * * * * *	********	* * * *	0.050
3.600	.******	*******	****	0.050
3.550	. * * * * * * *	* * * * * * * * * *	****	0.050
3.500	. * * * * * * *	********	* * * *	0.050
3.450	.******	*******	****	0.050
3.400	. * * * * * * *	* * * * * * * * * *	****	0.050
3.350	. * * * * * * *	********	* * * *	0.050
3.300	.******	*******	****	0.050
3.250	. * * * * * * *	********	* * * *	0.050
3.200	. * * * * * * *	********	* * * *	0.050
3.150	. * * * * * * *	*******	****	0.050
3.100	. * * * * * * *	********	* * * *	0.050
3.050	. * * * * * * *	********	* * * *	0.050
3.000	. * * * * * * *	*******	****	0.050
2.950	. * * * * * * *	*******	* * * *	0.050
2.900	. * * * * * * *	*******	* * * *	0.050
2.850	. * * * * * * *	********	* * * *	0.050
2.800	. * * * * * * *	********	* * * *	0.050
2.750	. * * * * * * *	*******	* * * *	0.050
2.700	. * * * * * * *	*******	* * * *	0.050
2.650	. * * * * * * *	*******	* * * *	0.050
	+,	+,	+	
	0.000	0.500	1.000	

V_{OL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	first pas	s data
	+,	-+,	+		
3.650	.******	*********	***	0.050	
3.600	.*******	* * * * * * * * * * *	***	0.050	
3.550	.*******	*********	***	0.050	
3.500	.*******	*********	***	0.050	
3.450	.*******	*********	***	0.050	
3.400	.*******	*********	***	0.050	
3.350	.*******	*********	***	0.050	
3.300	.*******	* * * * * * * * * * *	***	0.050	
3.250	.*******	*********	***	0.050	
3.200	.*******	*********	***	0.050	
3.150	.******	*********	***	0.050	
3.100	. * * * * * * * *	*********	***	0.050	
3.050	.*******	*********	***	0.050	
3.000	. * * * * * * * *	*********	***	0.050	
2.950	. * * * * * * * *	*********	***	0.050	
2.900	. * * * * * * * *	*********	***	0.050	
2.850	. * * * * * * * *	*********	***	0.050	
2.800	.******	*********	***	0.050	
2.750	. * * * * * * * *	*********	***	0.050	
2.700	. * * * * * * * *	*********	***	0.050	
2.650	. * * * * * * * *	*********	***	0.050	
	+,	- + ,	· - +		
	0.000	0.500	1.000		



Qualification Database

V_{IH} vs. V_{IO} @ 105°C

	0.500	1.000	1.500	2.000	2.500	first pass data
	+,	+,	+,	+,	+	
3.000		•••••	* * * '	* * * * * * * * * * *	* * * *	1.700
2.950			• • • • • • • • * * *	* * * * * * * * * * *	* * * *	1.700
2.900			• • • • • • * * * *	* * * * * * * * * * *	* * * *	1.650
2.850			• • • • • • * * * *	* * * * * * * * * * *	* * * *	1.650
2.800			* * * * *	* * * * * * * * * * *	* * * *	1.600
2.750			* * * * *	*******	* * * *	1.600
2.700			* * * * * *	*******	* * * *	1.550
2.650			* * * * * * *	********	* * * *	1.500
2.600			* * * * * * *	* * * * * * * * * * *	* * * *	1.500
2.550			* * * * * * * * *	* * * * * * * * * * *	* * * *	1.450
2.500			* * * * * * * * *	* * * * * * * * * * *	* * * *	1.450
2.450			. * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.400
2.400			. * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.400
2.350			* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.350
2.300			* * * * * * * * * *	* * * * * * * * * *	* * * *	1.350
2.250		**	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.300
2.200		* :	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.300
2.150		* * *	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.250
2.100		* * * *	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.200
2.050		***	* * * * * * * * * * *	* * * * * * * * * * *	* * * *	1.200
2.000		* * * *	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.200
1.950		****	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.150
1.900		*****	* * * * * * * * * *	*******	****	1.100
1.850		*****	* * * * * * * * * *	* * * * * * * * * *	****	1.100
1.800		*****	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.100
1.750		******	* * * * * * * * * *	*******	* * * *	1.050
1.700	1	* * * * * * * *	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.000
1.650		* * * * * * *	* * * * * * * * * *	* * * * * * * * * *	* * * *	1.000
	+,	+ ,	+,	+,	+	
	0.500	1.000	1.500	2.000	2.500	

V_{IH} vs. V_{IO} @ 85°C

	0.500	1.000	1.500	2.000	2.500	first p	pass data
	+,	+,	+,-	+,-	+		
3.000			* * *	******	****	1.700	
2.950			* * *	******	****	1.700	
2.900			* * * *	******	****	1.650	
2.850			* * * *	*******	* * * *	1.650	
2.800			* * * * *	*******	****	1.600	
2.750			* * * * *	*******	****	1.600	
2.700			* * * * * *	*******	****	1.550	
2.650			* * * * * * *	*******	****	1.500	
2.600			* * * * * * *	*******	****	1.500	
2.550			* * * * * * * *	******	****	1.450	
2.500			* * * * * * * *	*******	****	1.450	
2.450			. * * * * * * * * *	*******	****	1.400	
2.400			. * * * * * * * * *	******	****	1.400	
2.350			* * * * * * * * * *	*******	****	1.350	
2.300			* * * * * * * * * *	*******	****	1.350	
2.250		* *	* * * * * * * * * *	******	****	1.300	
2.200		*	* * * * * * * * * *	*******	****	1.300	
2.150		* * *	* * * * * * * * * *	*******	****	1.250	
2.100		* * *	* * * * * * * * * *	******	****	1.250	
2.050		* * * *	* * * * * * * * * *	*******	****	1.200	
2.000			* * * * * * * * * *	*******	****	1.150	
1.950	1	* * * * *	* * * * * * * * * *	* * * * * * * * * *	****	1.150	
1.900		* * * * * *	* * * * * * * * * *	*******	****	1.100	
1.850		*****	* * * * * * * * * *	*******	****	1.100	
1.800		* * * * * * *	* * * * * * * * * *	* * * * * * * * * *	****	1.050	
1.750		* * * * * * *	* * * * * * * * * *	*******	****	1.050	
1.700		* * * * * * * *	* * * * * * * * * *	*******	****	1.000	
1.650		* * * * * * * *	* * * * * * * * * *	* * * * * * * * * *	****	1.000	
	+,	+,	+,-	+,-	+		
	0.500	1.000	1.500	2.000	2.500		



V_{IH} vs. V_{IO} @ 25°C

	0.500	1.000	1.500	2.000	2.500	first pass data
	+,	+,	+,-	+,	+	
3.000		•••••	* * *	*******	* * * *	1.700
2.950		• • • • • • • • • • •	* * *	*******	* * * *	1.700
2.900			* * * *	*******	* * * *	1.650
2.850			* * * *	*******	* * * *	1.650
2.800			* * * * *	******	* * * *	1.600
2.750			* * * * *	******	* * * *	1.600
2.700			* * * * * *	******	* * * *	1.550
2.650			* * * * * * *	*******	* * * *	1.500
2.600			* * * * * * *	******	* * * *	1.500
2.550			* * * * * * * *	******	* * * *	1.450
2.500			* * * * * * * * *	*******	* * * *	1.450
2.450			. * * * * * * * * *	*******	* * * *	1.400
2.400			. * * * * * * * * *	*******	* * * *	1.400
2.350			* * * * * * * * * *	********	* * * *	1.350
2.300			* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.350
2.250		* *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.300
2.200		* '	* * * * * * * * * *	*******	* * * *	1.300
2.150		* * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.250
2.100		* * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.200
2.050		* * * *	* * * * * * * * * *	********	* * * *	1.200
2.000		* * * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.150
1.950	1	* * * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	1.150
1.900	1	* * * * * *	* * * * * * * * * *	*******	****	1.100
1.850	1	* * * * * *	* * * * * * * * * *	******	* * * *	1.100
1.800		* * * * * * *	* * * * * * * * * *	*******	* * * *	1.050
1.750	1	* * * * * * *	* * * * * * * * * *	*******	****	1.050
1.700	1	* * * * * * *	* * * * * * * * * *	******	* * * *	1.000
1.650	1	* * * * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	* * * *	0.950
	+,	+,	+,-	+,	+İ	
	0.500	1.000	1.500	2.000	2.500	

V_{IH} vs. V_{IO} @ -40°C

	0.500	1.000	1.500	2.000	2.500	first pa	ass data
	+,	+,	+,-	+,-	+		
3.000		•••••	* * *	*******	* * * *	1.700	
2.950		• • • • • • • • • • •	* * *	********	****	1.700	
2.900		• • • • • • • • • •	* * * *	********	* * * *	1.650	
2.850			* * * *	*******	* * * *	1.650	
2.800			* * * * *	*******	* * * *	1.600	
2.750			* * * * *	*******	* * * *	1.600	
2.700			* * * * * *	******	* * * *	1.550	
2.650			* * * * * *	*******	* * * *	1.550	
2.600			* * * * * * *	* * * * * * * * * * *	* * * *	1.500	
2.550			* * * * * * * *	* * * * * * * * * * *	* * * *	1.450	
2.500			* * * * * * * *	********	* * * *	1.450	
2.450			. * * * * * * * * *	********	****	1.400	
2.400	1		. * * * * * * * * *	*******	* * * *	1.400	
2.350	1		* * * * * * * * * *	*******	* * * *	1.350	
2.300	1		* * * * * * * * * *	*******	* * * *	1.350	
2.250	1	*****	* * * * * * * * * *	*******	* * * *	1.300	
2.200	1	*****	* * * * * * * * * *	******	* * * *	1.300	
2.150	1	* * '	* * * * * * * * * *	*******	* * * *	1.250	
2.100	1	* * '	* * * * * * * * * *	*******	* * * *	1.250	
2.050	1	***	* * * * * * * * * *	*******	* * * *	1.200	
2.000	1	***	* * * * * * * * * *	*******	* * * *	1.200	
1.950		****	* * * * * * * * * *	*******	* * * *	1.150	
1.900		*****	* * * * * * * * * *	*******	****	1.100	
1.850	1	*****	* * * * * * * * * *	*******	****	1.100	
1.800	1	******	* * * * * * * * * *	*******	* * * *	1.050	
1.750	1	* * * * * * *	* * * * * * * * * *	*******	* * * *	1.000	
1.700	1	* * * * * * *	* * * * * * * * * *	*******	* * * *	1.000	
1.650	1	. * * * * * * * *	* * * * * * * * * *	*******	* * * *	0.950	
	1+	+,	+	+	+		
	0.500	1.000	1.500	2.000	2.500		



Qualification Database

V_{IL} vs. V_{IO} @ 105°C

	0.000	0.500	1.000	1.500	2.000	first pass data
2 000	+,	+,	+,	+,	+	1 050
3.000		**********		• • • • • • • • • • •		1.250
2.950	*******	********	**********	•••••		1.250
2.900	*******	********	********	••••		1.200
2.850	******	*******	*******	••••		1.200
2.800	******	*******	*******	•••••		1.150
2.750	******	******	******	•••••		1.150
2.700	*******	*****	******	• • • • • • • • • • •		1.150
2.650	******	******	******			1.100
2.600	******	******	******			1.100
2.550	*******	*******	*****			1.100
2.500	******	******	*****			1.100
2.450	******	******	*****			1.050
2.400	******	******	*****			1.050
2.350	******	******	****			1.000
2.300	******	*******	****			1.000
2.250	******	*******	****			1.000
2.200	******	*******	***			0.950
2.150	******	*******	***			0.950
2.100	******	*******	**			0.900
2.050	******	*******	**			0.900
2.000	******	******	**			0.900
1.950	******	*******	*			0.850
1.900	******	*******	*			0.850
1.850	******	*******	*			0.850
1.800	******	*******	*			0.850
1.750	******	*******	*			0.850
1.700	******	*******	*			0.850
1.650	******	*******				0.800
	+	+,	+	+	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{IO} @ 85°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+,	+,	+,-	+,	+			
3.000	*******	******	*********			1.250		
2.950	*******	* * * * * * * * * *	*********	• • • • • • • • • • •		1.250		
2.900	*******	*******	* * * * * * * * • • •			1.200		
2.850	******	******	* * * * * * * * • • •			1.200		
2.800	******	*******	* * * * * * * * • • •			1.200		
2.750	******	******	* * * * * * * • • • •			1.150		
2.700	******	*******	* * * * * * *			1.150		
2.650	******	*******	* * * * * * *			1.150		
2.600	******	*******	* * * * * *			1.100		
2.550	******	******	* * * * * *			1.100		
2.500	******	*******	* * * * * *			1.100		
2.450	* * * * * * * *	*******	* * * * *			1.050		
2.400	******	*******	* * * * *			1.050		
2.350	******	*******	* * * *			1.000		
2.300	******	*******	* * * *			1.000		
2.250	******	*******	* * * *			1.000		
2.200	******	*******	* * *			0.950		
2.150	******	*******	* * *			0.950		
2.100	******	*******	* * *		İ	0,950		
2.050	******	*******	**			0,900		
2.000	******	*******	**			0,900		
1.950	 * * * * * * * *	******	* *			0.900		
1.900	 * * * * * * * *	*******	*			0.850		
1 850	*******	*******	*			0 850		
1 800	 * * * * * * * *	******	*			0 850		
1 750	 * * * * * * * *	*******	*			0.850		
1 700	******	*******				0 800		
1 650	 * * * * * * * *	*******				0.800		
1.050	1					0.800		
	1+,	0 500	1 000	1 500	2 000			
	0.000	0.500	T.000	T.200	2.000			



V_{IL} vs. V_{IO} @ 25°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
3 000	+,	*********	+,	+,	+	1 200		
2 950		********	********	• • • • • • • • • • •		1 250		
2.950	+++++++		*********	•••••		1.250		
2.900	******	********	********			1 250		
2.030	* * * * * * * *	********				1 200		
2.800	+++++++		********	•••••		1.200		
2.750	*******	*******	******	• • • • • • • • • • •	• • • •	1 150		
2.700	* * * * * * * *	********	******			1 150		
2.030	*******	*******	******	• • • • • • • • • • •		1 150		
2.000	******	*******	*****			1 100		
2.550	 * * * * * * * * *	*******	*****			1 100		
2.300	 * * * * * * * * *	*******	*****			1 100		
2.400	 * * * * * * * * *	********	****			1 050		
2.400	 *******	********	····· ****			1 050		
2.300	 * * * * * * * * *	********	****			1 000		
2.300	 * * * * * * * * *	* * * * * * * * * *	····· * * * *			1 000		
2 200	 *******	********	****			1 000		
2.150	 * * * * * * * * *	* * * * * * * * * *	* * *			0 950		
2.100	*******	*******	***			0.950		
2 050	 *******	********	**			0 900		
2 000	 * * * * * * * * *	********	**			0 900		
1.950	 * * * * * * * *	********	**			0.900		
1 900	 * * * * * * * *	********	*			0 850		
1.850	 * * * * * * * *	********	*			0.850		
1.800	*******	********	*			0.850		
1.750	*******	********	*			0.850		
1.700	*******	********				0.800		
1.650	******	********				0.800		
	+	+	+	+	+			
	0.000	0.500	1.000	1.500	2.000			

V_{IL} vs. V_{IO} @ -40°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+,	+,	+,-	+,	+			
3.000	*******	*******	* * * * * * * * * * *	•••••		1.300		
2.950	*******	*******	* * * * * * * * * * .			1.250		
2.900	*******	*******	*********			1.250		
2.850	*******	*******	*********			1.250		
2.800	*******	*******	* * * * * * * * • • •			1.200		
2.750	******	*******	* * * * * * * * • • •			1.200		
2.700	******	*******	* * * * * * * * • • •			1.200		
2.650	******	********	* * * * * * * • • • •			1.150		
2.600	******	********	* * * * * * *			1.150		
2.550	******	********	* * * * * * *			1.150		
2.500	******	*******	*****			1.100		
2.450	******	*******	*****			1.100		
2.400	******	*******	*****			1.100		
2.350	******	*******	* * * * *			1.050		
2.300	******	*******	* * * * *			1.050		
2.250	******	*******	****			1.000		
2.200	******	*******	* * * *			1.000		
2.150	******	*******	* * * *			1.000		
2.100	******	*******	* * *			0.950		
2.050	******	*******	* * *			0.950		
2.000	******	*******	* *			0.900		
1.950	******	*******	**			0.900		
1.900	******	*******	**			0.900		
1.850	******	*******	*			0.850		
1.800	******	*******	*			0.850		
1.750	******	*******	*			0.850		
1.700	******	* * * * * * * * * *	*			0.850		
1.650	. * * * * * * * *	*******				0.800		
	+,	+ ,	+,	+,	+			
	0.000	0.500	1.000	1.500	2.000			



Qualification Database

V_{OH} vs. V_{IO} @ 105°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+,-	+, -	+, -	+,-	+	
3.000	******	* * * * * * * * * *	* * * * * * * * * *	***		2.950
2.950	******	* * * * * * * * * *	* * * * * * * * * *	**		2.900
2.900	******	* * * * * * * * * *	* * * * * * * * * *	*		2.850
2.850	******	* * * * * * * * * *	* * * * * * * * * *	• • • • • • • • • •		2.800
2.800	******	* * * * * * * * * *	*********			2.750
2.750	******	* * * * * * * * * *	* * * * * * * * • • •			2.700
2.700	******	* * * * * * * * * *	* * * * * * * • • • •			2.650
2.650	******	* * * * * * * * * *	* * * * * *			2.600
2.600	******	* * * * * * * * * *	* * * * *			2.550
2.550	******	* * * * * * * * * *	* * * *			2.500
2.500	******	* * * * * * * * * *	* * *			2.450
2.450	******	* * * * * * * * * *	* *			2.400
2.400	******	* * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *				2.300
2.300	******	*********				2.250
2.250	******	*******				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	*****				2.050
2.050	******	****				2.000
2.000	******	* * *				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******.					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+,-	+,-	+,-	+	
	1.500	2.000	2.500	3.000	3.500	

V_{OH} vs. V_{IO} @ 85°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+,-	+,	+,-	+,-	+	
3.000	******	******	* * * * * * * * * *	***		2.950
2.950	******	* * * * * * * * * * *	* * * * * * * * * *	**		2.900
2.900	******	* * * * * * * * * * *	* * * * * * * * * *	*		2.850
2.850	******	*****	* * * * * * * * * *			2.800
2.800	******	* * * * * * * * * * *	* * * * * * * * * .			2.750
2.750	******	* * * * * * * * * * *	* * * * * * * * • • •			2.700
2.700	******	*****	* * * * * * *			2.650
2.650	******	*****	* * * * * *			2.600
2.600	******	*****	* * * * *			2.550
2.550	******	******	* * * *			2.500
2.500	******	******	* * *			2.450
2.450	******	******	* *			2.400
2.400	******	* * * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *				2.300
2.300	******	*********				2.250
2.250	******	*******				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	*****				2.050
2.050	******	****				2.000
2.000	******	***				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******				[1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+,	+,-	+,-	+ İ	
	1.500	2.000	2.500	3.000	3.500	



V_{OH} vs. V_{IO} @ 25°C

	1.500	2.000	2.500	3.000	3.500	first pass data
2 000	+,-	+, -		· + , ·	+	2 050
3.000				* * * *		2.950
2.950	*****	* * * * * * * * * * * * *		***		2.900
2.900	*****	*********	*****	**		2.850
2.850	******	* * * * * * * * * * * * *	*********	•••••		2.800
2.800	******	**********	********			2.750
2.750	******	**********	********			2.700
2.700	******	*********	*******			2.650
2.650	*****	*********	******			2.600
2.600	******	*********	*****			2.550
2.550	******	*********	*****			2.500
2.500	******	*********	****			2.450
2.450	*****	*********	***			2.400
2.400	*****	*********	**			2.350
2.350	******	*********	*			2.300
2.300	*****	**********				2.250
2.250	*****	*********				2.200
2.200	*****	*******				2.150
2.150	*****	******				2.100
2.100	*****	*****				2.050
2.050	*****	****				2.000
2.000	*****	****				1.950
1.950	******	***				1.900
1.900	******	**				1.850
1.850	******	*				1.800
1.800	*****					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+	+		+,	+	
	1.500	2.000	2.500	3.000	3.500	

V_{OH} vs. V_{IO} @ -40°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+,-	+,	+,-	+,-	+	
3.000	******	******	* * * * * * * * * *	***		2.950
2.950	******	* * * * * * * * * * *	* * * * * * * * * *	**		2.900
2.900	******	* * * * * * * * * * *	* * * * * * * * * *	*		2.850
2.850	******	*****	* * * * * * * * * *			2.800
2.800	******	*****	* * * * * * * * * .			2.750
2.750	******	*****	* * * * * * * * • • •			2.700
2.700	******	*****	* * * * * * *			2.650
2.650	******	*****	* * * * * *			2.600
2.600	******	*****	* * * * *			2.550
2.550	******	******	* * * *			2.500
2.500	******	******	* * *			2.450
2.450	******	******	* *			2.400
2.400	******	* * * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *				2.300
2.300	******	*********				2.250
2.250	******	*******				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	*****				2.050
2.050	******	****				2.000
2.000	******	***				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******				[1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+,	+,-	+,-	+ İ	
	1.500	2.000	2.500	3.000	3.500	



Qualification Database

V_{OL} vs. V_{IO} @ 105°C

	0.000	0.500	1.000	first pass data
	+,	+,	+	
3.000	.******	*******	***	0.050
2.950	.******	*******	***	0.050
2.900	. * * * * * * *	* * * * * * * * * *	***	0.050
2.850	. * * * * * * *	* * * * * * * * * *	***	0.050
2.800	.******	*******	***	0.050
2.750	. * * * * * * *	* * * * * * * * * *	***	0.050
2.700	. * * * * * * *	* * * * * * * * * *	***	0.050
2.650	.******	*******	***	0.050
2.600	. * * * * * * *	* * * * * * * * * *	***	0.050
2.550	. * * * * * * *	* * * * * * * * * *	***	0.050
2.500	.******	*******	***	0.050
2.450	. * * * * * * *	* * * * * * * * * *	***	0.050
2.400	. * * * * * * *	* * * * * * * * * *	***	0.050
2.350	.******	*******	***	0.050
2.300	. * * * * * * *	* * * * * * * * * *	***	0.050
2.250	. * * * * * * *	* * * * * * * * * *	***	0.050
2.200	.******	*******	***	0.050
2.150	. * * * * * * *	* * * * * * * * * *	***	0.050
2.100	. * * * * * * *	* * * * * * * * * *	***	0.050
2.050	.******	*******	***	0.050
2.000	. * * * * * * *	* * * * * * * * * *	***	0.050
1.950	.******	*******	***	0.050
1.900	.******	*******	***	0.050
1.850	.******	*******	***	0.050
1.800	.******	*******	***	0.050
1.750	.******	*******	***	0.050
1.700	. * * * * * * *	* * * * * * * * * *	***	0.050
1.650	· * * * * * * *	* * * * * * * * * *	***	0.050
	+,	+,	+	
	0.000	0.500	1.000	

V_{OL} vs. V_{IO} @ 85°C

	0.000	0.500	1.000	first	pass	data
	+,	+,	+			
3.000	. * * * * * * *	*******	****	0.050		
2.950	. * * * * * * *	********	****	0.050		
2.900	. * * * * * * *	********	* * * *	0.050		
2.850	. * * * * * * *	*******	****	0.050		
2.800	. * * * * * * *	********	****	0.050		
2.750	. * * * * * * *	*******	****	0.050		
2.700	. * * * * * * *	*******	****	0.050		
2.650	. * * * * * * *	********	* * * *	0.050		
2.600	. * * * * * * *	********	* * * *	0.050		
2.550	. * * * * * * *	********	* * * *	0.050		
2.500	. * * * * * * *	********	* * * *	0.050		
2.450	. * * * * * * *	********	* * * *	0.050		
2.400	. * * * * * * *	********	* * * *	0.050		
2.350	. * * * * * * *	********	***	0.050		
2.300	. * * * * * * *	********	* * * *	0.050		
2.250	. * * * * * * *	********	* * * *	0.050		
2.200	. * * * * * * *	********	****	0.050		
2.150	. * * * * * * *	********	****	0.050		
2.100	. * * * * * * *	********	****	0.050		
2.050	. * * * * * * *	*******	***	0.050		
2.000	. * * * * * * *	********	****	0.050		
1.950	.******	********	****	0.050		
1.900	. * * * * * * *	*******	****	0.050		
1.850	. * * * * * * *	********	****	0.050		
1.800	.******	********	****	0.050		
1.750	. * * * * * * *	*******	****	0.050		
1.700	. * * * * * * *	*******	****	0.050		
1.650	i . * * * * * * *	*******	****	0.050		
	+,	+,	+İ			
	0.000	0.500	1.000			



V_{OL} vs. V_{IO} @ 25°C

	0.000	0.500	1.000	first	pass	data
	+,	+,	+			
3.000	.******	********	****	0.050		
2.950	.******	********	****	0.050		
2.900	.******	********	****	0.050		
2.850	.******	********	****	0.050		
2.800	.******	********	****	0.050		
2.750	.******	********	****	0.050		
2.700	.******	********	****	0.050		
2.650	.******	********	****	0.050		
2.600	.******	********	****	0.050		
2.550	.******	********	****	0.050		
2.500	.******	********	****	0.050		
2.450	.******	********	****	0.050		
2.400	.******	********	****	0.050		
2.350	.******	********	****	0.050		
2.300	.******	* * * * * * * * * *	****	0.050		
2.250	.******	********	****	0.050		
2.200	.******	********	****	0.050		
2.150	. * * * * * * *	* * * * * * * * * *	****	0.050		
2.100	.******	* * * * * * * * * *	****	0.050		
2.050	.******	* * * * * * * * * *	****	0.050		
2.000	. * * * * * * *	* * * * * * * * * *	****	0.050		
1.950	.******	* * * * * * * * * *	****	0.050		
1.900	.******	* * * * * * * * * *	****	0.050		
1.850	. * * * * * * *	* * * * * * * * * *	****	0.050		
1.800	.******	* * * * * * * * * *	****	0.050		
1.750	.******	* * * * * * * * * *	****	0.050		
1.700	.******	* * * * * * * * * *	***	0.050		
1.650	.******	* * * * * * * * * *	****	0.050		
	+,	+,	+			
	0.000	0.500	1.000			

V_{OL} vs. V_{IO} @ -40°C

	0.000	0.500	1.000	first	pass	data
	+,	+,	+			
3.000	.******	* * * * * * * * * *	***	0.050		
2.950	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.900	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.850	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.800	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.750	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.700	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.650	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.600	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.550	. * * * * * * *	* * * * * * * * * *	***	0.050		
2.500	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.450	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.400	. * * * * * * *	* * * * * * * * * *	***	0.050		
2.350	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.300	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.250	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.200	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.150	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.100	. * * * * * * *	* * * * * * * * * *	***	0.050		
2.050	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.000	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.950	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.900	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.850	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.800	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.750	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.700	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.650	. * * * * * * * *	* * * * * * * * * *	***	0.050		
	+,	+,	+			
	0.000	0.500	1.000			



16. Quality Assurance Guidelines

Cypress is totally committed to shipping the highest quality product to its customers.

To assure this quality commitment, each commercial manufacturing lot must meet the requirements defined in all of the specifications listed below:

Procedure	Test Method	Quality Test
Electrical Classification Tests	Guard banded to Data Sheet Specification	100%
Mark	Cypress F16-018	100%
Lead Scan / Straighten	Cypress F16-049	100%
Visual / Mechanical Inspection	Cypress F16-049	100%
QA Documentation / Test verification	Cypress F06-027	100%
QA - Visual / Mechanical	Cypress F06-027	Sample
Excelsior Monitor (See Below)	Cypress F00-006	Sample
Qualification Maintenance Program	Cypress F01-002.18	Sample

16.1 Excelsior Quality Monitor

Cypress's Excelsior Quality Program is an in-line monitor of electrical, visual/mechanical, solderability and marking permanency quality. Data from Excelsior Electrical Monitor may be made available to customers on request. Samples are selected from production lots and subjected to data sheet electrical temperature requirements. Any failures are analyzed by product engineering and appropriate corrective action is implemented. The excelsior quality levels are summarized by each product line on a monthly basis. This monitor has proven to be instrumental in Cypress's drive to attain the highest quality levels in the industry.

16.2 Process Change Notification

The Cypress Process Change Notification System aims to notify the customer of major product changes 90 days prior to the implementation of that change. A change is considered to be major if it affects the application, performance, quality, reliability, parameter distribution, form, fit or function of the product. In addition we may also notify changes such as relocation of manufacturing sites, certain Data Sheet items, or other changes that may affect use or acceptance of the product. It should be noted that all changes are fully evaluated and qualified in accordance with well established and rigorous procedures. The changed product is not released for production or shipment until satisfactory qualification results, consistent with stable processes, predictable distributions and satisfactory and expected reliability figures and yields are achieved. Often shipment is recommended before the formal qualification report is available. The actual qualification tests, however, are completed and approved prior to shipment.

16.3 Customer Corrective Action Request

Cypress's Customer Corrective Action Request (CCAR) system provides a means for submitting customer perceived product problems to Cypress's factory for analysis. The analysis may be comprised of several stages, usually an initial analysis and follow-up analysis. A summary of Cypress's findings are issued. These may include corrective actions, requests for additional information or detailed failure analysis results.



17. Qualification Maintenance Program

The Cypress Qualification Maintenance Program (QMP) is used to measure the reliability of all process families on a regular basis. As it is not feasible to monitor the reliability of each of the literally hundreds of device types that Cypress produces, devices representative of the wafer fabrication process and the generic device grouping are selected on the basis of complexity, production volume, and strategic importance. These samples are subjected to the typical accelerated stress tests listed below on a monthly basis. Any failures encountered are analyzed by product engineering and appropriate corrective action is implemented. The results of this testing are summarized in the Cypress Quarterly Reliability Report (QRR).

17.1 Types of Stress

Several different process technology groups have been identified based on similarity of process parameters. Representative product types for each of these groups are listed in the Cypress QRR. Failure rates are tabulated for defective sub-populations and competing failure mechanisms. Two common measures of failure rates are early life failure rate (EL) and inherent life failure rate (IL). The early life period corresponds to approximately the first 4,000 hours at field use conditions. The inherent life corresponds to the useful life beyond the first 4000 of field operation. For these calculations, device operation temperature is assumed to be 55°C ambient unless otherwise noted. Voltage acceleration factors are used in the analysis wherever noted.

17.2 Reliability Monitor Stress Conditions

Stress	Package	Typical Duration	Target Sample Size	Typical Conditions
Early Life	All	24, 168 hours	350	125°C or 150°C, V _{CC} max
Inherent Life	All	1000 hours	120	125°C or 150°C, V _{CC} max
Endurance Cycling	All	10000 cycles	64	90°C
Data Retention Bake	All	1000 hours	64	150°C
Preconditioning (PC)	All	216 hours	231	30°C/70% RH Soak, 3X Reflow @ 260°C
PC + Temperature	Discrete, 2 die MCP	1000 cycles	77	–40°C to 150°C
Cycle	> 2 die MCP	Typical Duration Target Sample Size Typical Conditions All 24, 168 hours 350 125°C or 150°C, V _{CC} max All 1000 hours 120 125°C or 150°C, V _{CC} max All 1000 hours 64 90°C All 1000 hours 64 150°C All 1000 hours 64 90°C All 1000 hours 64 90°C All 1000 hours 64 150°C All 1000 hours 77 40°C All 216 hours 77 -40°C to 150°C ete, 2 die MCP 1000 cycles 77 -55°C to 125°C BGA 264 hours 77 110°C, 85% RH, V _{CC} max alt. bias ead Frame 96 hours 77 130°C, 85% RH, V _{CC} max alt. bias		
	BGA	264 hours	77	110°C, 85% RH, V _{CC} max alt. bias
FC + blased HAST	Lead Frame	96 hours	77	130°C, 85% RH, V _{CC} max alt. bias
PC + Unbiased HAST	All	96 hours	77	110°C, 85% RH, no bias

18. Statistical Process Management

Statistical Process Management is used extensively throughout manufacturing and engineering areas in Cypress to help in reducing process variation and optimizing product/process performance. Examples of the tools used are Statistical Process Control (SPC), Process Capability Studies, Design of Experiments, Measurement Systems Analysis, Systematic Problem Solving, Structured project management, and statistical yield analysis, etc.

Some highlights of our SPC program include:

- Ubiquitous and intelligent use of problem solving methodologies
- SPC is 100% automated in all manufacturing areas using both statistically and economically derived Control Limits
- Out of Control Trouble Shooting Guides
- Statistical Equipment Control, (monitoring and control of input variables)
- Advanced Process Control (model based, active run-to-run control of processes during wafer fabrication)
- Suppliers are encouraged to implement SPC
- Six-Sigma target for critical processes

18.1 Kaizen + Program

All the training of statistical analysis tools, as well as other hard and soft improvement skills such as FMEA, Lean, Error Proofing, Structured Teamwork, are provided to employees as a part of Cypress's Kaizen+ (continuous improvement) program. The program involves all functional groups by establishing a structure that consists of a Champion, internal/external certified Black, Brown, Green and Yellow Belts in each organization to drive for improvement projects. The results are shared in a Project Sharing Conference twice per year. Statistical thinking and use of statistical methods are a part of Cypress's Kaizen+ culture.



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19. Revision History

Section	Description
Revision 01 (June 20, 2013)	
	Initial release

Documen Documen	ocument Title: S29GL256S (WXIC) Qualification Database ocument Number: 002-00606						
Revision	ECN	Orig. of Change	Submission Date	Description of Change			
**	_	-	06/20/2013	Initial release			
*A	6204461	CNSO	06/12/2018	Updated Assembly Packaging Summary on page 10: Updated LAE064 on page 10: Changed value of Theta Ja from 39°C/W to 33°C/W. Changed value of Psi Jt from 11°C/W to 0.07°C/W. Updated LAA064 on page 10: Changed value of Theta Ja from 39°C/W to 24.1°C/W. Changed value of Psi Jt from 11°C/W to 0.07°C/W. Updated TS056 on page 11: Changed value of Theta Ja from 40°C/W to 46°C/W. Changed value of Theta Ja from 40°C/W to 0.21°C/W. Updated VBU056 on page 11: Changed value of Theta Ja from 39°C/W to 34.5°C/W. Updated VBU056 on page 11: Changed value of Psi Jt from 11°C/W to 0.10°C/W. Updated VBU056 on page 11: Changed value of Psi Jt from 11°C/W to 0.10°C/W. Updated Quality Assurance Guidelines on page 69: Updated Process Change Notification on page 69: Replaced "Advance Change Notification" with "Process Change Notification" in heading. Updated description. Updated to Cypress template. Completing Sunset Review.			



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S29GL01GS (XMC 85C 105C)



Qualification Database

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1. Introduction

The Cypress[®] S29GL01GS flash memory device has a die size of 6.803 × 7.455 mm.

2. Die Photograph

Figure 1. Die Photograph





1. X in the diagram is pad #1. Count counter clockwise.



3. Pad Definition

Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA	Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA
1	NC			38	VCC	43	G5
2	A23	1	C8	39	VSS	33,52	H7
3	A22	2	B8	40	VCC	43	G5
4	A15	3	D7	41	VSS	33,52	H7
5	A14	4	C7	42	VSS	33,52	H7
6	A13	5	A7	43	VCC	43	G5
7	A12	6	B7	44	A0	31	E2
8	A11	7	D6	45	CE#	32	F2
9	A10	8	C6	46	OE#	34	G2
10	A9	9	A6	47	NC		
11	A8	10	B6	48	DQ0	35	E3
12	A19	11	D5	49	DQ8	36	F3
13	A20	12	D4	50	VSS	33,52	H2, E8
14	WE#	13	A5	51	VIO	29	F1, D8
15	VSS	33, 52	H7	52	DQ1	37	H3
16	VCC	43	G5	53	DQ9	38	G3
17	VSS	33, 52	H7	54	DQ2	39	E4
18	VCC	43	G5	55	DQ10	40	F4
19	NC			56	DQ3	41	H4
20	RESET#	14	B5	57	DQ11	42	G4
21	A21	15	C5	58	DQ4	44	H5
22	WP#	16	B4	59	DQ12	45	F5
23	RY/BY#	17	A4	60	DQ5	46	E5
24	VIO	29	D8, F1	61	DQ13	47	G6
25	VSS	33, 52	H7	62	NC		
26	A18	18	C4	63	VSS	33,52	H7
27	A17	19	В3	64	VCC	43	G5
28	A7	20	A3	65	DQ6	48	H6
29	A6	21	C3	66	DQ14	49	F6
30	A5	22	D3	67	DQ7	50	E6
31	A4	23	B2	68	DQ15	51	G7
32	A3	24	A2	69	VIO	29	D8, F1
33	A2	25	C2	70	VSS	33, 52	E8, H2
34	A1	26	D2	71	A16	54	E7
35	DNU	28	E1	72	A25	55	G8
36	VCC	43	G5	73	A24	56	F8
37	VSS	33, 52	H7				



4. Physical Sector Layout

Internal Use Row 86	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use
Row 85	1020	1021	1022	1023					Internal Use	Internal Use	Internal Use	Internal Use
Row 84	1008	1009	1010	1011	1012	1013	1014	1015	1016	1017	1018	1019
Row 3	48	49	50	51	52	53	54	55	56	57	58	59
Row 2	32	33	34	35	36	37	38	39	40	41	42	43
Row 1	16	17	18	19	20	21	22	23	24	25	26	27
Row 0	0	1	2	3	4	5	6	7	8	9	10	11
Vertical Bank	0	1	2	3	0	1	2	3	0	1	2	3
Bank			0				1			1	2	

Figure 2. Physical Sector Layout



5. Sector Enlargement

Figure 3. Sector Enlargement

	IO Organization										
	Internal Use	0	1	2	3	4	5	6	7	8	9
M 3 B L	0-7	0-63	64-127	128-191	192-255	256-319	320-383	384-447	448-511	512-575	576-639
M1BL	8-15	0-127	128-255	256-383	384-511	512-639	640-767	768-895	896-1023	1024-1151	1152-1279

	10	11	12	13	14	15	Internal Use	Internal Use	Internal Use	Internal Use
M3BL	640-703	704-767	768-831	832-895	896-959	960-1023	1024-1063	1064-1071	1072-1079	0-7
M1BL	1280-1407	1408-1535	1536-1663	1664-1791	1792-1919	1920-2047	2048-2127	2128-2143	2144-2159	0-7



6. Die Processing Summary

The Cypress S29GL01GS flash memory device is manufactured using the 65 nm MirrorBit[®] Eclipse™ process technology.

The device is processed at WXIC, a 12-inch CMOS manufacturing facility located in Wuhan, China.

The device is manufactured on the highly reliable CS239LS process.





PERIPHERY



6.1 Key Features of the CS239LS MirrorBit Eclipse Process Technology

A. Technology

- CMOS Triple-well process
- Proven reliable Flash MirrorBit Eclipse Technology

B. Transistor Types

- n-channel enhancement
- n-channel intrinsic
- p-channel enhancement
- MirrorBit core cell

C. Process Features

- ONO (oxide nitride oxide) gate dielectric
- Silicon Nitride (SiN) data storage layer

D. Cypress Highlights

- Volume Production Fab
- Solely dedicated to Non-Volatile Memories
- Ongoing Statistical Process Control program



7. Assembly Packaging Summary

7.1 LAE064

Product Description:	S29GL01GS						
i rouder beschption	1-Gigabit, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse process technology						
Package:	LAE064	Qualification:	Q100127				
Description:	(9 x 9 x 1.4 mm) 64-ball, Fortified	d Ball Grid Array Package (fFBGA)					
Con-code:	40780KV-DWR	Theta Ja / Psi Jt:	27.3°C/W / 0.6°C/W				
Assembly Location:	Cypress Thailand	Molding Compound:	ShinEtsu KMC 3580LVA				
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	QMI 546				
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres	Bond Wire:	Copper				
Comments:							
Est. Field Temperature:	55°C	Life Test Temperature:	125°C				
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA				
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V				
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts				
Est. Field Delta Tj:	57.9°C	Est. Stress Delta Tj:	126.4°C				
Die:	98661B	Die Size:	6.803 x 7.455 mm				
Process:	CS239LS (65 nm)	Fab:	WXIC				
Туре:	MirrorBit Eclipse	Density:	1G				

7.2 TS056

Product Description:	S29GL01GS 1-Gigabit, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse process technology						
Package:	TS056	Q100127a					
Description:	(18.4 x 14.0 x 1.0 mm) 56-lead, Thin Small Outline Package (TSOP)						
Con-code:	40694EF-TXA	Theta Ja / Psi Jt:	38°C/W / 0.21°C/W				
Assembly Location:	Cypress Thailand	Molding Compound:	Hitachi CEL 9200HF10-U				
Substrate/Leadframe:	Copper Leadframe	Die Attachment:	Ablebond 8340				
Lead Finish:	100% Matte Sn Plating	Bond Wire:	Copper				
Comments:							
Est. Field Temperature:	72°C	Life Test Temperature:	125°C				
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA				
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V				
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts				
Est. Field Delta Tj:	75.0°C	Est. Stress Delta Tj:	126.4°C				
Die:	98661B	Die Size:	6.803 x 7.455 mm				
Process:	CS239LS (65 nm)	Fab:	WXIC				
Туре:	MirrorBit Eclipse	Density:	1G				



7.3 LAA064

Product Description:	S29GL01GS						
Floduci Description.	1-Gigabit, 3.0 Volt-Only Page Mode Flash Memory featuring 65 nm MirrorBit Eclipse process technology						
Package:	LAA064	Qualification:	Q100127b				
Description:	(13.0 x 11.0 x 1.4 mm) 64-ball, F	ortified Ball Grid Array Package (FE	3GA)				
Con-code:	40781KV-DWR	Theta Ja / Psi Jt:	19°C/W / 0.6°C/W				
Assembly Location:	Cypress Thailand	Molding Compound:	ShinEtsu KMC 3580LVA				
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	QMI 546				
Lead Finish:	96.5Sn 3.0Ag 0.5Cu Spheres	Bond Wire:	Copper				
Comments:							
Est. Field Temperature:	55°C	Life Test Temperature:	125°C				
Est. DC Field Current:	25 mA	Life Test Dynamic Current:	10 mA				
Est. Field Voltage:	3.0V	Life Test Voltage:	3.6V				
Est. Field Power Dissipation:	75 mWatts	Est. Stress Power Dissipation:	36 mWatts				
Est. Field Delta Tj:	57.9°C	Est. Stress Delta Tj:	126.4°C				
Die:	98661B	Die Size:	6.803 x 7.455 mm				
Process:	CS239LS (65 nm)	Fab:	WXIC				
Туре:	MirrorBit Eclipse	Density:	1G				



8. Assembly Bonding Diagram

8.1 TS056 Package

Figure 5. 56-Pin—TS056 Package





8.2 LAE064 Package



Figure 6. 64-Ball—LAE064 Package



8.3 LAA064 Package







9. Test Methodology

Testing includes

- 4 hour, 250°C Data Retention Bake (in wafer form)
- Special test mode for extended life operation
- Proprietary screens for endurance

Wafer Sort (Austin, Texas, USA)

At Wafer Sort, all die experience 100% testing for:

- DC Parametrics
- AC Functionality
- Programmability
- Erasability

Class Test (Bangkok, Thailand)

At Class Test, all devices are tested for:

- DC Parametrics
- AC Functionality
- AC Speed
- Programmability
- Erasability

Test Coverage

All parameters specified in the data sheet are 100% tested in production unless otherwise specified. Those parameters not tested in production are guaranteed by characterization or correlation to other tests. AC speed testing is performed at class test.

Test Correlation and Guard Banding

Tester correlation to bench set-up has been completed for all tested parameters. Tester repeatability studies have been run. These results have been evaluated and incorporated into the tester guard band strategy. Guard bands have been implemented which demonstrate acceptable yield, quality assurance and customer satisfaction.

Test Flow

See the generalized Test Flow for the S29GL01GS in Section 10.


10. Generalized Test Flow

The S29GL01GS Generalized Test Flow for Industrial Temperature Range:





11. Quality and Reliability Data

11.1 S29GL01GS High Temperature Operating Life Test Configuration

Pin/Pad #	Function	Resistor	Bias/CLK
1	A23	2.7K	CLK23
2	A22	2.7K	CLK22
3	A15	2.7K	CLK15
4	A14	2.7K	CLK14
5	A13	10K	CLK13
6	A12	2.7K	CLK12
7	A11	2.7K	CLK11
8	A10	2.7K	CLK10
9	A9	2.7K	CLK9
10	A8	2.7K	CLK8
11	A19	2.7K	CLK19
12	A20	2.7K	CLK20
13	WE#	2.7K	VCC
14	RESET#	2.7K	VCC
15	A21	2.7K	CLK21
16	WP#	2.7K	VCC
17	RY/BY#	2.7K	VCC
18	A18	2.7K	CLK18
19	A17	2.7K	CLK17
20	A7	2.7K	CLK7
21	A6	2.7K	CLK6
22	A5	2.7K	CLK5
23	A4	2.7K	CLK4
24	A3	2.7K	CLK3
25	A2	2.7K	CLK2
26	A1	2.7K	CLK1
27	RFU		NC
28	RFU		NC

Pin/Pad #	Function	Resistor	Bias/CLK
56	A24	2.7K	CLK24
55	A25	2.7K	CLK25
54	A16	2.7K	CLK16
53	RFU		NC
52	VSS		GND
51	DQ15	2.7K	VCC
50	DQ7	2.7K	VCC
49	DQ14	2.7K	VCC
48	DQ6	2.7K	VCC
47	DQ13	2.7K	VCC
46	DQ5	2.7K	VCC
45	DQ12	2.7K	VCC
44	DQ4	2.7K	VCC
43	VCC		VCC
42	DQ11	2.7K	VCC
41	DQ3	2.7K	VCC
40	DQ10	2.7K	VCC
39	DQ2	2.7K	VCC
38	DQ9	2.7K	VCC
37	DQ1	2.7K	VCC
36	DQ8	2.7K	VCC
35	DQ0	2.7K	VCC
34	OE#	2.7K	VCC
33	VSS		GND
32	CE#	2.7K	GND
31	A0	2.7K	CLK0
30	RFU		NC
29	VIO	2.7K	VCC



11.2 CS239/L Life Test Failure Rate Calculation

HTOL Stress Temperature @ 125°C

	Re	Read Points / Test Results		Мос	deling P	aramete	5°C	Average Failure Rate FITS @ 55°C, 60% Conf.		
Failure Mechanisms	24 hrs	168 hrs	1000 hrs	Ea eV	TAF	VAF	OAF	MTTF (yrs)	Early Life	Inherent Life
PLASTIC										
Sample Size	1745	3025	345							
Zero fails, Process ave. Ea	0 (1)	0	0	0.66	53	1	53		87	23
Totals	0	0	0					4963	87	23

Note:

1. Contributes to Early Life FITS.

Data Retention Bake @ 150°C

Reliability Stress	Number of Rejects	Sample Size	Failure Rate %	Failure Mechanism
500 hrs	0	300	0.00	No Failures
1000 hrs	0	300	0.00	No Failures



Stress Test	Condition	Package Type	Samples Size	Num. of Lots	Number of Fails	Failure Rate %	Comments
	Data F	rom Qualification C	100127				
HTOL (EL)	3.6V, 125°C	LAE064 (1)	192	2	0	0.00	168 hrs
HTOL (IL)	3.6V, 125°C	LAE064 (1)	192	2	0	0.00	500 hrs
Data Retention Bake	150°C	LAE064 (1)	118	2	0	0.00	500 hrs
ESD CDM	N/A	LAE064 (1)	30	2		Passed 1.0	kV
ESD HBM	(100 pF, 1500 Ohms)	LAE064 (1)	168	2		Passed 2.0	kV
Latch Up	125°C, ±100 mA	LAE064 (1)	12	2		Passed	
Endurance (10k)	90°C, 3.6V	LAE064 (1)	100	2	0	0.00	10k cycles
Endurance (10k)	105°C, 3.6V	TS056 (2)	240	3	0	0.00	10k cycles
Endurance (100k)	90°C, 3.6V	LAE064 (1)	50	1	0	0.00	100k cycles
Endurance (100k)	105°C, 3.6V	TS056 (2)	240	3	0	0.00	100k cycles
Preconditioning	PC9/260°C +0°C / -5°C	LAE064 (1)	230	1	Pass	ed Jedec L	3 (Accel.)
Preconditioning + Temp Cycle	PC9/260°C ,40°C / 150°C	LAE064 (1)	77	1	0	0.00	1000 cycles
Preconditioning + HAST	PC9/260°C, Biased, 110°C / 85% RH	LAE064 (1)	77	1	0	0.00	264 hrs
Preconditioning + uHAST	PC9/260°C, Unbiased, 130°C / 85% RH	LAE064 (1)	77	1	0	0.00	96 hrs
	G	eneric Reference D	ata				
Preconditioning	PC1/260°C, +0°C / -5°C	TS056 (3)	67	1	Passed	Jedec L3 / 、	Jeita Rank E
Teconoming	PC9/260°C, +0°C / -5°C	LAA064 (4)	77	1	Passed	Jedec L3 / 、	Jeita Rank E
Preconditioning + Temp Cycle	PC1/260°C, -40°C / 150°C	TS056 (3)	67	1	0	0.00	1000 cycles

Table 1. Summary of Stress Test Results

Notes:

1. Results from Qual Q100127, S29GL01GS, 1G CS239LS (65 nm) MirrorBit Eclipse in 64 Ball fFBGA (9 x 9 x 1.4 mm).

2. Results from QTP#184906, S29GL01GS in 56 Lead TSOP (18.4 x 14 x 1 mm) - Same TS056 Package, Same Product and Process Technology at Fab25.

3. Results from Qual Q100181a, S29GL01GS in 56 Lead TSOP (18.4 x 14 x 1 mm) - Same TS056 Package, Same Product and Process Technology at Fab25.

4. Results from Qual Q100182, S29GL01GS in 64 Ball fFBGA (13 x 11 x 1.4 mm) - Same LAA064 Package, Same Product and Process Technology at Fab25.

Preconditioning Flows

PC1 (Exceeds JEDEC Level 3 and JEITA Rank E) = Bake 125°C, 24hr --> Soak @ 30°C/70%RH, 216hr --> 3x Reflow.

PC9 (Accelerated JEDEC L3 / JEITA Rank E): Bake 125°C, 24hr => Soak @ 60°C/70%RH, 72hr => 3x Reflow.



12. Characterization Test Results

The data is pattern is "Random pattern" unless otherwise indicated.

12.1 DC Parameter Summary, 25°C

Room Temperature, 25°C, 3V V_{CC} Summary

Data Shoot Decemptore		Spec		Average	Min	Мах	Sigmo	Cnk
Data Sheet Parameters	Тур	Мах	Unit	Average	IVIIN	wax	Sigma	Срк
		DC Pa	arameters					
I_{CC1} (V _{CC} Active Read Current) 10 MHz			mA	97.3	91.1	103.1	2.1	
I_{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	51.6	49.1	54.2	0.9	3.1
I_{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	6.0	5.5	6.3	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.9	0.0	6.3	0.4	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.9	5.4	6.2	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.8	5.4	6.1	0.2	>5
I _{CC3} (V _{CC} Active Erase/Program Current)	45	100	mA	44.8	39.4	48.2	1.8	>5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	18.2	9.8	47.6	8.1	3.4
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.018	0.010	0.048	0.0	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μA	18.3	9.8	48.9	8.0	>5
I _{LI} (Input Leakage Current)	0.02	±1	μΑ	0.005	0.000	0.218	0.0	>5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	0.001	0.000	0.011	0.0	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	306.9	198.0	701.0	37.5	>5
Buffer Program Time (256 word)	340	750	μs	390.4	336.9	475.8	25.2	4.8
Buffer Program Time (128 word)	239	750	μs	298.6	256.3	358.3	17.5	>5
Buffer Program Time (64 word)	198	750	μs	247.9	215.6	297.1	13.5	>5
Buffer Program Time (32 word)	175	750	μs	218.9	189.3	258.3	11.6	>5
Buffer Program Time (16 word)	160	750	μs	196.4	171.9	229.2	10.5	>5
Single Word Program Time (1 word)	125	400	μs	185.8	163.1	224.3	10.0	>5

Notes:

1. Data was collected from 300 units with 3 different lots 5817940, 5817960, 5817970 (wlot : LD95284, wfno : 5 / wlot : LD95223, wfno : 16 wlot : LD95309, wfno : 24).

2. Sector Erase excludes Random data pattern programming prior to erasure.



12.2 DC Parameter Summary, 85°C

Hot Temperature, 85°C, 3V V_{CC} = V_{IO} Summary

Data Shoot Parametero		Spec		Average	Min	Max	Sigma	Cok
Data Sheet Parameters	Тур	Мах	Unit	Average	IAILL	IVIAX	Sigina	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	102.25	96.96	107.72	1.93	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	54.11	51.56	56.60	0.92	2.1
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	6.29	5.89	6.71	0.14	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	6.21	5.79	6.63	0.14	
I _{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	6.15	5.73	6.54	0.14	
I_{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	6.09	5.67	6.53	0.14	>5
I _{CC3} (V _{CC} Active Erase/Program Current)	45	100	mA	47.27	43.40	51.69	1.61	>5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	50.50	29.12	81.63	11.87	1.4
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.05	0.03	0.09	0.01	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μA	51.01	29.89	81.99	11.96	2.8
I _{LI} (Input Leakage Current)	0.02	±1	μA	0.005	0.000	0.375	0.0	>5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.001	0.000	0.011	0.0	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	220.7	147.0	385.0	22.4	>5
Buffer Program Time (256 word)	340	750	μs	343.5	281.6	404.9	22.9	>5
Buffer Program Time (128 word)	239	750	μs	265.2	216.5	323.3	16.5	>5
Buffer Program Time (64 word)	198	750	μs	221.7	184.5	259.3	13.4	>5
Buffer Program Time (32 word)	175	750	μs	195.8	162.2	228.2	11.3	>5
Buffer Program Time (16 word)	160	750	μs	176.8	153.4	202.9	9.7	>5
Single Word Program Time (1 word)	125	400	μs	170.8	146.6	199.1	9.4	>5

Notes:

1. Data was collected from 300 units with 3 different lots 5817940, 5817960, 5817970 (wlot : LD95284, wfno : 5 / wlot : LD95223, wfno : 16 wlot : LD95309, wfno : 24).

2. Sector Erase excludes Random data pattern programming prior to erasure.



12.3 DC Parameter Summary, 105°C

Data Sheet Parameters		Spec			Av	rage		Average	Min	Max	Sigma	Cnk
Data Sheet Farameters	Тур	Мах	Unit	-40	25	85	105	Average	IVIIII	Wax	Sigilia	Срк
			DC I	Param	eters							
I_{CC1} (V _{CC} Active Read Current) 10 MHz			mA	96.6	97.3	102.3	105.0	105.0	99.7	113.4	2.0	
I_{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	50.8	51.6	54.1	55.0	55.0	52.4	57.0	0.9	1.8
I_{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.8	6.0	6.3	6.4	6.4	5.8	6.7	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.7	5.9	6.2	6.3	6.3	5.7	6.6	0.2	
$I_{CC2}\left(V_{CC}\right.$ Intra-Page Read Current) 40 MHz			mA	5.7	5.9	6.2	6.2	6.2	5.6	6.5	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.6	5.8	6.1	6.2	6.2	5.6	6.5	0.2	>5
I _{CC3} (V _{CC} Active Erase/Program Current)	45	100	mA	41.2	44.8	47.3	54.9	54.9	52.5	57.1	1.0	>5
I _{CC4} (V _{CC} Standby Current)	70	200	μA	15.4	18.2	50.5	81.4	81.4	41.0	132.5	19.9	2.0
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.0	0.0	0.1	0.1	0.081	0.042	0.131	0.020	>5
I_{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	15.6	18.3	51.0	80.8	80.8	42.0	131.5	19.8	2.0
I _{LI} (Input Leakage Current)	0.02	±1	μA	0.0	0.0	0.0	0.0	0.004	-0.020	0.186	0.021	>5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.0	0.0	0.0	0.0	0.001	-0.009	0.013	0.003	>5
<u>م</u>	verag	e Sect	or Era	se/Pre	e-prog	rammin	g Time					
Sector Erase Time (64k word sector)	275	1100	ms					179.8	114.0	297.0	13.9	>5
Buffer Program Time (256 word)	420	1050	μs					313.8	269.0	383.0	16.6	>5
Buffer Program Time (128 word)	320	1050	μs					244.0	209.0	288.0	12.6	>5
Buffer Program Time (64 word)		1050	μs					205.3	178.0	243.0	10.6	>5
Buffer Program Time (32 word)	220	1050	μs					182.5	162.0	217.0	9.2	>5
Buffer Program Time (16 word)	200	1050	μs					164.1	144.0	196.0	7.9	>5
Single Word Program Time (1 word)	125	400	μs					159.5	139.0	191.0	8.2	>5

Hot Temperature, 105°C, 3V V_{CC} = V_{IO} Summary

Notes:

1. Data was collected from 70 units with 2 different lots 5877040 (wflot : LDW3821, wf14, wflot : LDW3961, wf14).

2. Sector Erase data excludes Random data pattern programming prior to erasure.



12.4 DC Parameter Summary, -40°C

Cold Temperature, -40°C, 3V $V_{CC}\,Summary$

Data Shoot Daramatara		Spec		Average	Min	Max	Sigma	Cok
Data Sheet Parameters	Тур	Max	Unit	Average	IAILLI	IVIAX	Sigina	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	96.6	90.5	102.0	2.2	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	50.8	47.9	53.5	1.0	2.9
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.8	5.4	6.3	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.7	5.3	6.2	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.7	5.3	6.1	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.6	5.2	6.1	0.2	>5
I _{CC3} (V _{CC} Active Erase/Program Current)	45	100	mA	41.2	37.1	44.9	1.6	>5
I _{CC4} (V _{CC} Standby Current)	70	100	μA	15.4	8.9	34.2	6.2	4.5
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.016	0.009	0.046	0.0	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	150	μA	15.6	8.8	34.7	6.1	>5
I _{LI} (Input Leakage Current)	0.02	±1	μΑ	0.005	0.000	0.232	0.0	>5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.002	0.000	0.012	0.0	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	363.4	225.0	815.0	46.9	>5
Buffer Program Time (256 word)	340	750	μs	373.7	313.0	469.0	23.1	>5
Buffer Program Time (128 word)	239	750	μs	286.2	245.0	343.0	16.4	>5
Buffer Program Time (64 word)	198	750	μs	239.0	206.0	285.0	13.2	>5
Buffer Program Time (32 word)	175	750	μs	212.1	183.0	258.0	11.2	>5
Buffer Program Time (16 word)	160	750	μs	194.0	166.0	233.0	10.2	>5
Single Word Program Time (1 word)	125	400	μs	183.0	161.0	220.0	9.1	>5

Notes:

1. Data was collected from 300 units with 3 different lots 5817940, 5817960, 5817970 (wlot : LD95284, wfno : 5 / wlot : LD95223, wfno : 16 wlot : LD95309, wfno : 24).

2. Sector Erase excludes Random data pattern programming prior to erasure.



13. DC Device Characterization Data

ICC1 (Asynchronous Read) vs. Temperature



ICC2 (Page Read) vs. Temperature



ICC3 (Active Write) vs. Temperature



ICC4 (Standby Current) vs. Temperature



ICC5 (Reset Current) vs. Temperature



ICC6 (CMOSASM) vs. Temperature





14. AC Device Characterization Data



tACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)

tCE vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tOE vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)





tPACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tDF vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tOH vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)





Cumulative Erase Times per Sector at 105°C (VCC 3V)

















Cumulative WB Program Times per Sector at 105°C (VCC 3V)



Cumulative WB Program Times per Sector at 85°C (VCC 3V)



Cumulative WB Program Times per Sector at 25°C (VCC 3V)









Cumulative WB 256 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB 256 Program Times per Buffer at 85°C (VCC 3V)













Cumulative WB 128 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB 128 Program Times per Buffer at 85°C (VCC 3V)













Cumulative WB 64 Program Times per Buffer at 105°C (VCC 3V)

















Cumulative WB 32 Program Times per Buffer at 105°C (VCC 3V)

















Cumulative WB 16 Program Times per Buffer at 105°C (VCC 3V)

















Cumulative Single Word Program Times per Buffer at 105°C (VCC 3V)

















15. Shmoo Plots

t_{ACC} vs. V_{CC}=V_{IO} @ 25°C

	80.0	90.0	100.0	110.0	first pass	data
	+,	-+,	-+,	-+		
3.650		* * * * * *	*******	**	93.0	
3.600		* * * * * *	*******	**	93.0	
3.550		* * * * * *	*******	**	93.0	
3.500		* * * * * *	*******	**	93.0	
3.450		* * * * * *	*******	**	93.0	
3.400		* * * * * *	********	**	93.0	
3.350		* * * * * *	*******	**	93.0	
3.300		* * * * * *	*******	**	93.0	
3.250		* * * * *	********	**	94.0	
3.200		* * * * *	*******	**	94.0	
3.150		* * * * *	*******	**	94.0	
3.100		* * * * *	********	**	94.0	
3.050		* * * * *	*******	**	94.0	
3.000		* * * * *	*******	**	94.0	
2.950		* * * * *	*******	**	94.0	
2.900		* * * * *	*******	**	94.0	
2.850		* * * * *	* * * * * * * * * *	**	94.0	
2.800		* * * * *	* * * * * * * * * *	**	94.0	
2.750		* * * * *	*******	**	94.0	
2.700		* * * * *	* * * * * * * * * *	**	94.0	
2.650		* * * * *	* * * * * * * * * *	**	94.0	
	+,	-+,	-+,	-+		
	80.0	90.0	100.0	110.0		

t_{ACC} vs. V_{CC}=V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	-+,	· - +	
3.650		* * * * *	* * * * * * * * * *	***	94.0
3.600		* * * *	********	***	95.0
3.550		* * * * *	********	***	94.0
3.500		* * * *	*******	***	95.0
3.450		* * * *	********	***	95.0
3.400		* * * *	********	***	95.0
3.350		* * * *	* * * * * * * * * *	***	95.0
3.300	1	* * * *	*******	***	95.0
3.250		* * * *	* * * * * * * * * *	***	95.0
3.200		* * * *	********	***	95.0
3.150		* * * *	* * * * * * * * * *	**	95.0
3.100		* * * *	********	**	95.0
3.050		* * * *	********	**	95.0
3.000		* * * *	********	**	95.0
2.950		* * * *	* * * * * * * * * *	***	95.0
2.900		* * * *	* * * * * * * * * *	***	95.0
2.850		* * * *	* * * * * * * * * *	***	95.0
2.800		* * * *	* * * * * * * * * *	***	95.0
2.750		* * * *	*******	***	95.0
2.700		* * * *	* * * * * * * * * *	***	95.0
2.650		* * * *	* * * * * * * * * *	***	95.0
	+,	-+,	-+,	· - +	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{CC} = V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first pass d	lata
	+,	+,	+,	+		
3.650		* * '	* * * * * * * * * *	***	96.0	
3.600		* * *	*******	***	96.0	
3.550		* * :	* * * * * * * * * *	***	96.0	
3.500		* * '	* * * * * * * * * *	***	96.0	
3.450		* * :	* * * * * * * * * *	***	96.0	
3.400		* * :	* * * * * * * * * *	***	96.0	
3.350		* * *	* * * * * * * * * *	***	96.0	
3.300		* * :	* * * * * * * * * *	***	96.0	
3.250		* * :	* * * * * * * * * *	***	96.0	
3.200		* * '	* * * * * * * * * *	***	96.0	
3.150		* * :	* * * * * * * * * *	***	96.0	
3.100		* * :	* * * * * * * * * *	***	96.0	
3.050		* * '	* * * * * * * * * *	***	96.0	
3.000		* * :	* * * * * * * * * *	***	96.0	
2.950		*	* * * * * * * * * *	***	97.0	
2.900		* '	* * * * * * * * * *	***	97.0	
2.850		*	* * * * * * * * * *	***	97.0	
2.800		*	* * * * * * * * * *	***	97.0	
2.750		* '	* * * * * * * * * *	***	97.0	
2.700		*	* * * * * * * * * *	***	97.0	
2.650		*	* * * * * * * * * *	***	97.0	
	+,	+,	+,	+		
	80.0	90.0	100.0	110.0		

t_{ACC} vs. V_{CC}=V_{IO} @ -40°C

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	-+,	+	
3.650	1	* * *	*******	***	96.0
3.600	1	* * *	*******	* * *	96.0
3.550			******	* * *	96.0
3.500		***	*******	* * *	96.0
3.450		***	******	***	96.0
3 400		***	******	* * *	96.0
3 350		***	*******	* * *	96.0
3 300		***	******	***	96.0
3 250		***	*******	***	96.0
2 200		***	*******	***	96.0
3.200			******	+++	90.0
3.150			*********	***	96.0
3.100			*******	* * *	96.0
3.050		* * *	*******	***	96.0
3.000		* * *	******	***	96.0
2.950		* * *	******	***	96.0
2.900		* * *	******	* * *	96.0
2.850		* * *	******	* * *	96.0
2.800	1	* * *	* * * * * * * * *	* * *	96.0
2.750	1	* * *	* * * * * * * * *	***	96.0
2.700		* *	* * * * * * * * *	***	97.0
2,650		*	******	***	98.0
	+	-+	-+	+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass d	lata
	+,	+,	+,	+		
3.000		* * * * *	* * * * * * * * * *	* * *	94.0	
2.950		* * * *	* * * * * * * * * *	***	94.0	
2.900		* * * *	* * * * * * * * * *	* * *	94.0	
2.850		* * * *	* * * * * * * * * *	* * *	94.0	
2.800		* * * *	* * * * * * * * * *	***	94.0	
2.750		* * * *	* * * * * * * * * *	***	94.0	
2.700		* * * *	* * * * * * * * * *	* * *	94.0	
2.650		* * * *	* * * * * * * * * *	***	94.0	
2.600		* * * *	* * * * * * * * * *	***	94.0	
2.550		* * * *	* * * * * * * * * *	***	94.0	
2.500		* * * *	* * * * * * * * * *	* * *	94.0	
2.450		* * * *	* * * * * * * * * *	***	94.0	
2.400		* * * *	* * * * * * * * * *	***	94.0	
2.350		* * * *	* * * * * * * * * *	***	94.0	
2.300		* * * *	* * * * * * * * * *	***	94.0	
2.250		* * * *	* * * * * * * * * *	***	94.0	
2.200		* * * *	* * * * * * * * * *	***	94.0	
2.150		* * * *	* * * * * * * * * *	***	94.0	
2.100		* * * *	* * * * * * * * * *	***	94.0	
2.050		* * * *	* * * * * * * * * *	***	95.0	
2.000		* * * *	* * * * * * * * * *	* * *	95.0	
1.950		* * * *	* * * * * * * * * *	* * *	95.0	
1.900		* * * *	* * * * * * * * * *	* * *	95.0	
1.850		* * * *	* * * * * * * * * *	* * *	95.0	
1.800	1	* * * *	* * * * * * * * * *	* * *	95.0	
1.750		* * *	* * * * * * * * * *	* * *	96.0	
1.700			* * * * * * * * * *	* * *	96.0	
1.650		* * *	* * * * * * * * * *	* * *	96.0	
	+,	+,	+,	+		
	80.0	90.0	100.0	110.0		

t_{ACC} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	+,	+	
3.000		* * * *	********	****	95.0
2.950	1	* * * *	* * * * * * * * * *	****	95.0
2.900		* * * *	* * * * * * * * * *	****	95.0
2.850		* * * *	* * * * * * * * * *	****	95.0
2.800		* * * *	* * * * * * * * * *	****	95.0
2.750		* * * *	* * * * * * * * * *	****	95.0
2.700		* * * *	* * * * * * * * * *	****	95.0
2.650		* * * *	* * * * * * * * * *	****	95.0
2.600		* * * *	* * * * * * * * * *	****	95.0
2.550		* * * *	* * * * * * * * * *	****	95.0
2.500		* * * *	* * * * * * * * * *	****	95.0
2.450		* * * *	* * * * * * * * * *	****	95.0
2.400		***	********	****	95.0
2.350		* * * *	* * * * * * * * * *	****	95.0
2.300		* * * *	* * * * * * * * * *	****	95.0
2.250		***	********	****	95.0
2.200		* * *	* * * * * * * * * *	****	96.0
2.150		* * :	* * * * * * * * * *	****	96.0
2.100		* * :	********	****	96.0
2.050		* * *	* * * * * * * * * *	****	96.0
2.000		* * :	* * * * * * * * * *	****	96.0
1.950		* * *	********	****	96.0
1.900		* * *	* * * * * * * * * *	****	96.0
1.850		* * *	********	****	96.0
1.800		***	********	****	96.0
1.750	1		********	****	97.0
1.700			********	****	97.0
1.650			********	****	97.0
	+	-+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.000			* * * * * * * * * * *	****	97.0
2.950		*	* * * * * * * * * * *	****	96.0
2.900			* * * * * * * * * * *	****	97.0
2.850			* * * * * * * * * * *	****	97.0
2.800			* * * * * * * * * * *	****	97.0
2.750			* * * * * * * * * * *	****	97.0
2.700			* * * * * * * * * * *	****	97.0
2.650			* * * * * * * * * * *	****	97.0
2.600			* * * * * * * * * * *	****	97.0
2.550			* * * * * * * * * * *	****	97.0
2.500			* * * * * * * * * * *	****	97.0
2.450			* * * * * * * * * * *	****	97.0
2.400			* * * * * * * * * * *	****	97.0
2.350			* * * * * * * * * * *	****	97.0
2.300			* * * * * * * * * * *	****	97.0
2.250		'	* * * * * * * * * * *	****	97.0
2.200			* * * * * * * * * * *	****	97.0
2.150			* * * * * * * * * * *	****	97.0
2.100			* * * * * * * * * * *	****	97.0
2.050			* * * * * * * * * * *	****	97.0
2.000			. * * * * * * * * * *	****	98.0
1.950			. * * * * * * * * * *	****	98.0
1.900			********	****	98.0
1.850			. * * * * * * * * * *	****	98.0
1.800			. * * * * * * * * * *	****	98.0
1.750			. * * * * * * * * * *	****	98.0
1.700	1		********	****	98.0
1.650			* * * * * * * * *	****	99.0
	+,	+,	+,-	+	
	80.0	90.0	100.0	110.0	

 t_{ACC} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	-+,	+	
3.000		* * *	*******	***	96.0
2.950	1	* * *	*******	***	96.0
2.900		* * *	*******	***	96.0
2.850		* * *	*******	***	96.0
2.800		* * *	* * * * * * * * *	***	96.0
2.750		* * *	* * * * * * * * *	***	96.0
2.700		* * *	* * * * * * * * *	***	96.0
2.650		* * *	*******	***	96.0
2.600		* * *	*******	***	96.0
2.550		* * *	* * * * * * * * *	***	96.0
2.500		* *	*******	***	97.0
2.450		* *	*******	***	97.0
2.400		* *	* * * * * * * * *	***	97.0
2.350		* *	*******	***	97.0
2.300		* *	* * * * * * * * *	***	97.0
2.250		* *	*******	***	97.0
2.200		* *	* * * * * * * * *	***	97.0
2.150		* *	* * * * * * * * *	***	97.0
2.100		* *	*******	***	97.0
2.050		* *	* * * * * * * * *	***	97.0
2.000		* *	* * * * * * * * *	***	97.0
1.950	1	* *	* * * * * * * * *	***	97.0
1.900		*	*******	***	98.0
1.850		*	* * * * * * * * *	***	98.0
1.800		*	* * * * * * * * *	***	98.0
1.750	1	*	*******	***	98.0
1.700			*******	***	99.0
1.650			*******	***	99.0
	+,	-+,	-+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. $V_{CC}{=}V_{IO} @~25^\circ C$

	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.650		* * * * *	*******	* * *	93.0
3.600		* * * * *	*******	* * *	93.0
3.550	1	* * * * *	*******	* * *	93.0
3.500		* * * *	*******	* * *	94.0
3.450		* * * *	*******	* * *	94.0
3.400	1	* * * *	*******	* * *	94.0
3.350		* * * *	*******	* * *	94.0
3.300		* * * *	*******	* * *	94.0
3.250	1	* * * *	*******	***	94.0
3.200		* * * *	*******	* * *	94.0
3.150		* * * *	*******	* * *	94.0
3.100	1	* * * *	*******	* * *	94.0
3.050		* * * *	*******	* * *	94.0
3.000		* * * *	*******	* * *	94.0
2.950	1	* * * *	*******	* * *	94.0
2.900		* * * *	*******	* * *	94.0
2.850		* * * *	*******	* * *	94.0
2.800		* * * *	*******	* * *	94.0
2.750		* * * *	*******	* * *	94.0
2.700		* * * *	*******	* * *	94.0
2.650		* * * *	*******	* * *	94.0
	+,	+,	+,	+	
	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{CC}=V_{IO} @ 85°C

	80.0	90.0	100.0	110.0	first pass da	ta
	+,	-+,	-+,	-+		
3.650		* * * * *	*******	**	95.0	
3.600		* * * * *	* * * * * * * * * *	**	95.0	
3.550		* * * * *	* * * * * * * * * *	**	95.0	
3.500		* * * * *	* * * * * * * * * *	**	95.0	
3.450		* * * * *	* * * * * * * * * *	**	95.0	
3.400		* * * * *	* * * * * * * * * *	**	95.0	
3.350		* * * * *	* * * * * * * * * *	**	95.0	
3.300		* * * * *	* * * * * * * * * *	**	95.0	
3.250		* * * * *	* * * * * * * * * *	**	95.0	
3.200		* * * * *	* * * * * * * * * *	**	95.0	
3.150		* * * * *	* * * * * * * * * *	**	95.0	
3.100		* * * * *	* * * * * * * * * *	**	95.0	
3.050		* * * * *	* * * * * * * * * *	**	95.0	
3.000		* * * * *	* * * * * * * * * *	**	95.0	
2.950		* * * * *	* * * * * * * * * *	**	95.0	
2.900		* * * * *	* * * * * * * * * *	**	95.0	
2.850		* * * * *	* * * * * * * * * *	**	95.0	
2.800		* * * *	* * * * * * * * * *	**	96.0	
2.750		* * * *	* * * * * * * * * *	**	96.0	
2.700		* * * *	* * * * * * * * * *	**	96.0	
2.650		* * * *	* * * * * * * * * *	**	96.0	
	+,	-+,	-+,	-+		
	80.0	90.0	100.0	110.0		



t_{CE} vs. V_{CC}=V_{IO} @ 105°C

	80.0	90.0	100.0	110.0	first pass data
	+,	+, -	+,	+	
3.650		* *	* * * * * * * * * * *	* * * *	95.0
3.600		* *	* * * * * * * * * * *	* * * *	95.0
3.550	1	* *	* * * * * * * * * *	****	95.0
3.500	1	* *	* * * * * * * * * * *	****	95.0
3.450		* *	* * * * * * * * * * *	****	95.0
3.400	1	* *	* * * * * * * * * *	****	95.0
3.350	1	* *	* * * * * * * * * * *	****	95.0
3.300		* *	* * * * * * * * * * *	****	95.0
3.250	1	* *	* * * * * * * * * *	****	95.0
3.200		* *	* * * * * * * * * * *	* * * *	95.0
3.150		* *	* * * * * * * * * * *	****	95.0
3.100	1	* *	* * * * * * * * * * *	****	95.0
3.050		* *	* * * * * * * * * * *	****	95.0
3.000		* *	* * * * * * * * * * *	* * * *	95.0
2.950	1	* *	* * * * * * * * * * *	****	95.0
2.900		* *	* * * * * * * * * * *	****	95.0
2.850		* *	* * * * * * * * * * *	****	95.0
2.800		* *	* * * * * * * * * *	****	95.0
2.750		*	* * * * * * * * * * *	****	96.0
2.700		*	* * * * * * * * * * *	****	96.0
2.650		*	* * * * * * * * * *	****	96.0
	+,	+, -	+,	+	
	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{CC}=V_{IO} @ -40°C

	80.0	90.0	100.0	110.0	first pass data
	+,	+ ,	-+,	+	
3.650		* * *	******	* * *	96.0
3.600	1	* * *	******	***	96.0
3.550		* * *	******	* * *	96.0
3.500		* * *	******	* * *	96.0
3.450		* * *	******	***	96.0
3.400		* * *	******	***	96.0
3.350		* * *	******	* * *	96.0
3.300	1	* * *	******	***	96.0
3.250		* * *	******	* * *	96.0
3.200		* * *	******	* * *	96.0
3.150	1	* * *	******	* * *	96.0
3.100		* * *	******	* * *	96.0
3.050		* * *	******	* * *	96.0
3.000	1	* *	******	* * *	97.0
2.950	1	* *	******	***	97.0
2.900		* *	******	***	97.0
2.850	1	* *	******	* * *	97.0
2.800		* *	******	* * *	97.0
2.750		* *	******	* * *	97.0
2.700	1		*******	***	97.0
2.650	1	* *	******	* * *	97.0
	+,	-+,	-+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass	data
	+,	+,	+,	· +		
3.000		* * * * *	********	****	94.0	
2.950		* * * * *	********	****	94.0	
2.900	1	* * * * *	* * * * * * * * * *	****	94.0	
2.850		* * * * *	********	****	94.0	
2.800		* * * * *	********	****	94.0	
2.750	1	* * * * *	* * * * * * * * * *	****	94.0	
2.700		* * * * *	********	****	94.0	
2.650		* * * * *	********	****	94.0	
2.600		* * * * *	* * * * * * * * * *	****	94.0	
2.550		* * * * *	********	****	94.0	
2.500		* * * * *	********	****	94.0	
2.450		* * * * *	* * * * * * * * * *	****	94.0	
2.400		* * * * *	********	****	94.0	
2.350		* * * * *	********	****	94.0	
2.300		* * * *	********	****	95.0	
2.250		* * * *	* * * * * * * * * *	****	95.0	
2.200		* * * *	********	****	95.0	
2.150		* * * *	********	****	95.0	
2.100		* * * *	* * * * * * * * * *	****	95.0	
2.050		* * * *	********	****	95.0	
2.000		* * * *	********	****	95.0	
1.950		* * * *	********	***	95.0	
1.900		* * * *	********	***	95.0	
1.850	1	* * * *	********	****	95.0	
1.800		* * *	********	***	96.0	
1.750		* * *	********	***	96.0	
1.700	1	* *	********	****	97.0	
1.650		* *	********	***	97.0	
	+,	+,	+,	·+		
	80.0	90.0	100.0	110.0		

t_{CE} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	-+,	+,	+	
3.000		* * * *	********	***	95.0
2.950		* * * *	* * * * * * * * * *	***	95.0
2.900		* * * *	* * * * * * * * * *	***	95.0
2.850		* * * *	* * * * * * * * * *	***	95.0
2.800		* * * *	* * * * * * * * * *	***	95.0
2.750		* * * *	* * * * * * * * * *	***	95.0
2.700		* * * *	* * * * * * * * * *	***	95.0
2.650		* * * *	* * * * * * * * * *	***	95.0
2.600		* * * *	* * * * * * * * * *	***	95.0
2.550		* * :	* * * * * * * * * *	***	96.0
2.500		* *	* * * * * * * * * *	***	96.0
2.450		* * :	* * * * * * * * * *	***	96.0
2.400		* * :	********	***	96.0
2.350		* *	* * * * * * * * * *	***	96.0
2.300		* * :	* * * * * * * * * *	***	96.0
2.250		* * :	********	***	96.0
2.200		* *	* * * * * * * * * *	***	96.0
2.150		* * :	* * * * * * * * * *	***	96.0
2.100		**	* * * * * * * * * *	***	96.0
2.050		* *	* * * * * * * * * *	***	96.0
2.000		**	* * * * * * * * * *	***	96.0
1.950	1	***	*******	***	96.0
1.900	1		* * * * * * * * * *	***	97.0
1.850		* :	********	***	97.0
1.800		* :	*******	***	97.0
1.750	1		* * * * * * * * * *	***	97.0
1.700			********	***	98.0
1.650			*******	***	98.0
	İ+,	-+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass	data
	+,	+,	+,	+		
3.000		* * *	********	***	95.0	
2.950		* * *	*********	***	95.0	
2.900		* * *	******	* * *	95.0	
2.850		* * *	*******	* * *	95.0	
2.800		* * *	******	* * *	95.0	
2.750		* * *	*******	* * *	95.0	
2.700		* * *	*******	* * *	95.0	
2.650		* * *	*******	* * *	95.0	
2.600		* * *	*******	* * *	95.0	
2.550		* * *	*******	* * *	95.0	
2.500		* * *	*******	* * *	95.0	
2.450		* *	*******	* * *	96.0	
2.400		* *	*******	* * *	96.0	
2.350		* *	*******	* * *	96.0	
2.300		* *	*******	* * *	96.0	
2.250		* *	*******	* * *	96.0	
2.200		* *	*******	* * *	96.0	
2.150		* *	*******	* * *	96.0	
2.100		* *	*******	* * *	96.0	
2.050		* *	*******	* * *	96.0	
2.000		**	******	* * *	96.0	
1.950		* * '	*******	* * *	96.0	
1.900		*	********	* * *	97.0	
1.850	1	*	******	* * *	97.0	
1.800		*	*******	* * *	97.0	
1.750		*	*******	* * *	97.0	
1.700			******	***	98.0	
1.650			******	* * *	98.0	
	+,	+,	+,	+		
	80.0	90.0	100.0	110.0		

 t_{CE} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	80.0	90.0	100.0	110.0	first pass data
	+,	+,	+,	+	
3.000		* :	*******	* * *	97.0
2.950		* :	*******	***	97.0
2.900		* :	*******	***	97.0
2.850			*******	***	97.0
2.800		*	*******	***	97.0
2.750		* :	*******	***	97.0
2.700			*******	***	97.0
2.650		*	*******	***	97.0
2.600		* :	*******	***	97.0
2.550			*******	***	97.0
2.500		*	*******	***	97.0
2.450		* :	*******	***	97.0
2.400			*******	***	97.0
2.350		* :	* * * * * * * * * *	***	97.0
2.300		* :	*******	***	97.0
2.250			*******	***	97.0
2.200		*	*******	***	97.0
2.150		*	*******	***	97.0
2.100		*	******	***	97.0
2.050			* * * * * * * * * *	***	98.0
2.000			*******	***	98.0
1.950	1		******	***	98.0
1.900			*******	***	98.0
1.850			*******	***	98.0
1.800			******	***	98.0
1.750			. * * * * * * * * *	***	99.0
1.700			. * * * * * * * * *	***	99.0
1.650			. * * * * * * * * *	***	99.0
	+,	+,	+,	+	
	80.0	90.0	100.0	110.0	



t_{OE} vs. V_{CC}=V_{IO} @ 25°C

	0.0	10.0	20.0
	+,	+,	-+,
3.650	**	*********	******
3.600	**	*********	******
3.550	**	*********	******
3.500	**	*********	******
3.450	**	*********	******
3.400	**	*********	******
3.350	**	*********	******
3.300	**	*********	******
3.250	**	*********	******
3.200	**	*********	******
3.150	**	*********	******
3.100	**	*********	******
3.050	**	*********	******
3.000	**	*********	******
2.950	**	* * * * * * * * * * *	******
2.900	**	* * * * * * * * * * *	******
2.850	**	* * * * * * * * * * *	******
2.800	**	* * * * * * * * * * *	******
2.750	**	* * * * * * * * * * *	******
2.700	**	* * * * * * * * * * *	******
2.650	**	* * * * * * * * * * *	******
	+,	+,	-+,
	0.0	10.0	20.0

6.0 6.0

t_{OE} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0	first pass data
	+,	+,	+,	
3.650	**	******	****	6.0
3.600	1**	******	****	6.0
3.550	**	******	* * * * * * *	6.0
3.500	**	*******	* * * * * * *	6.0
3.450	1**	******	****	6.0
3.400	**	******	* * * * * * *	6.0
3.350	**	* * * * * * * * * *	****	6.0
3.300	1**	******	****	6.0
3.250	**	* * * * * * * * * *	****	6.0
3.200	**	* * * * * * * * * *	****	6.0
3.150	1**	******	****	6.0
3.100	**	* * * * * * * * * *	****	6.0
3.050	**	* * * * * * * * * *	****	6.0
3.000	**	******	*****	6.0
2.950	**	* * * * * * * * * *	*****	6.0
2.900	**	* * * * * * * * * *	****	6.0
2.850	**	* * * * * * * * * *	****	6.0
2.800	**	* * * * * * * * * *	*****	6.0
2.750	**	* * * * * * * * * *	*****	6.0
2.700	*	* * * * * * * * * *	****	7.0
2.650	İ *	* * * * * * * * * *	*****	7.0
	+,	+,	+,	
	0.0	10.0	20.0	

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 $\begin{array}{c} . \ . \ 0 \\ 6 \ . \ 0 \ . \ 0 \\ 6 \ . \ 0 \ . \ 0 \\ 6 \ . \ 0 \$

6.0 6.0 6.0 6.0 6.0 6.0

6.0

pass data

t_{OE} vs. V_{CC}=V_{IO} @ 105°C

	0.0	10.0	20.0
	+,	- + ,	-+,
3.650	***	********	******
3.600	***	*******	******
3.550	***	* * * * * * * * * *	******
3.500	***	*******	******
3.450	***	* * * * * * * * * *	******
3.400	***	* * * * * * * * * * *	******
3.350	***	********	******
3.300	***	*******	******
3.250	***	********	******
3.200	***	* * * * * * * * * *	******
3.150	***	*******	******
3.100	***	* * * * * * * * * * *	******
3.050	***	* * * * * * * * * *	******
3.000	***	* * * * * * * * * *	******
2.950	* * *	*******	******
2.900	* * *	* * * * * * * * * * *	******
2.850	* * *	* * * * * * * * * * *	******
2.800		*******	******
2.750		* * * * * * * * * * *	******
2.700	* * *	* * * * * * * * * * *	******
2.650	***	********	******
	+,	+,	-+,
	0.0	10.0	20.0

t_{OE} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first
	+,	+,-	+,	
3.650	***	******	*******	5.0
3.600	***	******	*******	5.0
3.550	***	******	*******	5.0
3.500	***	******	*******	5.0
3.450	***	******	*******	5.0
3.400	***	******	*******	5.0
3.350	***	******	*******	5.0
3.300	***	*******	*******	5.0
3.250	***	******	*******	5.0
3.200	***	******	*******	5.0
3.150	***	******	*******	5.0
3.100	***	******	*******	5.0
3.050	***	******	*******	5.0
3.000	***	******	*******	5.0
2.950	***	******	*******	5.0
2.900	**	*******	*******	6.0
2.850	**	******	*******	6.0
2.800	**	******	*******	6.0
2.750	**	*******	*******	6.0
2.700	**	******	*******	6.0
2.650	**	******	*******	6.0
	+,	+,-	+,	
	0.0	10.0	20.0	

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6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0

6.0 7.0 7.0 7.0

7.0 7.0 7.0 7.0 7.0 7.0 7.0

8.0 8.0 8.0 9.0 9.0

t_{OE} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	0.0	10.0	20.0
	+,-	+, -	+,
3.000	*	* * * * * * * * * *	* * * * * * * * *
2.950	*	* * * * * * * * * *	* * * * * * * * *
2.900	*	* * * * * * * * * *	* * * * * * * * *
2.850	*	* * * * * * * * * *	* * * * * * * * *
2.800	*	* * * * * * * * * *	* * * * * * * * *
2.750	*	* * * * * * * * * *	* * * * * * * * *
2.700	*	* * * * * * * * * *	* * * * * * * * *
2.650	*	* * * * * * * * * *	* * * * * * * * *
2.600	*	* * * * * * * * * *	* * * * * * * * *
2.550	*	* * * * * * * * * *	* * * * * * * * *
2.500	*	* * * * * * * * * *	* * * * * * * * *
2.450	*	* * * * * * * * * *	* * * * * * * * *
2.400	*	* * * * * * * * * *	* * * * * * * * *
2.350	*	* * * * * * * * * *	* * * * * * * * *
2.300		* * * * * * * * * *	* * * * * * * * *
2.250		* * * * * * * * * *	* * * * * * * * *
2.200		* * * * * * * * * *	* * * * * * * * *
2.150		* * * * * * * * * *	* * * * * * * * *
2.100		* * * * * * * * * *	* * * * * * * * *
2.050		* * * * * * * * * *	* * * * * * * * *
2.000		* * * * * * * * * *	* * * * * * * * *
1.950	1	* * * * * * * * * *	* * * * * * * * *
1.900		* * * * * * * * * *	* * * * * * * * *
1.850		. * * * * * * * * *	* * * * * * * * *
1.800		.*******	* * * * * * * * *
1.750		.*******	* * * * * * * * *
1.700		* * * * * * * *	* * * * * * * * *
1.650		* * * * * * * *	* * * * * * * * *
	+,-	+,-	+,
	0.0	10.0	20.0

 t_{OE} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	0.0	10.0	20.0
	+,	+,	-+,
3.000	****	*******	******
2.950	****	*******	******
2.900	****	* * * * * * * * *	******
2.850	* * * *	*******	******
2.800	****	******	******
2.750	****	*******	******
2.700	* * *	*******	******
2.650		*******	******
2.600	* * *	*******	******
2.550	* * *	*******	******
2,500		*******	******
2.450		*******	******
2.400	* * *	*******	******
2.350		*******	******
2.300		*******	******
2.250	* * *	*******	******
2.200		*******	******
2.150		*******	******
2.100		*******	******
2.050	***	******	******
2.000	**	*******	******
1,950	**	*******	******
1.900	**	*******	******
1.850	**	*******	******
1,800	**	*******	******
1,750	**	*******	******
1.700	*	*******	******
1,650	*	*******	******
• •	+	+	-+
	0.0	10.0	20.0

first pass data

- 6.0 6.0 6.0 6.0 6.0 6.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0
- 7.0 8.0

8.0 8.0

8.0 8.0 8.0

9.0

9.0



t_{OE} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	0.0 10.0 20.0	
	+,+,+,	
3.000		İ
2.950	*******************	İ.
2,900	***************	i -
2.850	**********************	İ.
2,800	***********	İ.
2.750	*************	i.
2 700	***********	
2 650	*************	
2 600	******************	Ł
2.550	************	
2.500	*************	ł
2.300	************	Ł
2.430	+++++++++++++++++++++++++++++++++++++++	
2.400		Ł
2.350		
2.300	······	
2.250		
2.200		
2.150		
2.100		
2.050	· · · · · · * * * * * * * * * * * * *	
2.000		
1.950	********************	
1.900		
1.850		Ĺ
1.800		
1.750		
1.700		İ
1.650		İ
	1+,+,+,	İ
	0.0 10.0 20.0	•

 t_{OE} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	0.0	10.0	20.0
	+,	. + ,	-+,
3.000	* * * * *	********	******
2.950	* * * * *	******	******
2.900	* * * *	* * * * * * * * * *	******
2.850	* * * *	*******	******
2.800	****	*******	******
2.750	* * * *	* * * * * * * * * *	******
2.700	* * * *	*******	******
2.650	****	*******	******
2.600	* * * *	* * * * * * * * * *	******
2.550	* * * *	*******	******
2.500	****	******	******
2.450	* * * *	********	******
2.400	* * * *	********	******
2.350	***	*******	******
2.300	* * * *	********	******
2.250	****	********	******
2.200	***	*******	******
2.150	****	********	******
2.100	****	********	******
2.050	**	*******	******
2.000	***	********	******
1.950	* * *	*******	******
1.900	***	*******	******
1.850	* * *	*******	******
1.800	* *	*******	******
1.750	* *	*******	******
1.700	* *	********	******
1.650	*	*******	******
	+,	+,	-+,
	0.0	10.0	20.0

first pass data 6.0

6.0

6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 7.0 8.0 8.0 8.0 8.0

8.0 8.0

5.0

first pass data

5.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0 6.0

6.0 6.0 6.0

6.0 6.0

6.0 6.0

7.0 7.0 7.0

7.0 8.0

8.0

8.0 9.0



data

t_{PACC} vs. V_{CC} = V_{IO} @ 25°C

	0.0	10.0	20.0	first	pass	data
	+,	-+,	-+			
3.650		.*******	**	10.0		
3.600		.*******	**	10.0		
3.550		. * * * * * * * * *	**	10.0		
3.500		.*******	**	10.0		
3.450		. * * * * * * * * *	**	10.0		
3.400		. * * * * * * * * *	**	10.0		
3.350		.*******	**	10.0		
3.300		.*******	**	10.0		
3.250		. * * * * * * * * *	**	10.0		
3.200		.*******	**	10.0		
3.150		.*******	**	10.0		
3.100		.*******	**	10.0		
3.050		.*******	**	10.0		
3.000		.*******	**	10.0		
2.950		. * * * * * * * * *	**	10.0		
2.900		. * * * * * * * * *	**	10.0		
2.850		. * * * * * * * * *	**	10.0		
2.800		. * * * * * * * * *	**	10.0		
2.750		. * * * * * * * * *	**	10.0		
2.700		. * * * * * * * * *	**	10.0		
2.650		. * * * * * * * * *	**	10.0		
	+,	-+,	-+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0	first pass
	+,	-+,	+	
3.650		* * * * * * * *	***	11.0
3.600		* * * * * * * *	***	11.0
3.550		* * * * * * * *	***	11.0
3.500		* * * * * * * *	***	11.0
3.450		* * * * * * * *	***	11.0
3.400		* * * * * * * *	***	11.0
3.350		* * * * * * * *	***	11.0
3.300		* * * * * * * *	***	11.0
3.250		* * * * * * * *	***	11.0
3.200		* * * * * * * *	***	11.0
3.150		* * * * * * * *	***	11.0
3.100		* * * * * * * *	***	11.0
3.050		* * * * * * * *	***	11.0
3.000		* * * * * * * *	***	11.0
2.950		* * * * * * * *	***	11.0
2.900		* * * * * * * *	***	11.0
2.850		* * * * * * * *	***	11.0
2.800		* * * * * * * *	***	11.0
2.750		* * * * * * * *	***	11.0
2.700		* * * * * * * *	***	11.0
2.650		* * * * * * * *	***	11.0
	+,	-+,	· - +	
	0.0	10.0	20.0	



t_{PACC} vs. V_{CC} = V_{IO} @ 105°C

	0.0	10.0	20.0	first	pass	data
	+,	-+,	-+			
3.650		* * * * * * * *	**	11.0		
3.600		* * * * * * * *	**	11.0		
3.550		* * * * * * * *	**	11.0		
3.500		* * * * * * * *	**	11.0		
3.450		* * * * * * * *	**	11.0		
3.400		* * * * * * * *	**	11.0		
3.350		* * * * * * * *	**	11.0		
3.300		* * * * * * * *	**	11.0		
3.250		* * * * * * * *	**	11.0		
3.200		* * * * * * * *	**	11.0		
3.150		* * * * * * * *	**	11.0		
3.100		* * * * * * * *	**	11.0		
3.050		* * * * * * * *	**	11.0		
3.000		* * * * * * * *	**	11.0		
2.950	1	* * * * * * * *	**	11.0		
2.900		******	**	11.0		
2.850		* * * * * * * *	**	11.0		
2.800		* * * * * * * *	**	11.0		
2.750		******	**	11.0		
2.700		* * * * * * * *	**	11.0		
2.650		* * * * * * * *	**	11.0		
	+,	-+,	-+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first j	pass	data
	+,	-+,	-+			
3.650		. * * * * * * * * *	**	10.0		
3.600		. * * * * * * * * *	**	10.0		
3.550		* * * * * * * * * *	**	9.0		
3.500		. * * * * * * * * *	**	10.0		
3.450		* * * * * * * * * *	**	9.0		
3.400		* * * * * * * * * *	**	9.0		
3.350		* * * * * * * * * *	**	9.0		
3.300		* * * * * * * * * *	**	9.0		
3.250		* * * * * * * * * *	**	9.0		
3.200		* * * * * * * * * *	**	9.0		
3.150		* * * * * * * * * *	**	9.0		
3.100		* * * * * * * * * *	**	9.0		
3.050		* * * * * * * * * *	**	9.0		
3.000		* * * * * * * * * *	**	9.0		
2.950		. * * * * * * * * *	**	10.0		
2.900		. * * * * * * * * *	**	10.0		
2.850		* * * * * * * * * *	**	9.0		
2.800		* * * * * * * * * *	**	9.0		
2.750		. * * * * * * * * *	**	10.0		
2.700		. * * * * * * * * *	**	10.0		
2.650		. * * * * * * * * *	**	10.0		
	+,	-+,	-+			
	0.0	10.0	20.0			

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pass data

t_{PACC} vs. V_{IO} @ 25°C (V_{CC} = 3V)

	0.0	10.0	20.0	first	pass	data
	+,	+,	+			
3.000		* * * * * * * *	***	10.0		
2.950		* * * * * * * *	***	10.0		
2.900		* * * * * * * *	***	10.0		
2.850		* * * * * * * *	***	10.0		
2.800		* * * * * * * *	***	10.0		
2.750		* * * * * * * *	***	10.0		
2.700		* * * * * * * *	***	10.0		
2.650		* * * * * * * *	***	10.0		
2.600		* * * * * * * *	***	10.0		
2.550		* * * * * * * *	***	10.0		
2.500		* * * * * * * *	***	10.0		
2.450		* * * * * * * *	***	10.0		
2.400		* * * * * * * *	***	10.0		
2.350		* * * * * * * *	***	10.0		
2.300		* * * * * * * *	***	10.0		
2.250		* * * * * * * *	***	10.0		
2.200		* * * * * * * *	***	10.0		
2.150		* * * * * * *	***	11.0		
2.100		* * * * * * *	***	11.0		
2.050		* * * * * * *	***	11.0		
2.000		* * * * * * *	***	11.0		
1.950		* * * * * * *	***	11.0		
1.900		* * * * * * *	***	11.0		
1.850		* * * * * * *	***	11.0		
1.800		* * * * * * *	***	11.0		
1.750		* * * * * *	***	12.0		
1.700	1	* * * * * *	***	12.0		
1.650		* * * * * *	***	12.0		
	+,	+,	+			
	0.0	10.0	20.0			

 t_{PACC} vs. V_{IO} @ 85°C (V_{CC} = 3V)

	0.0	10.0	20.0	first
	+,	+, -	+	
3.000		*****	****	11.0
2.950		*****	****	11.0
2.900		*****	****	11.0
2.850		*****	****	11.0
2.800		* * * * * *	* * * *	11.0
2.750		*****	****	11.0
2.700		*****	****	11.0
2.650		* * * * * *	* * * *	11.0
2.600		*****	****	11.0
2.550		* * * * * *	****	11.0
2.500		* * * * * *	* * * *	11.0
2.450		*****	****	11.0
2.400		*****	****	11.0
2.350		* * * * * *	* * * *	11.0
2.300		*****	****	11.0
2.250		*****	****	11.0
2.200	1	*****	****	11.0
2.150		*****	****	11.0
2.100		* * * * * *	****	11.0
2.050		* * * * * *	****	11.0
2.000		*****	****	11.0
1.950	1	*****	****	11.0
1.900	1	* * * * *	****	12.0
1.850		* * * * *	****	12.0
1.800		* * * * *	****	12.0
1.750		* * * * *	****	12.0
1.700		* * * * *	****	12.0
1.650		* * * *	****	13.0
	+,	+,-	+İ	
	0.0	10.0	20.0	



t_{PACC} vs. V_{IO} @ 105°C (V_{CC} = 3V)

	0.0	10.0	20.0	first
	+,	+,	+	
3.000		* * * * * * *	***	11.0
2.950		* * * * * * *	***	11.0
2.900		* * * * * * *	***	11.0
2.850		* * * * * * *	***	11.0
2.800		* * * * * * *	***	11.0
2.750		* * * * * * *	***	11.0
2.700		* * * * * * *	***	11.0
2.650		* * * * * * *	***	11.0
2.600		* * * * * * *	***	11.0
2.550		* * * * * * *	***	11.0
2.500		* * * * * * *	***	11.0
2.450		* * * * * * *	***	11.0
2.400		* * * * * * *	***	11.0
2.350		* * * * * * *	***	11.0
2.300		* * * * * *	***	12.0
2.250		* * * * * *	***	12.0
2.200		* * * * * *	***	12.0
2.150		* * * * * *	***	12.0
2.100		* * * * * *	***	12.0
2.050		* * * * * *	***	12.0
2.000		* * * * * *	***	12.0
1.950		* * * * * *	r * * *	12.0
1.900		* * * * * *	r * * *	12.0
1.850		* * * * * *	***	12.0
1.800		* * * * * *	r * * *	12.0
1.750		* * * * *	r * * *	13.0
1.700		* * * * *	***	13.0
1.650		* * * * *	r * * *	13.0
	+,	+,	· +	
	0.0	10.0	20.0	

t_{PACC} vs. V_{IO} @ -40°C (V_{CC} = 3V)

	0.0	10.0	20.0	firs
	+,	+, -	+	
3.000		* * * * * * * *	****	9.0
2.950	1	* * * * * * *	****	10.0
2.900		* * * * * * * *	****	9.0
2.850		* * * * * * * *	****	9.0
2.800		* * * * * * * *	****	9.0
2.750		* * * * * * * *	****	9.0
2.700		* * * * * * *	****	10.0
2.650		* * * * * * *	****	10.0
2.600		* * * * * * *	****	10.0
2.550		* * * * * * *	****	10.0
2.500		* * * * * * *	****	10.0
2.450		* * * * * * *	****	10.0
2.400		* * * * * * *	****	10.0
2.350		* * * * * * *	****	10.0
2.300		* * * * * * *	****	10.0
2.250		* * * * * * *	****	10.0
2.200		* * * * * * *	****	10.0
2.150		* * * * * * *	****	10.0
2.100		* * * * * * *	****	10.0
2.050		* * * * * * *	****	10.0
2.000		* * * * * * *	****	10.0
1.950		* * * * * * *	****	10.0
1.900	1	* * * * * *	****	11.0
1.850		* * * * * *	****	11.0
1.800		* * * * * *	****	11.0
1.750	1	* * * * * *	****	11.0
1.700		* * * * *	****	12.0
1.650		* * * * *	****	12.0
	+,	+, -	· +	
	0.0	10.0	20.0	

first pass data

9.0
10.0
9.0
9.0
9.0
9.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
10.0
11.0
11.0
11.0
11.0
12.0



V_{IH} vs. $V_{\text{CC}}\text{=}V_{\text{IO}}$ @ 25°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+,	+,	+,	,	+	
3.650			* * * * * * * *	*******	* * * *	2.000
3.600			* * * * * * * *	*******	* * * *	2.000
3.550	1		. * * * * * * * * *	*******	****	1.950
3.500			. * * * * * * * * *	*******	* * * *	1.950
3.450			********	*******	* * * *	1.900
3.400	1		* * * * * * * * * *	*******	****	1.900
3.350		*	********	*******	* * * *	1.850
3.300		*	********	*******	* * * *	1.850
3.250		* *	* * * * * * * * * *	*******	* * * *	1.800
3.200		* * *	********	*******	* * * *	1.750
3.150		* * *	********	*******	* * * *	1.750
3.100		* * * *	* * * * * * * * * *	*******	* * * *	1.700
3.050		* * * *	********	*******	* * * *	1.700
3.000		* * * * *	********	*******	* * * *	1.650
2.950	1	* * * * *	* * * * * * * * * *	*******	* * * *	1.650
2.900		* * * * * *	* * * * * * * * * *	********	* * * *	1.600
2.850		* * * * * *	* * * * * * * * * *	********	* * * *	1.600
2.800	1	* * * * * * *	* * * * * * * * * *	*******	* * * *	1.550
2.750		* * * * * * *	* * * * * * * * * *	********	* * * *	1.550
2.700		* * * * * * * *	* * * * * * * * * *	********	* * * *	1.500
2.650		. * * * * * * * * *	* * * * * * * * * *	*******	* * * *	1.450
	+,	+,	+,	+,	+	
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. V_{CC}=V_{IO} @ 85°C

	1.000	1.500	2.000	2.500	3.000	first pass 🤇	data
	+,	-+,	-+,	-+,	+		
3.650			.*******	********	***	2.000	
3.600			.*******	* * * * * * * * * *	***	2.000	
3.550	1		*******	*******	***	1.950	
3.500			*******	********	***	1.950	
3.450		*	*******	********	***	1.900	
3.400	1	*	*******	********	***	1.900	
3.350		* *	*******	********	***	1.850	
3.300		***	*******	********	***	1.800	
3.250	1	* * *	*******	********	***	1.800	
3.200		* * * *	*******	********	***	1.750	
3.150		* * * *	*******	********	***	1.750	
3.100	1	* * * * *	*******	********	***	1.700	
3.050		* * * * *	*******	*******	***	1.700	
3.000		* * * * * *	*******	********	***	1.650	
2.950	1	* * * * * *	* * * * * * * * * *	********	***	1.650	
2.900		* * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	***	1.600	
2.850		* * * * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.600	
2.800		* * * * * * * *	* * * * * * * * * *	********	***	1.550	
2.750		. * * * * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	***	1.500	
2.700		. * * * * * * * * *	* * * * * * * * * *	* * * * * * * * * * *	***	1.500	
2.650	1	* * * * * * * * * *	* * * * * * * * * *	********	***	1.450	
	+,	-+,	-+,	-+,	+		
	1.000	1.500	2.000	2.500	3.000		


V_{IH} vs. V_{CC} = V_{IO} @ 105°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+,	-+,	+,	+,	+	
3.650			* * * * * * * *	* * * * * * * * * *	* * * *	2.000
3.600			. * * * * * * * * *	* * * * * * * * * *	* * * *	1.950
3.550			. * * * * * * * * *	* * * * * * * * * *	* * * *	1.950
3.500			******	* * * * * * * * * *	* * * *	1.900
3.450			******	* * * * * * * * * *	* * * *	1.900
3.400		*	******	* * * * * * * * * *	* * * *	1.850
3.350		*	******	* * * * * * * * * *	* * * *	1.850
3.300		**	******	* * * * * * * * * *	* * * *	1.800
3.250		**	******	* * * * * * * * *	* * * *	1.800
3.200		* * * *	******	* * * * * * * * * *	* * * *	1.750
3.150		***	******	* * * * * * * * * *	* * * *	1.750
3.100		* * * *	******	* * * * * * * * *	* * * *	1.700
3.050		*****	******	* * * * * * * * * *	* * * *	1.650
3.000		*****	******	* * * * * * * * * *	* * * *	1.650
2.950	1	* * * * * *	******	* * * * * * * * *	* * * *	1.600
2.900		* * * * * *	*******	* * * * * * * * * *	* * * *	1.600
2.850		* * * * * * *	*******	* * * * * * * * * *	* * * *	1.550
2.800		* * * * * * *	******	* * * * * * * * *	* * * *	1.550
2.750		.*******	*******	* * * * * * * * * *	* * * *	1.500
2.700		.*******	*******	* * * * * * * * * *	* * * *	1.500
2.650		* * * * * * * * *	* * * * * * * * * *	* * * * * * * * *	****	1.450
	+,	-+,	+,	+,	+	
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. V_{CC}=V_{IO} @ -40°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+	-+,	-+,	-+,	-+	
3.650			* * * * * * * *	******	**	2.050
3.600			.*******	******	**	2.000
3.550	1		. * * * * * * * * *	******	**	2.000
3.500			* * * * * * * * * *	******	**	1.950
3.450		*	********	*******	**	1.900
3.400	1	*	*******	******	**	1.900
3.350		* *	* * * * * * * * * *	******	**	1.850
3.300		* *	********	*******	**	1.850
3.250	1	* * *	*******	******	**	1.800
3.200		* * *	* * * * * * * * * *	*******	**	1.800
3.150		* * * *	********	******	**	1.750
3.100		* * * *	* * * * * * * * * *	******	**	1.750
3.050		* * * * *	* * * * * * * * * *	*******	**	1.700
3.000		* * * * *	********	******	**	1.650
2.950	1	* * * * *	* * * * * * * * * *	******	**	1.650
2.900		* * * * * *	********	*******	**	1.600
2.850		* * * * * * *	********	******	**	1.600
2.800		* * * * * * * *	* * * * * * * * * *	******	**	1.550
2.750		* * * * * * * *	********	*******	**	1.550
2.700		.*******	********	******	**	1.500
2.650		.*******	* * * * * * * * * *	******	**	1.500
	+,	-+,	-+,	-+,	-+	
	1.000	1.500	2.000	2.500	3.000	



V_{IL} vs. V_{CC} = V_{IO} @ 25°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	+,	+,	+	
3.650	******	* * * * * * * * * *	*******	* * * *		1.550
3.600	*******	*******	*******	* * *		1.500
3.550	******	*******	*******	* * *		1.500
3.500	*******	********	*******	* * *		1.500
3.450	*******	*******	*******	**		1.450
3.400	*******	*******	*******	**		1.450
3.350	*******	*******	*******	**		1.450
3.300	*******	*******	*******	*		1.400
3.250	*******	*******	*******	*		1.400
3.200	*******	* * * * * * * * * *	*******	*		1.400
3.150	*******	*******	*******			1.350
3.100	*******	*******	*******			1.350
3.050	*******	********	*******			1.350
3.000	*******	*******	*********			1.300
2.950	******	* * * * * * * * * *	********			1.300
2.900	******	* * * * * * * * * *	*******			1.250
2.850	******	******	*******			1.250
2.800	******	* * * * * * * * * *	*******			1.250
2.750	******	* * * * * * * * * *	******			1.200
2.700	******	******	******			1.200
2.650	******	* * * * * * * * * *	******			1.200
	+,	+,	+,	+,	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{CC} =V_{IO} @ 85°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	+,	+,	+	
3.650	******	*******	********	***		1.500
3.600	******	******	********	***		1.500
3.550	* * * * * * * *	******	********	***		1.500
3.500	*******	******	********	**		1.450
3.450	*******	******	********	**		1.450
3.400	******	******	********	*		1.400
3.350	*******	******	********	*		1.400
3.300	*******	******	********	*		1.400
3.250	******	******	********			1.350
3.200	*******	******	********	•		1.350
3.150	*******	******	********	•		1.350
3.100	******	******	********			1.300
3.050	******	*******	********			1.300
3.000	*******	******	********			1.300
2.950		******	*******			1.250
2.900	******	******	*******			1.250
2.850	******	******	*******			1.250
2.800	******	******	******			1.200
2.750	******	******	******			1.200
2.700	******	******	******			1.200
2.650	******	*****	*****			1.150
	+,	+,	+,	+,	+	
	0.000	0.500	1.000	1.500	2.000	



$V_{IL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	+,	-+,	+	
3.650	******	* * * * * * * * * * *	* * * * * * * * * * *	***		1.500
3.600	******	*******	* * * * * * * * * * *	***		1.500
3.550	******	*******	* * * * * * * * * * *	**		1.450
3.500	******	* * * * * * * * * * *	* * * * * * * * * * *	**		1.450
3.450	******	*******	* * * * * * * * * * *	**		1.450
3.400	******	******	*********		İ	1.400
3.350	******	*******	* * * * * * * * * * *			1.400
3.300	******	*******	*********			1.400
3,250	******	******	*********		İ	1,350
3.200	******	*******	*********			1.350
3.150	******	*******	*********			1.350
3.100	******	******	********			1.300
3.050	******	*******	********			1.300
3.000	******	*******	*******			1.250
2.950	******	******	*******		İ	1.250
2.900	*******	*******	*******			1.250
2.850	*******	*******	******			1.200
2.800	******	******	******		İ	1.200
2.750	*******	*******	******			1.200
2.700	*******	*******	*****			1.150
2.650	******	******	*****			1.150
	+,	+,	+,	-+,	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+,	+,	-+,	-+,	+	
3.650	*******	*******	********	***		1.550
3.600	*******	*******	********	***		1.550
3.550	*******	*******	********	***		1.550
3.500	*******	*******	********	**		1.500
3.450	*******	*******	********	**		1.500
3.400	*******	*******	********	*		1.450
3.350	*******	*******	********	*		1.450
3.300	*******	*******	********	*		1.450
3.250	*******	*******	********	•		1.400
3.200	*******	*******	********			1.400
3.150	*******	*******	********	• • • • • • • • • • •		1.400
3.100	*******	*******	**********			1.350
3.050	*******	*******	**********			1.350
3.000	*******	*******	**********			1.350
2.950	******	* * * * * * * * * * *	********			1.300
2.900	******	* * * * * * * * * * *	********			1.300
2.850	******	******	********			1.300
2.800	******	* * * * * * * * * *	*******			1.250
2.750	******	* * * * * * * * * * *	*******			1.250
2.700	******	******	******			1.200
2.650	******	* * * * * * * * * * *	******			1.200
	+,	+,	-+,	-+,	+	
	0.000	0.500	1.000	1.500	2.000	



$V_{OH}\,vs.~V_{CC}\text{=}V_{IO} \textcircled{@}25^\circ\text{C}$

	2.000	2.500	3.000	3.500	4.000	first	pass	data
	+,	-+,	-+,	-+,	- +			
3.650	*******	* * * * * * * * * *	* * * * * * * * * *	****		3.600		
3.600	*******	* * * * * * * * * *	********	***		3.550		
3.550	*******	* * * * * * * * * *	* * * * * * * * * *	**		3.500		
3.500	*******	* * * * * * * * * *	* * * * * * * * * *	*		3.450		
3.450	*******	* * * * * * * * * *	* * * * * * * * * *			3.400		
3,400	*******	* * * * * * * * * *	********		i	3,350		
3,350	*******	* * * * * * * * * *	*******			3.300		
3,300	*******	* * * * * * * * * *	******			3,250		
3,250	*******	* * * * * * * * * *	*****			3,200		
3.200	*******	* * * * * * * * * *	****			3.150		
3.150	*******	* * * * * * * * * *	****			3.100		
3,100	*******	* * * * * * * * * *	***			3,050		
3.050	*******	* * * * * * * * * *	**			3.000		
3.000	*******	* * * * * * * * * *	*			2.950		
2,950	*******	* * * * * * * * * *			İ	2,900		
2.900	*******	********				2.850		
2.850	*******	*******				2.800		
2,800	*******	******			İ	2,750		
2.750	*******	*****				2.700		
2,700	*******	****				2,650		
2,650	*******	****				2,600		
	+	-+,	-+	-+	- +			
	2.000	2.500	3.000	3.500	4.000			

V_{OH} vs. V_{CC}=V_{IO} @ 85°C

	2.000	2.500	3.000	3.500	4.000	first pass data
	+,	+,	+,	+,	+	
3.650	*******	* * * * * * * * * *	********	*****		3.600
3.600	*******	*******	*******	****		3.550
3.550	*******	* * * * * * * * * *	* * * * * * * * *	***		3.500
3.500	*******	* * * * * * * * * *	********	**		3.450
3.450	*******	* * * * * * * * * *	********	*		3.400
3.400	******	*******	********			3.350
3.350	*******	* * * * * * * * * *	********			3.300
3.300	*******	* * * * * * * * * *	*******			3.250
3.250	******	******	******			3.200
3.200	*******	* * * * * * * * * *	*****			3.150
3.150	******	* * * * * * * * * *	*****			3.100
3.100	******	*******	****			3.050
3.050	*******	* * * * * * * * * *	***			3.000
3.000	*******	* * * * * * * * * *	**			2.950
2.950	******	******	*			2.900
2.900	******	* * * * * * * * * *				2.850
2.850	******	********				2.800
2.800	******	*******				2.750
2.750	*******	******				2.700
2.700	******	*****				2.650
2.650	******	*****				2.600
	+,	+,	+,	+,	+	
	2.000	2.500	3.000	3.500	4.000	



$V_{OH}\,vs.\,V_{CC}{=}V_{IO}\,@\,105^\circ C$

	2.000	2.500	3.000	3.500	4.000	first pass data
	+,	+,	+, -	+, -	+	
3.650	*******	********	********	******		3.600
3.600	******	********	*********	*****		3.550
3.550	******	********	* * * * * * * * * *	****]	3.500
3.500	******	********	* * * * * * * * * *	***		3.450
3.450	******	********	* * * * * * * * * *	**		3.400
3.400	******	********	********	*	İ	3.350
3.350	******	********	*******			3.300
3.300	******	********	********			3.250
3.250	******	********	*******		İ	3.200
3.200	******	********	******			3.150
3.150	******	********	*****			3.100
3.100	******	********	****		İ	3.050
3.050	******	********	****			3.000
3.000	******	********	**			2.950
2.950	******	********	**		İ	2.900
2.900	******	********				2.850
2.850	******	********				2.800
2.800	******	*******			İ	2.750
2.750	******	******				2.700
2.700	******	*****				2.650
2.650	* * * * * * * *	*****			İ	2.600
	+,	+,	+,	+,-	+	
	2.000	2.500	3.000	3.500	4.000	

V_{OH} vs. V_{CC}=V_{IO} @ -40°C

	2.000	2.500	3.000	3.500	4.000	first pass data
	+,	+,	+,	+ ,	+	
3.650	*******	********	*********	*****		3.600
3.600	*******	********	*********	****		3.550
3.550	********	********	********	***		3.500
3.500	*******	********	********	**		3.450
3.450	*******	*******	********	*		3.400
3.400	*******	*******	*******			3.350
3.350	*******	*******	********			3.300
3.300	*******	*******	*******			3.250
3.250	*******	*******	******			3.200
3.200	*******	*******	*****			3.150
3.150	*******	*******	****			3.100
3.100	*******	*******	****			3.050
3.050	*******	*******	***			3.000
3.000	*******	********	**			2.950
2.950	******	*******	*]	2.900
2.900	*******	*******				2.850
2.850	*******	********				2.800
2.800	*******	*******]	2.750
2.750	*******	******				2.700
2.700	*******	*****				2.650
2.650	*******	*****				2.600
	+,	+,	+,	+ ,	+	
	2.000	2.500	3.000	3.500	4.000	



data

V_{OL} vs. V_{CC} = V_{IO} @ 25°C

	0.000	0.500	1.000	first	pass	data
	+,	-+,	-+			
3.650	.*******	* * * * * * * * * *	**	0.050		
3.600	.*******	* * * * * * * * * *	**	0.050		
3.550	.*******	* * * * * * * * * *	***	0.050		
3.500	.*******	* * * * * * * * * *	**	0.050		
3.450	.*******	* * * * * * * * * *	**	0.050		
3.400	.*******	* * * * * * * * * *	***	0.050		
3.350	.*******	* * * * * * * * * *	**	0.050		
3.300	.*******	* * * * * * * * * *	**	0.050		
3.250	.*******	* * * * * * * * * *	**	0.050		
3.200	.*******	* * * * * * * * * *	**	0.050		
3.150	.*******	* * * * * * * * * *	**	0.050		
3.100	.*******	* * * * * * * * * *	***	0.050		
3.050	.*******	* * * * * * * * * *	**	0.050		
3.000	.*******	* * * * * * * * * *	**	0.050		
2.950	.******	* * * * * * * * * *	**	0.050		
2.900	.*******	* * * * * * * * * *	**	0.050		
2.850	. * * * * * * * *	*********	**	0.050		
2.800	.******	* * * * * * * * * *	**	0.050		
2.750	.*******	* * * * * * * * * *	**	0.050		
2.700	.*******	* * * * * * * * * *	**	0.050		
2.650	.******	* * * * * * * * * *	**	0.050		
	+,	-+,	· - +			
	0.000	0.500	1.000			

V_{OL} vs. V_{CC}=V_{IO} @ 85°C

	0.000	0.500	1.000	first pass
	+,	+, -	+	
3.650	. * * * * *	* * * * * * * * * * *	****	0.050
3.600	.****	*******	****	0.050
3.550	.****	* * * * * * * * * * *	****	0.050
3.500	.****	*******	****	0.050
3.450	.****	*******	****	0.050
3.400	.****	* * * * * * * * * * *	****	0.050
3.350	.****	*******	****	0.050
3.300	.****	********	****	0.050
3.250	.****	* * * * * * * * * * *	****	0.050
3.200	.****	*******	****	0.050
3.150	.****	********	****	0.050
3.100	.****	* * * * * * * * * * *	****	0.050
3.050	.****	*******	****	0.050
3.000	.****	********	****	0.050
2.950	. * * * * *	*******	****	0.050
2.900	. * * * * *	*******	****	0.050
2.850	.****	*******	****	0.050
2.800	. * * * * *	*******	****	0.050
2.750	. * * * * *	*******	****	0.050
2.700	.****	*******	****	0.050
2.650	. * * * * *	*******	****	0.050
	+,	, -	+	
	0.000	0.500	1.000	



$V_{OL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	first pas	ss data
	+,	+, -	+		
3.650	.******	*******	* * * *	0.050	
3.600	.******	*******	****	0.050	
3.550	.******	*******	* * * *	0.050	
3.500	.******	* * * * * * * * *	* * * *	0.050	
3.450	.******	*******	* * * *	0.050	
3,400	. * * * * * * *	*******	****	0.050	
3.350	******	*******	* * * *	0.050	
3.300	******	*******	* * * *	0.050	
3.250	.******	*******	* * * *	0.050	
3.200	.******	*******	****	0.050	
3.150	.******	******	****	0.050	
3.100	.******	*******	****	0.050	
3.050	.******	* * * * * * * * *	****	0.050	
3.000	.******	*******	****	0.050	
2.950	.******	* * * * * * * * *	* * * *	0.050	
2.900	.******	* * * * * * * * *	* * * *	0.050	
2.850	.******	*******	****	0.050	
2.800	.******	*******	* * * *	0.050	
2.750	.******	* * * * * * * * *	* * * *	0.050	
2.700	.******	* * * * * * * * *	* * * *	0.050	
2.650	.******	******	* * * *	0.050	
	+,	+,-	+		
	0.000	0.500	1.000		

V_{OL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	first	pass	data
	+,	-+,	-+			
3.650	.*******	* * * * * * * * * *	**	0.050		
3.600	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.550	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.500	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.450	.*******	* * * * * * * * * *	**	0.050		
3.400	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.350	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.300	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.250	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.200	.*******	* * * * * * * * * *	**	0.050		
3.150	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.100	. * * * * * * * *	* * * * * * * * * *	**	0.050		
3.050	.*******	* * * * * * * * * *	**	0.050		
3.000	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.950	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.900	.******	* * * * * * * * * *	**	0.050		
2.850	.******	* * * * * * * * * *	**	0.050		
2.800	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.750	.******	* * * * * * * * * *	**	0.050		
2.700	.******	* * * * * * * * * *	**	0.050		
2.650	. * * * * * * * *	* * * * * * * * * *	**	0.050		
	+,	-+,	-+			
	0.000	0.500	1.000			



V_{IH} vs. V_{IO} @ 25°C

	0.500	1.000	1.500	2.000	2.500	first	pass	data
	+,	+,	+, -	+,	+			
3.000			* * * *	*******	* * * *	1.650		
2.950			* * * *	*******	****	1.650		
2.900			* * * * *	*******	****	1.600		
2.850			* * * * *	*******	****	1.600		
2.800			* * * * * *	*******	****	1.550		
2.750			* * * * * *	*******	* * * *	1.550		
2.700			* * * * * * *	*******	****	1.500		
2.650			* * * * * * *	*******	****	1.500		
2.600			* * * * * * * *	*******	* * * *	1.450		
2.550			. * * * * * * * * *	*******	****	1.400		
2.500			. * * * * * * * * *	*******	****	1.400		
2.450			* * * * * * * * * *	********	****	1.350		
2.400			* * * * * * * * * * *	*******	****	1.350		
2.350		*	* * * * * * * * * *	*******	****	1.300		
2.300		*	* * * * * * * * * *	********	****	1.300		
2.250		* * '	* * * * * * * * * * *	*******	****	1.250		
2.200		* * '	* * * * * * * * * *	*******	****	1.250		
2.150		* * * '	* * * * * * * * * *	*******	****	1.200		
2.100		* * * '	* * * * * * * * * * *	*******	****	1.200		
2.050		* * * *	* * * * * * * * * *	*******	****	1.150		
2.000		* * * *	* * * * * * * * * *	*******	****	1.150		
1.950		* * * * *	* * * * * * * * * *	*******	****	1.100		
1.900		* * * * *	* * * * * * * * * *	*******	****	1.100		
1.850		* * * * * *	* * * * * * * * * *	*******	****	1.050		
1.800		* * * * * *	* * * * * * * * * *	*******	****	1.050		
1.750		* * * * * * * *	* * * * * * * * * *	*******	****	1.000		
1.700		* * * * * * * * *	* * * * * * * * * *	*******	****	0.950		
1.650		* * * * * * * * *	* * * * * * * * * *	*******	****	0.950		
	+,	+,	+,-	+,	+			
	0.500	1.000	1.500	2.000	2.500			

V_{IH} vs. V_{IO} @ 85°C

3.000		0.500	1.000	1.500	2.000	2.500	first pass da	ata
3.000		+,	+,	+,-	+,-	+		
2.950	3.000			* * * *	******	****	1.650	
2.900	2.950			* * * *	*******	****	1.650	
2.850	2.900			* * * * *	*******	****	1.600	
2.800	2.850			* * * * * *	******	* * * *	1.550	
2.750	2.800			* * * * * *	*******	* * * *	1.550	
2.700	2.750			* * * * * * *	*******	****	1.500	
2.650	2.700			* * * * * * *	********	****	1.500	
2.600	2.650	1		* * * * * * * *	********	* * * *	1.450	
2.550	2.600			* * * * * * * *	********	****	1.450	
2.500	2.550			. * * * * * * * * *	*******	****	1.400	
2.450	2.500	1		. * * * * * * * * *	******	* * * *	1.400	
2.400	2.450			* * * * * * * * * *	********	****	1.350	
2.350	2.400			* * * * * * * * * *	*******	****	1.350	
2.300	2.350	1		* * * * * * * * * *	*******	* * * *	1.300	
2.250	2.300			* * * * * * * * * *	********	****	1.300	
2.200	2.250		* * *	* * * * * * * * * *	*******	****	1.250	
2.150	2.200	1	* * *	* * * * * * * * * *	******	****	1.250	
2.100	2.150		* * * *	* * * * * * * * * *	********	****	1.200	
2.050	2.100		* * * *	* * * * * * * * * *	*******	****	1.200	
2.000	2.050	1	****	* * * * * * * * * *	******	****	1.150	
1.950	2.000			* * * * * * * * * *	*******	* * * *	1.150	
1.900	1.950	1	*****	* * * * * * * * * *	*******	****	1.100	
1.850	1.900	1	* * * * * *	* * * * * * * * * *	*******	****	1.100	
1.800	1.850		*****	* * * * * * * * * *	*******	* * * *	1.050	
1.750	1.800		*****	*******	*******	****	1.050	
1.700	1 750		******	* * * * * * * * * *	*******	* * * *	1 000	
1.650	1 700		******	* * * * * * * * * *	*******	* * * *	1 000	
1.000 1.000 1.500 2.000 2.500	1 650		*******	* * * * * * * * * *	*******	****	0.950	
	1.000	1					0.000	
0.500 1.000 1.500 2.000 2.500		0.500	1.000	1.500	2.000	2.500		



V_{IH} vs. V_{IO} @ 105°C

	0.500	1.000	1.500	2.000	2.500	first pass	data
	+,	+,	,	+,	+		
3.000			* * * *	* * * * * * * * * * *	* * * *	1.650	
2.950			*****	********	* * * *	1.600	
2.900			*****	* * * * * * * * * * *	* * * *	1.600	
2.850			******	********	* * * *	1.550	
2.800			******	*******	* * * *	1.550	
2.750			* * * * * * *	* * * * * * * * * * *	* * * *	1.500	
2.700			* * * * * * * *	********	* * * *	1.500	
2.650			. * * * * * * * * *	*******	* * * *	1.450	
2.600			. * * * * * * * *	* * * * * * * * * * *	* * * *	1.450	
2.550			*******	********	* * * *	1.400	
2.500			*******	********	* * * *	1.400	
2.450		*	*******	* * * * * * * * * * *	* * * *	1.350	
2.400		*	*******	* * * * * * * * * * *	* * * *	1.350	
2.350		* *	*******	********	* * * *	1.300	
2.300		* *	*******	* * * * * * * * * * *	* * * *	1.300	
2.250		* * *	*******	* * * * * * * * * * *	* * * *	1.250	
2.200		* * *	*******	********	* * * *	1.250	
2.150		* * * *	*******	* * * * * * * * * * *	* * * *	1.200	
2.100		* * * *	*******	********	* * * *	1.200	
2.050		* * * * *	*******	********	* * * *	1.150	
2.000		* * * * *	********	* * * * * * * * * * *	* * * *	1.150	
1.950		* * * * * *	*******	*******	* * * *	1.100	
1.900		* * * * * *	*******	*******	****	1.100	
1.850		* * * * * * *	*******	* * * * * * * * * * *	* * * *	1.050	
1.800		* * * * * * *	*******	********	* * * *	1.050	
1.750		* * * * * * * *	*******	********	* * * *	1.000	
1.700		* * * * * * * *	*******	* * * * * * * * * * *	* * * *	1.000	
1.650		.*******	*******	* * * * * * * * * * *	* * * *	0.950	
	+,	+,	+,	+,	+		
	0.500	1.000	1.500	2.000	2.500		

V_{IH} vs. V_{IO} @ -40°C

	0.500	1.000	1.500	2.000	2.500	first pass data
	+,	-+,	+,	+,	+	
3.000			* * * * *	* * * * * * * * * *	***	1.650
2.950			* * * * *	* * * * * * * * * *	***	1.650
2.900			* * * * * *	* * * * * * * * * *	***	1.600
2.850			* * * * *	* * * * * * * * * *	***	1.600
2.800			* * * * * * *	* * * * * * * * * *	***	1.550
2.750			* * * * * * *	* * * * * * * * * *	***	1.550
2.700			* * * * * * * *	* * * * * * * * * *	***	1.500
2.650			* * * * * * * *	* * * * * * * * * *	***	1.500
2.600			. * * * * * * * * *	* * * * * * * * * *	***	1.450
2.550			. * * * * * * * * *	* * * * * * * * * *	***	1.450
2.500			* * * * * * * * * *	* * * * * * * * * *	***	1.400
2.450			* * * * * * * * * *	* * * * * * * * * *	***	1.400
2.400		*	* * * * * * * * * *	* * * * * * * * * *	***	1.350
2.350		**	* * * * * * * * * *	* * * * * * * * * *	***	1.300
2.300		**	* * * * * * * * * *	* * * * * * * * * *	***	1.300
2.250		* * *	* * * * * * * * * *	* * * * * * * * * *	***	1.250
2.200		* * *	* * * * * * * * * *	* * * * * * * * * *	***	1.250
2.150		* * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.200
2.100		* * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.200
2.050		* * * * *	*******	* * * * * * * * * *	***	1.150
2.000		* * * * *	* * * * * * * * * *	* * * * * * * * * *	***	1.150
1,950		* * * * * *	*******	* * * * * * * * * *	***	1.100
1.900		******	*******	* * * * * * * * * *	***	1.100
1.850		******	*******	*******	***	1.050
1.800		*******	*******	* * * * * * * * * *	***	1.000
1 750		*******	*******	* * * * * * * * * *	***	1 000
1 700		********	*******	* * * * * * * * * *	***	0.950
1 650		*******	*******	*******	***	0.950
1.000						0.000
	0.500	1.000	1.500	2.000	2.500	



V_{IL} vs. V_{IO} @ 25°C

	0.000	0.500	1.000	1.500	2.000	first pass data
2 000	+,	+,	+,	+,	+	1 200
3.000	1++++++++		* * * * * * * * * * *			1.300
2.950				•••••		1.300
2.900	++++++++		*********			1.250
2.850	+++++++		*********			1.250
2.800				•••••		1.250
2.750	++++++++		********			1.200
2.700	+++++++++++++++++++++++++++++++++++++++					1.200
2.650				•••••		1.200
2.600	++++++++		*******			1.150
2.550	+++++++		******			1.150
2.500						1.100
2.450	******		* * * * * * *	• • • • • • • • • • •		1.100
2.400	+++++++++++++++++++++++++++++++++++++++		*****			1.100
2.350			* * * * * * · · · · · · · · · · · · · ·	• • • • • • • • • • •		1.050
2.300	*******	*********	* * * * * *	•••••		1.050
2.250	××××××××	**********	* * * * * *	• • • • • • • • • • •		1.050
2.200	******	* * * * * * * * * * *	* * * * *	•••••		1.000
2.150	******	* * * * * * * * * * *	* * * *	•••••		1.000
2.100	******	* * * * * * * * * * *	* * *	• • • • • • • • • • •		0.950
2.050	******	*******	* * *	•••••		0.950
2.000	******	*******	* * *	• • • • • • • • • • •		0.950
1.950	******	******	* *			0.900
1.900	******	******	* *			0.900
1.850	*******	*******	* *			0.900
1.800	*******	*******	*			0.850
1.750	******	*******	*			0.850
1.700	*******	*******	*			0.850
1.650	******	*******	*			0.850
	+,	+,	+,	+,	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{IO} @ 85°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+,	+,	+,	+,	+			
3.000	******	*******	*******			1.300		
2.950	******	******	*********			1.250		
2.900	******	******	*********			1.250		
2.850	******	*******	*********			1.250		
2.800	******	*******	********			1.200		
2.750	******	*******	*******			1.200		
2.700	******	*******	*******			1.200		
2.650	******	*******	******			1.150		
2.600	******	*******	******			1.150		
2.550	******	*******	*****			1.100		
2.500	******	*******	*****			1.100		
2.450	******	*******	*****			1.100		
2.400	******	*******	*****			1.050		
2.350	******	*******	*****			1.050		
2.300	******	*******	*****			1.050		
2.250	******	*******	****			1.000		
2.200	******	*******	****			1.000		
2.150	******	*******	***			0.950		
2.100	******	*******	***			0.950		
2.050	******	*******	***			0.950		
2.000	******	*******	**			0.900		
1.950	******	******	**			0.900		
1.900	******	*******	**			0.900		
1.850	******	*******	**			0.900		
1.800	******	*******	*			0.850		
1.750	******	*******	*		İ	0,850		
1.700	******	*******	*			0.850		
1.650	******	*******	*			0.850		
	+	+,	+	+	+			
	0.000	0.500	1.000	1.500	2.000			



V_{IL} vs. V_{IO} @ 105°C

	0.000	0.500	1.000	1.500	2.000	first pass data
2 000	+,	+,	+,	+,	+	1 050
3.000	1					1.250
2.950				• • • • • • • • • • •		1.250
2.900	* * * * * * * * * *	**********	*********	• • • • • • • • • • •		1.250
2.850						1.200
2.800			· · · · · · · · · · · · · · · · · · ·	• • • • • • • • • • •		1.200
2.750	******	*********	********	•••••		1.200
2.700		********	* * * * * * * *	• • • • • • • • • • •		1.150
2.650	******	*******	* * * * * * * *	•••••		1.150
2.600	******	*******	* * * * * * * *	•••••		1.150
2.550	******	********	* * * * * * *	• • • • • • • • • • •		1.100
2.500	******	*******	* * * * * *	•••••		1.100
2.450	******	******	* * * * *	• • • • • • • • • • •		1.050
2.400	******	******	* * * * *			1.050
2.350	******	******	* * * * *	• • • • • • • • • • •		1.050
2.300	******	******	* * * *			1.000
2.250	******	*******	* * * *			1.000
2.200	******	*******	* * * *			1.000
2.150	******	******	* * *			0.950
2.100	******	******	* * *			0.950
2.050	******	******	* * *			0.950
2.000	******	*******	* *			0.900
1.950	******	*******	**			0.900
1.900	******	*******	**			0.900
1.850	******	******	*			0.850
1.800	******	*******	*			0.850
1.750	******	******	*			0.850
1.700	******	*******	*			0.850
1.650	******	*******				0.800
	+,	+,	+,	+,	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{IO} @ -40°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+,	+,	+,	+,	+			
3.000	******	********	*******	*		1.350		
2.950	******	********	********			1.300		
2.900	******	********	*******			1.300		
2.850	******	********	*******			1.300		
2.800	******	* * * * * * * * * *	********			1.250		
2.750	******	********	********			1.250		
2.700	******	*******	*******			1.200		
2.650	******	* * * * * * * * * *	*******			1.200		
2.600	******	********	*******			1.200		
2.550	******	*******	******			1.150		
2.500	******	* * * * * * * * * *	******			1.150		
2.450	******	* * * * * * * * * *	*****			1.100		
2.400	******	*******	*****			1.100		
2.350	******	*******	*****			1.100		
2.300	******	* * * * * * * * * *	****			1.050		
2.250	******	*******	****			1.050		
2.200	******	*******	****			1.000		
2.150	******	* * * * * * * * * *	****			1.000		
2.100	******	*******	****			1.000		
2.050	******	*******	***			0.950		
2.000	******	********	***			0.950		
1.950	******	* * * * * * * * * *	**			0.950		
1.900	******	********	*			0.900		
1.850	******	********	*			0.900		
1.800	******	********	*			0.900		
1.750	******	*******	•		İ	0,850		
1.700	******	********	•			0.850		
1.650	******	********				0.850		
	+,	+	+	+	+			
	0.000	0.500	1.000	1.500	2.000			



V_{OH} vs. V_{IO} @ 25°C

	1.500	2.000	2.500	3.000	3.500	first pass data
3 000	+,-	· + , - : * * * * * * * * * * *	*********	,· * * * *	+	2 950
2 950	******	********	*******	***		2 900
2 900	* * * * * * *	*********	*******	**		2 850
2 850	******	********	********	*		2.800
2.800	******	********	********			2.750
2 750	******	********	******			2 700
2.700	******	********	· *******			2.650
2.650	******	********	*****			2.600
2.600	******	********	****			2.550
2.550	******	********	****			2.500
2.500	******	********	***			2.450
2.450	******	********	**			2.400
2.400	******	********	*			2.350
2.350	******	********				2.300
2.300	******	*********				2.250
2.250	******	********				2.200
2.200	******	*******				2.150
2.150	******	******				2.100
2.100	******	*****				2.050
2.050	******	****				2.000
2.000	******	****				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******	•				1.800
1.800	*****					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+ , .	,-	,	+	
	1.500	2.000	2.500	3.000	3.500	

V_{OH} vs. V_{IO} @ 85°C

	1.500	2.000	2.500	3.000	3.500	first pass data
2 222	+,	+,	+,-	+,-	+	0.050
3.000				* * *		2.950
2.950	******	* * * * * * * * * * * * *	*********	**		2.900
2.900	******	* * * * * * * * * * * * *	* * * * * * * * * * *	*		2.850
2.850	******	* * * * * * * * * * * *	*******			2.800
2.800	******	* * * * * * * * * * *	*********			2.750
2.750	******	* * * * * * * * * * *	********			2.700
2.700	******	* * * * * * * * * * *	*******			2.650
2.650	******	* * * * * * * * * * * *	*****			2.600
2.600	******	* * * * * * * * * * *	*****			2.550
2.550	******	* * * * * * * * * * *	****			2.500
2.500	******	* * * * * * * * * * *	***			2.450
2.450	******	* * * * * * * * * * *	**			2.400
2.400	******	* * * * * * * * * * *	*			2.350
2.350	******	**********				2.300
2.300	******	*********				2.250
2.250	******	* * * * * * * *				2.200
2.200	******	* * * * * * *				2.150
2.150	******	* * * * * *				2.100
2.100	******	* * * * *				2.050
2.050	******	****				2.000
2.000	******	* * *				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,	+,	,	+, -	+	
	1.500	2.000	2.500	3.000	3.500	



V_{OH} vs. V_{IO} @ 105°C

	1.500	2.000	2.500	3.000	3.500	first pass data
2 000	+,-	+,-	*********	,· * * * *	+	2 950
2 950	******	********	******	* * *		2.950
2.990		********	*******	**		2.900
2.900	******	*******	*******	*		2.830
2 800	******	********	********			2.000
2 750	******	********	*******			2 700
2 700	******	********				2.700
2 650	******	********				3 600
2 600	******	********	*****			2 550
2 550	******	********	****			2.500
2.500	******	********	****			2.450
2.450	******	********	***			2.400
2.400	******	*******	**			2.350
2.350	******	*******	•			2.300
2.300	******	*******				2.250
2.250	******	*******				2.200
2.200	******	******				2.150
2.150	******	*****				2.100
2.100	******	****				2.050
2.050	******	****				2.000
2.000	******	***				1.950
1.950	*****	**				1.900
1.900	******	*				1.850
1.850	******	• • • • • • • • • • •				1.800
1.800	******					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+, -	+,	,	+	
	1.500	2.000	2.500	3.000	3.500	

V_{OH} vs. V_{IO} @ -40°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+,-	+, -	+,-	+,-	+	
3.000	******	* * * * * * * * * * *	* * * * * * * * * *	***		2.950
2.950	******	* * * * * * * * * * *	* * * * * * * * * * *	**		2.900
2.900	******	* * * * * * * * * * *	* * * * * * * * * *	*		2.850
2.850	******	* * * * * * * * * *	* * * * * * * * * *			2.800
2.800	******	* * * * * * * * * * *	* * * * * * * * * .			2.750
2.750	******	* * * * * * * * * * *	* * * * * * * *			2.700
2.700	******	* * * * * * * * * * *	* * * * * * *			2.650
2.650	******	* * * * * * * * * * *	* * * * * *]	2.600
2.600	******	* * * * * * * * * * *	* * * * *			2.550
2.550	******	* * * * * * * * * *	* * * *			2.500
2.500	******	* * * * * * * * * *	* * *		[2.450
2.450	******	* * * * * * * * * *	* *			2.400
2.400	******	* * * * * * * * * *	*			2.350
2.350	******	* * * * * * * * * *			[2.300
2.300	******	********				2.250
2.250	******	*******				2.200
2.200	******	* * * * * * *				2.150
2.150	******	*****				2.100
2.100	******	*****				2.050
2.050	******	* * * *				2.000
2.000	******	* * *				1.950
1.950	******	**				1.900
1.900	******	*				1.850
1.850	******					1.800
1.800	******.					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+,-	+,-	+,-	+,-	+	
	1.500	2.000	2.500	3.000	3.500	



V_{OL} vs. V_{IO} @ 25°C

	0.000	0.500	1.000) fi	rst	pass	data
	+,	,-	· +				
3.000	. * * * * *	*********	****	0	.05	0	
2.950	.****	*********	****	0	.05	0	
2.900	. * * * * *	*********	****	0	.05	0	
2.850	.****	*********	****	0	.05	0	
2.800	.****	*********	****	0	.05	0	
2.750	. * * * * *	*********	****	0	.05	0	
2.700	.****	*********	****	0	.05	0	
2.650	.****	*********	****	0	.05	0	
2.600	. * * * * *	*********	****	0	.05	0	
2.550	.****	*********	****	0	.05	0	
2.500	.****	*********	****	0	.05	0	
2.450	.****	*********	****	0	.05	0	
2.400	.****	*********	****	0	.05	0	
2.350	.****	*********	****	0	.05	0	
2.300	.****	* * * * * * * * * * *	****	0	.05	0	
2.250	.****	*********	****	0	.05	0	
2.200	. * * * * *	*********	****	0	.05	0	
2.150	.****	* * * * * * * * * * *	****	0	.05	0	
2.100	.****	*********	****	0	.05	0	
2.050	. * * * * *	*********	****	0	.05	0	
2.000	.****	* * * * * * * * * * *	****	0	.05	0	
1.950	.****	* * * * * * * * * * *	****	0	.05	0	
1.900	.****	* * * * * * * * * *	****	0	.05	0	
1.850	.****	*********	****	0	.05	0	
1.800	İ.****	* * * * * * * * * * *	****	0	.05	0	
1.750	.****	*********	****	0	.05	0	
1.700	j.****	*********	****	0	.05	0	
1.650	.****	*********	****	0	.05	0	
	+,	+, -	·+				
	0.000	0.500	1.00	00			

V_{OL} vs. V_{IO} @ 85°C

	0.000	0.500	1.000	first	pass	data
	+,	+,	+			
3.000	.******	*******	***	0.050		
2.950	. * * * * * * *	********	***	0.050		
2.900	. * * * * * * *	*******	***	0.050		
2.850	. * * * * * * *	*******	***	0.050		
2.800	. * * * * * * *	********	***	0.050		
2.750	. * * * * * * *	*******	* * * *	0.050		
2.700	.******	*******	***	0.050		
2.650	. * * * * * * *	********	***	0.050		
2.600	. * * * * * * *	*******	***	0.050		
2.550	. * * * * * * *	*******	***	0.050		
2.500	. * * * * * * *	********	***	0.050		
2.450	. * * * * * * *	*******	***	0.050		
2.400	. * * * * * * *	*******	***	0.050		
2.350	. * * * * * * *	* * * * * * * * * *	***	0.050		
2.300	.******	* * * * * * * * * *	***	0.050		
2.250	. * * * * * * *	*******	***	0.050		
2.200	. * * * * * * *	*******	***	0.050		
2.150	.******	* * * * * * * * * *	***	0.050		
2.100	. * * * * * * *	*******	***	0.050		
2.050	. * * * * * * *	*******	***	0.050		
2.000	. * * * * * * *	* * * * * * * * * *	***	0.050		
1.950	. * * * * * * *	*******	***	0.050		
1.900	. * * * * * * *	* * * * * * * * * *	***	0.050		
1.850	. * * * * * * *	********	***	0.050		
1.800	.******	*******	***	0.050		
1.750	.******	* * * * * * * * * *	***	0.050		
1.700	.******	* * * * * * * * * *	***	0.050		
1.650	.******	* * * * * * * * * *	***	0.050		
	+,	+,	· + İ			
	0.000	0.500	1.000			



V_{OL} vs. V_{IO} @ 105°C

	0.000	0.500	1	.000	first	pass	data
	+,	+,	+				
3.000	.******	*******	***		0.050		
2.950	. * * * * * * *	*******	***		0.050		
2.900	.******	* * * * * * * * * *	***		0.050		
2.850	. * * * * * * *	*******	***		0.050		
2.800	.******	*******	***		0.050		
2.750	.******	******	***		0.050		
2.700	. * * * * * * *	*******	***		0.050		
2.650	. * * * * * * *	*******	***		0.050		
2.600	.******	******	***	ĺ	0.050		
2.550	.******	******	***		0.050		
2.500	.******	******	***		0.050		
2.450	.******	******	***	İ	0.050		
2.400	.******	******	***		0.050		
2.350	.******	******	***		0.050		
2.300	.******	******	***	ĺ	0.050		
2.250	.******	******	***		0.050		
2.200	. * * * * * * *	******	***		0.050		
2.150	.******	******	***	ĺ	0.050		
2.100	.******	******	***		0.050		
2.050	.******	******	***		0.050		
2.000	.******	******	***	İ	0.050		
1.950	.******	*******	***		0.050		
1.900	.******	*******	***		0.050		
1.850	.******	******	***	İ	0.050		
1.800	.******	*******	***		0.050		
1.750	.******	*******	***		0.050		
1.700	.******	******	***	İ	0.050		
1.650	. * * * * * * *	*******	***		0.050		
	+,	+,	+				
	0.000	0.500	1	.000			

V_{OL} vs. V_{IO} @ -40°C

	0.000	0.500	1.000	first	pass	data
	+,	-+,	+			
3.000	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.950	. * * * * * * * *	* * * * * * * * *	***	0.050		
2.900	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.850	. * * * * * * * *	* * * * * * * * * *	***	0.050		
2.800	. * * * * * * * *	* * * * * * * * *	***	0.050		
2.750	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.700	.******	* * * * * * * * * *	* * *	0.050		
2.650	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.600	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.550	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.500	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.450	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.400	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.350	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.300	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.250	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.200	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.150	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.100	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.050	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
2.000	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
1.950	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.900	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.850	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.800	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.750	. * * * * * * * *	* * * * * * * * * *	* * *	0.050		
1.700	. * * * * * * * *	* * * * * * * * * *	***	0.050		
1.650	. * * * * * * * *	* * * * * * * * * *	***	0.050		
	+,	-+,	+			
	0.000	0.500	1.000			



16. Quality Assurance Guidelines

Cypress is totally committed to shipping the highest quality product to its customers.

To assure this quality commitment, each commercial manufacturing lot must meet the requirements defined in all of the specifications listed below:

Procedure	Test Method	Quality Test
Electrical Classification Tests	Guard banded to Data Sheet Specification	100%
Mark	Cypress F16-018	100%
Lead Scan / Straighten	Cypress F16-049	100%
Visual / Mechanical Inspection	Cypress F16-049	100%
QA Documentation / Test verification	Cypress F06-027	100%
QA - Visual / Mechanical	Cypress F06-027	Sample
Excelsior Monitor (See Below)	Cypress F00-006	Sample
Qualification Maintenance Program	Cypress F01-002.18	Sample

16.1 Excelsior Quality Monitor

Cypress's Excelsior Quality Program is an in-line monitor of electrical, visual/mechanical, solderability and marking permanency quality. Data from Excelsior Electrical Monitor may be made available to customers on request. Samples are selected from production lots and subjected to data sheet electrical temperature requirements. Any failures are analyzed by product engineering and appropriate corrective action is implemented. The excelsior quality levels are summarized by each product line on a monthly basis. This monitor has proven to be instrumental in Cypress's drive to attain the highest quality levels in the industry.

16.2 Advance Change Notification

The Cypress Advance Change Notification System aims to notify the customer of major product changes 90 days prior to the implementation of that change. A change is considered to be major if it affects the application, performance, quality, reliability, parameter distribution, form, fit or function of the product. In addition we may also notify changes such as relocation of manufacturing sites, certain Data Sheet items, or other changes that may affect use or acceptance of the product.

It should be noted that all changes are fully evaluated and qualified in accordance with well established and rigorous procedures. The changed product is not released for production or shipment until satisfactory qualification results, consistent with stable processes, predictable distributions and satisfactory and expected reliability figures and yields are achieved. Often shipment is recommended before the formal qualification report is available. The actual qualification tests, however, are completed and approved prior to shipment.

16.3 Customer Corrective Action Request

Cypress's Customer Corrective Action Request (CCAR) system provides a means for submitting customer perceived product problems to Cypress's factory for analysis. The analysis may be comprised of several stages, usually an initial analysis and follow-up analysis. A summary of Cypress's findings are issued. These may include corrective actions, requests for additional information or detailed failure analysis results.



17. Qualification Maintenance Program

The Cypress Qualification Maintenance Program (QMP) is used to measure the reliability of all process families on a regular basis. As it is not feasible to monitor the reliability of each of the literally hundreds of device types that Cypress produces, devices representative of the wafer fabrication process and the generic device grouping are selected on the basis of complexity, production volume, and strategic importance. These samples are subjected to the typical accelerated stress tests listed below on a monthly basis. Any failures encountered are analyzed by product engineering and appropriate corrective action is implemented. The results of this testing are summarized in the Cypress Quarterly Reliability Report (QRR).

17.1 Types of Stress

Several different process technology groups have been identified based on similarity of process parameters. Representative product types for each of these groups are listed in the Cypress QRR. Failure rates are tabulated for defective sub-populations and competing failure mechanisms. Two common measures of failure rates are early life failure rate (EL) and inherent life failure rate (IL). The early life period corresponds to approximately the first 4,000 hours at field use conditions. The inherent life corresponds to the useful life beyond the first 4000 of field operation. For these calculations, device operation temperature is assumed to be 55°C ambient unless otherwise noted. Voltage acceleration factors are used in the analysis wherever noted.

17.2 Reliability Monitor Stress Conditions

Stress	Package	Typical Duration	Target Sample Size	Typical Conditions
Early Life	All	24, 168 hours	350	125°C or 150°C, V _{CC} max
Inherent Life	All	1000 hours	120	125°C or 150°C, V _{CC} max
Endurance Cycling	All	10000 cycles	64	90°C
Data Retention Bake	All	1000 hours	64	150°C
Preconditioning (PC)	All	216 hours	231	30°C/70% RH Soak, 3X Reflow @ 260°C
PC + Temperature	Discrete, 2 die MCP	1000 cycles	77	–40°C to 150°C
Cycle	> 2 die MCP	1000 cycles	77	–55°C to 125°C
	BGA	264 hours	77	110°C, 85% RH, V _{CC} max alt. bias
FC + Diaseu HAST	Lead Frame	96 hours	77	130°C, 85% RH, V _{CC} max alt. bias
PC + Unbiased HAST	All	96 hours	77	110°C, 85% RH, no bias



18. Statistical Process Management

Statistical Process Management is used extensively throughout manufacturing and engineering areas in Cypress to help in reducing process variation and optimizing product/process performance. Examples of the tools used are Statistical Process Control (SPC), Process Capability Studies, Design of Experiments, Measurement Systems Analysis, Systematic Problem Solving, Structured project management, and statistical yield analysis, etc.

Some highlights of our SPC program include:

- Ubiquitous and intelligent use of problem solving methodologies
- SPC is 100% automated in all manufacturing areas using both statistically and economically derived Control Limits
- Out of Control Trouble Shooting Guides
- Statistical Equipment Control, (monitoring and control of input variables)
- Advanced Process Control (model based, active run-to-run control of processes during wafer fabrication)
- Suppliers are encouraged to implement SPC
- Six-Sigma target for critical processes

18.1 Kaizen + Program

All the training of statistical analysis tools, as well as other hard and soft improvement skills such as FMEA, Lean, Error Proofing, Structured Teamwork, are provided to employees as a part of Cypress's Kaizen+ (continuous improvement) program. The program involves all functional groups by establishing a structure that consists of a Champion, internal/external certified Black, Brown, Green and Yellow Belts in each organization to drive for improvement projects. The results are shared in a Project Sharing Conference twice per year. Statistical thinking and use of statistical methods are a part of Cypress's Kaizen+ culture.



19. Revision History

Section	Description
Revision 01 (December 20, 2011)	
	Initial release

Document Document	Document Title: S29GL01GS (XMC 85C 105C) Qualification Database Document Number: 002-00861							
Revision	ECN	Orig. of Change	Submission Date	Description of Change				
**	-	_	12/20/2011	Initial release.				
*A	6639209	CNSO	08/01/2019	Updated Document Title to read as "S29GL01GS (XMC 85C 105C) Qualification Database". Added 105°C Temperature Range related information in all instances across the document. Updated Assembly Packaging Summary: Updated LAE064: Updated details under "Theta Ja / Psi Jt". Updated TS056: Updated details under "Assembly Location" and "Theta Ja / Psi Jt". Updated LAA064: Updated LAA064: Updated details under "Theta Ja / Psi Jt". Updated Test Methodology: Replaced "Class Test (Bangkok, Thailand; Kuala Lumpur, Malaysia)" with "Class Test (Bangkok, Thailand)". Updated to Cypress template.				



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S29GL128S (XMC 85C 105C)



Qualification Database

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Additionally, the package details (material set, assembly location, etc.) are specific to the qual vehicle used for the qualification. Alternate material sets and assembly locations may be qualified for the product. Production material can be assembled with any qualified material set and at any qualified assembly location. Tests are performed in accordance with AEC-Q100 and relevant JEDEC specifications.

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1. Introduction

The Cypress S29GL128S flash memory device has a die size of 4.589 × 4.201 mm.

2. Die Photograph

Figure 2.1 Die Photograph



Note: 1. X in the diagram is pad #1. Count counter clockwise.



3. Pad Definition Table

Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA	Die Pad Index	Pad Name	Pin # TSOP	Pin # BGA
1	VSS	33, 52	H7	37	VCC	43	G5
2	VCC	43	G5	38	VSS	33, 52	H7
3	NC			39	VCC	43	G5
4	A22	2	B8	40	VSS	33, 52	H7
5	A15	3	D7	41	A0	31	E2
6	A14	4	C7	42	CE#	32	F2
7	A13	5	A7	43	OE#	34	G2
8	VSS	33, 52	H7	44	DQ0	35	E3
9	VCC	43	G5	45	DQ8	36	F3
10	A12	6	B7	46	DQ1	37	H3
11	A11	7	D6	47	DQ9	38	G3
12	A10	8	C6	48	VSS	33, 52	H2, E8
13	A9	9	A6	49	VIO	29	F1, D8
14	A8	10	B6	50	DQ2	39	E4
15	A19	11	D5	51	DQ10	40	F4
16	A20	12	D4	52	DQ3	41	H4
17	WE#	13	A5	53	DQ11	42	G4
18	NC			54	VCC	43	G5
19	RESET#	14	B5	55	VSS	33, 52	H7
20	A21	15	C5	56	DQ4	44	H5
21	WP#	16	B4	57	DQ12	45	F5
22	RY/BY#	17	A4	58	DQ5	46	E5
23	VIO	29	D8, F1	59	VSS	33, 52	H7
24	VSS	33, 52	H7	60	VCC	43	G5
25	A18	18	C4	61	DQ13	47	G6
26	A17	19	B3	62	NC		
27	A7	20	A3	63	VSS	33, 52	E8, H2
28	A6	21	C3	64	VIO	29	D8, F1
29	A5	22	D3	65	DQ6	48	H6
30	A4	23	B2	66	DQ14	49	F6
31	A3	24	A2	67	DQ7	50	E6
32	A2	25	C2	68	DQ15	51	G7
33	A1	26	D2	69	VCC	43	G5
34	DNU	28	E1	70	VSS	33, 52	H7
35	VCC	43	G5	71	A16	54	E7
36	VSS	33, 52	H7				

Qualification Database

4. Physical Sector Layout

Internal Use Row (17)	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use	Internal Use
Internal Use Row (16)					Internal Use	Internal Use	Internal Use	Internal Use
Row 15	120	121	122	123	124	125	126	127
Row 14	112	113	114	115	116	117	118	119
Row 3	24	25	26	27	28	29	30	31
Row 2	16	17	18	19	20	21	22	23
Row 1	8	9	10	11	12	13	14	15
Row 0	0	1	2	3	4	5	6	7
VerticalBank	0	1	2	3	0	1	2	3
Bank		()			1		

Figure 4.1 Physical Sector Layout



Figure 5.1 Sector Enlargement

IO Organization

	Internal Use	0	1	2	3	4	5	6	7	8	9
M 3B L	0-7	0-63	64-127	128-191	192-255	256-319	320-383	384-447	448-511	512-575	576-639
M1BL	8-15	0-127	128-255	256-383	384-511	512-639	640-767	768-895	896-1023	1024-1151	1152-1279

	10	11	12	13	14	15	Internal Use	Internal Use	Internal Use	Internal Use
M 3BL	640-703	704-767	768-831	832-895	896-959	960-1023	1024-1063	1064-1071	1072-1079	0-7
M1BL	1280-1407	1408-1535	1536-1663	1664-1791	1792-1919	1920-2047	2048-2127	2128-2143	2144-2159	0-7



6. Die Processing Summary

The Cypress S29GL128S flash memory device is manufactured using the 65 nm MirrorBit[®] Eclipse™ process technology.

The device is processed at WXIC, a 12-inch CMOS manufacturing facility located in Wuhan, China.

The device is manufactured on the highly reliable CS239LS process.



Figure 6.1 Die Process

PERIPHERY



6.1 Key Features of the CS239LS MirrorBit Eclipse Process Technology

A. Technology

- CMOS Triple-well process
- Proven reliable Flash MirrorBit Eclipse Technology

B. Transistor Types

- n-channel enhancement
- n-channel intrinsic
- p-channel enhancement
- MirrorBit core cell

C. Process Features

- ONO (oxide nitride oxide) gate dielectric
- Silicon Nitride (SiN) data storage layer

D. Spansion Highlights

- Volume Production Fab
- Solely dedicated to Non-Volatile Memories
- Ongoing Statistical Process Control program



7. Product Information

7.1 LAE064

Product Description:	S29GL128S					
rioduct Description.	128-Mbit, 3.0 Volt-only Page Mo	ode Flash Memory Featuring 65nm N	VirrorBit Eclipse Process Technology			
Package:	LAE064	Q100255				
Description:	(9 x 9 x 1.4 mm) 64 Ball, Fortifie					
Theta Ja:	34.1 °C/W	Psi Jt:	0.1 °C/W			
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin			
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste			
Lead Finish:	96.5Sn3.0Ag0.5Cu Spheres	Bond Wire:	Copper			
Comments:						
Est. Field Temperature:	55 °C	Life Test Temperature:	125 °C			
Est. DC Field Current:	55 mA	Life Test Dynamic Current:	10 mA			
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V			
Est. Field Power Dissipation:	165 mWatts	Est. Stress Power Dissipation:	36 mWatts			
Est. Field Delta Tj:	61.4 °C	Est. Stress Delta Tj:	126.4 °C			
Die:	98741B	Die Size:	4.58 × 4.20 mm			
Process:	CS239LS (65 nm)	Fab:	WXIC			
Туре:	MirrorBit Eclipse	Density:	128M			

7.2 LAA064

	S29GL128S	S29GL128S					
Product Description:	128-Mbit, 3.0 Volt-only Page M	ode Flash Memory Featuring 65nm I	MirrorBit Eclipse Process Technology				
Package:	LAA064	Qualification:	Q100313				
Description:	(13.0 x 11.0 x 1.4 mm) 64 Ball,	Fortified Ball Grid Array Package (FI	3GA)				
Theta Ja:	25.2 °C/W	Psi Jt:	0.1 °C/W				
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin				
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste				
Lead Finish:	96.5Sn3.0Ag0.5Cu Spheres	Bond Wire:	Copper				
Comments:							
Est. Field Temperature:	55 °C	Life Test Temperature:	125 °C				
Est. DC Field Current:	55 mA	Life Test Dynamic Current:	10 mA				
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V				
Est. Field Power Dissipation:	165 mWatts	Est. Stress Power Dissipation:	36 mWatts				
Est. Field Delta Tj:	61.4 °C	Est. Stress Delta Tj:	126.4 °C				
Die:	98741B	Die Size:	4.58 × 4.20 mm				
Process:	CS239LS (65 nm)	Fab:	WXIC				
Туре:	MirrorBit Eclipse	Density:	128M				



7.3 VBU056

Product Description:	S29GL256S					
rioduct Description.	128-Mbit, 3.0 Volt-only Page M	lode Flash Memory Featuring 65nm N	VirrorBit Eclipse Process Technology			
Package:	VBU056	Qualification:	Q100373			
Description:	(9.0 x 7.0 x 1.0 mm) 56 Ball, V	ery Thin Fine Pitch Ball Grid Array Pa	ckage (FBGA)			
Theta Ja:	36.0 °C/W	Psi Jt:	0.1 °C/W			
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin			
Substrate/Leadframe:	Laminate Substrate	Die Attachment:	Paste			
Lead Finish:	96.5Sn3.0Ag0.5Cu Spheres	Bond Wire:	Copper			
Comments:						
Est. Field Temperature:	55 °C	Life Test Temperature:	125 °C			
Est. DC Field Current:	55 mA	Life Test Dynamic Current:	10 mA			
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V			
Est. Field Power Dissipation:	165 mWatts	Est. Stress Power Dissipation:	36 mWatts			
Est. Field Delta Tj:	61.4 °C	Est. Stress Delta Tj:	126.4 °C			
Die:	98741B	Die Size:	4.58 x 4.20 mm			
Process:	CS239LS (65 nm)	Fab:	WXIC			
Туре:	MirrorBit Eclipse	Density:	128M			

7.4 TS056

Broduct Description:	S29GL128SH					
Floduct Description.	128-Mbit, 3.0 Volt-only Page Mo	ode Flash Memory Featuring 65nm I	NirrorBit Eclipse Process Technology			
Package:	TS056	Qualification:	Q100315			
Description:	(20.0 x 14.0 x 1.2 mm) 56 Lead,	, Thin Small Outline Package (TSOF	°)			
Theta Ja:	61.7 °C/W	Psi Jt:	0.21 °C/W			
Assembly Location:	Cypress Thailand	Molding Compound:	RoHS Compliant Epoxy Resin			
Substrate/Leadframe:	Copper Leadframe	Die Attachment:	Paste			
Lead Finish:	100% Matte Sn Plating	Bond Wire:	Copper			
Comments:						
Est. Field Temperature:	55 °C	Life Test Temperature:	125 °C			
Est. DC Field Current:	55 mA	Life Test Dynamic Current:	10 mA			
Est. Field Voltage:	3.0 V	Life Test Voltage:	3.6 V			
Est. Field Power Dissipation:	165 mWatts	Est. Stress Power Dissipation:	36 mWatts			
Est. Field Delta Tj:	68.8 °C	Est. Stress Delta Tj:	128.0 °C			
Die:	98741B	Die Size:	4.58 × 4.20 mm			
Process:	CS239LS (65 nm)	Fab:	WXIC			
Туре:	MirrorBit Eclipse	Density:	128M			



8. Assembly Bonding Diagram

8.1 TS056 Package





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Figure 8.2 64-Ball—LAE064/LAA064 Package



PIN 1 ID (A1 CORNER)



8.3 VBU056 Package







9. Test Methodology

Testing includes

- 4 hour, 250°C Data Retention Bake (in wafer form)
- Special test mode for extended life operation
- Proprietary screens for endurance

Wafer Sort (Austin, Texas, USA)

At Wafer Sort, all die experience 100% testing for:

- DC Parametrics
- AC Functionality
- Programmability
- Erasability

Class Test (Bangkok, Thailand)

At Class Test, all devices are tested for:

- DC Parametrics
- AC Functionality
- AC Speed
- Programmability
- Erasability

Test Coverage

All parameters specified in the data sheet are 100% tested in production unless otherwise specified. Those parameters not tested in production are guaranteed by characterization or correlation to other tests. AC speed testing is performed at class test.

Test Correlation and Guard Banding

Tester correlation to bench set-up has been completed for all tested parameters. Tester repeatability studies have been run. These results have been evaluated and incorporated into the tester guard band strategy. Guard bands have been implemented which demonstrate acceptable yield, quality assurance and customer satisfaction.

Test Flow

See the generalized Test Flow for the S29GL128S in Section 10.



10. Generalized Test Flow

The S29GL128S Generalized Test Flow for Industrial Temperature Range:




11. Quality and Reliability Data

11.1 S29GL128S High Temperature Operating Life Test Configuration

Pin/Pad #	Function	Resistor	Bias/CLK	
1	NC		NC	
2	A22	2.7K	CLK22	
3	A15	2.7K	CLK15	
4	A14	2.7K	CLK14	
5	A13	10K	CLK13	
6	A12	2.7K	CLK12	
7	A11	2.7K	CLK11	
8	A10	2.7K	CLK10	
9	A9	2.7K	CLK9	
10	A8	2.7K	CLK8	
11	A19	2.7K	CLK19	
12	A20	2.7K	CLK20	
13	WE#	2.7K	VCC	
14	RESET#	2.7K	VCC	
15	A21	2.7K	CLK21	
16	WP#	2.7K	VCC	
17	RY/BY#	2.7K	VCC	
18	A18	2.7K	CLK18	
19	A17	2.7K	CLK17	
20	A7	2.7K	CLK7	
21	A6	2.7K	CLK6	
22	A5	2.7K	CLK5	
23	A4	2.7K	CLK4	
24	A3	2.7K	CLK3	
25	A2	2.7K	CLK2	
26	A1	2.7K	CLK1	
27	RFU		NC	
28	RFU		NC	

Pin/Pad #	Function	Resistor	Bias/CLK	
56	NC		NC	
55	NC		NC	
54	A16	2.7K	CLK16	
53	RFU		NC	
52	VSS		GND	
51	DQ15	2.7K	VCC	
50	DQ7	2.7K	VCC	
49	DQ14	2.7K	VCC	
48	DQ6	2.7K	VCC	
47	DQ13	2.7K	VCC	
46	DQ5	2.7K	VCC	
45	DQ12	2.7K	VCC	
44	DQ4	2.7K	VCC	
43	VCC		VCC	
42	DQ11	2.7K	VCC	
41	DQ3	2.7K	VCC	
40	DQ10	2.7K	VCC	
39	DQ2	2.7K	VCC	
38	DQ9	2.7K	VCC	
37	DQ1	2.7K	VCC	
36	DQ8	2.7K	VCC	
35	DQ0	2.7K	VCC	
34	OE#	2.7K	VCC	
33	VSS		GND	
32	CE#	2.7K	GND	
31	A0	2.7K	CLK0	
30	RFU		NC	
29	VIO	2.7K	VCC	



11.2 CS239LS Life Test Failure Rate Calculation

HTOL Stress Temperature @ 125 °C

	Read Points / Test Results			Modeling Parameters @ 55°C					Average Failure Rate FITS @ 55°C, 60% Conf.		
Failure Mechanisms	24 hrs	168 hrs	1000 hrs	2000 hrs	Ea eV	TAF	VAF	OAF	MTTF (yrs)	Early Life	Inherent Life
PLASTIC											
Sample Size	4950	4615	842	50							
Zero fails, Process ave. Ea	0	0 <mark>(1)</mark>	0	0	0.66	53	1	53		48	11
Totals	0	0	0	0					10378	48	11

Note:

1. Contributes to Early Life FITS.

Data Retention Bake @ 150 °C

Reliability Stress	Number of Rejects	Sample Size	Failure Rate%	Failure Mechanism
500 hrs	0	1735	0.00	No Failures
1000 hrs	0	1208	0.00	No Failures



12. Summary of Stress Test Results

Stress Test	Stress Condition	Package Type	Samples Size	Number of Lots	Number of Fails	Failure Rate%	Comments
	Data From Qualification Q1	100255, Q100313, Q	100315:				
HTOL (EL)	3.6 V, 125 °C	LAE064 (1)	154	2	0	0.00	168 hrs
HTOL (IL)	3.6 V, 125 °C	LAE064 (1)	154	2	0	0.00	504 hrs
HTOL (XL)	3.6 V, 125 °C	LAE064 (1)	154	2	0	0.00	1000 hrs
	N/A	LAE064 (1)	15	1		Passed 1.0	kV
ESD CDM	N/A	LAA064 (2)	15	1		Passed 1.0	kV
	N/A	WND008 (3)	15	1		Passed 1.0	kV
ESD HBM	100 pF, 1500 Ohms	LAE064 (1)	84	2		Passed 2.0	kV
Latch Up	125 °C, ±100 mA	LAE064 (1)	6	1		Passed	
	105 °C, 3.6 V	LAE064 (1)	64	1	0	0.00	10k cycles
Endurance (10k)	-40 °C, 3.6 V	LAE064 (1)	64	1	0	0.00	10k cycles
1	90 °C, 3.6 V	LAE064 (1)	64	1	0	0.00	10k cycles
	105 °C, 3.6 V	LAE064 (1)	40	1	0	0.00	100k cycles
Endurance (100k)	90 °C, 3.6 V	LAE064 (1)	60	1	0	0.00	100k cycles
	Generic Ref	erence Data	<u>.</u> I		i		
High Tomp Bake (200 °C)	200 °C	LAE064 (5)	45	1	0	0.00	500 hrs
High Temp Bake (200 °C)	200 °C	TS048 (7)	45	1	0	0.00	350 hours
ESD CDM	N/A	LAE064 (4)	15	1		Passed 1.0	kV
	PC1/260 °C, +0 °C / -5 °C	LAE064 (5)	231	1	Passed .	Jedec L3 / J	eita Rank E
Broconditioning	PC9/260 °C, +0 °C / -5 °C	LAA064 (6)	77	1	Passed .	Jedec L3 / J	eita Rank E
Preconditioning	PC9/260 °C, +0 °C / -5 °C	TS048 (7)	392	2	Passed .	Jedec L3 / J	eita Rank E
	PC1/260 °C, +0 °C / -5 °C	FAB024 (8)	154	1	Passed .	Jedec L3 / J	eita Rank E
	PC1/260 °C, -40 °C / 150 °C	LAE064 (5)	77	1	0	0.00	1000 cycles
Preconditioning + Temp Cycle	PC9/260 °C, -40 °C / 150 °C	TS048 (7)	154	2	0	0.00	1000 cycles
	PC1/260 °C, -40 °C / 150 °C	FAB024 (8)	77	1	0	0.00	1000 cycles
Dressenditioning + UAST	PC1/260 °C, Biased, 110 °C / 85% RH	LAE064 (5)	77	1	0	0.00	264 hrs
Preconditioning + HAST	PC9/260 °C, Biased, 130 °C / 85% RH	TS048 (7)	84	2	0	0.00	96 hrs
	PC1/260 °C, Unbiased, 130 °C / 85% RH	LAE064 (5)	76	1	0	0.00	96 hrs
Preconditioning + uHAST	PC9/260 °C, Unbiased, 130 °C / 85% RH	TS048 (7)	154	2	0	0.00	96 hrs
	PC1/260 °C, Unbiased, 130 °C / 85% RH	FAB024 (8)	77	1	0	0.00	96 hrs

Table 12.1 Summary of Stress Test Results

Notes / Justification:

1. Results from Qual Q100255, S29GL128S, CS239LS (65 nm) MirrorBit Eclipse in 64 Ball fFBGA (9 x 9 x 1.4 mm).

2. Results from Qual Q100313, S29GL128S, CS239LS (65 nm) MirrorBit Eclipse in 64 Ball fFBGA (13 x 11 x 1.4 mm).

3. Results from Qual Q100315, S29GL128SH, CS239LS (65 nm) MirrorBit Eclipse in 56 Lead TSOP (20 x 14 x 1.2 mm).

4. Results from Qual Q100314, S29GL128SH in 64 Ball fFBGA (9 x 9 x 1.4 mm).

5. Results from Qual Q100167, S29GL01GS in 64 Ball fFBGA (9 x 9 x 1.4 mm) - Same Fab location and Same Flash.

6. Results from Qual Q100182, S29GL01GS in 64 Ball fFBGA (13 x 11 x 1.4 mm) - Same Package and Package BOM.

7. Results from Qual Q100252, 3ML01G12 in 48 Lead TSOP (20 x 12 x 1.2 mm) - Same Package and Package BOM.

8. Results from Qual Q100087, S25FL256S in 24 Ball FBGA (8 x 6 x 1.2 mm) - Same Package and Same Package BOM.

Preconditioning Flows

PC1 (Exceeds JEDEC L3 and JEITA Rank E) = Bake 125 °C, 24 hr --> Soak @ 30 °C/70%RH, 216 hr --> 3x Reflow. PC9 (Accelerated JEDEC L3 / JEITA Rank E): Bake 125 °C, 24 hr => Soak @ 60 °C/70%RH, 72 hr => 3x Reflow.

13. Characterization Test Results

The data pattern is "Random pattern" unless otherwise indicated.

13.1 DC Parameter Summary, 25°C

Room Temperature, 25°C, 3V, V_{CC}=V_{IO} Summary

Data Shoot Parametera		Spec		Average	Min	Max	Sigma	Cok
Data Sheet Parameters	Тур	Мах	Unit	Average	IAILLI	IVIAX	Sigma	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	87.6	81.3	95.4	2.5	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	46.4	44.2	49.4	1.1	4.0
I _{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.7	4.8	6.1	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.6	4.8	6.0	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.5	4.7	5.9	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.5	4.7	5.9	0.2	>5
I _{CC3} (V _{CC} Active Program/Erase Current)	45	100	mA	46.9	44.5	49.7	1.2	>5
I _{CC4} (V _{CC} Standby Current)	70	200	μΑ	14.5	8.5	68.3	9.7	>5
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.015	0.008	0.068	0.010	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	14.7	8.5	68.5	9.9	>5
I _{LI} (Input Leakage Current)	0.02	±1	μΑ	0.006	-0.012	0.395	0.025	>5
I _{LO} (Output Leakage Current)	0.02	±1	μΑ	0.002	-0.006	0.014	0.003	>5
	Average	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	262	1100	ms	282.0	178.0	479.0	36.4	>5
Buffer Program Time (256 word)	420	1050	μs	390.3	349.0	443.0	16.1	>5
Buffer Program Time (128 word)	320	1050	μs	313.1	280.0	351.0	11.2	>5
Buffer Program Time (64 word)	250	1050	μs	265.3	242.0	298.0	8.9	>5
Buffer Program Time (32 word)	220	1050	μs	236.7	215.0	265.0	8.1	>5
Buffer Program Time (16 word)	200	1050	μs	214.3	197.0	239.0	7.2	>5
Single Word Program Time (1 word)	125	400	μs	206.5	186.0	241.0	7.7	>5

Notes:

1. Data was collected from 70 units with 2 different lots 5878180 and 5878200 (wflot: LD00647, wf14, wflot: LD00647, wf17).



13.2 DC Parameter Summary, 85°C

Hot Temperature, 85°C, 3V, $V_{CC}\text{=}V_{\text{IO}}$ Summary

Data Shaat Daramatara		Spec		Average	Min	Мах	Sigma	Cnk
Data Sheet Parameters	Тур	Мах	Unit	Average	IVIITI	IVIAX	Sigma	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	92.5	88.2	99.5	2.4	
I_{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	48.4	46.2	51.5	1.1	3.4
I_{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.9	5.5	6.3	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.8	5.4	6.2	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.8	5.4	6.1	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.7	5.3	6.1	0.2	>5
I _{CC3} (V _{CC} Active Program/Erase Current)	45	100	mA	49.8	47.6	52.3	0.9	>5
I _{CC4} (V _{CC} Standby Current)	70	200	μA	32.1	17.3	93.5	11.1	>5
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.032	0.018	0.093	0.011	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	32.1	17.3	93.5	11.2	5.0
ILI (Input Leakage Current)	0.02	±1	μΑ	0.005	-0.018	0.181	0.022	>5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.001	-0.008	0.013	0.003	>5
	Averag	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	262	1100	ms	199.4	141.0	298.0	20.1	>5
Buffer Program Time (256 word)	420	1050	μs	332.9	279.0	426.0	19.4	>5
Buffer Program Time (128 word)	320	1050	μs	275.7	242.0	339.0	14.2	>5
Buffer Program Time (64 word)	250	1050	μs	236.0	206.0	288.0	11.4	>5
Buffer Program Time (32 word)	220	1050	μs	210.7	186.0	254.0	10.0	>5
Buffer Program Time (16 word)	200	1050	μs	190.1	168.0	225.0	8.2	>5
Single Word Program Time (1 word)	125	400	μs	185.7	165.0	219.0	8.7	>5

Notes:

1. Data was collected from 70 units with 2 different lots 5878180 and 5878200 (wflot: LD00647, wf14, wflot: LD00647, wf17).



13.3 DC Parameter Summary, 105°C

Hot Temperature, 105°C, 3V, $V_{CC} {=} V_{IO}$ Summary

Data Sheat Paramatara		Spec		Average	Min	Max	Sigma	Cok
Data Sheet Parameters	Тур	Мах	Unit	Average	IVIITI	IVIAX	Sigma	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	93.9	88.4	99.3	2.3	
I_{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	48.9	46.1	51.7	1.2	3.1
I_{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	6.0	5.3	6.5	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.9	5.3	6.4	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.8	5.2	6.3	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.8	5.1	6.3	0.2	>5
I _{CC3} (V _{CC} Active Program/Erase Current)	45	100	mA	50.3	48.0	52.4	0.9	>5
I _{CC4} (V _{CC} Standby Current)	70	200	μA	40.2	21.9	98.8	14.7	3.6
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.041	0.022	0.099	0.016	>5
I_{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	40.9	16.7	99.0	15.5	3.4
ILI (Input Leakage Current)	0.02	±1	μΑ	0.005	-0.013	0.226	0.022	>5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.002	-0.008	0.057	0.003	>5
	Averag	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	275	1100	ms	195.7	137.0	305.0	18.5	>5
Buffer Program Time (256 word)	420	1050	μs	338.4	281.0	423.0	19.8	>5
Buffer Program Time (128 word)	320	1050	μs	278.1	230.0	338.0	14.9	>5
Buffer Program Time (64 word)	250	1050	μs	238.5	198.0	288.0	12.0	>5
Buffer Program Time (32 word)	220	1050	μs	213.1	181.0	256.0	10.1	>5
Buffer Program Time (16 word)	200	1050	μs	193.4	172.0	229.0	8.3	>5
Single Word Program Time (1 word)	125	400	μs	191.0	168.0	229.0	9.2	>5

Notes:

1. Data was collected from 70 units with 2 different lots 5878180 and 5878200 (wflot: LD00647, wf14, wflot: LD00647, wf17).



13.4 DC Parameter Summary, -40°C

Cold Temperature, -40°C, 3V, $V_{CC}=V_{IO}$ Summary

Data Shaat Daramatara		Spec		Average	Min	Мах	Sigma	Cok
Data Sheet Parameters	Тур	Мах	Unit	Average	IVIITI	IVIAX	Sigma	Срк
		DC Pa	arameters					
I _{CC1} (V _{CC} Active Read Current) 10 MHz			mA	86.1	78.3	93.7	3.0	
I _{CC1} (V _{CC} Active Read Current) 5 MHz	55	60	mA	45.5	42.5	48.6	1.3	3.8
I_{CC2} (V _{CC} Intra-Page Read Current) 66 MHz			mA	5.4	4.7	5.9	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 50 MHz			mA	5.4	4.6	5.8	0.2	
I_{CC2} (V _{CC} Intra-Page Read Current) 40 MHz			mA	5.3	4.6	5.7	0.2	
I _{CC2} (V _{CC} Intra-Page Read Current) 33 MHz	9	25	mA	5.3	4.6	5.7	0.2	>5
I _{CC3} (V _{CC} Active Program/Erase Current)	45	100	mA	41.5	38.9	45.9	1.4	>5
I _{CC4} (V _{CC} Standby Current)	70	200	μΑ	13.1	8.1	65.4	9.1	>5
I _{CC5} (V _{CC} Reset Current)	10	20	mA	0.013	0.008	0.065	0.009	>5
I _{CC6} (V _{CC} Automatic Sleep Mode Current)	100	200	μA	13.5	8.1	65.1	9.6	>5
I _{LI} (Input Leakage Current)	0.02	±1	μΑ	0.006	-0.051	0.220	0.026	>5
I _{LO} (Output Leakage Current)	0.02	±1	μA	0.002	-0.021	0.013	0.003	>5
	Averag	e Sector Eras	e/Pre-progra	mming Time				
Sector Erase Time (64 kword sector)	262	1100	ms	374.6	232.0	501.0	45.7	>5
Buffer Program Time (256 word)	420	1050	μs	393.5	181.0	509.0	33.9	>5
Buffer Program Time (128 word)	320	1050	μs	316.1	195.0	417.0	25.1	>5
Buffer Program Time (64 word)	250	1050	μs	269.1	173.0	339.0	18.5	>5
Buffer Program Time (32 word)	220	1050	μs	240.7	159.0	296.0	14.7	>5
Buffer Program Time (16 word)	200	1050	μs	222.7	201.0	266.0	9.5	>5
Single Word Program Time (1 word)	125	400	μs	210.3	191.0	260.0	8.8	>5

Notes:

1. Data was collected from 70 units with 2 different lots 5878180 and 5878200 (wflot: LD00647, wf14, wflot: LD00647, wf17).



14. DC Device Characterization Data

ICC1 (Asynchronous Read) vs. Temperature



ICC2 (Page Read) vs. Temperature



ICC4 (Standby Current) vs. Temperature



ICC5 (Reset Current) vs. Temperature



ICC3 (Active Write) vs. Temperature



ICC6 (CMOSASM) vs. Temperature





15. AC Device Characterization Data



tACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)











tPACC vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tDF vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)



tOH vs. Temperature (VCCVIO = VCC 3.00V/VIO 3.00V, VIO = VCC 3.00V/VIO 1.65V)





Cumulative Erase Times per Sector at 25°C (VCC 3V)



Cumulative Erase Times per Sector at 85°C (VCC 3V)



Cumulative Erase Times per Sector at 105°C (VCC 3V)



Cumulative Erase Times per Sector at -40°C (VCC 3V)





Cumulative WB Program Times per Sector at 25°C (VCC 3V)



Cumulative WB Program Times per Sector at 85°C (VCC 3V)



Cumulative WB Program Times per Sector at 105°C (VCC 3V)



Cumulative WB Program Times per Sector at -40°C (VCC 3V)





Cumulative WB 256 Program Times per Buffer at 25°C (VCC 3V)



Cumulative WB 256 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 256 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB Program Times per Sector at -40°C (VCC 3V)





Cumulative WB 128 Program Times per Buffer at 25°C (VCC 3V)



Cumulative WB 128 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 128 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB 128 Program Times per Buffer at -40°C (VCC 3V)





Cumulative WB 64 Program Times per Buffer at 25°C (VCC 3V)



Cumulative WB 64 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 64 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB 64 Program Times per Buffer at -40°C (VCC 3V)





Cumulative WB 32 Program Times per Buffer at 25°C (VCC 3V)



Cumulative WB 32 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 32 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB 32 Program Times per Buffer at -40°C (VCC 3V)





Cumulative WB 16 Program Times per Buffer at 25°C (VCC 3V)



Cumulative WB 16 Program Times per Buffer at 85°C (VCC 3V)



Cumulative WB 16 Program Times per Buffer at 105°C (VCC 3V)



Cumulative WB 16 Program Times per Buffer at -40°C (VCC 3V)





Cumulative Single Word Program Times per Buffer at 25°C (VCC 3V)



Cumulative Single Word Program Times per Buffer at 85°C (VCC 3V)



Cumulative Single Word Program Times per Buffer at 105°C (VCC 3V)



Cumulative Single Word Program Times per Buffer at -40°C (VCC 3V)





t_{ACC} vs. V_{CC}=V_{IO} @ 25°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+;	+;-	;;	+	
3.650			* * * * *	********	* * * *	92
3.600			* * * * *	*******	****	92
3.550			* * * * *	*******	* * * *	92
3.500			*****	*******	****	92
3.450	1		* * * * *	******	* * * *	92
3.400			* * * * *	*******	****	92
3.350			*****	*******	****	92
3.300	1		* * * * *	******	* * * *	92
3.250			* * * *	*******	****	93
3.200			* * * *	*******	****	93
3.150	1		* * * *	******	* * * *	93
3.100			* * * *	*******	****	93
3.050			* * * *	*******	****	93
3.000	1		* * * *	******	* * * *	93
2.950			* * * *	*******	****	93
2.900			* * * *	*******	****	93
2.850	1		* * * *	******	* * * *	93
2.800			* * * *	*******	****	93
2.750			* * * *	*******	****	93
2.700	1		* * * *	******	* * * *	93
2.650			* * * *	*******	****	93
	+;	+;	+ ; -	+;	+	
	70.0	80.0	90.0	100.0	110.0	

t_{ACC} vs. V_{CC}=V_{IO} @ 85°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+;	+;	+;	+	
3.650			******	* * * * * * * * * * *	***	91
3.600			******	* * * * * * * * * * *	***	91
3.550			******	* * * * * * * * * * *	***	91
3.500			******	* * * * * * * * * * *	***	91
3.450			******	* * * * * * * * * * *	***	91
3.400			******	* * * * * * * * * * *	***	91
3.350			******	* * * * * * * * * * *	***	91
3.300			******	* * * * * * * * * * *	***	91
3.250			******	* * * * * * * * * * *	***	91
3.200			******	* * * * * * * * * * *	***	91
3.150			******	* * * * * * * * * * *	***	92
3.100			*****	* * * * * * * * * * *	***	92
3.050			******	*******	***	92
3.000			*****	* * * * * * * * * * *	***	92
2.950			*****	********	***	92
2.900			* * * * * *	*******	***	92
2.850			* * * * * *	* * * * * * * * * * *	***	92
2.800			*****	********	***	92
2.750			* * * * * *	*******	***	92
2.700			* * * * * *	* * * * * * * * * * *	***	92
2.650			* * * * * *	*******	***	92
	+;	+;		+;	+	
	70.0	80.0	90.0	100.0	110.0	



data

Qualification Database

t_{ACC} vs. V_{CC}=V_{IO} @ 105°C

	70.0	80.0	90.0	100.0	110.0	first pass
	+;	+;	+;	+ ;	+	
3.650			* * * * * *	* * * * * * * * * * *	***	93
3.600			* * * * * *	* * * * * * * * * * *	***	93
3.550			* * * * * *	* * * * * * * * * *	***	93
3.500			* * * * * *	* * * * * * * * * *	***	93
3.450			* * * * * *	* * * * * * * * * *	***	93
3.400			* * * * *	* * * * * * * * * *	***	93
3.350			* * * * * *	* * * * * * * * * *	***	93
3.300			* * * * * *	* * * * * * * * * *	***	93
3.250			* * * * *	* * * * * * * * * *	***	93
3.200			* * * * * *	* * * * * * * * * *	***	93
3.150				* * * * * * * * * * *	***	93
3.100			* * * * *	* * * * * * * * * *	***	94
3.050			* * * * *	* * * * * * * * * *	***	94
3.000			* * * * *	* * * * * * * * * *	***	94
2.950			* * * * *	* * * * * * * * * *	***	94
2.900			* * * * *	* * * * * * * * * *	***	94
2.850			* * * * *	* * * * * * * * * * *	***	94
2.800			* * * * *	* * * * * * * * * *	***	94
2.750			* * * * *	* * * * * * * * * *	***	94
2.700			****	* * * * * * * * * * *	***	94
2.650			* * * *	* * * * * * * * * * *	***	95
	+;	+;	+;	+ ;	+	
	70.0	80.0	90.0	100.0	110.0	

t_{ACC} vs. V_{CC}=V_{IO} @ -40^{\circ}C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;;	+ ;	+ ;	+;	+	
3.650			*	* * * * * * * * * *	***	97
3.600			*	* * * * * * * * * *	***	97
3.550			*	* * * * * * * * * *	***	97
3.500			*	* * * * * * * * * *	***	97
3.450			*	* * * * * * * * * *	***	97
3.400	1		*	* * * * * * * * * *	***	97
3.350			*	* * * * * * * * * *	***	97
3.300			*	* * * * * * * * * *	***	97
3.250	1		*	* * * * * * * * * *	***	97
3.200			*	* * * * * * * * * *	***	97
3.150			*	* * * * * * * * * *	***	97
3.100			*	* * * * * * * * * *	***	97
3.050			*	* * * * * * * * * *	***	97
3.000			*	* * * * * * * * * *	***	97
2.950	1		*	* * * * * * * * * *	***	97
2.900			*	* * * * * * * * * *	***	97
2.850			*	* * * * * * * * * *	***	97
2.800			*	* * * * * * * * * *	***	97
2.750			*	* * * * * * * * * *	***	97
2.700			*	* * * * * * * * * *	***	97
2.650				* * * * * * * * * *	***	98
	+;;	;;	+;	+;	+	
	70.0	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+;	;-;-	+;	+	
3.000			* * * *	* * * * * * * * * * * *	***	93
2.950			* * * *	* * * * * * * * * * *	***	93
2.900			* * * *	* * * * * * * * * * *	***	93
2.850			* * * *	********	***	93
2.800			* * * *	********	***	93
2.750			* * * *	* * * * * * * * * * *	***	93
2.700			* * * *	* * * * * * * * * * *	***	93
2.650			* * * *	* * * * * * * * * * *	***	93
2.600			* * * *	* * * * * * * * * * *	***	93
2.550			* * * *	* * * * * * * * * * *	***	93
2.500			* * * *	* * * * * * * * * * *	***	93
2.450			* * * *	* * * * * * * * * * *	***	93
2.400			* * * *	* * * * * * * * * * *	***	93
2.350			* * * *	* * * * * * * * * * *	***	93
2.300			* * * *	* * * * * * * * * * *	***	93
2.250			* * * *	* * * * * * * * * * *	***	93
2.200			* * * *	* * * * * * * * * * *	***	93
2.150			* * * *	* * * * * * * * * * *	***	93
2.100			* * * *	* * * * * * * * * * *	***	93
2.050			* * * *	* * * * * * * * * * *	***	93
2.000			* * * *	* * * * * * * * * * *	***	94
1.950			* * * *	* * * * * * * * * * *	***	94
1.900			* * * *	* * * * * * * * * * *	***	94
1.850			* * * *	* * * * * * * * * * *	***	94
1.800			* * * *	* * * * * * * * * * *	***	94
1.750			* * * *	* * * * * * * * * * *	***	94
1.700	1		**	********	***	95
1.650			* *	* * * * * * * * * * *	***	95
	+;	+;	+;-	+;	·+	
	70.0	80.0	90.0	100.0	110.0	

t_{ACC} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+; -	+;-	;;	+	
3.000			* * * * *	*******	****	92
2.950			* * * * *	********	****	92
2.900			* * * * *	********	* * * *	92
2.850			* * * * *	********	* * * *	92
2.800	1		* * * * *	*******	****	92
2.750			* * * * *	*******	****	92
2.700			* * * * *	********	* * * *	92
2.650	1		* * * * *	*******	****	92
2.600			* * * * *	*******	****	92
2.550			* * * * *	*******	****	92
2.500	1		* * * * *	*******	****	92
2.450			* * * * *	*******	****	92
2.400			* * * * *	*******	****	92
2.350	1		* * * * *	*******	****	92
2.300			* * * * *	*******	****	92
2.250			* * * * *	*******	****	92
2.200	1		* * * * *	*******	****	92
2.150			* * * * *	*******	****	92
2.100			* * * * *	*******	****	92
2.050	1		* * * * *	*******	****	92
2.000			* * * *	*******	****	93
1.950			* * * *	*******	****	93
1.900	1		* * * *	******	****	93
1.850	1		* * * *	*******	****	93
1.800	1		* * * *	*******	****	93
1.750	1		* * * *	******	****	93
1.700			* * * *	*******	****	93
1.650			* * *	*******	****	94
	+:	+;-	+;-	+;	+	
	70.0	80.0	90.0	100.0	110.0	



t_{ACC} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	· + ; - ·	+ ; -	+;	+	
3.000		• • • • • • • • • •	* * *	********	***	94
2.950		•••••	* * *	*********	***	94
2.900			* * *	*******	***	94
2.850			* * *	*******	***	94
2.800		• • • • • • • • • •	* * *	*******	***	94
2.750			* * *	* * * * * * * * * * * *	***	94
2.700			* * *	*******	***	94
2.650			* * *	* * * * * * * * * * *	***	94
2.600			* * *	*******	***	94
2.550			* * *	* * * * * * * * * * *	***	94
2.500			* * *	********	***	94
2.450			* * *	* * * * * * * * * * *	***	94
2.400			* * *	* * * * * * * * * * *	***	94
2.350			* * *	* * * * * * * * * * *	***	94
2.300			* * *	* * * * * * * * * * *	***	94
2.250			* * *	* * * * * * * * * * *	***	94
2.200			* * *	******	***	94
2.150			* * *	* * * * * * * * * * *	***	94
2.100			* * *	* * * * * * * * * * *	***	94
2.050			**	* * * * * * * * * * *	***	95
2.000			* *	* * * * * * * * * * *	***	95
1.950			* *	* * * * * * * * * * *	***	95
1.900			* *	* * * * * * * * * * *	***	95
1.850			* *	* * * * * * * * * * *	***	95
1.800			* *	* * * * * * * * * * *	***	95
1.750			**	* * * * * * * * * * *	***	95
1.700			* *	********	***	95
1.650			* *	********	***	95
	+;	+ ;		+;	+	
	70.0	80.0	90.0	100.0	110.0	

t_{ACC} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	-+;	-+;	-+;	-+	
3.000			· · · · · · · · * * '	******	**	97
2.950			* * *	*******	**	97
2.900			* * '	******	**	97
2.850			**	******	**	97
2.800			* * *	*******	**	97
2.750			* * *	* * * * * * * * * *	**	97
2.700			**:	* * * * * * * * * *	**	97
2.650			**	* * * * * * * * * *	**	97
2.600			**	*******	**	97
2.550			***	******	**	97
2.500			**	*******	**	97
2.450			**	* * * * * * * * * *	**	97
2.400			**:	*******	**	97
2,350				*******	**	97
2.300			*	******	**	98
2.250			**	******	**	98
2 200			*:	*******	**	98
2 150			*:	*******	**	98
2 100			*:	******	**	98
2.100			*:	******	**	98
2.000			**	******	**	98
1 950			**	*********	**	00
1 000			••••	*********	++	20
1.900	• • • • • • • • •		· · · · · · · · · · · · · · · · · · ·	**********	* * ^ ^	98
1.850				**********	* * I	98
1.800						99
1.750				*********	**	99
1.700				*******	**	99
1.650				******	**	99
	+;	-+;	-+;	-+;	-+	
	70.0	80.0	90.0	100.0	110.0	



t_{CE} vs. $V_{CC}{=}V_{IO} @~25^\circ C$

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;-	+;-	+;-	+;	· +	
3.650			* * * * * *	* * * * * * * * * * *	***	91
3.600			* * * * * *	* * * * * * * * * * *	***	91
3.550	1		* * * * * *	* * * * * * * * * * *	***	91
3.500	1		* * * * * *	* * * * * * * * * * *	***	91
3.450	1		* * * * *	* * * * * * * * * * *	***	92
3.400	1		* * * * *	* * * * * * * * * * *	***	92
3.350	1		* * * * *	* * * * * * * * * * *	***	92
3.300	1		* * * * *	* * * * * * * * * * *	***	92
3.250	1		* * * * *	* * * * * * * * * * *	***	92
3.200	1		* * * * *	* * * * * * * * * * *	***	92
3.150	1		* * * * *	* * * * * * * * * * *	***	92
3.100	1		* * * * *	* * * * * * * * * * *	***	92
3.050	1		* * * * *	* * * * * * * * * * *	***	92
3.000			* * * * *	* * * * * * * * * * *	***	92
2.950	1		* * * * *	* * * * * * * * * * *	***	92
2.900			* * * * *	* * * * * * * * * * *	***	92
2.850			* * * * *	* * * * * * * * * * *	***	92
2.800	1		* * * * *	*******	***	92
2.750			* * * * *	* * * * * * * * * * *	***	92
2.700			* * * * *	* * * * * * * * * * *	***	92
2.650			* * * * *	* * * * * * * * * * *	***	92
	+;-	+;-	+;-	+;	+	
	70.0	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{CC}=V_{IO} @ 85°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+;	+;	+ ;	+	
3.650			* * * * * * * *	*********	***	91
3.600			* * * * * * * *	*********	***	91
3.550			* * * * * * *	*********	***	91
3.500			* * * * * * * *	* * * * * * * * * *	***	91
3.450			* * * * * * * *	*********	***	91
3.400	1		* * * * * * * *	* * * * * * * * * *	***	91
3.350			* * * * * * * *	* * * * * * * * * *	***	91
3.300			* * * * * * * *	*********	***	91
3.250	1		* * * * * * * *	* * * * * * * * * *	***	91
3.200			* * * * * * * *	*********	***	91
3.150			* * * * * * * *	*********	***	91
3.100	1		* * * * * * *	*********	***	91
3.050			* * * * * * * *	*********	***	91
3.000			* * * * * * * *	*********	***	91
2.950	1		******	* * * * * * * * * *	***	91
2.900			* * * * * * * *	* * * * * * * * * * *	***	91
2.850			******	* * * * * * * * * * *	***	91
2.800			******	* * * * * * * * * *	***	91
2.750			* * * * * * * *	* * * * * * * * * * *	***	91
2.700			******	* * * * * * * * * * *	***	91
2.650			* * * * * * *	* * * * * * * * * *	***	91
	+;	+;	+;	+ ;	+	
	70.0	80.0	90.0	100.0	110.0	



t_{CE} vs. $V_{CC}\text{=}V_{IO} \textcircled{@} 105^\circ\text{C}$

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;;	+;	+;	+ ;	-+	
3.650	1		******	* * * * * * * * * * *	**	92
3.600			******	* * * * * * * * * * *	***	92
3.550	1		* * * * * *	* * * * * * * * * * *	**	92
3.500	1		* * * * *	* * * * * * * * * * *	***	93
3.450	1		* * * * *	* * * * * * * * * * *	***	93
3.400	1		* * * * *	* * * * * * * * * * *	**	93
3.350	1		* * * * *	* * * * * * * * * * *	***	93
3.300	1		* * * * *	* * * * * * * * * * *	***	93
3.250	1		* * * * *	* * * * * * * * * * *	**	93
3.200	1		* * * * *	* * * * * * * * * * *	***	93
3.150			* * * * *	* * * * * * * * * * *	***	93
3.100	1		* * * * *	* * * * * * * * * * *	**	93
3.050	1		* * * * *	* * * * * * * * * * *	***	93
3.000	1		* * * * *	* * * * * * * * * * *	***	93
2.950	1		* * * * *	* * * * * * * * * * *	**	93
2.900			* * * * *	* * * * * * * * * * *	***	93
2.850			* * * * *	* * * * * * * * * * *	***	93
2.800	1		* * * * *	* * * * * * * * * * *	**	93
2.750			* * * * *	* * * * * * * * * * *	***	93
2.700			* * * * *	* * * * * * * * * * *	***	93
2.650	1		* * * *	* * * * * * * * * * *	**	94
	+:	+;	+;	+;	-+	
	70.0	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{CC}=V_{IO} @ -40°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;-	+;-	;-	;;	· +	
3.650				* * * * * * * * * * *	***	97
3.600				*********	***	97
3.550				*********	***	97
3.500				*********	***	97
3.450				*********	***	97
3.400	1			********	***	97
3.350				*********	***	97
3.300				*********	***	97
3.250	1			********	***	97
3.200				*********	***	97
3.150				*********	***	97
3.100	1			*********	***	97
3.050				*********	***	97
3.000				*********	***	97
2.950	1			*********	****	97
2.900				*********	****	97
2.850				*********	****	97
2.800				*********	****	97
2.750				*********	****	97
2.700				. * * * * * * * * * *	***	98
2.650				. * * * * * * * * * *	***	98
	+;-	;-	+;-	+;	· +	
	70.0	80.0	90.0	100.0	110.0	



t_{CE} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+;		+;	+	
3.000			*****	*******	***	92
2.950			* * * * *	*******	***	92
2.900			* * * * *	********	***	92
2.850			* * * * *	* * * * * * * * * * *	***	92
2.800			* * * * *	********	***	92
2.750			*****	* * * * * * * * * * *	***	92
2.700			* * * * *	* * * * * * * * * * *	***	92
2.650			*****	* * * * * * * * * * *	***	92
2.600			*****	********	***	92
2.550			*****	* * * * * * * * * * *	***	92
2.500			*****	* * * * * * * * * * *	***	92
2.450			* * * * *	******	***	92
2.400			* * * * *	* * * * * * * * * * *	***	92
2.350			*****	********	***	92
2.300			* * * *	******	***	93
2.250			* * * *	* * * * * * * * * * *	***	93
2.200			****	********	***	93
2.150			* * * *	*******	***	93
2.100			* * * *	* * * * * * * * * * *	***	93
2.050			****	********	***	93
2.000			* * * *	*******	***	93
1.950			****	* * * * * * * * * * *	***	93
1.900			****	*******	***	93
1,850			***	*******	***	94
1.800			***	* * * * * * * * * * *	***	94
1.750			***	*******	***	94
1,700	1		**	*******	***	95
1.650	1		**	********	***	95
	+;	+;	+;-	+;	+	
	70.0	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	70.0	80.0	90.0	100.0	110.0	first pass data	a
	+;	+;	+;	+ ;	- +		
3.000			*******	* * * * * * * * * * *	***	91	
2.950			* * * * * * *	* * * * * * * * * * *	***	91	
2.900			* * * * * * * *	* * * * * * * * * * *	***	91	
2.850			*******	* * * * * * * * * * *	***	91	
2.800			* * * * * * *	* * * * * * * * * * *	***	91	
2.750			* * * * * * * *	* * * * * * * * * * *	***	91	
2.700			* * * * * * * *	* * * * * * * * * * *	***	91	
2.650			******	* * * * * * * * * * *	***	91	
2.600			* * * * * * * *	* * * * * * * * * * *	***	91	
2.550			* * * * * * * *	* * * * * * * * * * *	***	91	
2.500			******	* * * * * * * * * * *	***	91	
2.450			* * * * * * * *	* * * * * * * * * * *	***	91	
2.400			* * * * * * * *	* * * * * * * * * * *	***	91	
2.350			******	* * * * * * * * * * *	***	91	
2.300			* * * * * * *	* * * * * * * * * * *	***	92	
2.250			* * * * * * *	* * * * * * * * * * *	***	92	
2.200			* * * * * *	* * * * * * * * * * *	***	92	
2.150			* * * * * * *	* * * * * * * * * * *	***	92	
2.100			* * * * * * *	* * * * * * * * * * *	***	92	
2.050			******	* * * * * * * * * * *	***	92	
2.000			* * * * * *	* * * * * * * * * * *	***	92	
1.950			* * * * * * *	* * * * * * * * * * *	***	92	
1.900			* * * * * *	* * * * * * * * * * *	***	92	
1.850			* * * * *	* * * * * * * * * * *	***	93	
1.800			* * * * * *	* * * * * * * * * * *	***	93	
1.750			* * * * *	* * * * * * * * * * *	***	93	
1.700			* * * * * *	* * * * * * * * * * *	***	93	
1.650			* * * * *	* * * * * * * * * * *	***	94	
	+;	+;	+;	+ ;	· - +		
	70.0	80.0	90.0	100.0	110.0		



t_{CE} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	;;	;-	;;	+	
3.000			* * * *	*********	****	93
2.950			* * * *	*********	****	93
2.900			* * * *	*********	****	93
2.850			* * * *	*********	****	93
2.800			* * * *	*********	****	93
2.750			* * * *	* * * * * * * * * * *	****	93
2.700			* * * *	* * * * * * * * * * *	****	93
2.650			* * * *	*********	****	93
2.600	1		* * * *	*********	****	93
2.550			* * * *	*********	****	93
2.500			* * * *	*********	****	93
2.450	1		* * * *	*********	****	93
2.400			* * * *	*********	****	93
2.350			* * * *	*********	****	93
2.300	1		* * *	*********	****	94
2.250			* * *	*********	****	94
2.200			* * *	*********	****	94
2.150	1		* * *	*********	****	94
2.100			* * *	*********	****	94
2.050			* * *	*********	****	94
2.000			* * *	*********	****	94
1.950	1		* * *	*********	****	94
1.900			**	*********	****	95
1.850	1		* *	*********	****	95
1.800	1		* *	*********	****	95
1.750	1		**	*********	****	95
1,700	1		*	********	****	96
1.650			*	*********	****	96
	+;	+;-	+;-	+:	+	
	70.0	80.0	90.0	100.0	110.0	

t_{CE} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	70.0	80.0	90.0	100.0	110.0	first pass data
	+;	+;	+;	· - + ;	-+	
3.000			**	********	**	97
2.950			* *	*******	**	97
2.900			* *	********	**	97
2.850			* *	*******	**	97
2.800			* *	*******	**	97
2.750			* *	*******	**	97
2.700			* *	*******	**	97
2.650	1		* *	*******	**	97
2.600			* *	********	**	97
2.550			* *	*******	**	97
2.500	1		* *	*******	**	97
2.450			* *	*******	**	97
2.400			*	*******	**	98
2.350	1		*	*******	**	98
2.300			*	*******	**	98
2.250			*	*******	**	98
2.200	1		,	*******	**	98
2.150			*	*******	**	98
2.100			*	*******	**	98
2.050	1		,	*******	**	98
2.000			*	*******	**	98
1.950				*******	**	99
1.900	1			*******	**	99
1.850	1			*******	**	99
1.800				* * * * * * * * *	**	100
1.750	1			* * * * * * * * *	**	100
1.700	1			* * * * * * * *	**	101
1.650	1			* * * * * * * *	**	101
	+;	+;	+;	+ ;	-+	
	70.0	80.0	90.0	100.0	110.0	



t_{OE} vs. V_{CC}=V_{IO} @ 25°C

	0.0	10.0	20.0
	+;	+ ;	· - + ;
3.650		* * * * * * * * * * *	******
3.600		* * * * * * * * * * *	******
3.550		* * * * * * * * * * *	******
3.500		* * * * * * * * * * *	******
3.450		*******	******
3.400		* * * * * * * * * * *	******
3.350	1	* * * * * * * * * * *	******
3.300	1	********	******
3.250		* * * * * * * * * * *	******
3.200	1	* * * * * * * * * * *	******
3.150	1	********	******
3.100		* * * * * * * * * * *	******
3.050		* * * * * * * * * * *	******
3.000	1	********	******
2,950	1	*******	******
2.900		* * * * * * * * * * *	******
2.850		* * * * * * * * * * *	******
2,800	1	*******	******
2.750		* * * * * * * * * * *	******
2.700		* * * * * * * * * * *	******
2.650		* * * * * * * * * * *	******
	+;	+;	-+;
	0.0	10.0	20.0

first pass data

- 8 8 8

8

8 8 8

8 8 8

- 8888888888
- 8

t_{OE} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0
	+;	-+;	-+;
3.650	**	* * * * * * * * * *	******
3.600	**	* * * * * * * * * *	******
3.550	**	* * * * * * * * * *	******
3.500	**	* * * * * * * * * *	******
3.450	**	* * * * * * * * * *	******
3.400	**	* * * * * * * * * *	******
3.350	**	* * * * * * * * * *	******
3.300	**	* * * * * * * * * *	******
3.250	**	* * * * * * * * * *	******
3.200	**	* * * * * * * * * *	******
3.150	**	* * * * * * * * * *	******
3.100	**	* * * * * * * * * *	******
3.050	**	* * * * * * * * * *	******
3.000	**	* * * * * * * * * *	******
2.950	**	* * * * * * * * * *	******
2.900	* *	* * * * * * * * * *	******
2.850	**	* * * * * * * * * *	******
2.800	**	* * * * * * * * * *	******
2.750	* *	* * * * * * * * * *	******
2.700	**	* * * * * * * * * *	******
2.650	**	* * * * * * * * * *	******
	+;	-+;	-+;
	0.0	10.0	20.0

first pass data

777777777777777777777777



t_{OE} vs. V_{CC}=V_{IO} @ 105°C

 t_{OE} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0
	+;	-+;	-+;
3.650		* * * * * * * * * *	******
3.600		* * * * * * * * * *	******
3.550		* * * * * * * * * *	******
3.500		* * * * * * * * * *	******
3,450		*******	******
3.400		*******	******
3.350		*******	******
3.300		*******	******
3 250		*******	******
3 200		*******	******
3 150		******	******
3 100		******	******
3 050		******	******
3 000		******	******
2 050		*******	******
2.950		+++++++++	+++++++
2.900		++++++++++	*******
2.850			*******
2.800		********	******
2.750		********	******
2.700		******	******
2.650		*******	******
	+;	-+;	-+;
	0.0	10.0	20.0

first pass data

9

	0.0	10.0	20.0
	+;	-+;	-+;
3.650	**	* * * * * * * * * *	******
3.600	**	* * * * * * * * * *	******
3.550	**	* * * * * * * * * *	******
3.500	**	* * * * * * * * * *	******
3.450	**	* * * * * * * * * *	******
3.400	**	* * * * * * * * * *	******
3.350	**	* * * * * * * * * *	******
3.300	**	* * * * * * * * * *	******
3.250	*	******	******
3.200	*	* * * * * * * * * *	******
3.150	*	* * * * * * * * * *	******
3,100	*	******	******
3.050	*	* * * * * * * * * *	******
3.000	*	* * * * * * * * * *	******
2,950	*	* * * * * * * * * *	******
2.900	*	* * * * * * * * * *	******
2.850	*	* * * * * * * * * *	******
2.800	*	* * * * * * * * * *	******
2.750	*	* * * * * * * * * *	******
2.700	*	* * * * * * * * * *	******
2.650	*	* * * * * * * * * *	******
	+;	-+;	-+;
	0.0	10.0	20.0

first pass data

8 8 8



t_{OE} vs. V_{IO} (V_{CC} = 3V) @ 25°C

2 000	; *
2 000 Í ***************	*
3.000 [- i
2.950******************	*
2.900******************	۴İ
2.850******************	*
2.800******************	۲İ
2.750*******************	۰İ
2.700******************	*
2.650******************	*
2.600******************	۰İ
2.550******************	*
2.500******************	* İ
2.450******************	ŧİ
2.400******************	*
2.350******************	*
2.300	ŧİ
2.250	*
2.200	*
2.150	+
2.100	*
2.050	*
2.000	+
1.950	+
1.900	+
1.850	+
1.800*****************	*
1.750	*
1.700	+
1.650*****************	+
+;+;+	:
0.0 10.0 20.0	

t_{OE} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	0.0	10.0	20.0
	+;	-+;	-+;
3.000	* *	* * * * * * * * * *	******
2.950	* *	* * * * * * * * * *	******
2.900	**	* * * * * * * * * *	******
2.850	* *	* * * * * * * * * *	******
2.800	* *	* * * * * * * * * *	******
2.750	**	* * * * * * * * * *	******
2.700	* *	* * * * * * * * * *	******
2.650	**	* * * * * * * * * *	******
2.600	**	* * * * * * * * * *	******
2.550	* *	* * * * * * * * * *	******
2.500	**	* * * * * * * * * *	******
2.450	**	* * * * * * * * * *	******
2.400	* *	* * * * * * * * * *	******
2.350	* *	* * * * * * * * * *	******
2.300	*	* * * * * * * * * *	******
2.250	*	* * * * * * * * * *	******
2.200	*	* * * * * * * * * *	******
2.150	*	* * * * * * * * * *	******
2.100	*	* * * * * * * * * *	******
2.050	*	* * * * * * * * * *	******
2.000	*	* * * * * * * * * *	******
1.950	*	* * * * * * * * * *	******
1.900	*	* * * * * * * * * *	******
1.850	*	* * * * * * * * * *	******
1.800		* * * * * * * * * *	******
1.750		* * * * * * * * * *	******
1.700		* * * * * * * * * *	******
1.650		* * * * * * * * * *	******
	+;	- + ;	-+;
	0.0	10.0	20.0

first pass data

8

first pass data

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t_{OE} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	0.0	10.0	20.0
	+;	-+;;	+;
3.000		* * * * * * * * * *	******
2.950		*******	******
2.900		*******	*******
2.850		*******	*******
2.800		*******	*******
2.750		*******	*******
2.700		*******	*******
2.650		*******	*******
2.600	1	*******	*******
2.550		*******	*******
2.500		*******	*******
2,450	1	******	******
2.400		*******	*******
2,350		*******	*******
2,300	1	******	******
2.250		*******	*******
2,200		*******	*******
2.150		******	*******
2.100		*******	*******
2.050		******	*******
2 000		*******	*******
1 950		*******	*******
1.900		*******	*******
1 850		*******	*******
1 800		*******	*******
1 750		· ********	*******
1 700		• *******	*******
1 650		· * * * * * * * *	******
1.000	1 +	···	
	0.0	10 0	20.0
	0.0	±0.0	20.0

t_{OE} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	0.0	10.0	20.0
	+;	-+;	-+;
3.000		* * * * * * * * * *	******
2,950	*	* * * * * * * * * *	******
2.900	*	* * * * * * * * * *	******
2.850	*	* * * * * * * * * *	******
2 800	*	* * * * * * * * * *	******
2 750	*	* * * * * * * * * *	******
2 700	*	* * * * * * * * * *	******
2.650		******	******
2.000	*	******	******
2.000	*	*******	******
2.550	•	********	*******
2.500		*********	
2.450			
2.400			
2.350	*	********	******
2.300	*	* * * * * * * * * * *	******
2.250	*	* * * * * * * * * *	******
2.200	*	* * * * * * * * * *	******
2.150	*	* * * * * * * * * *	******
2.100	*	* * * * * * * * * *	******
2.050		* * * * * * * * * *	******
2.000		* * * * * * * * * *	******
1.950		* * * * * * * * * *	******
1.900		* * * * * * * * * *	******
1.850		* * * * * * * * * *	******
1.800		* * * * * * * * * *	******
1.750		. * * * * * * * * *	* * * * * * *
1.700		. * * * * * * * * *	******
1.650		. * * * * * * * * *	******
	+;	-+;	-+;
	0.0	10.0	20.0

first pass data

first pass data



pass data

t_{PACC} vs. V_{CC}=V_{IO} @ 25°C

+;+ 3.650 3.600 3.600 3.550 3.550 3.550 3.450 3.450 3.450 3.350 3.350 3.350 3.350 3.350 3.300 3.300 3.300 3.300 3.300 3.300 3.300 3.300 3.300 3.300 3.300 3.300 3.450 3.300 3.300 3.300 3.300 3.300 3.300 3.450 3.300 3.450 3.300 3.450 3.100 3.100 3.100 3.100 3.100 3.100 3.100 3.100 3.100 3.100 3.100 3.100		0.0	10.0	20.0	first
2.650	3.650 3.600 3.550 3.450 3.450 3.350 3.250 3.200 3.120 3.100 2.950 2.950 2.850 2.800 2.850 2.750 2.750	0.0	10.0 	20.0 -+ *** *** *** *** *** *** *** *** ***	first 12 12 12 12 12 12 12 12 12 12 12 12 12
	2.650	 +; 0.0	******** -+; 10.0	** -+ 20.0	12

t_{PACC} vs. V_{CC}=V_{IO} @ 85°C

	0.0	10.0	20.0	first pass	data
	+;	-+;	-+		
3.650		. * * * * * * * * *	**	10	
3.600		. * * * * * * * * *	**	10	
3.550		. * * * * * * * * *	**	10	
3.500		. * * * * * * * * *	**	10	
3.450		. * * * * * * * * *	**	10	
3.400		. * * * * * * * * *	**	10	
3.350		. * * * * * * * * *	**	10	
3.300		. * * * * * * * * *	**	10	
3.250		. * * * * * * * * *	**	10	
3.200		. * * * * * * * * *	**	10	
3.150		. * * * * * * * * *	**	10	
3.100		. * * * * * * * * *	**	10	
3.050		. * * * * * * * * *	**	10	
3.000		. * * * * * * * * *	**	10	
2.950		. * * * * * * * * *	**	10	
2.900		. * * * * * * * * *	**	10	
2.850		. * * * * * * * * *	**	10	
2.800		. * * * * * * * * *	**	10	
2.750		. * * * * * * * * *	**	10	
2.700		. * * * * * * * * *	**	10	
2.650		. * * * * * * * * *	**	10	
	+;	-+;	- +		
	0.0	10.0	20.0		

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t_{PACC} vs. V_{CC} = V_{IO} @ 105°C

	0.0	10.0	20.0	first	pass	data
	+;	-+;	-+			
3.650		* * * * * *	**	12		
3.600		* * * * * *	**	12		
3.550		* * * * * *	**	12		
3.500		* * * * * *	**	12		
3.450		* * * * * *	**	12		
3.400		* * * * * *	**	12		
3.350		* * * * * *	**	12		
3.300		* * * * * *	**	12		
3.250		* * * * * *	**	12		
3.200		* * * * * *	**	12		
3.150		* * * * * *	**	12		
3.100		* * * * * *	**	12		
3.050		* * * * * *	**	12		
3.000		* * * * * *	**	12		
2.950	1	* * * * * *	**	12		
2.900		* * * * * *	**	12		
2.850		* * * * * *	**	12		
2.800		* * * * * *	**	12		
2.750		* * * * * *	**	12		
2.700		* * * * * *	**	12		
2.650		* * * * * *	**	12		
	+;	-+;	-+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{CC}=V_{IO} @ -40°C

	0.0	10.0	20.0	first	pass	data
	+;	-+;	-+			
3.650		* * * * * * * *	**	11		
3.600		* * * * * * * *	**	11		
3.550		* * * * * * * *	**	11		
3.500		* * * * * * * *	**	11		
3.450		* * * * * * * *	**	11		
3.400		* * * * * * * *	**	11		
3.350		* * * * * * * *	**	11		
3.300		* * * * * * * *	**	11		
3.250		* * * * * * * *	**	11		
3.200		* * * * * * * *	**	11		
3.150		* * * * * * * *	**	11		
3.100		* * * * * * * *	**	11		
3.050		* * * * * * * *	**	11		
3.000		* * * * * * * *	**	11		
2.950		* * * * * * * *	**	11		
2.900		* * * * * * * *	**	11		
2.850		* * * * * * * *	**	11		
2.800		* * * * * * * *	**	11		
2.750		* * * * * * * *	**	11		
2.700		* * * * * * * *	**	11		
2.650		* * * * * * * *	**	11		
	+;	-+;	-+			
	0.0	10.0	20.0			

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t_{PACC} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	0.0	10.0	20.0	first	pass	data
	+;	-+;	-+			
3.000		* * * * * *	**	12		
2.950		* * * * * * *	**	12		
2.900		* * * * * *	**	12		
2.850		* * * * * * *	**	12		
2.800		* * * * * * *	**	12		
2.750		* * * * * *	**	12		
2.700		* * * * * * *	**	12		
2.650		* * * * * * *	**	12		
2.600		* * * * * *	**	12		
2.550		* * * * * *	**	12		
2.500		* * * * * * *	**	12		
2.450		* * * * * *	**	12		
2.400		* * * * * *	***	12		
2.350		* * * * * * *	**	12		
2.300		* * * * * *	**	12		
2.250		* * * * * *	**	12		
2.200		* * * * * * *	**	12		
2.150		* * * * * *	**	12		
2.100		* * * * * *	***	12		
2.050		* * * * * *	**	12		
2.000		* * * * * *	**	12		
1.950		* * * * * *	**	12		
1.900		* * * * * *	**	12		
1.850		* * * * * *	**	13		
1.800		* * * * * *	**	13		
1.750		* * * * * *	**	13		
1.700		* * * * * *	**	13		
1.650		* * * * * *	**	13		
	+;	-+;	-+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	0.0	10.0	20.0	first	pass	data
	+;	-+;;	- +			
3.000		. * * * * * * * * *	**	10		
2.950		. * * * * * * * * *	**	10		
2.900		. * * * * * * * * *	**	10		
2.850		. * * * * * * * * *	**	10		
2.800		. * * * * * * * * *	**	10		
2.750		. * * * * * * * * *	**	10		
2.700		. * * * * * * * * *	**	10		
2.650		. * * * * * * * * *	**	10		
2.600		. * * * * * * * * *	**	10		
2.550		. * * * * * * * * *	**	10		
2.500		. * * * * * * * * *	**	10		
2.450		. * * * * * * * * *	**	10		
2.400		. * * * * * * * * *	**	10		
2.350		. * * * * * * * * *	**	10		
2.300		. * * * * * * * * *	**	10		
2.250		. * * * * * * * * *	**	10		
2.200		. * * * * * * * * *	**	10		
2.150		. * * * * * * * * *	**	10		
2.100		. * * * * * * * * *	**	10		
2.050		* * * * * * * *	**	11		
2.000		* * * * * * * *	**	11		
1.950		* * * * * * * *	**	11		
1.900		* * * * * * * *	**	11		
1.850		* * * * * * * *	**	11		
1.800		* * * * * * * *	**	11		
1.750		* * * * * * * *	**	11		
1.700		* * * * * * * *	**	11		
1.650		* * * * * * * *	**	11		
	+;	-+;	-+			
	0.0	10.0	20.0			



t_{PACC} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	0.0	10.0	20.0	first	pass	data
	+;	-+;	+			
3.000		* * * * * *	***	12		
2.950		******	***	12		
2.900		*****	***	12		
2.850		******	***	12		
2.800		******	***	12		
2.750		*****	***	12		
2.700		******	***	12		
2.650		******	***	12		
2.600		******	***	12		
2.550		******	***	12		
2.500		******	***	12		
2.450		******	***	12		
2.400		******	***	12		
2.350		******	***	12		
2.300		******	***	12		
2.250		*****	***	13		
2.200		*****	***	13		
2.150		*****	* * *	13		
2.100		*****	***	13		
2.050		*****	***	13		
2.000		*****	* * *	13		
1.950		*****	***	13		
1.900		*****	***	13		
1.850		* * * * * *	***	13		
1.800		*****	***	13		
1.750		*****	***	13		
1.700		* * * * *	***	14		
1.650		* * * * *	***	14		
	+;	-+;	+			
	0.0	10.0	20.0			

t_{PACC} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	0.0	10.0	20.0	first	pass	data
	+;	+ ;	-+			
3.000		* * * * * * * *	**	11		
2.950	1	* * * * * * * *	***	11		
2.900		* * * * * * * *	***	11		
2.850		* * * * * * * *	***	11		
2.800	1	* * * * * * * *	***	11		
2.750		* * * * * * * *	***	11		
2.700		* * * * * * * *	***	11		
2.650	1	* * * * * * * *	***	11		
2.600		* * * * * * * *	***	11		
2.550		* * * * * * * *	***	11		
2.500	1	* * * * * * * *	***	11		
2.450		* * * * * * * *	***	11		
2.400		* * * * * * * *	***	11		
2.350	1	* * * * * * * *	***	11		
2.300		* * * * * * * *	***	11		
2.250		* * * * * * * *	**	11		
2.200	1	* * * * * * * *	***	11		
2.150		* * * * * * * *	***	11		
2.100		* * * * * * * *	**	11		
2.050	1	* * * * * * *	***	12		
2.000		* * * * * * *	***	12		
1.950		* * * * * * *	**	12		
1.900	1	* * * * * * *	**	12		
1.850		* * * * * * *	**	12		
1.800		* * * * * * *	**	12		
1.750	1	* * * * * *	**	12		
1.700		* * * * * *	**	13		
1.650		* * * * *	**	13		
	+;	+ ;	· - +			
	0.0	10.0	20.0			



V_{IH} vs. V_{CC}=V_{IO} @ 25°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+;;	+ ;	;	+;	+	
3.650			* * * * * * * *	*******	****	2.000
3.600			* * * * * * * *	*******	****	2.000
3.550	1		.*******	*******	* * * *	1.950
3.500			*******	* * * * * * * * * * *	* * * *	1.900
3.450			*******	*******	* * * *	1.900
3,400	1	,	*******	******	* * * *	1.850
3.350	1	,	*******	*******	* * * *	1.850
3.300	1	* *	********	*******	****	1.800
3,250	1		*******	*******	****	1.800
3.200		* * *	********	*******	****	1.750
3,150	1	* * *	*******	*******	****	1.750
3.100		****	*******	*******	****	1.700
3.050		****	********	*******	****	1.700
3,000	1	****	*******	*******	****	1.650
2,950	1	* * * * *	*******	*******	****	1,600
2.900			*******	*******	****	1.600
2,850		******	********	*******	****	1.550
2.800		*****	*******	*******	****	1.550
2.750		*******	********	*******	****	1.500
2.700			*******	*******	****	1.500
2.650		*******	********	********	****	1.450
2.000	+	 + : - :	+:-	+:-	+	
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. V_{CC}=V_{IO} @ 85°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+;	+ ;	-+;	+ ;	+	
3.650			.*******	* * * * * * * * * *	***	2.000
3.600			.*******	* * * * * * * * * *	***	2.000
3.550	1		*******	* * * * * * * * * *	***	1.950
3.500	1		*******	* * * * * * * * * *	***	1.950
3.450	1	*	*******	* * * * * * * * * *	***	1.900
3,400	1		******	*******	***	1,900
3.350	1	**	******	* * * * * * * * * *	***	1.850
3,300	1	***	******	* * * * * * * * * *	***	1,800
3.250		***	*******	*******	***	1.800
3.200		****	******	*******	***	1.750
3,150	1	****	******	* * * * * * * * * *	***	1,750
3,100	1	*****	******	*******	***	1,700
3.050	1	*****	******	* * * * * * * * * *	***	1.700
3.000		* * * * * *	******	* * * * * * * * * *	***	1.650
2,950	1	* * * * *	******	* * * * * * * * * *	***	1,650
2.900		******	******	* * * * * * * * * *	***	1.600
2.850		* * * * * * * *	******	* * * * * * * * * *	***	1.550
2,800	1	* * * * * * * *	******	* * * * * * * * * *	***	1,550
2.750		*******	******	* * * * * * * * * *	***	1.500
2.700		*******	******	* * * * * * * * * *	***	1,500
2.650	1	*******	******	* * * * * * * * * *	***	1.450
2.000	+	.	-+	+:	+	
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. $V_{CC}\text{=}V_{IO}$ @ 105°C

	1.000	1.500	2.000	2.500	3.000	first pass data
	+;	+;	;-;-	+;	+	
3.650			* * * * * * * *	* * * * * * * * * * *	* * * *	2.000
3.600			* * * * * * *	* * * * * * * * * * *	****	2.000
3.550	1		. * * * * * * * * *	* * * * * * * * * * *	****	1.950
3.500	1		*******	* * * * * * * * * * *	****	1.900
3.450	1		*******	*******	* * * *	1.900
3.400	1	,	*******	* * * * * * * * * * *	* * * *	1.850
3.350	1	,	********	********	* * * *	1.850
3.300	1	* *	*******	*******	* * * *	1.800
3.250	1	* *	*******	* * * * * * * * * * *	* * * *	1.800
3.200	1	* * *	********	********	* * * *	1.750
3.150	1	* * *	********	********	* * * *	1.750
3,100	1	* * * *	*******	*******	* * * *	1,700
3.050		* * * * *	*******	*******	* * * *	1.650
3.000	1	* * * * *	********	********	* * * *	1.650
2,950	1		*******	*******	* * * *	1,600
2.900			*******	*******	* * * *	1.600
2,850		* * * * * *	*******	******	* * * *	1,550
2.800		******	*******	********	* * * *	1.550
2.750		. *******	*******	*******	* * * *	1.500
2.700		*******	*******	********	* * * *	1.500
2 650		*******	********	********	* * * *	1 450
2.000	+ ·				+	1.100
	1.000	1.500	2.000	2.500	3.000	

V_{IH} vs. V_{CC}=V_{IO} @ -40°C

	1.000	1.500	2.000	2.500	3.000	first pass	3 data
	+;	+;	+;	+;	+		
3.650			* * * * * * * *	*******	****	2.000	
3.600	1		* * * * * * * *	* * * * * * * * * *	****	2.000	
3.550	1		. * * * * * * * * *	********	****	1.950	
3.500	1		. * * * * * * * * *	* * * * * * * * * *	****	1.950	
3.450	1		*******	********	****	1.900	
3,400	1		*******	********	****	1,900	
3.350	1	*	*******	********	****	1.850	
3.300		* *	*******	********	****	1.800	
3,250	1	**	*******	********	****	1,800	
3.200	1	* * *	*******	********	****	1.750	
3.150	1	* * *	*******	********	****	1.750	
3.100	1	* * * *	*******	********	****	1.700	
3.050	1	* * * *	* * * * * * * * * *	* * * * * * * * * *	****	1.700	
3.000	1	* * * * *	*******	* * * * * * * * * *	****	1.650	
2.950	1	* * * * *	*******	********	****	1.650	
2.900		* * * * * *	* * * * * * * * * *	* * * * * * * * * *	****	1.600	
2.850		* * * * * *	*******	* * * * * * * * * *	****	1.600	
2.800	1	* * * * * * *	*******	********	****	1.550	
2.750	1	* * * * * * * *	* * * * * * * * * *	* * * * * * * * * *	****	1.500	
2.700		* * * * * * * *	*******	* * * * * * * * * *	****	1.500	
2.650	1	. * * * * * * * * *	*******	* * * * * * * * * *	****	1.450	
	+;	+;	+;	+;	· + İ		
	1.000	1.500	2.000	2.500	3.000		


V_{IL} vs. $V_{CC}=V_{IO}$ @ 25°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+;	+;	+;	+;	+	
3.650	******	* * * * * * * * * *	*******	****		1.550
3.600	******	* * * * * * * * * *	*******	****		1.550
3.550	******	* * * * * * * * * *	******	***		1.500
3.500	******	* * * * * * * * * *	******	***		1.500
3.450	******	*******	******	***		1.500
3.400	******	* * * * * * * * * *	*******	**		1.450
3.350	******	* * * * * * * * * *	******	**		1.450
3.300	******	*******	******	**		1.450
3.250	******	* * * * * * * * * *	******	*		1.400
3.200	******	* * * * * * * * * *	******	*		1.400
3.150	******	*******	*******	*		1.400
3.100	******	* * * * * * * * * *	******			1.350
3.050	******	* * * * * * * * * *	******			1.350
3.000	******	*******	*********			1.300
2.950	******	* * * * * * * * * *	********			1.300
2.900	******	*******	*********			1.300
2.850	******	*******	*******			1.250
2.800	******	* * * * * * * * * *	*******			1.250
2.750	******	*******	*******			1.250
2.700	******	*******	******			1.200
2.650	******	* * * * * * * * * *	******			1.200
	+;	+;	+;	+;	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{CC}=V_{IO} @ 85°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+;	+ ;	+;	+ ;	-+			
3.650	*******	********	*********	****		1.550		
3.600	*******	********	*********	***		1.500		
3.550	********	* * * * * * * * * *	* * * * * * * * * * *	***		1.500		
3.500	*******	* * * * * * * * * *	********	***		1.500		
3.450	*******	* * * * * * * * * *	********	**		1.450		
3.400	*******	*******	*********	**		1.450		
3.350	*******	* * * * * * * * * * *	*********	**		1.450		
3.300	*******	********	********	*		1.400		
3.250	*******	*******	*********	*		1.400		
3.200	*******	* * * * * * * * * * *	*********	*		1.400		
3.150	*******	* * * * * * * * * *	*********			1.350		
3.100	*******	*******	********			1.350		
3.050	*******	* * * * * * * * * *	*********			1.350		
3.000	*******	* * * * * * * * * *	********			1.300		
2.950		*******	********			1.300		
2.900	*******	* * * * * * * * * *	*******			1.250		
2.850	*******	******	*******			1.250		
2.800	*******	*******	*******			1.250		
2.750	*******	* * * * * * * * * *	******			1.200		
2.700	*******	*******	******			1.200		
2.650	*******	*******	******			1.200		
	+;	+;	+;	+ ;	-+			
	0.000	0.500	1.000	1.500	2.000			

$V_{IL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	1.500	2.000	first pass	data
3.650 3.500 3.550 3.450 3.450 3.350 3.250 3.200 3.150 3.150 3.000 2.950 2.900 2.850 2.850	0.000	0.500		1.500 **** **** **** **** **** ***	2.000	first pass 1.550 1.500 1.450 1.450 1.450 1.450 1.400 1.400 1.400 1.350 1.350 1.350 1.350 1.300 1.300 1.300 1.250 1.250	data
2.800 2.750 2.700	*******	***********	***************************************		· · · · · · · · · ·	1.250 1.200 1.200	
2.650	******** +; 0.000	*********** +; 0.500	******* +; 1.000	1.500	 + 2.000	1.150	

V_{IL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+;	+;	+;	+ ;	- +			
3.650	*******	* * * * * * * * * * *	*********	****		1.600		
3.600	*******	* * * * * * * * * *	********	****		1.550		
3.550	*******	* * * * * * * * * * *	* * * * * * * * * * *	****		1.550		
3.500	*******	* * * * * * * * * * *	*********	****		1.550		
3.450	******	* * * * * * * * * *	********	**		1.500		
3.400	*******	*******	*********	***		1.500		
3.350	******	* * * * * * * * * *	********	**		1.500		
3.300	******	* * * * * * * * * *	********	**		1.450		
3.250	*******	* * * * * * * * * *	********	**		1.450		
3.200	******	* * * * * * * * * *	********	**		1.450		
3.150	*******	* * * * * * * * * * *	*********	•		1.400		
3.100	*******	* * * * * * * * * *	********	•		1.400		
3.050	*******	* * * * * * * * * * *	*********	•		1.400		
3.000	*******	* * * * * * * * * * *	*********			1.350		
2.950	******	*******	********			1.350		
2.900	******	* * * * * * * * * *	********			1.350		
2.850	******	* * * * * * * * * *	********			1.300		
2.800	*******	* * * * * * * * * *	********			1.300		
2.750	******	* * * * * * * * * *	*******			1.250		
2.700	******	* * * * * * * * * *	*******			1.250		
2.650	******	* * * * * * * * * *	*******			1.250		
	+;	+;	+;	-+;	-+			
	0.000	0.500	1.000	1.500	2.000			



V_{OH} vs. V_{CC}=V_{IO} @ 25°C

	2.000	2.500	3.000	3.500	4.000	first pass data
	+;	+;	+ ;	+;	+	
3.650	*******	*******	*******	* * * * *		3.600
3.600	*******	*******	*******	****		3.550
3.550	******	* * * * * * * * * *	******	***		3.500
3.500	******	* * * * * * * * * *	*******	**		3.450
3.450	******	*******	*******	*		3.400
3.400	******	* * * * * * * * * *	******			3.350
3.350	******	* * * * * * * * * *	********			3.300
3.300	******	* * * * * * * * * *	*******			3.250
3.250	* * * * * * * * *	******	******		[3.200
3.200	******	* * * * * * * * * *	*****			3.150
3.150	******	* * * * * * * * * *	*****			3.100
3.100	* * * * * * * * *	******	****		[3.050
3.050	******	* * * * * * * * * *	***			3.000
3.000	******	* * * * * * * * * *	**			2.950
2.950	******	*******	*			2.900
2.900	******	*******				2.850
2.850	******	********				2.800
2.800	******	*******				2.750
2.750	******	******				2.700
2.700	******	*****				2.650
2.650	******	*****				2.600
	+;	+;	+;	+;	+ İ	
	2.000	2.500	3.000	3.500	4.000	

V_{OH} vs. V_{CC}=V_{IO} @ 85°C

2.000	2.500	3.000	3.500	4.000	first pass data
+;	+;	+;-	+;	+	
******	*******	*********	*****		3.600
******	********	********	*****		3.550
*******	*******	********	****	[3.500
******	********	*******	***		3.450
******	********	* * * * * * * * * *	**		3.400
İ * * * * * * * *	*******	********	*		3.350
İ * * * * * * * *	*******	*******			3.300
*******	********	*********			3.250
İ * * * * * * * *	*******	*******			3.200
İ * * * * * * * *	*******	******			3.150
******	********	*****			3.100
İ * * * * * * * *	*******	*****			3.050
******	********	****			3.000
******	********	***			2.950
******	*******	**		[2.900
******	*******	•			2.850
******	********				2.800
******	*******			[2.750
******	******				2.700
******	*****				2.650
* * * * * * * *	****				2.600
+;	+;	+;-	+;	+	
2.000	2.500	3.000	3.500	4.000	
	2.000 +; ******* ******* ******** ********	2.000 2.500 +;+; **********************	2.000 2.500 3.000 +	2.000 2.500 3.000 3.500 +	2.000 2.500 3.000 3.500 4.000



$V_{OH}\,vs.\,V_{CC}{=}V_{IO}\,@\,105^\circ C$

	2.000	2.500	3.000	3.500	4.000	first pass	data
3.650 3.500 3.550 3.450 3.400 3.350 3.300 3.250 3.200 3.150	2.000 +; ******* ******* ******* ******* ******	2.500	3.000 **********************************	3.500 ***** ***** **** **** ***	4.000	first pass 3.600 3.550 3.500 3.450 3.400 3.350 3.300 3.250 3.200 3.150 3.100	data
3.200 3.150 3.100 3.050 3.000 2.950 2.900 2.850	**************************************	· · · · · · · · · · · · · · · · · · ·	* * * * * * * * * * * * * * * * * * *		· · · · · · · · · · · · · · · · · · ·	3.150 3.100 3.050 3.000 2.950 2.950 2.850 2.850	
2.800 2.750 2.700 2.650	******** ******** ******** +; 2.000	**************************************			· · · · · · · · · · · · + 4 . 000	2.750 2.700 2.650 2.600	

V_{OH} vs. V_{CC}=V_{IO} @ -40°C

2.000	2.500	3.000	3.500	4.000	first pass data
+;	+;	+;-	+;	+	
******	*******	*********	*****		3.600
******	********	********	*****		3.550
*******	*******	********	****	[3.500
******	********	*******	***		3.450
******	********	* * * * * * * * * *	**		3.400
İ * * * * * * * *	*******	********	*		3.350
İ * * * * * * * *	*******	*******			3.300
*******	********	*********			3.250
İ * * * * * * * *	*******	*******			3.200
İ * * * * * * * *	*******	******			3.150
******	********	*****			3.100
İ * * * * * * * *	*******	*****			3.050
******	********	****			3.000
******	********	***			2.950
******	*******	**		[2.900
******	*******	•			2.850
******	********				2.800
******	*******			[2.750
******	******				2.700
******	*****				2.650
* * * * * * * *	****				2.600
+;	+;	+;-	+;	+	
2.000	2.500	3.000	3.500	4.000	
	2.000 +; ******* ******* ******** ********	2.000 2.500 +;+; **********************	2.000 2.500 3.000 +	2.000 2.500 3.000 3.500 +	2.000 2.500 3.000 3.500 4.000



V_{OL} vs. V_{CC} = V_{IO} @ 25°C

	0.000	0.500	1.000	first	pass	data
	+;	+;	+			
3.650	.******	********	****	0.050		
3.600	.******	********	****	0.050		
3.550	.******	********	****	0.050		
3.500	.******	********	****	0.050		
3.450	.******	********	****	0.050		
3.400	.******	*******	****	0.050		
3.350	.******	*******	****	0.050		
3.300	.******	********	****	0.050		
3.250	.******	*******	****	0.050		
3.200	.******	*******	****	0.050		
3.150	.******	********	****	0.050		
3.100	.******	*******	****	0.050		
3.050	.******	********	****	0.050		
3.000	.******	********	****	0.050		
2.950	.******	********	***	0.050		
2.900	.******	********	****	0.050		
2.850	.******	********	****	0.050		
2.800	.******	*******	****	0.050		
2.750	.******	********	****	0.050		
2.700	.******	********	****	0.050		
2.650	.******	*******	****	0.050		
	+;	+;	+			
	0.000	0.500	1.000			

V_{OL} vs. V_{CC}=V_{IO} @ 85°C

	0.000	0.500	1.000	first	pass	data
	+;	-+;	-+			
3.650	.*******	* * * * * * * * * *	**	0.050		
3.600	.*******	* * * * * * * * * *	***	0.050		
3.550	.*******	* * * * * * * * * *	**	0.050		
3.500	.*******	* * * * * * * * * *	***	0.050		
3.450	.*******	* * * * * * * * * *	***	0.050		
3.400	.*******	* * * * * * * * * *	**	0.050		
3.350	.*******	* * * * * * * * * *	***	0.050		
3.300	.*******	* * * * * * * * * *	***	0.050		
3.250	.*******	* * * * * * * * * *	**	0.050		
3.200	.*******	* * * * * * * * * *	***	0.050		
3.150	.*******	* * * * * * * * * *	***	0.050		
3.100	.*******	* * * * * * * * * *	***	0.050		
3.050	.*******	* * * * * * * * * *	***	0.050		
3.000	.*******	* * * * * * * * * *	***	0.050		
2.950	. * * * * * * * *	* * * * * * * * * *	**	0.050		
2.900	.******	* * * * * * * * * *	**	0.050		
2.850	.******	* * * * * * * * * *	**	0.050		
2.800	.*******	* * * * * * * * * *	**	0.050		
2.750	.******	* * * * * * * * * *	**	0.050		
2.700	.******	* * * * * * * * * *	**	0.050		
2.650	.******	* * * * * * * * * *	**	0.050		
	+;	-+;	-+			
	0.000	0.500	1.000			



$V_{OL} \text{ vs. } V_{CC} \text{=} V_{IO} \textcircled{@} 105^{\circ}\text{C}$

	0.000	0.500	1.000	first pass	data
	+;	-+;	+		
3.650	.*******	* * * * * * * * * *	***	0.050	
3.600	.*******	* * * * * * * * * *	***	0.050	
3.550	. * * * * * * * *	* * * * * * * * * *	***	0.050	
3.500	.*******	* * * * * * * * * *	***	0.050	
3.450	.*******	* * * * * * * * * *	***	0.050	
3.400	. * * * * * * * *	* * * * * * * * * *	***	0.050	
3.350	.*******	* * * * * * * * * *	***	0.050	
3.300	.*******	* * * * * * * * * *	***	0.050	
3.250	. * * * * * * * *	* * * * * * * * * *	***	0.050	
3.200	.*******	* * * * * * * * * *	***	0.050	
3.150	.*******	* * * * * * * * * *	***	0.050	
3.100	. * * * * * * * *	* * * * * * * * * *	***	0.050	
3.050	.*******	* * * * * * * * * *	***	0.050	
3.000	.******	* * * * * * * * * *	***	0.050	
2.950	. * * * * * * * *	* * * * * * * * * *	***	0.050	
2.900	. * * * * * * * *	* * * * * * * * * *	***	0.050	
2.850	.******	* * * * * * * * * *	***	0.050	
2.800	.******	* * * * * * * * * *	***	0.050	
2.750	. * * * * * * * *	* * * * * * * * * *	***	0.050	
2.700	.******	* * * * * * * * * *	***	0.050	
2.650	. * * * * * * * *	* * * * * * * * * *	***	0.050	
	+;	-+;	+		
	0.000	0.500	1.000		

V_{OL} vs. V_{CC}=V_{IO} @ -40°C

	0.000	0.500	1.000	first p	ass data
	+;	+;	+		
3.650	.******	* * * * * * * * * *	***	0.050	
3.600	.******	*******	***	0.050	
3.550	.******	******	***	0.050	
3.500	.******	* * * * * * * * * *	***	0.050	
3.450	.******	*******	***	0.050	
3.400	.******	******	***	0.050	
3.350	.******	* * * * * * * * * *	***	0.050	
3.300	.******	* * * * * * * * * *	***	0.050	
3.250	.******	******	***	0.050	
3.200	.******	* * * * * * * * * *	***	0.050	
3.150	.******	* * * * * * * * * *	***	0.050	
3.100	.******	******	***	0.050	
3.050	.******	* * * * * * * * * *	***	0.050	
3.000	.******	* * * * * * * * * *	***	0.050	
2.950	.******	******	***	0.050	
2.900	.******	* * * * * * * * * *	***	0.050	
2.850	.******	*******	***	0.050	
2.800	.******	******	***	0.050	
2.750	.******	* * * * * * * * * *	***	0.050	
2.700	.******	********	***	0.050	
2.650	.******	* * * * * * * * * *	***	0.050	
	+;	+;	+		
	0.000	0.500	1.000		



V_{IH} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	0.500	1.000	1.500	2.000	2.500	first pass dat	а
	+;	+;	+ ;	+;	+		
3.000			****	********	* * * *	1.650	
2.950			* * * * * *	********	****	1.600	
2.900			*****	* * * * * * * * * * *	* * * *	1.600	
2.850			******	* * * * * * * * * * *	****	1.550	
2.800			******	********	****	1.550	
2.750			* * * * * * * *	* * * * * * * * * * *	****	1.500	
2.700			* * * * * * * *	* * * * * * * * * * *	****	1.500	
2.650			. * * * * * * * * *	********	****	1.450	
2.600			. * * * * * * * * *	* * * * * * * * * * *	****	1.450	
2.550			*******	* * * * * * * * * * *	****	1.400	
2.500			*******	********	****	1.400	
2.450		*	*******	* * * * * * * * * * *	****	1.350	
2.400		*	********	* * * * * * * * * * *	****	1.350	
2.350		* *	********	********	****	1.300	
2.300		* *	*******	* * * * * * * * * * *	****	1.300	
2.250		* * *	********	* * * * * * * * * * *	****	1.250	
2.200		* * *	********	* * * * * * * * * * *	****	1.250	
2.150		* * * *	*******	* * * * * * * * * * *	****	1.200	
2.100		* * * * *	********	* * * * * * * * * * *	****	1.150	
2.050		* * * * *	********	* * * * * * * * * * *	****	1.150	
2.000		* * * * * *	*******	* * * * * * * * * * *	****	1.100	
1.950		* * * * * *	*******	* * * * * * * * * * *	****	1.100	
1.900		* * * * * * *	*******	* * * * * * * * * * *	****	1.050	
1.850		* * * * * *	*******	* * * * * * * * * * *	* * * *	1.050	
1.800		* * * * * * * *	*******	* * * * * * * * * * *	****	1.000	
1.750		* * * * * * * *	*******	* * * * * * * * * * *	****	1.000	
1.700		. * * * * * * * * *	*******	* * * * * * * * * * *	* * * *	0.950	
1.650		. * * * * * * * * *	*******	* * * * * * * * * * *	****	0.950	
	+;	+;	+ ;	+;	+		
	0.500	1.000	1.500	2.000	2.500		

V_{IH} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	0.500	1.000	1.500	2.000	2.500	first pass data
	+;	-+;	-+;	-+;	-+	
3.000			· · · · * * * * * *	******	**	1.650
2.950			******	*******	**	1.650
2.900			******	******	**	1.600
2.850			******	*******	**	1.600
2.800			* * * * * * * *	******	**	1.550
2.750			.*******	********	**	1.500
2.700			.*******	********	**	1.500
2.650			*******	******	**	1.450
2.600			*******	******	**	1.450
2.550		*	*****	******	**	1.400
2.500		*	******	* * * * * * * * * *	**	1.400
2.450		* *	*******	* * * * * * * * * *	**	1.350
2.400		* *	******	* * * * * * * * * *	**	1.350
2.350		* * *	*****	* * * * * * * * * *	**	1.300
2.300		* * *	******	* * * * * * * * * *	**	1.300
2.250		* * * *	*****	* * * * * * * * * *	**	1.250
2.200		* * * *	*****	* * * * * * * * * *	**	1.250
2.150		* * * * *	*****	* * * * * * * * * *	**	1.200
2.100		* * * * *	*****	* * * * * * * * * *	**	1.200
2.050		* * * * * *	*****	* * * * * * * * * *	**	1.150
2.000		* * * * * *	*****	* * * * * * * * * *	**	1.150
1.950		* * * * * *	******	******	**	1.100
1.900		* * * * * * * *	******	******	**	1.050
1.850		* * * * * * * *	******	* * * * * * * * * *	**	1,050
1,800		*******	******	*******	**	1,000
1.750		*******	******	******	**	1.000
1.700		********	******	******	**	0.950
1.650		*******	*****	******	**	0.950
2.000	+	-+	-+	-+	-+	
	0.500	1.000	1.500	2.000	2.500	

V_{IH} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	0.500	1.000	1.500	2.000	2.500	first pass data
	+;	+;	+;	;-	+	
3.000			****	*******	****	1.650
2.950			*****	*******	****	1.600
2.900			*****	*******	****	1.600
2.850			*****	*******	****	1.550
2.800			*****	*******	****	1.550
2.750			* * * * * * * *	******	****	1.500
2.700			******	******	****	1.500
2.650			.******	******	****	1.450
2.600			. * * * * * * * * *	*******	****	1.450
2.550			*******	*******	****	1.400
2.500			******	******	****	1.400
2.450		*	*******	*******	****	1.350
2.400		*	*******	*******	****	1.350
2.350		**	*******	*******	****	1.300
2.300		**	*******	*******	****	1.300
2.250		* * *	******	******	****	1.250
2.200		* * * *	******	******	****	1.200
2.150		* * * *	******	*******	****	1.200
2.100		* * * * *	*******	*******	****	1.150
2.050		* * * * *	******	******	****	1.150
2.000		* * * * * *	*******	*******	****	1.100
1.950		* * * * * *	*******	*******	****	1.100
1.900		* * * * * * *	*******	*******	****	1.050
1.850		* * * * * * *	*******	*******	****	1.050
1.800		* * * * * * * *	*******	*******	****	1.000
1.750		* * * * * * * *	*******	*******	****	1.000
1.700		* * * * * * * *	*******	*******	****	1.000
1.650		*******	******	*******	* * * *	0,950
	+:	+:	+:	+	+	
	0.500	1.000	1.500	2.000	2,500	
			2.200		2.300	

V_{IH} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	0.500	1.000	1.500	2.000	2.500	first pas	s data
2 000	+;	+;	+;	+;	+	1 (50	
3.000		•••••			***	1.650	
2.950		•••••	* * * * `	* * * * * * * * * * * *	***	1.650	
2.900		• • • • • • • • •	* * * * *	* * * * * * * * * * * *	***	1.600	
2.850		• • • • • • • • • •	* * * * * *	* * * * * * * * * * *	***	1.600	
2.800		•••••	* * * * * *	********	***	1.550	
2.750		• • • • • • • • •	* * * * * * * *	* * * * * * * * * * *	***	1.500	
2.700			* * * * * * * *	********	***	1.500	
2.650			* * * * * * * * *	* * * * * * * * * * *	***	1.450	
2.600			* * * * * * * * *	* * * * * * * * * * *	***	1.450	
2.550			. * * * * * * * * * *	*******	***	1.400	
2.500			********	* * * * * * * * * * *	***	1.400	
2.450			********	* * * * * * * * * * *	***	1.350	
2.400			********	* * * * * * * * * * *	***	1.350	
2.350		* .	********	* * * * * * * * * * *	***	1.300	
2.300		* '	********	* * * * * * * * * * *	***	1.300	
2.250		* * *	********	* * * * * * * * * * *	***	1.250	
2.200		* * *	********	* * * * * * * * * * *	***	1.250	
2.150		* * * *	* * * * * * * * * *	* * * * * * * * * * *	***	1.200	
2.100		* * * * *	*******	* * * * * * * * * * *	***	1.150	
2.050		* * * * *	********	* * * * * * * * * * *	***	1.150	
2.000		* * * * * *	* * * * * * * * * *	* * * * * * * * * * *	***	1.100	
1.950		* * * * * *	* * * * * * * * * *	* * * * * * * * * * *	***	1.100	
1.900	1	* * * * * * *	********	* * * * * * * * * * *	***	1.050	
1.850		* * * * * * *	********	* * * * * * * * * * *	***	1.050	
1.800		* * * * * * * *	********	*******	***	1.000	
1.750	1	. * * * * * * * * *	*******	*******	***	0,950	
1.700	1	. * * * * * * * * *	*******	* * * * * * * * * * *	***	0,950	
1.650		*******	*******	*******	***	0,950	
	+	· +	+	+	+		
	0.500	1.000	1.500	2.000	2.500		



V_{IL} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	0.000	0.500	1.000	1.500	2.000	first pass dat	a
	+;	+;	+;	+;	+		
3.000	******	*******	*******			1.300	
2.950	*******	*******	*******			1.300	
2.900	******	*******	* * * * * * * * * *			1.300	
2.850	******	******	*********			1.250	
2.800	*******	******	*********			1.250	
2.750	******	*******	*********			1.250	
2.700	******	*******	*******			1.200	
2.650	******	*******	********			1.200	
2.600	******	*******	*******			1.200	
2.550	******	*******	******			1.150	
2.500	******	*******	******			1.150	
2.450	******	******	*****			1.100	
2.400	******	*******	*****			1.100	
2.350	******	******	*****			1.100	
2.300	******	*******	*****			1.050	
2.250	******	*******	* * * * *			1.050	
2.200	******	*******	* * * *			1.000	
2.150	******	******	* * * *			1.000	
2.100	******	*******	****			1.000	
2.050	******	*******	* * *			0.950	
2.000	******	******	***			0.950	
1.950	******	*******	**			0.900	
1.900	******	*******	**			0.900	
1.850	******	*******	**			0.900	
1.800	******	*******	**			0.900	
1.750	******	*******	*			0.850	
1.700	******	******	*			0.850	
1.650	******	******				0.800	
	+:	+;	+;	+;	+		
	0.000	0.500	1.000	1.500	2.000		

V_{IL} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	0.000	0.500	1.000	1.500	2.000	first	pass	data
	+;	- + ;	-+;	-+;	-+			
3.000	*******	********	*********			1.300		
2.950	*******	*********	********			1.300		
2.900	********	*********	*******			1.250		
2.850	*******	*********	*******			1.250		
2.800	*******	*********	*******			1.250		
2.750	*******	*********	******			1.200		
2.700	*******	*********	******			1.200		
2.650	********	*********	******			1.200		
2.600	*******	*********	*****			1.150		
2.550	*******	*********	*****			1.150		
2.500	*******	*********	*****			1.150		
2.450	*******	*********	****			1.100		
2.400	*******	*********	****			1.100		
2.350	*******	*********	***			1.050		
2.300	*******	*********	***			1.050		
2.250	*******	*********	***			1.050		
2.200	*******	*********	**			1.000		
2.150	*******	*********	**			1.000		
2.100	*******	*********	*			0.950		
2.050	*******	*********	*			0.950		
2.000	*******	*********	*			0.950		
1.950	*******	*********	•			0.900		
1.900	*******	********	•			0.900		
1.850	*******	********	•			0.900		
1.800	*******	*********	•			0.900		
1.750	*******	*********				0.850		
1.700	* * * * * * * * *	*********				0.850		
1.650	******	********				0.800		
	+;	- + ;	-+;	-+;	-+			
	0.000	0.500	1.000	1.500	2.000			



V_{IL} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	0.000	0.500	1.000	1.500	2.000	first pass data
	+;	+;	+;	+;-	+	
3.000	******	********	**********			1.300
2.950	******	******	**********			1.300
2.900	******	******	*********			1.250
2.850	******	******	*********			1.250
2.800	******	******	*********			1.250
2.750	*******	******	********			1.200
2.700	*******	*******	********			1.200
2.650	*******	*******	******			1.150
2.600	*******	*******	******			1.150
2.550	******	*******	******			1.150
2.500	******	*******	*****			1.100
2.450	******	******	*****		[1.100
2.400	******	*******	*****			1.100
2.350	******	*******	*****			1.050
2.300	******	******	*****		[1.050
2.250	******	******	****			1.000
2.200	******	******	****			1.000
2.150	******	*******	****			1.000
2.100	******	******	***			0.950
2.050	******	******	***			0.950
2.000	******	*******	***			0.950
1.950	******	********	**			0.900
1.900	******	********	**			0.900
1.850	******	********	**		İ	0.900
1.800	******	********	*			0.850
1.750	******	********	*			0.850
1.700	******	********				0.800
1.650	******	*******				0.800
	+;	+;	+;	+;-	+	
	0.000	0.500	1.000	1.500	2.000	

V_{IL} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	0.000	0.500	1.000	1.500	2.000	first pass data
2 000	+;;	+;	+;	-+;	+	1 250
3.000						1.350
2.950			************	• • • • • • • • • • •		1.350
2.900			**************************************			1.300
2.850	*******		**********	• • • • • • • • • • •		1.300
2.800	*******	*********	*********			1.300
2.750	*******	* * * * * * * * * * * *	********			1.250
2.700	*******	* * * * * * * * * * * *	********			1.250
2.650	*******	*********	********	• • • • • • • • • • • •		1.250
2.600	*******	*********	*******			1.200
2.550	******	******	*******			1.200
2.500	*******	*******	*****			1.150
2.450	*******	********	******			1.150
2.400	*******	*******	******			1.150
2.350	*******	*******	*****			1.100
2.300	*******	*******	*****			1.100
2.250	*******	*******	****			1.050
2.200	*******	*******	****			1.050
2.150	*******	*******	****			1.050
2.100	*******	*******	***			1.000
2.050	*******	* * * * * * * * * *	***			1.000
2.000	*******	* * * * * * * * * *	**			0.950
1.950	*******	*******	**			0.950
1.900	*******	* * * * * * * * * *	**		[0.950
1.850	*******	* * * * * * * * * *	*			0.900
1.800	*******	* * * * * * * * * *	*			0.900
1.750	*******	* * * * * * * * * *				0.850
1.700	*******	* * * * * * * * * *				0.850
1.650	*******	*******				0.850
	+;;	+;	+;	-+;	+	
	0.000	0.500	1.000	1.500	2.000	



V_{OH} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	1.500	2.000	2.500	3.000	3.500	first	pass	data
	+;	-+;	-+;	-+;	-+			
3.000	*******	* * * * * * * * * * *	********	*		2.950		
2.950	*******	* * * * * * * * * * *	*******			2.900		
2.900	*******	* * * * * * * * * *	*********			2.850		
2.850	*******	* * * * * * * * * *	*******			2.800		
2.800	*******	* * * * * * * * * * *	******			2.750		
2.750	*******	* * * * * * * * * *	*****			2.700		
2.700	*******	* * * * * * * * * *	*****			2.650		
2.650	*******	* * * * * * * * * * *	****			2.600		
2.600	*******	* * * * * * * * * *	***			2.550		
2.550	*******	* * * * * * * * * *	**			2.500		
2.500	*******	* * * * * * * * * *	*			2.450		
2.450	*******	* * * * * * * * * *				2.400		
2.400	*******	********				2.350		
2.350	*******	*******				2.300		
2.300	*******	* * * * * * *				2.250		
2.250	*******	*****				2.200		
2.200	*******	*****				2.150		
2.150	*******	* * * *				2.100		
2.100	*******	***				2.050		
2.050	*******	**				2.000		
2.000	*******	*				1.950		
1.950	*******					1.900		
1.900	********					1.850		
1.850	*******					1.800		
1.800	******					1.750		
1.750	*****					1.700		
1.700	****					1.650		
1.650	***					1.600		
	+;	-+;	-+;	-+;	-+			
	1.500	2.000	2.500	3.000	3.500			

V_{OH} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	1.500	2.000	2.500	3.000	3.500	first	pass	data
	+;	+;;	+;	+ ;	+			
3.000	*******	*******	*********	**		2.950		
2.950	******	* * * * * * * * * * *	*******	*		2.900		
2.900	*******	*******	********			2.850		
2.850	*******	******	********			2.800		
2.800	*******	*******	*******			2.750		
2.750	*******	* * * * * * * * * * *	******			2.700		
2.700	*******	* * * * * * * * * * *	*****			2.650		
2.650	******	* * * * * * * * * * *	*****			2.600		
2.600	*******	* * * * * * * * * * *	****			2.550		
2.550	*******	*******	***			2.500		
2.500	******	* * * * * * * * * *	**			2.450		
2.450	*******	*******	*			2.400		
2.400	*******	*******				2.350		
2.350	******	*********				2.300		
2.300	*******	*******				2.250		
2.250	*******	******				2.200		
2.200	******	*****				2.150		
2.150	*******	*****				2.100		
2.100	*******	****				2.050		
2.050	******	***]	2.000		
2.000	*******	**				1.950		
1.950	*******	*				1.900		
1.900	*******]	1.850		
1.850	*******					1.800		
1.800	******					1.750		
1.750	*****					1.700		
1.700	****					1.650		
1.650	***					1.600		
	+;;	+;	+;	+ ;	+ İ			
	1.500	2.000	2.500	3.000	3.500			



V_{OH} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	1.500	2.000	2.500	3.000	3.500	first pass data
	+;	+ ;	+;	+ ; -	+	
3.000	*******	********	*******	**		2.950
2.950	*******	********	*******	*		2.900
2.900	*******	******	******		[2.850
2.850	*******	* * * * * * * * * *	*********			2.800
2.800	*******	*******	*******			2.750
2.750	*******	******	******		[2.700
2.700	*******	* * * * * * * * * *	*****			2.650
2.650	*******	* * * * * * * * * *	*****			2.600
2.600	*******	*******	****			2.550
2.550	*******	*******	***			2.500
2.500	*******	* * * * * * * * * *	**			2.450
2.450	*******	******	*			2.400
2.400	*******	* * * * * * * * * *				2.350
2.350	*******	*********				2.300
2.300	*******	*******			[2.250
2.250	*******	******				2.200
2.200	*******	*****				2.150
2.150	*******	*****			[2.100
2.100	*******	****				2.050
2.050	*******	***				2.000
2.000	*******	**			[1.950
1.950	*******	•				1.900
1.900	*******					1.850
1.850	*******					1.800
1.800	******					1.750
1.750	*****					1.700
1.700	****					1.650
1.650	***					1.600
	+;	+ ;	+;	+;-	+	
	1.500	2.000	2.500	3.000	3.500	

V_{OH} vs. V_{IO} (V_{CC} = 3V) @ -40°C

1.500 2.000 2.500 3.000 3.500 f.	irst pass	data
+;+;+;+ 	050	
3.000	.950	
2.950	.900	
	.850	
2.850	.800	
2.800 ***********************************	.750	
2.750	.700	
2.700 ***********************************	.650	
2.650 ************************************	.600	
2.600 ***********************************	.550	
2.550 ***********************************	.500	
2.500 ***********************************	.450	
2.450 ************************************	.400	
2.400 ***********************************	.350	
2.350 ************************************	.300	
2.300 ***********************************	.250	
2.250 ************************************	.200	
2.200 **********************************	.150	
2.150 ************************************	.100	
2.100 ***********************************	.050	
2.050 ***********************************	.000	
2.000 *********	.950	
1.950 ********	.900	
1 900 *******	850	
1 850 ******	800	
1 800 *****	750	
1 750 *****	700	
1 700 ****	650	
1 650 ***	600	



V_{OL} vs. V_{IO} (V_{CC} = 3V) @ 25°C

	0.000	0.500	1	.000	first	pass	data
	+;	+;	+				
3.000	.******	*********	***		0.050		
2.950	.******	*********	***		0.050		
2.900	.******	*********	***		0.050		
2.850	. * * * * * * *	*********	***		0.050		
2.800	. * * * * * * *	*********	***		0.050		
2.750	.******	* * * * * * * * * * *	***	Ì	0.050		
2.700	. * * * * * * *	*********	***		0.050		
2.650	. * * * * * * *	*********	***		0.050		
2.600	. * * * * * * *	* * * * * * * * * * *	***	Ì	0.050		
2.550	. * * * * * * *	*********	***	ĺ	0.050		
2.500	. * * * * * * *	*********	***		0.050		
2.450	.******	* * * * * * * * * * *	***	Ì	0.050		
2.400	. * * * * * * *	*********	***	ĺ	0.050		
2.350	. * * * * * * *	*********	***		0.050		
2.300	.******	* * * * * * * * * * *	***	Ì	0.050		
2.250	. * * * * * * *	*********	***		0.050		
2.200	. * * * * * * *	*********	***		0.050		
2.150	.******	* * * * * * * * * * *	***	Ì	0.050		
2.100	. * * * * * * *	*********	***	ĺ	0.050		
2.050	. * * * * * * *	*********	***		0.050		
2.000	.******	* * * * * * * * * * *	***	Ì	0.050		
1.950	.******	*********	***	ĺ	0.050		
1.900	.******	*********	***		0.050		
1.850	.******	* * * * * * * * * *	***	İ	0.050		
1.800	. * * * * * * *	* * * * * * * * * *	***	İ	0.050		
1.750	.******	*********	***	İ	0.050		
1.700	.******	* * * * * * * * * *	***	ĺ	0.050		
1.650	. * * * * * * *	* * * * * * * * * * *	***	1	0.050		
	+;	+ ;	+	1			
	0.000	0.500	1	.000			

V_{OL} vs. V_{IO} (V_{CC} = 3V) @ 85°C

	0.000	0.500	1.0	00 :	Eirst	pass	data
	+;	+;	+				
3.000	. * * * * * * *	*******	****		0.050		
2.950	. * * * * * * *	*******	***		0.050		
2.900	. * * * * * * *	*******	****		0.050		
2.850	. * * * * * * *	*******	****		0.050		
2.800	. * * * * * * *	*******	****	(0.050		
2.750	. * * * * * * *	*******	****		0.050		
2.700	. * * * * * * *	*******	****		0.050		
2.650	. * * * * * * *	*******	****	(0.050		
2.600	. * * * * * * *	*******	****		0.050		
2.550	. * * * * * * *	*******	****		0.050		
2.500	. * * * * * * *	*******	****	(0.050		
2.450	. * * * * * * *	*******	****		0.050		
2.400	. * * * * * * *	*******	****		0.050		
2.350	. * * * * * * *	*******	****		0.050		
2.300	. * * * * * * *	*******	****		0.050		
2.250	. * * * * * * *	*******	****		0.050		
2.200	.******	*******	****		0.050		
2.150	. * * * * * * *	* * * * * * * * * *	****		0.050		
2.100	. * * * * * * *	*******	****		0.050		
2.050	.******	*******	****		0.050		
2.000	. * * * * * * *	*******	****		0.050		
1.950	.******	*******	****	(0.050		
1.900	. * * * * * * *	* * * * * * * * *	****		0.050		
1.850	.******	*******	****		0.050		
1.800	.******	*******	****		0.050		
1.750	. * * * * * * *	******	****		0.050		
1.700	.******	*******	****		0.050		
1.650	.******	******	****		0.050		
	+;	+;	+ İ				
	0.000	0.500	1.0	00			



V_{OL} vs. V_{IO} (V_{CC} = 3V) @ 105°C

	0.000	0.500	1	.000	first	pass	data
	+;;	+;	+				
3.000	.******	********	***		0.050		
2.950	.******	*******	***		0.050		
2.900	. * * * * * * * *	* * * * * * * * * *	***		0.050		
2.850	.******	* * * * * * * * * *	***		0.050		
2.800	.******	* * * * * * * * * *	***		0.050		
2.750	.******	* * * * * * * * * *	***		0.050		
2.700	.******	* * * * * * * * * *	***		0.050		
2.650	.******	* * * * * * * * * *	***	ĺ	0.050		
2.600	.******	* * * * * * * * * *	***	İ	0.050		
2.550	. * * * * * * *	* * * * * * * * * *	***	İ	0.050		
2.500	.******	* * * * * * * * * *	***	İ	0.050		
2.450	******	********	***	İ	0.050		
2.400	.******	* * * * * * * * * *	***		0.050		
2.350	.******	* * * * * * * * * *	***	İ	0.050		
2.300	******	********	***	İ	0.050		
2.250	. * * * * * * *	* * * * * * * * * *	***	İ	0.050		
2.200	.******	* * * * * * * * * *	***	İ	0.050		
2.150	.******	* * * * * * * * * *	***	İ	0.050		
2.100	. * * * * * * *	* * * * * * * * * *	***	İ	0.050		
2.050	.******	* * * * * * * * * *	***	İ	0.050		
2.000	.******	* * * * * * * * * *	***	İ	0.050		
1.950	******	* * * * * * * * * *	***	İ	0.050		
1.900	.******	* * * * * * * * * *	***	İ	0.050		
1.850	.******	* * * * * * * * * *	***	İ	0.050		
1.800	.******	* * * * * * * * * *	***	İ	0.050		
1.750	.******	* * * * * * * * * *	***	İ	0.050		
1.700	.******	* * * * * * * * * *	***	İ	0.050		
1.650	******	*******	***	ĺ	0.050		
	+;;	+:	+				
	0.000	0.500	1	.000			

V_{OL} vs. V_{IO} (V_{CC} = 3V) @ -40°C

	0.000	0.500	1.000) first	pass	data
	+;	+; -	+			
3.000	. * * * * * * *	******	****	0.050		
2.950	. * * * * * * *	*******	* * * *	0.050		
2.900	. * * * * * * *	*******	* * * *	0.050		
2.850	. * * * * * * *	*******	* * * *	0.050		
2.800	. * * * * * * *	******	* * * *	0.050		
2.750	. * * * * * * *	*******	****	0.050		
2.700	. * * * * * * *	******	****	0.050		
2.650	.******	*******	****	0.050		
2.600	. * * * * * * *	*******	****	0.050		
2.550	. * * * * * * *	******	****	0.050		
2.500	.******	*******	****	0.050		
2.450	.******	*******	****	0.050		
2.400	. * * * * * * *	******	****	0.050		
2.350	.******	*******	****	0.050		
2.300	.******	*******	****	0.050		
2.250	. * * * * * * *	******	****	0.050		
2.200	.******	*******	****	0.050		
2.150	.******	*******	****	0.050		
2.100	.******	*******	****	0.050		
2.050	.******	*******	****	0.050		
2.000	.******	*******	****	0.050		
1.950	.******	*******	****	0.050		
1.900	. * * * * * * *	*******	****	0.050		
1.850	.******	*******	****	0.050		
1.800	.******	*******	****	0.050		
1.750	.******	*******	****	0.050		
1.700	.******	*******	****	0.050		
1.650	.******	*******	****	0.050		
	+;	+;-	+			
	0.000	0.500	1.000	C		



17. Revision History

Document Document	Document Title: S29GL128S (XMC 85C 105C) Qualification Database Document Number: 002-21356				
Revision	ECN	Orig. of Change	Submission D <i>a</i> te	Description of Change	
**	-	-	03/31/2013	Initial release.	
*A	5896366	NFB	09/26/2017	Updated to Cypress template.	
*В	6650400	CNSO	08/09/2019	Updated Document Title to read as "S29GL128S (XMC 85C 105C) Qualification Database". Added "Introduction". Added "Die Photograph". Added "Pad Definition Table". Added "Physical Sector Layout". Added "Sector Enlargement". Added "Sector Enlargement". Added "Die Processing Summary". Updated Product Information: Updated LAE064: Updated details under "Theta Ja" and "Psi Jt". Updated details under "Theta Ja" and "Psi Jt". Updated details under "Theta Ja" and "Psi Jt". Updated VBU056: Updated details under "Product Description", "Theta Ja", "Psi Jt", "Die", "Die Size" and "Density". Updated TS056: Updated details under "Theta Ja" and "Psi Jt". Added "Assembly Bonding Diagram". Added "Test Methodology". Added "Generalized Test Flow". Updated Quality and Reliability Data: Added "S29GL128S High Temperature Operating Life Test Configuration". Added "Characterization Test Results". Added "Chevice Characterization Data". Added "AC Device Characterization Data". Added "Shmoo Plots". Updated to new template.	



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Marketing Part Number	Sample Order Part Number	Sample Availability			
00003302768	S29GL01GS10DHA020-002	2-4 weeks lead time			
00003302776	S29GL512S10DHA020-002	2-4 weeks lead time			
051GL256S90TFI010	S29GL256S90TFA010-002	2-4 weeks lead time			
051GL512S10TFI010	S29GL512S10TFA010-002	2-4 weeks lead time			
0791074549RFU00	S29GL256S10TFB010-002	2-4 weeks lead time			
0791075319RFU00	S29GL01GS11TFB020-002	2-4 weeks lead time			
0791077399RQA00	S29GL512S11TFB010-002	2-4 weeks lead time			
0791085869RCP00	S29GL128S10TFB010-002	2-4 weeks lead time			
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110778	S29GL128S10DHB010-002	2-4 weeks lead time			
121877	S29GL256S10DHB020-002	2-4 weeks lead time			
122046	S29GL128S10DHB020-002	2-4 weeks lead time			
156739-1 A	S29GL128S10DHA020-002	2-4 weeks lead time			
170-0121-000	S29GL512S11DHA020-002	2-4 weeks lead time			
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2437528	S29GL256S90DHA020-002	2-4 weeks lead time			
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28328261 A	S29GL512S10TFA020-002	2-4 weeks lead time			
28329184 A	S29GL01GS11DHAV20-002	2-4 weeks lead time			
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28633886 A	S29GL01GS11DHB020-002	2-4 weeks lead time			
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315-0825-000 AAA	S29GL128S90DHA020-002	2-4 weeks lead time			
457780-8510	S29GL256S90TFA010-002	2-4 weeks lead time			
457780-8520	S29GL128S90TFA010-002	2-4 weeks lead time			
462791-0870	S29GL512S11TFAV10-002	2-4 weeks lead time			
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51-22113Z01-A	S29GL512S10TFA010-002	2-4 weeks lead time			
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51-28571Z01-A	S29GL01GS10DHA020-002	2-4 weeks lead time
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8 611 200 160	S29GL01GS11TFA020-002	2-4 weeks lead time
8 611 200 891	S29GL512S10DHA020-002	2-4 weeks lead time
8 611 200 914	S29GL01GS10DHA020-002	2-4 weeks lead time
8 611 200 915	S29GL512S10DHA020-002	2-4 weeks lead time
8 611 200 948	S29GL01GS10DHA020-002	2-4 weeks lead time
8 611 200 975	S29GL512S11TFA020-002	2-4 weeks lead time
8 611 200 976	S29GL128S10DHB020-002	2-4 weeks lead time
8 611 200 977	S29GL256S90TFA020-002	2-4 weeks lead time
8 611 200 989	S29GL512S11DHB020-002	2-4 weeks lead time
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811600-81300870	S29GL256S90TFA010-002	2-4 weeks lead time
8611200171	S29GL01GS11TFB020-002	2-4 weeks lead time
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949587-9970	S29GL256S90TFA010-002	2-4 weeks lead time
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99326-1241	S29GL512S11DHA020-002	2-4 weeks lead time
99326-E1241	S29GL512S11DHA020-002	2-4 weeks lead time
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99326-E1270-A	S29GL512S10DHA020-002	2-4 weeks lead time
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S29GL512S11DHB023	S29GL512S11DHB020-002	2-4 weeks lead time
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